

CPC COOPERATIVE PATENT CLASSIFICATION

H ELECTRICITY

(NOTE omitted)

H01 BASIC ELECTRIC ELEMENTS

(NOTE omitted)

H01L SEMICONDUCTOR DEVICES; ELECTRIC SOLID STATE DEVICES NOT OTHERWISE PROVIDED FOR (use of semiconductor devices for measuring [G01](#); resistors in general [H01C](#); magnets, inductors {in general} , transformers [H01F](#); capacitors in general [H01G](#); electrolytic devices [H01G 9/00](#); batteries, accumulators [H01M](#); waveguides, resonators or lines of the waveguide type [H01P](#); line connectors, current collectors [H01R](#); stimulated emission devices [H01S](#); electromechanical resonators [H03H](#); loudspeakers, microphones, gramophone pick-ups or like acoustic electromechanical transducers [H04R](#); electric light sources in general [H05B](#); printed circuits, hybrid circuits, casings or constructional details of electric apparatus, manufacture of assemblages of electrical components [H05K](#); use of semiconductor devices in circuits having a particular application, see the subclass for the application)

NOTES

1. This subclass covers:
 - electric solid state devices which are not covered by any other subclass and details thereof, and includes: semiconductor devices adapted for rectifying, amplifying, oscillating or switching; semiconductor devices sensitive to radiation; electric solid state devices using thermoelectric, superconductive, piezo-electric, electrostrictive, magnetostrictive, galvano-magnetic or bulk negative resistance effects and integrated circuit devices;
 - photoresistors, magnetic field dependent resistors, field effect resistors, capacitors with potential-jump barrier, resistors with potential-jump barrier or surface barrier, incoherent light emitting diodes and thin-film or thick-film circuits;
 - processes and apparatus adapted for the manufacture or treatment of such devices, except where such processes relate to single-step processes for which provision exists elsewhere.
2. In this subclass, the following terms or expressions are used with the meaning indicated:
 - "wafer" means a slice of semiconductor or crystalline substrate material, which can be modified by impurity diffusion (doping), ion implantation or epitaxy, and whose active surface can be processed into arrays of discrete components or integrated circuits;
 - "solid state body" means the body of material within which, or at the surface of which, the physical effects characteristic of the device occur. In thermoelectric devices, it includes all materials in the current path.
Regions in or on the body of the device (other than the solid state body itself), which exert an influence on the solid state body electrically, are considered to be "electrodes" whether or not an external electrical connection is made thereto. An electrode may include several portions and the term includes metallic regions which exert influence on the solid state body through an insulating region (e.g. capacitive coupling) and inductive coupling arrangements to the body. The dielectric region in a capacitive arrangement is regarded as part of the electrode. In arrangements including several portions, only those portions which exert an influence on the solid state body by virtue of their shape, size, or disposition or the material of which they are formed are considered to be part of the electrode. The other portions are considered to be "arrangements for conducting electric current to or from the solid state body" or "interconnections between solid state components formed in or on a common substrate", i.e. leads;
 - "device" means an electric circuit element; where an electric circuit element is one of a plurality of elements formed in or on a common substrate it is referred to as a "component";
 - "complete device" is a device in its fully assembled state which may or may not require further treatment, e.g. electroforming, before it is ready for use but which does not require the addition of further structural units;
 - "parts" includes all structural units which are included in a complete device;
 - "container" is an enclosure forming part of the complete device and is essentially a solid construction in which the body of the device is placed, or which is formed around the body without forming an intimate layer thereon. An enclosure which consists of one or more layers formed on the body and in intimate contact therewith is referred to as an "encapsulation";
 - "integrated circuit" is a device where all components, e.g. diodes, resistors, are built up on a common substrate and form the device including interconnections between the components;
 - "assembly" of a device is the building up of the device from its component constructional units and includes the provision of fillings in containers.
3. In this subclass, both the process or apparatus for the manufacture or treatment of a device and the device itself are classified, whenever both of these are described sufficiently to be of interest.

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(continued)

4. Attention is drawn to Note (3) after the title of section [C](#), which Note indicates to which version of the periodic table of chemical elements the IPC refers. In this subclass, the Periodic System used is the 8 group system indicated by Roman numerals in the Periodic Table thereunder.

WARNINGS

1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups:

H01L 21/301	covered by	H01L 21/30
H01L 21/328	covered by	H01L 29/66075
H01L 21/329	covered by	H01L 29/66083
H01L 21/33	covered by	H01L 29/66227
H01L 21/331	covered by	H01L 29/66234
H01L 21/332	covered by	H01L 29/66363
H01L 21/334	covered by	H01L 29/66075
H01L 21/335	covered by	H01L 29/66409
H01L 21/336	covered by	H01L 29/66477
H01L 21/337	covered by	H01L 29/66893
H01L 21/338	covered by	H01L 29/66848
H01L 21/339	covered by	H01L 29/66946
H01L 21/36-H01L 21/368	covered by	
H01L 21/58	covered by	H01L 24/80
H01L 21/60	covered by	H01L 24/80
H01L 21/66	covered by	H01L 22/00
H01L 21/603	covered by	H01L 24/80
H01L 21/607	covered by	H01L 24/80
H01L 21/8242	covered by	H01L 27/10844
H01L 21/8244	covered by	H01L 27/11
H01L 21/8246	covered by	H01L 27/112
H01L 21/98	covered by	H01L 25/50
H01L 29/38	covered by	H01L 29/04-H01L 29/365
H01L 29/96	covered by	H01L 29/68-H01L 29/945
H01L 51/30	covered by	H01L 51/0032
H01L 51/40	covered by	H01L 51/0001
H01L 51/46	covered by	H01L 51/0032
H01L 51/48	covered by	H01L 51/0001
H01L 51/54	covered by	H01L 51/0032

2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

21/00

Processes or apparatus adapted for the manufacture or treatment of semiconductor or solid state devices or of parts thereof ({testing or measuring during manufacture or treatment, or reliability measurements [H01L 22/00](#); multistep manufacturing processes for passive two-terminal components without a potential-jump or surface barrier for integrated circuits [H01L 28/00](#); } processes or apparatus peculiar to the manufacture or treatment of devices provided for in groups [H01L 31/00](#) - [H01L 51/00](#) or of parts thereof, [see](#) these groups; single-step processes covered by other subclasses, [see](#) the relevant subclasses, e.g. [C23C](#), [C30B](#); photomechanical production of textured or patterned surfaces, materials or originals therefor, apparatus specially adapted therefor, in general [G03F](#))

21/02 . Manufacture or treatment of semiconductor devices or of parts thereof

21/02002 . . {Preparing wafers}

NOTES

1. This group covers processes for manufacturing wafers prior to the fabrication of any device, i.e. between the sawing of ingots (covered by [B28D](#)) and the cleaning of substrates (covered by [H01L 21/02041](#)).

2. This group does not cover:

- simple use of grinding or polishing machines [B24B](#)
- thermal smoothening [H01L 21/324](#)

21/02005 . . . {Preparing bulk and homogeneous wafers}

21/02008 {Multistep processes}

21/0201 {Specific process step}

21/02013 {Grinding, lapping}

21/02016 {Backside treatment}

21/02019 {Chemical etching}

21/02021 {Edge treatment, chamfering}

21/02024 {Mirror polishing}

21/02027 {Setting crystal orientation}

21/0203 {Making porous regions on the surface}

21/02032 {by reclaiming or re-processing}

21/02035 {Shaping}

21/02041 . . {Cleaning}

21/02043 . . . {Cleaning before device manufacture, i.e. Begin-Of-Line process}

21/02046 {Dry cleaning only ([H01L 21/02085](#) takes precedence)}

21/02049 {with gaseous HF}

21/02052 {Wet cleaning only ([H01L 21/02085](#) takes precedence)}

- 21/02054 {combining dry and wet cleaning steps
([H01L 21/02085](#) takes precedence)}
- 21/02057 . . . {Cleaning during device manufacture}
- 21/0206 {during, before or after processing of
insulating layers}
- 21/02063 {the processing being the formation of vias
or contact holes}
- 21/02065 {the processing being a planarization of
insulating layers}
- 21/02068 {during, before or after processing of
conductive layers, e.g. polysilicon or
amorphous silicon layers}
- 21/02071 {the processing being a delineation, e.g.
RIE, of conductive layers}
- 21/02074 {the processing being a planarization of
conductive layers}
- 21/02076 . . . {Cleaning after the substrates have been
singulated}
- 21/02079 . . . {Cleaning for reclaiming}
- 21/02082 . . . {product to be cleaned}
- 21/02085 {Cleaning of diamond}
- 21/02087 {Cleaning of wafer edges}
- 21/0209 {Cleaning of wafer backside}
- 21/02093 {Cleaning of porous materials}
- 21/02096 . . . {only mechanical cleaning}
- 21/02098 . . . {only involving lasers, e.g. laser ablation}
- 21/02101 . . . {only involving supercritical fluids}
- 21/02104 . . {Forming layers ([deposition in general C23C](#);
[crystal growth in general C30B](#))}

WARNING

Groups [H01L 21/02104](#) – [H01L 21/02694](#)
are incomplete pending reclassification
of documents from groups [H01L 21/06](#),
[H01L 21/16](#), and [H01L 21/20](#).

Groups [H01L 21/02104](#) – [H01L 21/02694](#),
[H01L 21/06](#), [H01L 21/20](#), and [H01L 21/16](#)
should be considered in order to perform a
complete search.

- 21/02107 . . . {Forming insulating materials on a substrate}

WARNING

Groups [H01L 21/02107](#) – [H01L 21/02326](#)
are incomplete pending reclassification
of documents from groups [H01L 21/312](#),
[H01L 21/314](#), [H01L 21/316](#), and
[H01L 21/318](#).

Groups [H01L 21/02107](#) – [H01L 21/02326](#),
[H01L 21/312](#), [H01L 21/314](#), [H01L 21/316](#),
and [H01L 21/318](#) should be considered in
order to perform a complete search.

- 21/02109 {characterised by the type of layer, e.g. type
of material, porous/non-porous, pre-cursors,
mixtures or laminates}
- 21/02112 {characterised by the material of the layer}

NOTE

Layers comprising sublayers,
i.e. multi-layers, are additionally
classified in [H01L 21/022](#); porous
layers are additionally classified in
[H01L 21/02203](#)

- 21/02115 {the material being carbon, e.g. alpha-C,
diamond or hydrogen doped carbon}
- 21/02118 {carbon based polymeric organic or
inorganic material, e.g. polyimides, poly
cyclobutene or PVC ([polymers per se
C08G](#), [photoresist per se G03F](#))}
- 21/0212 {the material being fluoro carbon
compounds, e.g.(CF_x)_n, (CH_xF_y)_n
or polytetrafluoroethylene}
- 21/02123 {the material containing silicon}
- 21/02126 {the material containing Si, O, and at
least one of H, N, C, F, or other non-
metal elements, e.g. SiOC, SiOC:H or
SiONC}
- 21/02129 {the material being boron or
phosphorus doped silicon oxides,
e.g. BPSG, BSG or PSG}

NOTE

Halogen, e.g. fluorine,
containing BPSG, PSG, BSG,
and the like, are additionally
classified in [H01L 21/02131](#)

- 21/02131 {the material being halogen doped
silicon oxides, e.g. FSG}
- 21/02134 {the material comprising hydrogen
silsesquioxane, e.g. HSQ}
- 21/02137 {the material comprising alkyl
silsesquioxane, e.g. MSQ}
- 21/0214 {the material being a silicon
oxynitride, e.g. SiON or SiON:H}
- 21/02142 {the material containing silicon and
at least one metal element, e.g. metal
silicate based insulators or metal
silicon oxynitrides}
- 21/02145 {the material containing
aluminium, e.g. AlSiO_x}
- 21/02148 {the material containing hafnium,
e.g. HfSiO_x or HfSiON}
- 21/0215 {the material containing tantalum,
e.g. TaSiO_x}
- 21/02153 {the material containing titanium,
e.g. TiSiO_x}
- 21/02156 {the material containing at least one
rare earth element, e.g. silicate of
lanthanides, scandium or yttrium}
- 21/02159 {the material containing zirconium,
e.g. ZrSiO_x}
- 21/02161 {the material containing more than
one metal element}
- 21/02164 {the material being a silicon oxide,
e.g. SiO₂}

NOTE

The formation of silicon oxide
layers is classified in this group
regardless of the precursor or
of the process of formation;
in case of explicit statements
on doping, on rest-groups, or
on material components see
[H01L 21/02126](#) and subgroups;
deposition of silicon oxide from
organic precursors without
further statements on film

H01L

H01L 21/02164

(continued)

composition is classified here and in [H01L 21/02205](#) and subgroups

- 21/02167 {the material being a silicon carbide not containing oxygen, e.g. SiC, SiC:H or silicon carbonitrides ([H01L 21/02126](#) and [H01L 21/0214](#) take precedence)}
- 21/0217 {the material being a silicon nitride not containing oxygen, e.g. SixNy or SixByNz ([H01L 21/02126](#) and [H01L 21/0214](#) take precedence)}
- 21/02172 {the material containing at least one metal element, e.g. metal oxides, metal nitrides, metal oxynitrides or metal carbides (materials containing silicon [H01L 21/02123](#); metal silicates [H01L 21/02142](#))}
- 21/02175 {characterised by the metal ([H01L 21/02197](#) takes precedence)}
- 21/02178 {the material containing aluminium, e.g. Al₂O₃}
- 21/02181 {the material containing hafnium, e.g. HfO₂}
- 21/02183 {the material containing tantalum, e.g. Ta₂O₅}
- 21/02186 {the material containing titanium, e.g. TiO₂}
- 21/02189 {the material containing zirconium, e.g. ZrO₂}
- 21/02192 {the material containing at least one rare earth metal element, e.g. oxides of lanthanides, scandium or yttrium}
- 21/02194 {the material containing more than one metal element}
- 21/02197 {the material having a perovskite structure, e.g. BaTiO₃}
- 21/022 {the layer being a laminate, i.e. composed of sublayers, e.g. stacks of alternating high-k metal oxides (adhesion layers or buffer layers [H01L 21/02304](#), [H01L 21/02362](#))}
- 21/02203 {the layer being porous}
- 21/02205 {the layer being characterised by the precursor material for deposition}
- 21/02208 {the precursor containing a compound comprising Si}
- 21/02211 {the compound being a silane, e.g. disilane, methylsilane or chlorosilane}
- 21/02214 {the compound comprising silicon and oxygen}

NOTE

This group does not cover mixtures of a silane and oxygen

- 21/02216 {the compound being a molecule comprising at least one silicon-oxygen bond and the compound having hydrogen or an organic group attached to the silicon or oxygen, e.g. a siloxane}

- 21/02219 {the compound comprising silicon and nitrogen}

NOTE

This group does not cover mixtures of silane and nitrogen

- 21/02222 {the compound being a silazane}
- 21/02225 {characterised by the process for the formation of the insulating layer}
- 21/02227 {formation by a process other than a deposition process}

NOTE

Subject matter classified in the range of [H01L 21/0223](#) - [H01L 21/02249](#) is additionally classified in [H01L 21/02249](#), [H01L 21/02255](#) and [H01L 21/02252](#), depending on the type of reaction

- 21/0223 {formation by oxidation, e.g. oxidation of the substrate}
- 21/02233 {of the semiconductor substrate or a semiconductor layer}
- 21/02236 {group IV semiconductor}
- 21/02238 {silicon in uncombined form, i.e. pure silicon}
- 21/02241 {III-V semiconductor}
- 21/02244 {of a metallic layer}
- 21/02247 {formation by nitridation, e.g. nitridation of the substrate}
- 21/02249 {formation by combined oxidation and nitridation performed simultaneously}
- 21/02252 {formation by plasma treatment, e.g. plasma oxidation of the substrate (after treatment of an insulating film by plasma [H01L 21/3105](#) and subgroups)}
- 21/02255 {formation by thermal treatment ([H01L 21/02252](#) takes precedence; after treatment of an insulating film [H01L 21/3105](#) and subgroups)}
- 21/02258 {formation by anodic treatment, e.g. anodic oxidation}
- 21/0226 {formation by a deposition process ([per se C23C](#))}
- 21/02263 {deposition from the gas or vapour phase}

NOTE

This group and subgroups also cover deposition methods in which the gas or vapour is produced by physical means, e.g. ablation from targets or heating of source material

- 21/02266 {deposition by physical ablation of a target, e.g. sputtering, reactive sputtering, physical vapour deposition or pulsed laser deposition}

21/02269 {deposition by thermal evaporation
([H01L 21/02293](#) takes precedence)}

NOTE

Subject matter relating to molecular beam epitaxy is classified in this group

21/02271 {deposition by decomposition or reaction of gaseous or vapour phase compounds, i.e. chemical vapour deposition ([H01L 21/02266](#) takes precedence)}

21/02274 {in the presence of a plasma [PECVD]}

21/02277 {the reactions being activated by other means than plasma or thermal, e.g. photo-CVD}

21/0228 {deposition by cyclic CVD, e.g. ALD, ALE, pulsed CVD}

NOTE

Subject matter relating to cyclic plasma CVD is additionally classified in [H01L 21/02274](#)

21/02282 {liquid deposition, e.g. spin-coating, sol-gel techniques, spray coating}

21/02285 {Langmuir-Blodgett techniques}

21/02288 {printing, e.g. ink-jet printing ([per se B41J](#))}

21/0229 {liquid atomic layer deposition}

21/02293 {formation of epitaxial layers by a deposition process ([epitaxial growth per se C30B](#))}

NOTE

Formation of non-epitaxial layers by MBE, ALE, etc. is not covered by this group; for MBE [see H01L 21/02269](#); for ALE [see H01L 21/0228](#)

21/02296 {characterised by the treatment performed before or after the formation of the layer ([H01L 21/02227](#) and subgroups take precedence)}

NOTE

This group and subgroups only cover processes which are directly linked to the layer formation; routine anneals, i.e. thermal treatment without further features like a special atmosphere, presence of a plasma, thermally induced chemical reactions, change of phase (crystal structure) etc. are not classified here; for cleaning [see H01L 21/02041](#) and subgroups; for etching processes [see H01L 21/311](#) and subgroups; for planarization processes [see H01L 21/31051](#) and subgroups; for processes to repair etch damage [see H01L 21/3105](#) and subgroups

21/02299 {pre-treatment}

NOTE

This group and subgroups cover treatments to improve adhesion or change the surface termination; for etching [see H01L 21/306](#) and subgroups and [H01L 21/311](#) and subgroups

21/02301 {in-situ cleaning}

NOTE

Subject matter relating to the cleaning processes for semiconductor devices in general is covered by [H01L 21/02041](#) and subgroups

21/02304 {formation of intermediate layers, e.g. buffer layers, layers to improve adhesion, lattice match or diffusion barriers}

21/02307 {treatment by exposure to a liquid}

21/0231 {treatment by exposure to electromagnetic radiation, e.g. UV light}

21/02312 {treatment by exposure to a gas or vapour}

21/02315 {treatment by exposure to a plasma}

21/02318 {post-treatment}

NOTE

This group only covers processes that are part of the layer formation; treatments which are performed after completion of the insulating layer are covered by [H01L 21/3105](#) and subgroups

21/02321 {introduction of substances into an already existing insulating layer ([H01L 21/02227](#) and subgroups take precedence)}

NOTE

processes like the introduction of phosphorus into silicon oxide by diffusion, or doping of an already existing insulating layer are covered by this group and subgroups; for the method of introduction, [see H01L 21/02337](#), [H01L 21/02343](#), [H01L 21/02345](#) and subgroups

21/02323 {introduction of oxygen}

21/02326 {into a nitride layer, e.g. changing SiN to SiON}

21/02329 {introduction of nitrogen}

21/02332 {into an oxide layer, e.g. changing SiO to SiON}

21/02334 {in-situ cleaning after layer formation, e.g. removing process residues}

NOTE

Subject matter relating to the cleaning processes for semiconductor

H01L

H01L 21/02334

(continued)

devices in general is covered by
[H01L 21/02041](#) and subgroups

- 21/02337 {treatment by exposure to a gas or vapour}
- 21/0234 {treatment by exposure to a plasma}
- 21/02343 {treatment by exposure to a liquid}
- 21/02345 {treatment by exposure to radiation, e.g. visible light}
- 21/02348 {treatment by exposure to UV light}
- 21/02351 {treatment by exposure to corpuscular radiation, e.g. exposure to electrons, alpha-particles, protons or ions}
- 21/02354 {using a coherent radiation, e.g. a laser}
- 21/02356 {treatment to change the morphology of the insulating layer, e.g. transformation of an amorphous layer into a crystalline layer}
- 21/02359 {treatment to change the surface groups of the insulating layer}
- 21/02362 {formation of intermediate layers, e.g. capping layers or diffusion barriers}
- 21/02365 . . . {Forming inorganic semiconducting materials on a substrate (for light-sensitive devices [H01L 31/00](#))}

WARNING

Group [H01L 21/02365](#) is incomplete pending reclassification of documents from groups [H01L 21/06](#), [H01L 21/16](#), and [H01L 21/20](#)

Groups [H01L 21/06](#), [H01L 21/16](#), and [H01L 21/20](#) should be considered in order to perform a complete search.

- 21/02367 {Substrates}
- 21/0237 {Materials}
- 21/02373 {Group 14 semiconducting materials}
- 21/02376 {Carbon, e.g. diamond-like carbon}
- 21/02378 {Silicon carbide}
- 21/02381 {Silicon, silicon germanium, germanium}
- 21/02384 {including tin}
- 21/02387 {Group 13/15 materials}
- 21/02389 {Nitrides}
- 21/02392 {Phosphides}
- 21/02395 {Arsenides}
- 21/02398 {Antimonides}
- 21/024 {Group 12/16 materials}
- 21/02403 {Oxides}
- 21/02406 {Sulfides}
- 21/02409 {Selenides}
- 21/02411 {Tellurides}
- 21/02414 {Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}
- 21/02417 {Chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}
- 21/0242 {Crystalline insulating materials}
- 21/02422 {Non-crystalline insulating materials, e.g. glass, polymers}

- 21/02425 {Conductive materials, e.g. metallic silicides}
- 21/02428 {Structure}
- 21/0243 {Surface structure}
- 21/02433 {Crystal orientation}
- 21/02436 {Intermediate layers between substrates and deposited layers}
- 21/02439 {Materials}
- 21/02441 {Group 14 semiconducting materials}
- 21/02444 {Carbon, e.g. diamond-like carbon}
- 21/02447 {Silicon carbide}
- 21/0245 {Silicon, silicon germanium, germanium}
- 21/02452 {including tin}
- 21/02455 {Group 13/15 materials}
- 21/02458 {Nitrides}
- 21/02461 {Phosphides}
- 21/02463 {Arsenides}
- 21/02466 {Antimonides}
- 21/02469 {Group 12/16 materials}
- 21/02472 {Oxides}
- 21/02474 {Sulfides}
- 21/02477 {Selenides}
- 21/0248 {Tellurides}
- 21/02483 {Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}
- 21/02485 {Other chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}
- 21/02488 {Insulating materials}
- 21/02491 {Conductive materials}
- 21/02494 {Structure}
- 21/02496 {Layer structure}
- 21/02499 {Monolayers}
- 21/02502 {consisting of two layers}
- 21/02505 {consisting of more than two layers}
- 21/02507 {Alternating layers, e.g. superlattice}
- 21/0251 {Graded layers}
- 21/02513 {Microstructure}
- 21/02516 {Crystal orientation}
- 21/02518 {Deposited layers}
- 21/02521 {Materials}
- 21/02524 {Group 14 semiconducting materials}
- 21/02527 {Carbon, e.g. diamond-like carbon}
- 21/02529 {Silicon carbide}
- 21/02532 {Silicon, silicon germanium, germanium}
- 21/02535 {including tin}
- 21/02538 {Group 13/15 materials}
- 21/0254 {Nitrides}
- 21/02543 {Phosphides}
- 21/02546 {Arsenides}
- 21/02549 {Antimonides}
- 21/02551 {Group 12/16 materials}
- 21/02554 {Oxides}
- 21/02557 {Sulfides}
- 21/0256 {Selenides}
- 21/02562 {Tellurides}

21/02565	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}	21/02678	{Beam shaping, e.g. using a mask}
21/02568	{Chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	21/0268	{Shape of mask}
21/0257	{Doping during depositing}	21/02683	{Continuous wave laser beam}
21/02573	{Conductivity type}	21/02686	{Pulsed laser beam}
21/02576	{N-type}	21/02689	{using particle beams}
21/02579	{P-type}	21/02691	{Scanning of a beam}
21/02581	{Transition metal or rare earth elements}	21/02694	{Controlling the interface between substrate and epitaxial layer, e.g. by ion implantation followed by annealing}
21/02584	{Delta-doping}	21/02697	. . .	{Forming conducting materials on a substrate}
21/02587	{Structure}	21/027	. .	Making masks on semiconductor bodies for further photolithographic processing not provided for in group H01L 21/18 or H01L 21/34 {(photographic masks or originals per se G03F 1/00 ; registration or positioning of photographic masks or originals G03F 9/00 ; photographic cameras G03B ; control of position G05D 3/00)}
21/0259	{Microstructure}	21/0271	. . .	{comprising organic layers}
21/02592	{amorphous}	21/0272	{for lift-off processes}
21/02595	{polycrystalline}	21/0273	{characterised by the treatment of photoresist layers}
21/02598	{monocrystalline}	21/0274	{Photolithographic processes}
21/02601	{Nanoparticles (fullerenes H01L 51/0046)}	21/0275	{using lasers}
21/02603	{Nanowires}	21/0276	{using an anti-reflective coating (anti-reflective coating for lithography in general G03F 7/09)}
21/02606	{Nanotubes (carbon nanotubes H01L 51/0048)}	21/0277	{Electrolithographic processes}
21/02609	{Crystal orientation}	21/0278	{Röntgenlithographic or X-ray lithographic processes}
21/02612	{Formation types}	21/0279	{Ionlithographic processes}
21/02614	{Transformation of metal, e.g. oxidation, nitridation}	21/033	. . .	comprising inorganic layers
21/02617	{Deposition types}	21/0331	{for lift-off processes}
21/0262	{Reduction or decomposition of gaseous compounds, e.g. CVD}	21/0332	{characterised by their composition, e.g. multilayer masks, materials}
21/02623	{Liquid deposition}	21/0334	{characterised by their size, orientation, disposition, behaviour, shape, in horizontal or vertical plane}
21/02625	{using melted materials}	21/0335	{characterised by their behaviour during the process, e.g. soluble masks, redeposited masks}
21/02628	{using solutions}	21/0337	{characterised by the process involved to create the mask, e.g. lift-off masks, sidewalls, or to modify the mask, e.g. pre-treatment, post-treatment}
21/02631	{Physical deposition at reduced pressure, e.g. MBE, sputtering, evaporation}	21/0338	{Process specially adapted to improve the resolution of the mask}
21/02634	{Homoepitaxy}	21/04	. .	the devices having at least one potential-jump barrier or surface barrier, e.g. PN junction, depletion layer, carrier concentration layer {(multistep processes specially adapted for the manufacture of said devices H01L 29/66007 , H01L 29/401 ; details of semiconductor bodies H01L 29/02)}
21/02636	{Selective deposition, e.g. simultaneous growth of mono- and non-monocrystalline semiconductor materials}	21/0405	. . .	{the devices having semiconductor bodies comprising semiconducting carbon, e.g. diamond, diamond-like carbon (multistep processes for the manufacture of said devices H01L 29/66015)}
21/02639	{Preparation of substrate for selective deposition}	NOTE		
21/02642	{Mask materials other than SiO ₂ or SiN}	This group covers passivation		
21/02645	{Seed materials}	21/041	{Making n- or p-doped regions}
21/02647	{Lateral overgrowth}	21/0415	{using ion implantation}
21/0265	{Pendeoepitaxy}			
21/02653	{Vapour-liquid-solid growth}			
21/02656	{Special treatments}			
21/02658	{Pretreatments (cleaning in general H01L 21/02041)}			
21/02661	{In-situ cleaning}			
21/02664	{Aftertreatments (planarisation in general H01L 21/304)}			
21/02667	{Crystallisation or recrystallisation of non-monocrystalline semiconductor materials, e.g. regrowth}			
21/02669	{using crystallisation inhibiting elements}			
21/02672	{using crystallisation enhancing elements}			
21/02675	{using laser beams}			

- 21/042 {Changing their shape, e.g. forming recesses (etching of the semiconductor body [H01L 21/302](#))}
- 21/0425 {Making electrodes}
- 21/043 {Ohmic electrodes}
- 21/0435 {Schottky electrodes}
- 21/044 {Conductor-insulator-semiconductor electrodes}
- 21/0445 . . . {the devices having semiconductor bodies comprising crystalline silicon carbide (multistep processes for the manufacture of said devices [H01L 29/66053](#))}
- 21/045 {passivating silicon carbide surfaces}
- 21/0455 {Making n or p doped regions or layers, e.g. using diffusion}
- 21/046 {using ion implantation}

NOTE

Processes where ion implantation of boron and subsequent annealing does not produce a p-doped region are classified elsewhere, e.g. [H01L 21/0445](#)

- 21/0465 {using masks}
- 21/047 {characterised by the angle between the ion beam and the crystal planes or the main crystal surface}
- 21/0475 {Changing the shape of the semiconductor body, e.g. forming recesses, (etching of the semiconductor body [H01L 21/302](#))}
- 21/048 {Making electrodes}
- 21/0485 {Ohmic electrodes}
- 21/049 {Conductor-insulator-semiconductor electrodes, e.g. MIS contacts}
- 21/0495 {Schottky electrodes}
- 21/06 . . . the devices having semiconductor bodies comprising selenium or tellurium in uncombined form other than as impurities in semiconductor bodies of other materials

WARNING

Group [H01L 21/06](#) is impacted by reclassification into groups [H01L 21/02365](#) – [H01L 21/02694](#).

Groups [H01L 21/06](#) and [H01L 21/02365](#) – [H01L 21/02694](#) should be considered in order to perform a complete search.

- 21/08 Preparation of the foundation plate
- 21/10 Preliminary treatment of the selenium or tellurium, its application to the foundation plate, or the subsequent treatment of the combination
- 21/101 {Application of the selenium or tellurium to the foundation plate}
- 21/103 Conversion of the selenium or tellurium to the conductive state
- 21/105 Treatment of the surface of the selenium or tellurium layer after having been made conductive
- 21/108 Provision of discrete insulating layers, i.e. non-genetic barrier layers

- 21/12 Application of an electrode to the exposed surface of the selenium or tellurium after the selenium or tellurium has been applied to the foundation plate
- 21/14 Treatment of the complete device, e.g. by electroforming to form a barrier
- 21/145 Ageing
- 21/16 . . . the devices having semiconductor bodies comprising cuprous oxide or cuprous iodide

WARNING

Group [H01L 21/16](#) is impacted by reclassification into groups [H01L 21/02365](#) – [H01L 21/02694](#).

Groups [H01L 21/16](#) and [H01L 21/02365](#) – [H01L 21/02694](#) should be considered in order to perform a complete search.

- 21/161 {Preparation of the foundation plate, preliminary treatment oxidation of the foundation plate, reduction treatment}
- 21/162 {Preliminary treatment of the foundation plate}
- 21/164 {Oxidation and subsequent heat treatment of the foundation plate ([H01L 21/165](#) takes precedence)}
- 21/165 {Reduction of the copper oxide, treatment of the oxide layer}
- 21/167 {Application of a non-genetic conductive layer}
- 21/168 {Treatment of the complete device, e.g. electroforming, ageing}
- 21/18 . . . the devices having semiconductor bodies comprising elements of Group IV of the Periodic System or $A_{III}B_V$ compounds with or without impurities, e.g. doping materials {([H01L 21/041](#) - [H01L 21/0425](#), [H01L 21/045](#) - [H01L 21/048](#) take precedence)}

NOTE

This group covers also processes and apparatus which, by using the appropriate technology, are clearly suitable for manufacture or treatment of devices whose bodies comprise elements of Group IV of the Periodic System or $A_{III}B_V$ compounds, even if the material used is not explicitly specified.

- 21/182 {Intermixing or interdiffusion or disordering of III-V heterostructures, e.g. IILD}
- 21/185 {Joining of semiconductor bodies for junction formation}
- 21/187 {by direct bonding}
- 21/20 Deposition of semiconductor materials on a substrate, e.g. epitaxial growth {solid phase epitaxy}

WARNING

Group [H01L 21/20](#) is impacted by reclassification into groups [H01L 21/02365](#) – [H01L 21/02694](#).

Groups [H01L 21/20](#) and [H01L 21/02365](#) – [H01L 21/02694](#) should be considered in order to perform a complete search.

21/2003	{Characterised by the substrate (H01L 21/203 , H01L 21/205 , H01L 21/208 take precedence)}	21/2233	{Diffusion into or out of $A_{III}B_V$ compounds}
21/2007	{Bonding of semiconductor wafers to insulating substrates or to semiconducting substrates using an intermediate insulating layer (H01L 21/2011 takes precedence; bonding of semiconductor wafers to semiconductor wafers for junction formation H01L 21/187)}	21/2236	{from or into a plasma phase}
21/2011	{the substrate being of crystalline insulating material, e.g. sapphire}	21/225	using diffusion into or out of a solid from or into a solid phase, e.g. a doped oxide layer {(H01L 21/221 - H01L 21/222 take precedence)}
21/2015	{the substrate being of crystalline semiconductor material, e.g. lattice adaptation, heteroepitaxy}	21/2251	{Diffusion into or out of group IV semiconductors}
21/2018	{Selective epitaxial growth, e.g. simultaneous deposition of mono - and non-mono semiconductor materials}	21/2252	{using predeposition of impurities into the semiconductor surface, e.g. from a gaseous phase}
21/2022	{Epitaxial regrowth of non- monocrystalline semiconductor materials, e.g. lateral epitaxy by seeded solidification, solid-state crystallization, solid-state graphoeptitaxy, explosive crystallization, grain growth in polycrystalline materials}	21/2253	{by ion implantation}
21/2026	{using a coherent energy beam, e.g. laser or electron beam}	NOTE In groups H01L 21/2254 - H01L 21/2257 one should consider the main compositional parts of the applied layer just before the diffusion step		
21/203	using physical deposition, e.g. vacuum deposition, sputtering	21/2254	{from or through or into an applied layer, e.g. photoresist, nitrides}
21/2033	{Epitaxial deposition of elements of Group IV of the Periodic System, e.g. Si, Ge}	21/2255	{the applied layer comprising oxides only, e.g. P_2O_5 , PSG, H_3BO_3 , doped oxides}
21/2036	{Epitaxial deposition of $A_{III}B_V$ compounds}	21/2256	{through the applied layer}
21/205	using reduction or decomposition of a gaseous compound yielding a solid condensate, i.e. chemical deposition	21/2257	{the applied layer being silicon or silicide or SIPOS, e.g. polysilicon, porous silicon}
21/2053	{Epitaxial deposition of elements of Group IV of the Periodic System, e.g. Si, Ge}	21/2258	{Diffusion into or out of $A_{III}B_V$ compounds}
21/2056	{Epitaxial deposition of $A_{III}B_V$ compounds}	21/228	using diffusion into or out of a solid from or into a liquid phase, e.g. alloy diffusion processes {(H01L 21/221 - H01L 21/222 take precedence)}
21/208	using liquid deposition	21/24	Alloying of impurity materials, e.g. doping materials, electrode materials, with a semiconductor body {(H01L 21/182 takes precedence)}
21/2085	{Epitaxial deposition of $A_{III}B_V$ compounds}	21/242	{Alloying of doping materials with $A_{III}B_V$ compounds}
21/22	Diffusion of impurity materials, e.g. doping materials, electrode materials, into or out of a semiconductor body, or between semiconductor regions; {Interactions between two or more impurities; Redistribution of impurities}	21/244	{Alloying of electrode materials}
21/2205	{from the substrate during epitaxy, e.g. autodoping; Preventing or using autodoping}	21/246	{with $A_{III}B_V$ compounds}
21/221	{of killers}	21/248	{Apparatus specially adapted for the alloying}
21/2215	{in $A_{III}B_V$ compounds}	21/26	Bombardment with radiation {(H01L 21/3105 takes precedence)}
21/222	{Lithium-drift}	21/2605	{using natural radiation, e.g. alpha, beta or gamma radiation}
21/2225	{Diffusion sources}	21/261	to produce a nuclear reaction transmuting chemical elements
21/223	using diffusion into or out of a solid from or into a gaseous phase {(H01L 21/221 - H01L 21/222 take precedence; diffusion through an applied layer H01L 21/225)}	21/263	with high-energy radiation (H01L 21/261 takes precedence)
			21/2633	{for etching, e.g. sputteretching}
			21/2636	{for heating, e.g. electron beam heating}

21/265	producing ion implantation (ion beam tubes for localised treatment H01J 37/30)	21/28026	{characterised by the conductor (H01L 21/28176 takes precedence)}
		WARNING			NOTE
		Groups H01L 21/26566 , H01L 21/2658 and H01L 21/26593 are incomplete pending reclassification of documents from groups H01L 21/26506 and H01L 21/2654 .			When the final conductor comprises a superconductor, subject matter is not classified according to the subgroups H01L 21/28035 - H01L 21/28097 . Instead, it is classified in H01L 21/28026
		Groups H01L 21/26566 , H01L 21/2658 , H01L 21/26593 , H01L 21/26506 and H01L 21/2654 should be considered in order to perform a complete search.	21/28035	{the final conductor layer next to the insulator being silicon, e.g. polysilicon, with or without impurities (H01L 21/28105 takes precedence)}
21/26506	{in group IV semiconductors}			NOTE
21/26513	{of electrically active species}			A very thin, e.g. silicon, adhesion or seed layer is not considered as the one next to the insulator
21/2652	{Through-implantation}	21/28044	{the conductor comprising at least another non-silicon conductive layer}
21/26526	{Recoil-implantation}	21/28052	{the conductor comprising a silicide layer formed by the silicidation reaction of silicon with a metal layer (formed by metal ion implantation H01L 21/28044)}
21/26533	{of electrically inactive species in silicon to make buried insulating layers}	21/28061	{the conductor comprising a metal or metallic silicide formed by deposition, e.g. sputter deposition, i.e. without a silicidation reaction (H01L 21/28052 takes precedence)}
21/2654	{in A _{III} B _V compounds}			NOTE
21/26546	{of electrically active species}			To assess the coverage of groups H01L 21/28052 and H01L 21/28061 , barrier layers, e.g. TaSiN, are not considered
21/26553	{Through-implantation}	21/2807	{the final conductor layer next to the insulator being Si or Ge or C and their alloys except Si}
21/2656	{characterised by the implantation of both electrically active and inactive species in the same semiconductor region to be doped}	21/28079	{the final conductor layer next to the insulator being a single metal, e.g. Ta, W, Mo, Al}
21/26566	{of a cluster, e.g. using a gas cluster ion beam}	21/28088	{the final conductor layer next to the insulator being a composite, e.g. TiN}
2021/26573	{in diamond}	21/28097	{the final conductor layer next to the insulator being a metallic silicide}
21/2658	{of a molecular ion, e.g. decaborane}	21/28105	{the final conductor next to the insulator having a lateral composition or doping variation, or being formed laterally by more than one deposition step}
21/26586	{characterised by the angle between the ion beam and the crystal planes or the main crystal surface}			
21/26593	{at a temperature lower than room temperature}			
21/266	using masks {(H01L 21/26586 takes precedence)}			
21/268	using electromagnetic radiation, e.g. laser radiation			
21/2683	{using X-ray lasers}			
21/2686	{using incoherent radiation}			
21/28	Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in H01L 21/20 - H01L 21/268 ; {(etching for patterning the electrodes H01L 21/311 and H01L 21/3213)}			
21/28008	{Making conductor-insulator-semiconductor electrodes}			
21/28017	{the insulator being formed after the semiconductor body, the semiconductor being silicon}			
		NOTE			
		This group covers deposition of the insulators, including epitaxial insulators, and the conductors within the same process or chamber			

21/28114	{characterised by the sectional shape, e.g. T, inverted-T}	21/2822	{with substrate doping, e.g. N, Ge, C implantation, before formation of the insulator}
	NOTE	21/28229	{by deposition of a layer, e.g. metal, metal compound or polysilicon, followed by transformation thereof into an insulating layer}
	Documents are also classified in groups	21/28238	{with sacrificial oxide}
	H01L 21/28035 - H01L 21/2810	21/28247	{passivation or protection of the electrode, e.g. using re-oxidation}
	when the composition is also relevant	21/28255	{the insulator being formed after the semiconductor body, the semiconductor belonging to Group IV and not being elemental silicon, e.g. Ge, SiGe, SiGeC}
21/28123	{Lithography-related aspects, e.g. sub-lithography lengths; Isolation-related aspects, e.g. to solve problems arising at the crossing with the side of the device isolation; Planarisation aspects}	21/28264	{the insulator being formed after the semiconductor body, the semiconductor being a III-V compound}
21/28132	{conducting part of electrode is defined by a sidewall spacer or a similar technique, e.g. oxidation under mask, plating}	21/28273	{Making conductor-insulator-conductor-insulator-semiconductor electrodes (H01L 21/28291 takes precedence)}
21/28141	{insulating part of the electrode is defined by a sidewall spacer, e.g. dummy spacer, or a similar technique, e.g. oxidation under mask, plating}	21/28282	{comprising a charge trapping insulator}
21/2815	{part or whole of the electrode is a sidewall spacer or made by a similar technique, e.g. transformation under mask, plating}	21/28291	{comprising a layer which is used for its ferroelectric properties}
21/28158	{Making the insulator}	21/283	Deposition of conductive or insulating materials for electrodes {conducting electric current}
21/28167	{on single crystalline silicon, e.g. using a liquid, i.e. chemical oxidation}	21/285	from a gas or vapour, e.g. condensation
21/28176	{with a treatment, e.g. annealing, after the formation of the definitive gate conductor}	21/28506	{of conductive layers}
21/28185	{with a treatment, e.g. annealing, after the formation of the gate insulator and before the formation of the definitive gate conductor}	21/28512	{on semiconductor bodies comprising elements of Group IV of the Periodic System}
21/28194	{by deposition, e.g. evaporation, ALD, CVD, sputtering, laser deposition (H01L 21/28202 takes precedence)}	21/28518	{the conductive layers comprising silicides (H01L 21/28537 takes precedence)}
21/28202	{in a nitrogen-containing ambient, e.g. nitride deposition, growth, oxynitridation, NH ₃ nitridation, N ₂ O oxidation, thermal nitridation, RTN, plasma nitridation, RPN}	21/28525	{the conductive layers comprising semiconducting material (H01L 21/28518 , H01L 21/28537 take precedence)}
21/28211	{in a gaseous ambient using an oxygen or a water vapour, e.g. RTO, possibly through a layer (H01L 21/28194 and H01L 21/28202 take precedence)}	21/28531	{Making of side-wall contacts}
	NOTE	21/28537	{Deposition of Schottky electrodes}
	thin oxidation layers used as a barrier layer or as a buffer layer, e.g. before the formation of a high-k insulator, are classified here only if important <u>per se</u>	2021/28543	{on semiconductor bodies comprising diamond}
		21/2855	{by physical means, e.g. sputtering, evaporation (H01L 21/28518 - H01L 21/28537 and H01L 21/28568 take precedence)}
		21/28556	{by chemical means, e.g. CVD, LPCVD, PECVD, laser CVD (H01L 21/28518 - H01L 21/28537 and H01L 21/28568 take precedence)}
		21/28562	{Selective deposition}
		21/28568	{the conductive layers comprising transition metals (H01L 21/28518 takes precedence)}
		21/28575	{on semiconductor bodies comprising A _{III} B _V compounds}
		21/28581	{Deposition of Schottky electrodes}

- 21/28587 {characterised by the sectional shape, e.g. T, inverted T}
- 21/28593 {asymmetrical sectional shape}
- 21/288 from a liquid, e.g. electrolytic deposition
- 21/2885 {using an external electrical current, i.e. electro-deposition}
- 21/30 Treatment of semiconductor bodies using processes or apparatus not provided for in groups [H01L 21/20](#) - [H01L 21/26](#) (manufacture of electrodes thereon [H01L 21/28](#))
- 21/3003 {Hydrogenation or deuterisation, e.g. using atomic hydrogen from a plasma}
- 21/3006 {of A_{III}B_V compounds}
- 21/302 to change their surface-physical characteristics or shape, e.g. etching, polishing, cutting
- 21/304 Mechanical treatment, e.g. grinding, polishing, cutting {([H01L 21/30625](#) takes precedence)}
- 21/3043 {Making grooves, e.g. cutting}
- 21/3046 {using blasting, e.g. sand-blasting ([H01L 21/2633](#) takes precedence)}
- 21/306 Chemical or electrical treatment, e.g. electrolytic etching (to form insulating layers [H01L 21/31](#))
- 21/30604 {Chemical etching}
- 21/30608 {Anisotropic liquid etching ([H01L 21/3063](#) takes precedence)}
- 21/30612 {Etching of A_{III}B_V compounds}
- 21/30617 {Anisotropic liquid etching}
- 21/30621 {Vapour phase etching}
- 21/30625 {With simultaneous mechanical treatment, e.g. mechanico-chemical polishing}
- 21/3063 Electrolytic etching
- 21/30635 {of A_{III}B_V compounds}
- 21/3065 Plasma etching; Reactive-ion etching
- 21/30655 {comprising alternated and repeated etching and passivation steps, e.g. Bosch process}
- 21/308 using masks ([H01L 21/3063](#), [H01L 21/3065](#) take precedence)
- 21/3081 {characterised by their composition, e.g. multilayer masks, materials}
- 21/3083 {characterised by their size, orientation, disposition, behaviour, shape, in horizontal or vertical plane}
- 21/3085 {characterised by their behaviour during the process, e.g. soluble masks, redeposited masks}
- 21/3086 {characterised by the process involved to create the mask, e.g. lift-off masks, sidewalls, or to modify the mask, e.g. pre-treatment, post-treatment}
- 21/3088 {Process specially adapted to improve the resolution of the mask}
- 21/31 to form insulating layers thereon, e.g. for masking or by using photolithographic techniques (layers forming electrodes [H01L 21/28](#); encapsulating layers [H01L 21/56](#)); After treatment of these layers
- 21/3105 After-treatment
- 21/31051 {Planarisation of the insulating layers ([H01L 21/31058](#) takes precedence)}
- 21/31053 {involving a dielectric removal step}
- 21/31055 {the removal being a chemical etching step, e.g. dry etching (etching per se [H01L 21/311](#))}
- 21/31056 {the removal being a selective chemical etching step, e.g. selective dry etching through a mask}
- 21/31058 {of organic layers}
- 21/311 Etching the insulating layers {by chemical or physical means ([H01L 21/31058](#) takes precedence)}
- 21/31105 {Etching inorganic layers}
- 21/31111 {by chemical means}
- 21/31116 {by dry-etching}
- 21/31122 {of layers not containing Si, e.g. PZT, Al₂O₃}
- 21/31127 {Etching organic layers}
- 21/31133 {by chemical means}
- 21/31138 {by dry-etching}
- 21/31144 {using masks}
- 21/3115 Doping the insulating layers
- 21/31155 {by ion implantation}
- 21/312 Organic layers, e.g. photoresist ([H01L 21/3105](#), [H01L 21/32](#) take precedence; {photoresists per se [G03C](#)})
- (Frozen)
- WARNING**
- Groups [H01L 21/312](#) – [H01L 21/3128](#) are no longer used for the classification of documents as of May 1, 2011. The content of these groups is being reclassified into groups [H01L 21/02107](#) – [H01L 21/02326](#).
- Groups [H01L 21/02107](#) – [H01L 21/02326](#) should be considered in order to perform a complete search.
- 21/3121 {Layers comprising organo-silicon compounds} (Frozen)
- 21/3122 {layers comprising polysiloxane compounds} (Frozen)
- 21/3124 {layers comprising hydrogen silsesquioxane} (Frozen)
- 21/3125 {layers comprising silazane compounds} (Frozen)
- 21/3127 {Layers comprising fluoro (hydro)carbon compounds, e.g. polytetrafluoroethylene} (Frozen)
- 21/3128 {by Langmuir-Blodgett techniques} (Frozen)

21/314 (Frozen) Inorganic layers (H01L 21/3105 , H01L 21/32 take precedence)	21/31625 (Frozen) {Deposition of boron or phosphorus doped silicon oxide, e.g. BSG, PSG, BPSG}
	WARNING	21/31629 (Frozen) {Deposition of halogen doped silicon oxide, e.g. fluorine doped silicon oxide}
	Groups H01L 21/314 – H01L 21/3185 are no longer used for the classification of documents as of May 1, 2011. The content of these group is being reclassified into group H01L 21/02107 – H01L 21/02326 .	21/31633 (Frozen) {Deposition of carbon doped silicon oxide, e.g. SiOC}
	Groups H01L 21/02107 – H01L 21/02326 should be considered in order to perform a complete search.	21/31637 (Frozen) {Deposition of Tantalum oxides, e.g. Ta ₂ O ₅ }
21/3141 (Frozen) {Deposition using atomic layer deposition techniques [ALD]}	21/31641 (Frozen) {Deposition of Zirconium oxides, e.g. ZrO ₂ }
21/3142 (Frozen) {of nano-laminates, e.g. alternating layers of Al ₂ O ₃ -HfO ₂ }	21/31645 (Frozen) {Deposition of Hafnium oxides, e.g. HfO ₂ }
21/3143 (Frozen) {composed of alternated layers or of mixtures of nitrides and oxides or of oxinitrides, e.g. formation of oxinitride by oxidation of nitride layers}	21/3165 (Frozen) {formed by oxidation (H01L 21/31691 , H01L 21/31695 take precedence)}
21/3144 (Frozen) {on silicon}	21/31654 (Frozen) {of semiconductor materials, e.g. the body itself}
21/3145 (Frozen) {formed by deposition from a gas or vapour}	21/31658 (Frozen) {by thermal oxidation, e.g. of SiGe}
21/3146 (Frozen) {Carbon layers, e.g. diamond-like layers}	21/31662 (Frozen) {of silicon in uncombined form}
21/3147 (Frozen) {Epitaxial deposition of insulating materials}	21/31666 (Frozen) {of AIII BV compounds}
21/3148 (Frozen) {Silicon Carbide layers}	21/3167 (Frozen) {of anodic oxidation}
2021/3149 (Frozen) {Langmuir-Blodgett techniques}	21/31675 (Frozen) {of silicon}
21/316 (Frozen) composed of oxides or glassy oxides or oxide based glass	21/31679 (Frozen) {of AIII BV compounds}
	WARNING	21/31683 (Frozen) {of metallic layers, e.g. Al deposited on the body, e.g. formation of multi-layer insulating structures}
	Group H01L 21/316 is no longer used for the classification of documents as of May 1, 2011. The content of this group is being reclassified into groups H01L 21/02107 – H01L 21/02326 .	21/31687 (Frozen) {by anodic oxidation}
	Groups H01L 21/02107 – H01L 21/02326 should be considered in order to perform a complete search.	21/31691 (Frozen) {with perovskite structure}
21/31604 (Frozen) {Deposition from a gas or vapour (H01L 21/31691 , H01L 21/31695 take precedence)}	21/31695 (Frozen) {Deposition of porous oxides or porous glassy oxides or oxide based porous glass}
21/31608 (Frozen) {Deposition of SiO ₂ (H01L 21/31625 , H01L 21/31629 and H01L 21/31633 take precedence)}	21/318 (Frozen) composed of nitrides
21/31612 (Frozen) {on a silicon body}		WARNING
21/31616 (Frozen) {Deposition of Al ₂ O ₃ }		Group H01L 21/318 is no longer used for the classification of documents as of May 1, 2011. The content of this group is being reclassified into groups H01L 21/02107 – H01L 21/02326 .
21/3162 (Frozen) {on a silicon body}		Groups H01L 21/02107 – H01L 21/02326 should be considered in order to perform a complete search.
		21/3185 (Frozen) {of siliconnitrides}
		21/32 using masks
		21/3205 Deposition of non-insulating-, e.g. conductive- or resistive-, layers on insulating layers; After-treatment of these layers (manufacture of electrodes H01L 21/28)

21/32051	{Deposition of metallic or metal-silicide layers}	21/324	Thermal treatment for modifying the properties of semiconductor bodies, e.g. annealing, sintering (H01L 21/20 - H01L 21/288 and H01L 21/302 - H01L 21/322 take precedence)
21/32053	{of metal-silicide layers}	21/3242	{for the formation of PN junctions without addition of impurities (H01L 21/22 takes precedence)}
21/32055	{Deposition of semiconductive layers, e.g. poly - or amorphous silicon layers}	21/3245	{of A _{III} B _V compounds}
21/32056	{Deposition of conductive or semi-conductive organic layers (H01L 21/32058 takes precedence)}	21/3247	{for altering the shape, e.g. smoothing the surface}
21/32058	{Deposition of superconductive layers}	WARNING		Group H01L 21/3247 is incomplete pending reclassification of documents from group H01L 21/324 .
21/321	After treatment	Groups H01L 21/324 and H01L 21/3247 should be considered in order to perform a complete search.		
21/32105	{Oxidation of silicon-containing layers}	21/326	Application of electric currents or fields, e.g. for electroforming (H01L 21/20 - H01L 21/288 and H01L 21/302 - H01L 21/324 take precedence)
21/3211	{Nitridation of silicon-containing layers}	21/34	the devices having semiconductor bodies not provided for in groups { H01L 21/0405 , H01L 21/0445 }, H01L 21/06 , H01L 21/16 and H01L 21/18 with or without impurities, e.g. doping materials
21/32115	{Planarisation}	21/38	Diffusion of impurity materials, e.g. doping materials, electrode materials, into or out of a semiconductor body, or between semiconductor regions
21/3212	{by chemical mechanical polishing [CMP]}	21/383	using diffusion into or out of a solid from or into a gaseous phase
21/32125	{by simultaneously passing an electrical current, i.e. electrochemical mechanical polishing, e.g. ECMP}	21/385	using diffusion into or out of a solid from or into a solid phase, e.g. a doped oxide layer
21/3213	Physical or chemical etching of the layers, e.g. to produce a patterned layer from a pre-deposited extensive layer	21/388	using diffusion into or out of a solid from or into a liquid phase, e.g. alloy diffusion processes
21/32131	{by physical means only}	21/40	Alloying of impurity materials, e.g. doping materials, electrode materials, with a semiconductor body
21/32132	{of silicon-containing layers}	21/42	Bombardment with radiation
21/32133	{by chemical means only}	21/423	with high-energy radiation
21/32134	{by liquid etching only}	21/425	producing ion implantation (ion beam tubes for localized treatment H01J 37/30)
21/32135	{by vapour etching only}	21/426	using masks
21/32136	{using plasmas}	21/428	using electromagnetic radiation, e.g. laser radiation
21/32137	{of silicon-containing layers}	21/44	Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in groups H01L 21/38 - H01L 21/428
21/32138	{pre- or post-treatments, e.g. anti-corrosion processes}	21/441	Deposition of conductive or insulating materials for electrodes
21/32139	{using masks}	21/443	from a gas or vapour, e.g. condensation
21/3215	Doping the layers	21/445	from a liquid, e.g. electrolytic deposition
21/32155	{Doping polycrystalline - or amorphous silicon layers}	21/447	involving the application of pressure, e.g. thermo-compression bonding
21/322	to modify their internal properties, e.g. to produce internal imperfections			
21/3221	{of silicon bodies, e.g. for gettering}			
21/3223	{using cavities formed by hydrogen or noble gas ion implantation}			
21/3225	{Thermally inducing defects using oxygen present in the silicon body for intrinsic gettering (H01L 21/3226 takes precedence)}			
NOTE					
Gettering using both extrinsic and intrinsic gettering techniques is classified in both H01L 21/3221 and H01L 21/3225					
21/3226	{of silicon on insulator}			
21/3228	{of A _{III} B _V compounds, e.g. to make them semi-insulating}			

21/449	involving the application of mechanical vibrations, e.g. ultrasonic vibrations	21/4803	{Insulating or insulated parts, e.g. mountings, containers, diamond heatsinks (H01L 21/4846 takes precedence; printed circuit boards H05K 1/00)}
21/46	Treatment of semiconductor bodies using processes or apparatus not provided for in groups H01L 21/428 (manufacture of electrodes thereon H01L 21/44)	21/4807	{Ceramic parts}
21/461	to change their surface-physical characteristics or shape, e.g. etching, polishing, cutting	21/481	{Insulating layers on insulating parts, with or without metallisation}
21/463	Mechanical treatment, e.g. grinding, ultrasonic treatment	21/4814	{Conductive parts}
21/465	Chemical or electrical treatment, e.g. electrolytic etching (to form insulating layers H01L 21/469)	21/4817	{for containers, e.g. caps (H01L 21/4871 takes precedence)}
21/467	using masks	21/4821	{Flat leads, e.g. lead frames with or without insulating supports}
21/469	to form insulating layers thereon, e.g. for masking or by using photolithographic techniques (layers forming electrodes H01L 21/44 ; encapsulating layers H01L 21/56); After-treatment of these layers	21/4825	{Connection or disconnection of other leads to or from flat leads, e.g. wires, bumps, other flat leads}
21/47	Organic layers, e.g. photoresist (H01L 21/475 , H01L 21/4757 take precedence)	21/4828	{Etching (etching for cleaning without patterning H01L 21/4835)}
21/471	Inorganic layers (H01L 21/475 , H01L 21/4757 take precedence)	21/4832	{Etching a temporary substrate after encapsulation process to form leads}
21/473	composed of oxides or glassy oxides or oxide based glass	21/4835	{Cleaning, e.g. removing of solder}
21/475	using masks	21/4839	{Assembly of a flat lead with an insulating support, e.g. for TAB}
21/4757	After-treatment	21/4842	{Mechanical treatment, e.g. punching, cutting, deforming, cold welding}
21/47573	{Etching the layer}	21/4846	{Leads on or in insulating or insulated substrates, e.g. metallisation (H01L 21/4821 takes precedence; metallisation of ceramics in general C04B 41/51 ; printed circuits H05K 3/00)}
21/47576	{Doping the layer}	21/485	{Adaptation of interconnections, e.g. engineering charges, repair techniques}
21/4763	Deposition of non-insulating, e.g. conductive -, resistive -, layers on insulating layers; After-treatment of these layers (manufacture of electrodes H01L 21/28 , { H01L 21/44 })	21/4853	{Connection or disconnection of other leads to or from a metallisation, e.g. pins, wires, bumps}
21/47635	{After-treatment of these layers}	21/4857	{Multilayer substrates (multilayer metallisation on monolayer substrate H01L 21/4846)}
21/477	Thermal treatment for modifying the properties of semiconductor bodies, e.g. annealing, sintering (H01L 21/38 - H01L 21/449 and H01L 21/461 - H01L 21/475 take precedence)	21/486	{Via connections through the substrate with or without pins}
21/479	Application of electric currents or fields, e.g. for electroforming (H01L 21/38 - H01L 21/449 and H01L 21/461 - H01L 21/475 take precedence)	21/4864	{Cleaning, e.g. removing of solder}
21/48	Manufacture or treatment of parts, e.g. containers, prior to assembly of the devices, using processes not provided for in a single one of the subgroups H01L 21/06 - H01L 21/326 ({apparatus therefor H01L 21/67005 ; insulative sealing of leads in bases H01L 21/50); containers, encapsulations, fillings, mountings per se H01L 23/00 ; {marking of parts H01L 23/544 })	21/4867	{Applying pastes or inks, e.g. screen printing (H01L 21/486 takes precedence)}
NOTE			21/4871	{Bases, plates or heatsinks}
In this group, the expression "treatment" covers also the removal of leads from parts			21/4875	{Connection or disconnection of other leads to or from bases or plates}
			21/4878	{Mechanical treatment, e.g. deforming}
			21/4882	{Assembly of heatsink parts}
			21/4885	{Wire-like parts or pins (wire ball formation B23K 20/00 ; methods related to connecting semiconductor or other solid state bodies H01L 24/00)}
			WARNING		
			The documents of this group and subgroups dealing with methods for connecting semiconductor or other solid state bodies are being continuously reclassified to H01L 24/43		
			21/4889	{Connection or disconnection of other leads to or from wire-like parts, e.g. wires}
			21/4892	{Cleaning}

21/4896	{Mechanical treatment, e.g. cutting, bending}	2021/60105	{using electromagnetic radiation}
21/50	. . .	Assembly of semiconductor devices using processes or apparatus not provided for in a single one of the subgroups H01L 21/06 - H01L 21/326 , {e.g. sealing of a cap to a base of a container}	2021/60112	{Coherent radiation, i.e. laser beam}
		NOTE Arrangements for connecting or disconnecting semiconductor or other solid state bodies, or methods related thereto, other than those arrangements or methods covered by the following subgroups, are covered by H01L 24/00	2021/6012	{Incoherent radiation, e.g. polychromatic heating lamp}
21/52	Mounting semiconductor bodies in containers	2021/60127	{Induction heating, i.e. eddy currents}
21/54	Providing fillings in containers, e.g. gas fillings	2021/60135	{using convection, e.g. reflow oven}
21/56	Encapsulations, e.g. encapsulation layers, coatings	2021/60142	{with a graded temperature profile}
21/561	{Batch processing}	2021/6015	{using conduction, e.g. chuck heater, thermocompression}
21/563	{Encapsulation of active face of flip-chip device, e.g. underfilling or underencapsulation of flip-chip, encapsulation preform on chip or mounting substrate}	2021/60157	{with a graded temperature profile}
21/565	{Moulds}	2021/60165	{using an electron beam}
21/566	{Release layers for moulds, e.g. release layers, layers against residue during moulding}	2021/60172	{using static pressure}
21/568	{Temporary substrate used as encapsulation process aid (H01L 21/4832 and H01L 21/566 take precedence)}	2021/6018	{Unidirectional static pressure}
2021/60	{Attaching or detaching leads or other conductive members, to be used for carrying current to or from the device in operation}	2021/60187	{Isostatic pressure, e.g. degassing using vacuum or pressurised liquid}
2021/60007	{involving a soldering or an alloying process}	2021/60195	{using dynamic pressure, e.g. ultrasonic or thermosonic bonding}
2021/60015	{using plate connectors, e.g. layer, film}	2021/60202	{using a protective atmosphere, e.g. with forming or shielding gas}
2021/60022	{using bump connectors, e.g. for flip chip mounting}	2021/6021	{using an autocatalytic reaction}
2021/6003	{Apparatus therefor}	2021/60217	{Detaching bump connectors, e.g. after testing}
2021/60037	{Right-up bonding}	2021/60225	{Arrangement of bump connectors prior to mounting}
2021/60045	{Pre-treatment step of the bump connectors prior to bonding}	2021/60232	{wherein the bump connectors are disposed only on the semiconductor chip}
2021/60052	{Oxide removing step, e.g. flux, rosin}	2021/6024	{wherein the bump connectors are disposed only on the mounting substrate}
2021/6006	{with temporary supporting member not part of an apparatus, e.g. removable coating, film or substrate}	2021/60247	{wherein the bump connectors are disposed on both the semiconductor chip and the mounting substrate, e.g. bump to bump}
2021/60067	{Aligning the bump connectors with the mounting substrate}	2021/60255	{wherein the bump connectors are provided as prepeg, e.g. are provided in an insulating plate member}
2021/60075	{involving active alignment, i.e. by apparatus steering, e.g. using alignment marks, sensors}	2021/60262	{Lateral distribution of bump connectors prior to mounting}
2021/60082	{involving passive alignment, e.g. using surface energy, chemical reactions, thermal equilibrium}	2021/6027	{Mounting on semiconductor conductive members}
2021/6009	{involving guiding structures, e.g. structures that are left at least partly in the bonded product, spacers}	2021/60277	{involving the use of conductive adhesives}
2021/60097	{Applying energy, e.g. for the soldering or alloying process}	2021/60285	{involving the use of mechanical auxiliary parts without the use of an alloying of soldering process, e.g. pressure contacts}
			2021/60292	{involving the use of an electron or laser beam}
			2021/603	{involving the application of pressure, e.g. thermo-compression bonding}
			2021/607	{involving the application of mechanical vibrations, e.g. ultrasonic vibrations}
			21/62	. .	the devices having no potential-jump barriers or surface barriers

- 21/64 {Apparatus for making assemblies not otherwise provided for, e.g. package constructions}
- 21/67 {Apparatus for sealing, encapsulating, glassing, decapsulating or the like ([processes H01L 23/02, H01L 23/28](#))}
- 21/67132 {Apparatus for placing on an insulating substrate, e.g. tape}
- 21/67138 {Apparatus for wiring semiconductor or solid state device}
- 21/67144 {Apparatus for mounting on conductive members, e.g. leadframes or conductors on insulating substrates}
- 21/6715 {Apparatus for applying a liquid, a resin, an ink or the like ([H01L 21/67126 takes precedence](#))}
- 21/67155 {Apparatus for manufacturing or treating in a plurality of work-stations}
- 21/67161 {characterized by the layout of the process chambers}
- 21/67167 {surrounding a central transfer chamber}
- 21/67173 {in-line arrangement}
- 21/67178 {vertical arrangement}
- 21/67184 {characterized by the presence of more than one transfer chamber}
- 21/6719 {characterized by the construction of the processing chambers, e.g. modular processing chambers}
- 21/67196 {characterized by the construction of the transfer chamber}
- 21/67201 {characterized by the construction of the load-lock chamber}
- 21/67207 {comprising a chamber adapted to a particular process}
- 21/67213 {comprising at least one ion or electron beam chamber (coating by ion implantation [C23C](#); ion or electron beam tubes [H01J 37/00](#))}
- 21/67219 {comprising at least one polishing chamber (polishing apparatuses [B24B](#))}
- 21/67225 {comprising at least one lithography chamber (lithographic apparatuses [G03F 7/00](#))}
- 21/6723 {comprising at least one plating chamber (electroless plating apparatuses [C23C](#), electroplating apparatuses [C25D](#))}
- 21/67236 {the substrates being processed being not semiconductor wafers, e.g. leadframes or chips}
- 21/67242 {Apparatus for monitoring, sorting or marking (testing or measuring during manufacture [H01L 22/00](#), marks per se [H01L 23/544](#); testing individual semiconductor devices [G01R 31/26](#))}
- 21/67248 {Temperature monitoring}
- 21/67253 {Process monitoring, e.g. flow or thickness monitoring}
- 21/67259 {Position monitoring, e.g. misposition detection or presence detection}
- 21/67265 {of substrates stored in a container, a magazine, a carrier, a boat or the like}
- 21/67271 {Sorting devices}
- 21/64 Manufacture or treatment of solid state devices other than semiconductor devices, or of parts thereof, not peculiar to a single device provided for in groups [H01L 31/00 - H01L 51/00](#)
- 21/67 Apparatus specially adapted for handling semiconductor or electric solid state devices during manufacture or treatment thereof; Apparatus specially adapted for handling wafers during manufacture or treatment of semiconductor or electric solid state devices or components {; Apparatus not specifically provided for elsewhere ([processes per se H01L 21/30, H01L 21/46, H01L 23/00](#); simple temporary support means, e.g. using adhesives, electric or magnetic means [H01L 21/68, H01L 21/302](#); apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies and for methods related thereto [H01L 24/74](#);)}
- NOTE**
- In this subgroup the term substrate designates a semiconductor or electric solid state device or component, or a wafer
- 21/67005 {Apparatus not specifically provided for elsewhere ([processes per se H01L 21/30, H01L 21/46, H01L 23/00](#); simple temporary support means, e.g. using adhesives, electric or magnetic means [H01L 21/68, H01L 21/302](#))}
- 21/67011 {Apparatus for manufacture or treatment ([processes H01L 21/30, H01L 21/46](#); for production or after-treatment of single crystals or homogeneous polycrystalline material [C30B 35/00](#))}
- 21/67017 {Apparatus for fluid treatment ([H01L 21/67126, H01L 21/6715 take precedence](#))}
- 21/67023 {for general liquid treatment, e.g. etching followed by cleaning}
- 21/67028 {for cleaning followed by drying, rinsing, stripping, blasting or the like}
- 21/67034 {for drying}
- 21/6704 {for wet cleaning or washing}
- 21/67046 {using mainly scrubbing means, e.g. brushes}
- 21/67051 {using mainly spraying means, e.g. nozzles}
- 21/67057 {with the semiconductor substrates being dipped in baths or vessels}
- 21/67063 {for etching}
- 21/67069 {for drying etching}
- 21/67075 {for wet etching}
- 21/6708 {using mainly spraying means, e.g. nozzles}
- 21/67086 {with the semiconductor substrates being dipped in baths or vessels}
- 21/67092 {Apparatus for mechanical treatment (or grinding or cutting, [see the relevant groups in subclasses B24B or B28D](#))}
- 21/67098 {Apparatus for thermal treatment}
- 21/67103 {mainly by conduction}
- 21/67109 {mainly by convection}
- 21/67115 {mainly by radiation}

- 21/67276 {Production flow monitoring, e.g. for increasing throughput ([program-control systems per se G05B 19/00](#), e.g. total factory control [G05B 19/418](#))}
- 21/67282 {Marking devices}
- 21/67288 {Monitoring of warpage, curvature, damage, defects or the like}
- 21/67294 {using identification means, e.g. labels on substrates or labels on containers}
- 21/673 . . . using specially adapted carriers {or holders; Fixing the workpieces on such carriers or holders ([holders for supporting a complete device in operation H01L 23/32](#))}
- 21/67303 . . . {Vertical boat type carrier whereby the substrates are horizontally supported, e.g. comprising rod-shaped elements}
- 21/67306 {characterized by a material, a roughness, a coating or the like}
- 21/67309 {characterized by the substrate support}
- 21/67313 . . . {Horizontal boat type carrier whereby the substrates are vertically supported, e.g. comprising rod-shaped elements}
- 21/67316 {characterized by a material, a roughness, a coating or the like}
- 21/6732 . . . {Vertical carrier comprising wall type elements whereby the substrates are horizontally supported, e.g. comprising sidewalls}
- 21/67323 {characterized by a material, a roughness, a coating or the like}
- 21/67326 . . . {Horizontal carrier comprising wall type elements whereby the substrates are vertically supported, e.g. comprising sidewalls}
- 21/6733 {characterized by a material, a roughness, a coating or the like}
- 21/67333 . . . {Trays for chips ([magazine for components H05K 13/0084](#))}
- 21/67336 {characterized by a material, a roughness, a coating or the like}
- 21/6734 . . . {specially adapted for supporting large square shaped substrates ([containers and packaging elements for glass sheets B65D 85/48](#), transporting of glass products during their manufacture [C03B 35/00](#))}
- 21/67343 {characterized by a material, a roughness, a coating or the like}
- 21/67346 . . . {characterized by being specially adapted for supporting a single substrate or by comprising a stack of such individual supports}
- 21/6735 . . . {Closed carriers}
- 21/67353 {specially adapted for a single substrate}
- 21/67356 {specially adapted for containing chips, dies or ICs}
- 21/67359 {specially adapted for containing masks, reticles or pellicles}
- 21/67363 {specially adapted for containing substrates other than wafers ([H01L 21/67356](#), [H01L 21/67359](#) take precedence)}
- 21/67366 {characterised by materials, roughness, coatings or the like ([materials relating to an injection moulding process B29C 45/00](#); [chemical composition of materials C08L 51/00](#))}
- 21/67369 {characterised by shock absorbing elements, e.g. retainers or cushions}
- 21/67373 {characterised by locking systems}
- 21/67376 {characterised by sealing arrangements}
- 21/67379 {characterised by coupling elements, kinematic members, handles or elements to be externally gripped}
- 21/67383 {characterised by substrate supports}
- 21/67386 {characterised by the construction of the closed carrier}
- 21/67389 {characterised by atmosphere control}
- 21/67393 {characterised by the presence of atmosphere modifying elements inside or attached to the closed carrier}
- 21/67396 {characterised by the presence of antistatic elements}
- 21/677 . . . for conveying, e.g. between different workstations
- 21/67703 . . . {between different workstations}
- 21/67706 {Mechanical details, e.g. roller, belt ([H01L 21/67709](#) takes precedence)}
- 21/67709 {using magnetic elements}
- 21/67712 {the substrate being handled substantially vertically}
- 21/67715 {Changing the direction of the conveying path}
- 21/67718 {Changing orientation of the substrate, e.g. from a horizontal position to a vertical position}
- 21/67721 {the substrates to be conveyed not being semiconductor wafers or large planar substrates, e.g. chips, lead frames ([H01L 21/6773](#) takes precedence)}
- 21/67724 {by means of a cart or a vehicle}
- 21/67727 {using a general scheme of a conveying path within a factory}
- 21/6773 {Conveying cassettes, containers or carriers}
- 21/67733 {Overhead conveying}
- 21/67736 {Loading to or unloading from a conveyor}
- 21/67739 . . . {into and out of processing chamber}
- 21/67742 {Mechanical parts of transfer devices ([robots in general in B25J](#))}
- 21/67745 {characterized by movements or sequence of movements of transfer devices}
- 21/67748 {horizontal transfer of a single workpiece}
- 21/67751 {vertical transfer of a single workpiece}
- 21/67754 {horizontal transfer of a batch of workpieces}
- 21/67757 {vertical transfer of a batch of workpieces}
- 21/6776 {Continuous loading and unloading into and out of a processing chamber, e.g. transporting belts within processing chambers}
- 21/67763 . . . {the wafers being stored in a carrier, involving loading and unloading ([H01L 21/6779](#) takes precedence)}
- 21/67766 {Mechanical parts of transfer devices ([robots in general in B25J](#))}
- 21/67769 {Storage means}
- 21/67772 {involving removal of lid, door, cover}
- 21/67775 {Docking arrangements}
- 21/67778 {involving loading and unloading of wafers}
- 21/67781 {Batch transfer of wafers}
- 21/67784 . . . {using air tracks}
- 21/67787 {with angular orientation of the workpieces}

- 21/6779 {the workpieces being stored in a carrier, involving loading and unloading}
- 21/67793 . . . {with orientating and positioning by means of a vibratory bowl or track}
- 21/67796 . . . {with angular orientation of workpieces ([H01L 21/67787](#) and [H01L 21/67793](#) take precedence)}
- 21/68 . . for positioning, orientation or alignment (for conveying [H01L 21/677](#))
- WARNING**
- This group is in reorganisation. See provisionally also group [H01L 21/6835](#)
- 21/681 . . . {using optical controlling means}
- 21/682 . . . {Mask-wafer alignment (in general [G03F 7/70](#), [G03F 9/70](#))}
- 21/683 . . for supporting or gripping (for conveying [H01L 21/677](#), for positioning, orientation or alignment [H01L 21/68](#))
- 21/6831 . . . {using electrostatic chucks}
- 21/6833 {Details of electrostatic chucks}
- 21/6835 . . . {using temporarily an auxiliary support}
- NOTE**
- [H01L 21/6835](#), details of the apparatus are to be further indexed using the indexing codes chosen from [H01L 2221/68304](#) and subgroups
- 21/6836 {Wafer tapes, e.g. grinding or dicing support tapes (adhesive tapes in general [C09J 7/20](#))}
- 21/6838 . . . {with gripping and holding devices using a vacuum; Bernoulli devices}
- 21/687 . . . using mechanical means, e.g. chucks, clamps or pinches {(using electrostatic chucks [H01L 21/6831](#))}
- 21/68707 {the wafers being placed on a robot blade, or gripped by a gripper for conveyance}
- 21/68714 {the wafers being placed on a susceptor, stage or support}
- 21/68721 {characterised by edge clamping, e.g. clamping ring}
- 21/68728 {characterised by a plurality of separate clamping members, e.g. clamping fingers}
- 21/68735 {characterised by edge profile or support profile}
- 21/68742 {characterised by a lifting arrangement, e.g. lift pins}
- 21/6875 {characterised by a plurality of individual support members, e.g. support posts or protrusions}
- 21/68757 {characterised by a coating or a hardness or a material}
- 21/68764 {characterised by a movable susceptor, stage or support, others than those only rotating on their own vertical axis, e.g. susceptors on a rotating carousel}
- 21/68771 {characterised by supporting more than one semiconductor substrate}
- 21/68778 {characterised by supporting substrates others than wafers, e.g. chips}
- 21/68785 {characterised by the mechanical construction of the susceptor, stage or support}
- 21/68792 {characterised by the construction of the shaft}
- 21/70 . . Manufacture or treatment of devices consisting of a plurality of solid state components formed in or on a common substrate or of parts thereof; Manufacture of integrated circuit devices or of parts thereof ({multistep manufacturing processes of assemblies consisting of a plurality of individual semiconductor or other solid state devices [H01L 25/00](#); } manufacture of assemblies consisting of preformed electrical components [H05K 3/00](#), [H05K 13/00](#))
- 21/702 . . . {of thick-or thin-film circuits or parts thereof}
- 21/705 {of thick-film circuits or parts thereof}
- 21/707 {of thin-film circuits or parts thereof}
- 21/71 . . Manufacture of specific parts of devices defined in group [H01L 21/70](#) ({[H01L 21/0405](#), [H01L 21/0445](#)}, [H01L 21/28](#), [H01L 21/44](#), [H01L 21/48](#) take precedence)
- 21/74 . . . Making of {localized} buried regions, e.g. buried collector layers, internal connections {substrate contacts}
- 21/743 {Making of internal connections, substrate contacts}
- 21/746 {for AIII-BV integrated circuits}
- 21/76 . . . Making of isolation regions between components
- 21/7602 {between components manufactured in an active substrate comprising SiC compounds}
- 21/7605 {between components manufactured in an active substrate comprising AIII BV compounds}
- 21/7607 {between components manufactured in an active substrate comprising $A_{II}B_{VI}$ compounds}
- 21/761 PN junctions
- 21/762 Dielectric regions {, e.g. EPIC dielectric isolation, LOCOS; Trench refilling techniques, SOI technology, use of channel stoppers}
- 21/76202 {using a local oxidation of silicon, e.g. LOCOS, SWAMI, SILO ([H01L 21/76235](#) takes precedence; together with vertical isolation, e.g. LOCOS in a SOI substrate, [H01L 21/76264](#))}
- 21/76205 {in a region being recessed from the surface, e.g. in a recess, groove, tub or trench region}
- 21/76208 {using auxiliary pillars in the recessed region, e.g. to form LOCOS over extended areas}
- 21/7621 {the recessed region having a shape other than rectangular, e.g. rounded or oblique shape ([H01L 21/76208](#) takes precedence)}
- 21/76213 {introducing electrical inactive or active impurities in the local oxidation region, e.g. to alter LOCOS oxide growth characteristics or for additional isolation purpose}
- 21/76216 {introducing electrical active impurities in the local oxidation region for the sole purpose of creating channel stoppers}

21/76218	{introducing both types of electrical active impurities in the local oxidation region for the sole purpose of creating channel stoppers, e.g. for isolation of complementary doped regions}	21/76267	{Vertical isolation by silicon implanted buried insulating layers, e.g. oxide layers, i.e. SIMOX techniques}
21/76221	{with a plurality of successive local oxidation steps}	21/7627	{Vertical isolation by full isolation by porous oxide silicon, i.e. FIPOS techniques}
21/76224	{using trench refilling with dielectric materials (trench filling with polycrystalline silicon H01L 21/763 ; together with vertical isolation, e.g. trench refilling in a SOI substrate H01L 21/76264)}	21/76272	{Vertical isolation by lateral overgrowth techniques, i.e. ELO techniques}
21/76227	{the dielectric materials being obtained by full chemical transformation of non-dielectric materials, such as polycrystalline silicon, metals}	21/76275	{Vertical isolation by bonding techniques}
21/76229	{Concurrent filling of a plurality of trenches having a different trench shape or dimension, e.g. rectangular and V-shaped trenches, wide and narrow trenches, shallow and deep trenches}	21/76278	{Vertical isolation by selective deposition of single crystal silicon, i.e. SEG techniques}
21/76232	{of trenches having a shape other than rectangular or V-shape, e.g. rounded corners, oblique or rounded trench walls (H01L 21/76229 takes precedence)}	21/76281	{Lateral isolation by selective oxidation of silicon}
21/76235	{trench shape altered by a local oxidation of silicon process step, e.g. trench corner rounding by LOCOS}	21/76283	{Lateral isolation by refilling of trenches with dielectric material}
21/76237	{introducing impurities in trench side or bottom walls, e.g. for forming channel stoppers or alter isolation behavior}	21/76286	{Lateral isolation by refilling of trenches with polycrystalline material}
21/7624	{using semiconductor on insulator [SOI] technology (H01L 21/76297 takes precedence ; manufacture of integrated circuits on insulating substrates H01L 21/84 ; silicon on sapphire [SOS] technology H01L 21/86)}	21/76289	{Lateral isolation by air gap}
21/76243	{using silicon implanted buried insulating layers, e.g. oxide layers, i.e. SIMOX techniques}	21/76291	{Lateral isolation by field effect}
21/76245	{using full isolation by porous oxide silicon, i.e. FIPOS techniques}	21/76294	{using selective deposition of single crystal silicon, i.e. SEG techniques}
21/76248	{using lateral overgrowth techniques, i.e. ELO techniques}	21/76297	{Dielectric isolation using EPIC techniques, i.e. epitaxial passivated integrated circuit}
21/76251	{using bonding techniques}	21/763	Polycrystalline semiconductor regions {(H01L 21/76264 takes precedence)}
21/76254	{with separation/delamination along an ion implanted layer, e.g. Smart-cut, Unibond}	21/764	Air gaps {(H01L 21/76264 takes precedence)}
21/76256	{using silicon etch back techniques, e.g. BESOI, ELTRAN}	21/765	by field effect {(H01L 21/76264 takes precedence)}
21/76259	{with separation/delamination along a porous layer}	21/768	Applying interconnections to be used for carrying current between separate components within a device {comprising conductors and dielectrics}
21/76262	{using selective deposition of single crystal silicon, i.e. SEG techniques}		NOTE
21/76264	{SOI together with lateral isolation, e.g. using local oxidation of silicon, or dielectric or polycrystalline material refilled trench or air gap isolation regions, e.g. completely isolated semiconductor islands}		Groups H01L 21/768 - H01L 21/76898 cover multi-step processes for manufacturing interconnections. Information peculiar to single-step processes should also be classified in the corresponding group, e.g. <ul style="list-style-type: none"> cleaning H01L 21/02041 etching H01L 21/311, H01L 21/3213 masking H01L 21/027, H01L 21/033, H01L 21/31144, H01L 21/32139 planarizing H01L 21/3105, H01L 21/321
		21/76801	{characterised by the formation and the after-treatment of the dielectrics, e.g. smoothing}
		21/76802	{by forming openings in dielectrics}
		21/76804	{by forming tapered via holes}
		21/76805	{the opening being a via or contact hole penetrating the underlying conductor}
		21/76807	{for dual damascene structures}
		21/76808	{involving intermediate temporary filling with material}
		21/7681	{involving one or more buried masks}
		21/76811	{involving multiple stacked pre-patterned masks}
		21/76813	{involving a partial via etch}

21/76814	{ post-treatment or after-treatment, e.g. cleaning or removal of oxides on underlying conductors }	21/7685	{ the layer covering a conductive structure (H01L 21/76849 takes precedence) }
21/76816	{ Aspects relating to the layout of the pattern or to the size of vias or trenches (layout of the interconnections per se H01L 23/528 ; CAD of ICs G06F 17/50) }	21/76852	{ the layer also covering the sidewalls of the conductive structure }
21/76817	{ using printing or stamping techniques }	21/76853	{ characterized by particular after-treatment steps }
21/76819	{ Smoothing of the dielectric (planarisation of insulating materials per se H01L 21/31051) }	21/76855	{ After-treatment introducing at least one additional element into the layer }
21/7682	{ the dielectric comprising air gaps }	21/76856	{ by treatment in plasmas or gaseous environments, e.g. nitriding a refractory metal liner }
21/76822	{ Modification of the material of dielectric layers, e.g. grading, after-treatment to improve the stability of the layers, to increase their density etc. }	21/76858	{ by diffusing alloying elements }
21/76823	{ transforming an insulating layer into a conductive layer }	21/76859	{ by ion implantation }
21/76825	{ by exposing the layer to particle radiation, e.g. ion implantation, irradiation with UV light or electrons etc. (plasma treatment H01L 21/76826) }	21/76861	{ Post-treatment or after-treatment not introducing additional chemical elements into the layer }
21/76826	{ by contacting the layer with gases, liquids or plasmas }	21/76862	{ Bombardment with particles, e.g. treatment in noble gas plasmas; UV irradiation }
21/76828	{ thermal treatment }	21/76864	{ Thermal treatment }
21/76829	{ characterised by the formation of thin functional dielectric layers, e.g. dielectric etch-stop, barrier, capping or liner layers }	21/76865	{ Selective removal of parts of the layer (H01L 21/76844 takes precedence) }
21/76831	{ in via holes or trenches, e.g. non-conductive sidewall liners }	21/76867	{ characterized by methods of formation other than PVD, CVD or deposition from a liquids (PVD H01L 21/2855 ; CVD H01L 21/28556 ; deposition from liquids H01L 21/288) }
21/76832	{ Multiple layers }	21/76868	{ Forming or treating discontinuous thin films, e.g. repair, enhancement or reinforcement of discontinuous thin films }
21/76834	{ formation of thin insulating films on the sidewalls or on top of conductors (H01L 21/76831 takes precedence) }	21/7687	{ Thin films associated with contacts of capacitors }
21/76835	{ Combinations of two or more different dielectric layers having a low dielectric constant (H01L 21/76832 takes precedence) }	21/76871	{ Layers specifically deposited to enhance or enable the nucleation of further layers, i.e. seed layers }
21/76837	{ Filling up the space between adjacent conductive structures; Gap-filling properties of dielectrics }	21/76873	{ for electroplating }
21/76838	{ characterised by the formation and the after-treatment of the conductors (etching for patterning the conductors H01L 21/3213) }	21/76874	{ for electroless plating }
NOTE			21/76876	{ for deposition from the gas phase, e.g. CVD }
When the interconnect is also used as the conductor part of a conductor insulator semiconductor electrode (gate level interconnections), documents are classified in the relevant electrode manufacture groups, e.g. H01L 21/28026			21/76877	{ Filling of holes, grooves or trenches, e.g. vias, with conductive material }
21/7684	{ Smoothing; Planarisation }	21/76879	{ by selective deposition of conductive material in the vias, e.g. selective C.V.D. on semiconductor material, plating (plating on semiconductors in general H01L 21/288) }
21/76841	{ Barrier, adhesion or liner layers }	21/7688	{ by deposition over sacrificial masking layer, e.g. lift-off (lift-off per se H01L 21/0272) }
21/76843	{ formed in openings in a dielectric }	21/76882	{ Reflowing or applying of pressure to better fill the contact hole }
21/76844	{ Bottomless liners }	21/76883	{ Post-treatment or after-treatment of the conductive material }
21/76846	{ Layer combinations }	21/76885	{ By forming conductive members before deposition of protective insulating material, e.g. pillars, studs }
21/76847	{ the layer being positioned within the main fill metal }	21/76886	{ Modifying permanently or temporarily the pattern or the conductivity of conductive members, e.g. formation of alloys, reduction of contact resistances }
21/76849	{ the layer being positioned on top of the main fill metal }			

21/76888	{ By rendering at least a portion of the conductor non conductive, e.g. oxidation}	21/8206	{ the substrate being a semiconductor, using diamond technology (H01L 21/8258 takes precedence)}
21/76889	{ by forming silicides of refractory metals}	21/8213	{ the substrate being a semiconductor, using SiC technology (H01L 21/8258 takes precedence)}
21/76891	{ by using superconducting materials}	21/822	the substrate being a semiconductor, using silicon technology (H01L 21/8258 takes precedence)
21/76892	{ modifying the pattern}	21/8221	{ Three dimensional integrated circuits stacked in different levels}
21/76894	{ using a laser, e.g. laser cutting, laser direct writing, laser repair}	21/8222	Bipolar technology
21/76895	{ Local interconnects; Local pads, as exemplified by patent document EP0896365}	21/8224	comprising a combination of vertical and lateral transistors
21/76897	{ Formation of self-aligned vias or contact plugs, i.e. involving a lithographically uncritical step (self-aligned silicidation on field effect transistors H01L 29/665)}	21/8226	comprising merged transistor logic or integrated injection logic
21/76898	{ formed through a semiconductor substrate}	21/8228	Complementary devices, e.g. complementary transistors
21/77	Manufacture or treatment of devices consisting of a plurality of solid state components or integrated circuits formed in, or on, a common substrate (electrically programmable read-only memories or multistep manufacturing processes therefor H01L 27/115)	21/82285	{ Complementary vertical transistors}
NOTE			21/8229	Memory structures
Integration processes for the manufacture of devices of the type classified in H01L 27/14 - H01L 27/32 are not classified in this group and its sub-groups. Instead, as they are peculiar to said devices, they are classified together with the devices Multistep processes for manufacturing memory structures in general using field effect technology are covered by H01L 27/1052 ; Multistep processes for manufacturing dynamic random access memory structures are covered by H01L 27/10844 ; Multistep processes for manufacturing static random access memory structures are covered by H01L 27/11 ; Multistep processes for manufacturing read-only memory structures are covered by H01L 27/112 ; Multistep processes for manufacturing electrically programmable read-only memory structures are covered by H01L 27/115			21/8232	Field-effect technology
			21/8234	MIS technology {, i.e. integration processes of field effect transistors of the conductor-insulator-semiconductor type}
			21/823406	{ Combination of charge coupled devices, i.e. CCD, or BBD}
			21/823412	{ with a particular manufacturing method of the channel structures, e.g. channel implants, halo or pocket implants, or channel materials}
			21/823418	{ with a particular manufacturing method of the source or drain structures, e.g. specific source or drain implants or silicided source or drain structures or raised source or drain structures}
2021/775	{ comprising a plurality of TFTs on a non-semiconducting substrate, e.g. driving circuits for AMLCDs}	21/823425	{ manufacturing common source or drain regions between a plurality of conductor-insulator-semiconductor structures}
21/78	with subsequent division of the substrate into plural individual devices (cutting to change the surface-physical characteristics or shape of semiconductor bodies H01L 21/304)	21/823431	{ with a particular manufacturing method of transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
21/7806	{ involving the separation of the active layers from a substrate}	21/823437	{ with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}
21/7813	{ leaving a reusable substrate, e.g. epitaxial lift off}	21/823443	{ silicided or salicided gate conductors}
21/782	to produce devices, each consisting of a single circuit element (H01L 21/82 takes precedence)	21/82345	{ gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}
21/784	the substrate being a semiconductor body	21/823456	{ gate conductors with different shapes, lengths or dimensions}
21/786	the substrate being other than a semiconductor body, e.g. insulating body			
21/82	to produce devices, e.g. integrated circuits, each consisting of a plurality of components			

21/823462	{with a particular manufacturing method of the gate insulating layers, e.g. different gate insulating layer thicknesses, particular gate insulator materials or particular gate insulator implants}	21/823857	{with a particular manufacturing method of the gate insulating layers, e.g. different gate insulating layer thicknesses, particular gate insulator materials or particular gate insulator implants}
21/823468	{with a particular manufacturing method of the gate sidewall spacers, e.g. double spacers, particular spacer material or shape}	21/823864	{with a particular manufacturing method of the gate sidewall spacers, e.g. double spacers, particular spacer material or shape}
21/823475	{interconnection or wiring or contact manufacturing related aspects}	21/823871	{interconnection or wiring or contact manufacturing related aspects}
21/823481	{isolation region manufacturing related aspects, e.g. to avoid interaction of isolation region with adjacent structure}	21/823878	{isolation region manufacturing related aspects, e.g. to avoid interaction of isolation region with adjacent structure}
21/823487	{with a particular manufacturing method of vertical transistor structures, i.e. with channel vertical to the substrate surface (with a current flow parallel to the substrate surface H01L 21/823431)}	21/823885	{with a particular manufacturing method of vertical transistor structures, i.e. with channel vertical to the substrate surface (with a current flow parallel to the substrate surface H01L 21/823821)}
21/823493	{with a particular manufacturing method of the wells or tubs, e.g. twin tubs, high energy well implants, buried implanted layers for lateral isolation [BILLI]}	21/823892	{with a particular manufacturing method of the wells or tubs, e.g. twin tubs, high energy well implants, buried implanted layers for lateral isolation [BILLI]}
21/8236	Combination of enhancement and depletion transistors	21/8239	Memory structures
21/8238	Complementary field-effect transistors, e.g. CMOS	21/8248	Combination of bipolar and field-effect technology
21/823807	{with a particular manufacturing method of the channel structures, e.g. channel implants, halo or pocket implants, or channel materials}	21/8249	Bipolar and MOS technology
21/823814	{with a particular manufacturing method of the source or drain structures, e.g. specific source or drain implants or silicided source or drain structures or raised source or drain structures}	21/8252	the substrate being a semiconductor, using III-V technology (H01L 21/8258 takes precedence)
21/823821	{with a particular manufacturing method of transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	21/8254	the substrate being a semiconductor, using II-VI technology (H01L 21/8258 takes precedence)
21/823828	{with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}	21/8256	the substrate being a semiconductor, using technologies not covered by one of groups (H01L 21/8206 , H01L 21/8213), H01L 21/822 , H01L 21/8252 and H01L 21/8254 (H01L 21/8258 takes precedence)
21/823835	{silicided or salicided gate conductors}	21/8258	the substrate being a semiconductor, using a combination of technologies covered by (H01L 21/8206 , H01L 21/8213), H01L 21/822 , H01L 21/8252 , H01L 21/8254 or H01L 21/8256
21/823842	{gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}	21/84	the substrate being other than a semiconductor body, e.g. being an insulating body
21/82385	{gate conductors with different shapes, lengths or dimensions}	21/845	{including field-effect transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
		21/86	the insulating body being sapphire, e.g. silicon on sapphire structure, i.e. SOS
		22/00	{Testing or measuring during manufacture or treatment; Reliability measurements, i.e. testing of parts without further processing to modify the parts as such; Structural arrangements therefor}

- 22/10 . {Measuring as part of the manufacturing process (burn-in [G01R 31/2855](#))}
- 22/12 . . {for structural parameters, e.g. thickness, line width, refractive index, temperature, warp, bond strength, defects, optical inspection, electrical measurement of structural dimensions, metallurgic measurement of diffusions (electrical measurement of diffusions [H01L 22/14](#))}
- 22/14 . . {for electrical parameters, e.g. resistance, deep-levels, CV, diffusions by electrical means}
- 22/20 . {Sequence of activities consisting of a plurality of measurements, corrections, marking or sorting steps}
- 22/22 . . {Connection or disconnection of sub-entities or redundant parts of a device in response to a measurement (testing and repair of stores after manufacture including at wafer scale [G11C 29/00](#); fuses per se [H01L 23/525](#))}
- 22/24 . . {Optical enhancement of defects or not directly visible states, e.g. selective electrolytic deposition, bubbles in liquids, light emission, colour change (voltage contrast [G01R 31/311](#))}
- 22/26 . . {Acting in response to an ongoing measurement without interruption of processing, e.g. endpoint detection, in-situ thickness measurement (endpoint detection arrangements in CMP apparatus [B24B 37/013](#), in discharge apparatus [H01J 37/32](#))}
- 22/30 . {Structural arrangements specially adapted for testing or measuring during manufacture or treatment, or specially adapted for reliability measurements}
- 22/32 . . {Additional lead-in metallisation on a device or substrate, e.g. additional pads or pad portions, lines in the scribe line, sacrificed conductors (arrangements for conducting electric current to or from the solid state body in operation [H01L 23/48](#))}
- 22/34 . . {Circuits for electrically characterising or monitoring manufacturing processes, e.g. whole test die, wafers filled with test structures, on-board-devices incorporated on each die, process control monitors or pad structures thereof, devices in scribe line (switching, multiplexing, gating devices [G01R 19/25](#); process control with lithography, e.g. dose control, [G03F 7/20](#); structures for alignment control by optical means [G03F 7/0633](#))}
- 23/00 Details of semiconductor or other solid state devices** ([H01L 25/00](#) takes precedence {; structural arrangements for testing or measuring during manufacture or treatment, or for reliability measurements [H01L 22/00](#); arrangements for connecting or disconnecting semiconductor or solid-state bodies, or methods related thereto [H01L 24/00](#); finger print sensors [G06K 9/00006](#)})
- NOTE**
- This group does not cover:
- details of semiconductor bodies or of electrodes of devices provided for in group [H01L 29/00](#), which details are covered by that group;
 - details peculiar to devices provided for in a single main group of groups
- [H01L 31/00](#) - [H01L 51/00](#), which details are covered by those groups.
- 23/02 . Containers; Seals ([H01L 23/12](#), [H01L 23/34](#), [H01L 23/48](#), [H01L 23/552](#), {[H01L 23/66](#)} take precedence; {for memories [G11C](#)})
- 23/04 . . characterised by the shape {of the container or parts, e.g. caps, walls}
- 23/041 . . . {the container being a hollow construction having no base used as a mounting for the semiconductor body}
- 23/043 . . . the container being a hollow construction and having a conductive base as a mounting as well as a lead for the semiconductor body
- 23/045 the other leads having an insulating passage through the base
- 23/047 the other leads being parallel to the base
- 23/049 the other leads being perpendicular to the base
- 23/051 another lead being formed by a cover plate parallel to the base plate, e.g. sandwich type
- 23/053 . . . the container being a hollow construction and having an insulating {or insulated} base as a mounting for the semiconductor body
- 23/055 the leads having a passage through the base {([H01L 23/057](#) takes precedence)}
- 23/057 the leads being parallel to the base
- 23/06 . . characterised by the material of the container or its electrical properties
- 23/08 . . . the material being an electrical insulator, e.g. glass
- 23/10 . . characterised by the material or arrangement of seals between parts, e.g. between cap and base of the container or between leads and walls of the container
- 23/12 . Mountings, e.g. non-detachable insulating substrates
- 23/13 . . characterised by the shape
- 23/14 . . characterised by the material or its electrical properties {(printed circuit boards [H05K 1/00](#))}
- 23/142 . . . {Metallic substrates having insulating layers}
- 23/145 . . . {Organic substrates, e.g. plastic}
- 23/147 . . . {Semiconductor insulating substrates (semiconductor conductive substrates [H01L 23/4926](#))}
- 23/15 . . . Ceramic or glass substrates {([H01L 23/142](#), [H01L 23/145](#), [H01L 23/147](#) take precedence)}
- 23/16 . Fillings or auxiliary members in containers {or encapsulations}, e.g. centering rings ([H01L 23/42](#), [H01L 23/552](#) take precedence)
- 23/18 . . Fillings characterised by the material, its physical or chemical properties, or its arrangement within the complete device
- NOTE**
- Group [H01L 23/26](#) takes precedence over groups [H01L 23/20](#) - [H01L 23/24](#)
- 23/20 . . . gaseous at the normal operating temperature of the device
- 23/22 . . . liquid at the normal operating temperature of the device
- 23/24 . . . solid or gel at the normal operating temperature of the device {([H01L 23/3135](#) takes precedence)}

- 23/26 . . . including materials for absorbing or reacting with moisture or other undesired substances {, e.g. getters}
- 23/28 . Encapsulations, e.g. encapsulating layers, coatings, {e.g. for protection} ([H01L 23/552](#) takes precedence; {insulating layers for contacts or interconnections [H01L 23/5329](#)})
- 23/29 . . characterised by the material {, e.g. carbon (interlayer dielectrics [H01L 23/5329](#))}
- 23/291 . . . {Oxides or nitrides or carbides, e.g. ceramics, glass}
- 23/293 . . . {Organic, e.g. plastic}
- 23/295 {containing a filler ([H01L 23/296](#) takes precedence)}
- 23/296 {Organo-silicon compounds}
- 23/298 . . . {Semiconductor material, e.g. amorphous silicon}
- 23/31 . . characterised by the arrangement {or shape}
- 23/3107 . . . {the device being completely enclosed}
- 23/3114 {the device being a chip scale package, e.g. CSP}
- 23/3121 {a substrate forming part of the encapsulation}
- 23/3128 {the substrate having spherical bumps for external connection}
- 23/3135 {Double encapsulation or coating and encapsulation}
- 23/3142 {Sealing arrangements between parts, e.g. adhesion promoters}
- 23/315 {the encapsulation having a cavity}
- 23/3157 . . . {Partial encapsulation or coating (mask layer used as insulation layer [H01L 21/31](#))}
- 23/3164 {the coating being a foil}
- 23/3171 {the coating being directly applied to the semiconductor body, e.g. passivation layer ([H01L 23/3178](#) takes precedence)}
- 23/3178 {Coating or filling in grooves made in the semiconductor body}
- 23/3185 {the coating covering also the sidewalls of the semiconductor body}
- 23/3192 {Multilayer coating}
- 23/32 . Holders for supporting the complete device in operation, i.e. detachable fixtures ([H01L 23/40](#) takes precedence; connectors, {e.g. sockets} , in general [H01R](#); for printed circuits [H05K](#))
- 23/34 . Arrangements for cooling, heating, ventilating or temperature compensation {; Temperature sensing arrangements (thermal treatment apparatus [H01L 21/00](#))}
- 23/345 . . {Arrangements for heating (thermal treatment apparatus [H01L 21/00](#))}
- 23/36 . . Selection of materials, or shaping, to facilitate cooling or heating, e.g. heatsinks {([H01L 23/28](#), [H01L 23/40](#), [H01L 23/42](#), [H01L 23/44](#), [H01L 23/46](#) take precedence; heating [H01L 23/345](#))}
- 23/367 . . . Cooling facilitated by shape of device {([H01L 23/38](#), [H01L 23/40](#), [H01L 23/42](#), [H01L 23/44](#), [H01L 23/46](#) take precedence)}
- 23/3672 {Foil-like cooling fins or heat sinks (being part of lead-frames [H01L 23/49568](#))}
- 23/3675 {characterised by the shape of the housing}
- 23/3677 {Wire-like or pin-like cooling fins or heat sinks}
- 23/373 . . . Cooling facilitated by selection of materials for the device {or materials for thermal expansion adaptation, e.g. carbon}
- 23/3731 {Ceramic materials or glass ([H01L 23/3732](#), [H01L 23/3733](#), [H01L 23/3735](#), [H01L 23/3737](#), [H01L 23/3738](#) take precedence)}
- 23/3732 {Diamonds}
- 23/3733 {having a heterogeneous or anisotropic structure, e.g. powder or fibres in a matrix, wire mesh, porous structures ([H01L 23/3732](#), [H01L 23/3737](#) take precedence)}
- 23/3735 {Laminates or multilayers, e.g. direct bond copper ceramic substrates}
- 23/3736 {Metallic materials ([H01L 23/3732](#), [H01L 23/3733](#), [H01L 23/3735](#), [H01L 23/3737](#), [H01L 23/3738](#) take precedence)}
- 23/3737 {Organic materials with or without a thermoconductive filler}
- 23/3738 {Semiconductor materials}
- 23/38 . . Cooling arrangements using the Peltier effect
- 23/40 . . Mountings or securing means for detachable cooling or heating arrangements {(heating [H01L 23/345](#)); fixed by friction, plugs or springs}
- 23/4006 . . . {with bolts or screws}
- 23/4012 {for stacked arrangements of a plurality of semiconductor devices (assemblies [per se](#) [H01L 25/00](#))}
- 2023/4018 {characterised by the type of device to be heated or cooled}
- 2023/4025 {Base discrete devices, e.g. presspack, disc-type transistors}
- 2023/4031 {Packaged discrete devices, e.g. to-3 housings, diodes}
- 2023/4037 {characterised by thermal path or place of attachment of heatsink}
- 2023/4043 {heatsink to have chip}
- 2023/405 {heatsink to package}
- 2023/4056 {heatsink to additional heatsink}
- 2023/4062 {heatsink to or through board or cabinet}
- 2023/4068 {Heatconductors between device and heatsink, e.g. compliant heat-spreaders, heat-conducting bands}
- 2023/4075 {Mechanical elements}
- 2023/4081 {Compliant clamping elements not primarily serving heat-conduction}
- 2023/4087 {Mounting accessories, interposers, clamping or screwing parts}
- 23/4093 . . . {Snap-on arrangements, e.g. clips}
- 23/42 . . Fillings or auxiliary members in containers {or encapsulations} selected or arranged to facilitate heating or cooling ({heating [H01L 23/345](#)}; characterised by selection of materials for the device [H01L 23/373](#))
- 23/427 . . . Cooling by change of state, e.g. use of heat pipes {(by liquefied gas [H01L 23/445](#))}
- 23/4275 {by melting or evaporation of solids}
- 23/433 . . . Auxiliary members {in containers} characterised by their shape, e.g. pistons
- 23/4332 {Bellows}
- 23/4334 {Auxiliary members in encapsulations ([H01L 23/49568](#) takes precedence)}
- 23/4336 {in combination with jet impingement}

- 23/4338 {Pistons, e.g. spring-loaded members}
- 23/44 . . the complete device being wholly immersed in a fluid other than air {(H01L 23/427 takes precedence)}
- 23/445 . . . {the fluid being a liquefied gas, e.g. in a cryogenic vessel}
- 23/46 . . involving the transfer of heat by flowing fluids (H01L 23/42, H01L 23/44 take precedence)
- 23/467 . . . by flowing gases, e.g. air {(H01L 23/473 takes precedence)}
- 23/473 . . . by flowing liquids {(H01L 23/4332, H01L 23/4338 take precedence)}
- 23/4735 {Jet impingement (H01L 23/4336 takes precedence)}
- 23/48 . . Arrangements for conducting electric current to or from the solid state body in operation, e.g. leads, terminal arrangements (in general H01R); {Selection of materials therefor}
- NOTE**
- Arrangements for connecting or disconnecting semiconductor or other solid state bodies, or methods related thereto, other than those arrangements or methods covered by the following subgroups, are covered by H01L 24/00
- 23/481 . . {Internal lead connections, e.g. via connections, feedthrough structures}
- 23/482 . . consisting of lead-in layers inseparably applied to the semiconductor body {(electrodes H01L 29/40)}
- 23/4821 . . . {Bridge structure with air gap}
- 23/4822 . . . {Beam leads}
- 23/4824 . . . {Pads with extended contours, e.g. grid structure, branch structure, finger structure}
- 23/4825 . . . {for devices consisting of semiconductor layers on insulating or semi-insulating substrates, e.g. silicon on sapphire devices, i.e. SOS}
- 23/4827 . . . {Materials}
- 23/4828 {Conductive organic material or pastes, e.g. conductive adhesives, inks}
- 23/485 . . . consisting of layered constructions comprising conductive layers and insulating layers, e.g. planar contacts {(H01L 23/4821, H01L 23/4822, H01L 23/4824, H01L 23/4825 take precedence; materials H01L 23/532, bond pads H01L 24/02, bump connectors H01L 24/10)}
- 23/4855 {Overhang structure}
- 23/488 . . consisting of soldered {or bonded} constructions {(bump connectors H01L 24/01)}
- 23/49 . . . wire-like {arrangements or pins or rods (using optical fibres H01L 23/48; pins attached to insulating substrates H01L 23/49811)}
- 23/492 . . . Bases or plates {or solder therefor}
- 23/4922 {having a heterogeneous or anisotropic structure}
- 23/4924 {characterised by the materials}
- 23/4926 {the materials containing semiconductor material}
- 23/4928 {the materials containing carbon}
- 23/495 . . . Lead-frames {or other flat leads (H01L 23/498 takes precedence; lead frame interconnections between components H01L 23/52)}
- 23/49503 {characterised by the die pad}
- 23/49506 {an insulative substrate being used as a diepad, e.g. ceramic, plastic (H01L 23/49531 takes precedence)}
- 23/4951 {Chip-on-leads or leads-on-chip techniques, i.e. inner lead fingers being used as die pad}
- 23/49513 {having bonding material between chip and die pad}
- 23/49517 {Additional leads}
- 23/4952 {the additional leads being a bump or a wire}
- 23/49524 {the additional leads being a tape carrier or flat leads}
- 23/49527 {the additional leads being a multilayer}
- 23/49531 {the additional leads being a wiring board}
- 23/49534 {Multi-layer}
- 23/49537 {Plurality of lead frames mounted in one device}
- 23/49541 {Geometry of the lead-frame}
- 23/49544 {Deformation absorbing parts in the lead frame plane, e.g. meanderline shape (H01L 23/49562 takes precedence)}
- 23/49548 {Cross section geometry (H01L 23/49562 takes precedence)}
- 23/49551 {characterised by bent parts}
- 23/49555 {the bent parts being the outer leads}
- 23/49558 {Insulating layers on lead frames, e.g. bridging members}
- 23/49562 {for devices being provided for in H01L 29/00}
- 23/49565 {Side rails of the lead frame, e.g. with perforations, sprocket holes}
- 23/49568 {specifically adapted to facilitate heat dissipation}
- 23/49572 {consisting of thin flexible metallic tape with or without a film carrier (H01L 23/49503 - H01L 23/49568 and H01L 23/49575 - H01L 23/49579 take precedence)}
- 23/49575 {Assemblies of semiconductor devices on lead frames}
- 23/49579 {characterised by the materials of the lead frames or layers thereon}
- 23/49582 {Metallic layers on lead frames}
- 23/49586 {Insulating layers on lead frames}
- 23/49589 {Capacitor integral with or on the leadframe}
- 23/49593 {Battery in combination with a leadframe}
- 23/49596 {Oscillators in combination with lead-frames}
- 23/498 . . . Leads, {i.e. metallisations or lead-frames} on insulating substrates, {e.g. chip carriers (shape of the substrate H01L 23/13)}
- 23/49805 {the leads being also applied on the sidewalls or the bottom of the substrate, e.g. leadless packages for surface mounting}
- 23/49811 {Additional leads joined to the metallisation on the insulating substrate, e.g. pins, bumps, wires, flat leads (H01L 23/49827 takes precedence)}
- 23/49816 {Spherical bumps on the substrate for external connection, e.g. ball grid arrays [BGA]}

- 23/49822 {Multilayer substrates (multilayer metallisation on monolayer substrate [H01L 23/498](#))}
- 23/49827 {Via connections through the substrates, e.g. pins going through the substrate, coaxial cables ([H01L 23/49822](#), [H01L 23/49833](#), [H01L 23/4985](#), [H01L 23/49861](#) take precedence)}
- 23/49833 {the chip support structure consisting of a plurality of insulating substrates}
- 23/49838 {Geometry or layout}
- 23/49844 {for devices being provided for in [H01L 29/00](#)}
- 23/4985 {Flexible insulating substrates ([H01L 23/49572](#) and [H01L 23/49855](#) take precedence)}
- 23/49855 {for flat-cards, e.g. credit cards ([cards per se G06K 19/00](#))}
- 23/49861 {Lead-frames fixed on or encapsulated in insulating substrates ([H01L 23/4985](#), [H01L 23/49805](#) take precedence)}
- 23/49866 {characterised by the materials (materials of the substrates [H01L 23/14](#), of the lead-frames [H01L 23/49579](#))}
- 23/49872 {the conductive materials containing semiconductor material}
- 23/49877 {Carbon, e.g. fullerenes (superconducting fullerenes [H01L 39/123](#))}
- 23/49883 {the conductive materials containing organic materials or pastes, e.g. for thick films (for printed circuits [H05K 1/092](#))}
- 23/49888 {the conductive materials containing superconducting material}
- 23/49894 {Materials of the insulating layers or coatings}
- 23/50 . . for integrated circuit devices, {e.g. power bus, number of leads} ([H01L 23/482](#) - [H01L 23/498](#) take precedence)
- 23/52 . . Arrangements for conducting electric current within the device in operation from one component to another {, i.e. interconnections, e.g. wires, lead frames (optical interconnections [G02B 6/00](#))}
- 23/522 . . including external interconnections consisting of a multilayer structure of conductive and insulating layers inseparably formed on the semiconductor body
- 23/5221 . . . {Crossover interconnections}
- 23/5222 . . . {Capacitive arrangements or effects of, or between wiring layers (other capacitive arrangements [H01L 23/642](#))}
- 23/5223 . . . {Capacitor integral with wiring layers}
- 23/5225 . . . {Shielding layers formed together with wiring layers}
- 23/5226 . . . {Via connections in a multilevel interconnection structure}
- 23/5227 . . . {Inductive arrangements or effects of, or between, wiring layers (other inductive arrangements [H01L 23/645](#))}
- 23/5228 . . . {Resistive arrangements or effects of, or between, wiring layers (other resistive arrangements [H01L 23/647](#))}
- 23/525 . . . with adaptable interconnections
- 23/5252 {comprising anti-fuses, i.e. connections having their state changed from non-conductive to conductive}
- 23/5254 {the change of state resulting from the use of an external beam, e.g. laser beam or ion beam}
- 23/5256 {comprising fuses, i.e. connections having their state changed from conductive to non-conductive}
- 23/5258 {the change of state resulting from the use of an external beam, e.g. laser beam or ion beam}
- 23/528 . . . {Geometry or} layout of the interconnection structure {([H01L 27/0207](#) takes precedence; algorithms [G06F 17/50](#))}
- 23/5283 {Cross-sectional geometry}
- 23/5286 {Arrangements of power or ground buses}
- 23/532 . . . characterised by the materials
- 23/53204 {Conductive materials}
- 23/53209 {based on metals, e.g. alloys, metal silicides ([H01L 23/53285](#) takes precedence)}
- 23/53214 {the principal metal being aluminium}
- 23/53219 {Aluminium alloys}
- 23/53223 {Additional layers associated with aluminium layers, e.g. adhesion, barrier, cladding layers}
- 23/53228 {the principal metal being copper}
- 23/53233 {Copper alloys}
- 23/53238 {Additional layers associated with copper layers, e.g. adhesion, barrier, cladding layers}
- 23/53242 {the principal metal being a noble metal, e.g. gold}
- 23/53247 {Noble-metal alloys}
- 23/53252 {Additional layers associated with noble-metal layers, e.g. adhesion, barrier, cladding layers}
- 23/53257 {the principal metal being a refractory metal}
- 23/53261 {Refractory-metal alloys}
- 23/53266 {Additional layers associated with refractory-metal layers, e.g. adhesion, barrier, cladding layers}
- 23/53271 {containing semiconductor material, e.g. polysilicon}
- 23/53276 {containing carbon, e.g. fullerenes (superconducting fullerenes [H01L 39/123](#))}
- 23/5328 {containing conductive organic materials or pastes, e.g. conductive adhesives, inks}
- 23/53285 {containing superconducting materials}
- 23/5329 {Insulating materials}
- 23/53295 {Stacked insulating layers}
- 23/535 . . including internal interconnections, e.g. cross-under constructions {(internal lead connections [H01L 23/481](#))}
- 23/538 . . the interconnection structure between a plurality of semiconductor chips being formed on, or in, insulating substrates {([H05K](#) takes precedence; manufacture or treatment [H01L 21/4846](#)) ; mountings per se [H01L 23/12](#); {materials [H01L 23/49866](#))}
- 23/5381 . . . {Crossover interconnections, e.g. bridge stepovers}
- 23/5382 . . . {Adaptable interconnections, e.g. for engineering changes}

- 23/5383 . . . {Multilayer substrates ([H01L 23/5385](#) takes precedence; multilayer metallisation on monolayer substrates [H01L 23/538](#))}
- 23/5384 . . . {Conductive vias through the substrate with or without pins, e.g. buried coaxial conductors ([H01L 23/5383](#), [H01L 23/5385](#) take precedence; pins attached to insulating substrates [H01L 23/49811](#))}
- 23/5385 . . . {Assembly of a plurality of insulating substrates}
- 23/5386 . . . {Geometry or layout of the interconnection structure}
- 23/5387 . . . {Flexible insulating substrates ([H01L 23/5388](#) takes precedence)}
- 23/5388 . . . {for flat cards, e.g. credit cards ([cards per se G06K 19/00](#))}
- 23/5389 . . . {the chips being integrally enclosed by the interconnect and support structures}
- 23/544 . Marks applied to semiconductor devices {or parts}, e.g. registration marks, {alignment structures, wafer maps (test patterns for characterising or monitoring manufacturing processes [H01L 22/00](#))}
- NOTE**
- When classifying in group [H01L 23/544](#), details are to be further indexed by using the indexing codes chosen from [H01L 2223/544](#) and subgroups
- 23/552 . Protection against radiation, e.g. light {or electromagnetic waves}
- 23/556 . . against alpha rays
- 23/562 . {Protection against mechanical damage ([H01L 23/02](#), [H01L 23/28](#) take precedence)}
- 23/564 . {Details not otherwise provided for, e.g. protection against moisture ([getters H01L 23/26](#))}
- 23/57 . {Protection from inspection, reverse engineering or tampering}
- 23/573 . . {using passive means}
- 23/576 . . {using active circuits}
- 23/58 . Structural electrical arrangements for semiconductor devices not otherwise provided for {, e.g. in combination with batteries ([H01L 23/49593](#), [H01L 23/49596](#) take precedence)}
- 23/585 . . {comprising conductive layers or plates or strips or rods or rings ([H01L 23/60](#), [H01L 23/62](#), [H01L 23/64](#), [H01L 23/66](#) take precedence)}
- 23/60 . . Protection against electrostatic charges or discharges, e.g. Faraday shields (in general [H05F](#))
- 23/62 . . Protection against overvoltage, e.g. fuses, shunts
- 23/64 . . Impedance arrangements
- 23/642 . . . {Capacitive arrangements ([H01L 23/49589](#), [H01L 23/645](#), [H01L 23/647](#), [H01L 23/66](#) take precedence; capacitive effects between wiring layers on the semiconductor body [H01L 23/5222](#))}
- 23/645 . . . {Inductive arrangements ([H01L 23/647](#), [H01L 23/66](#) take precedence)}
- 23/647 . . . {Resistive arrangements ([H01L 23/66](#), [H01L 23/62](#) take precedence)}
- 23/66 . . . High-frequency adaptations

NOTE

When classifying in group [H01L 23/66](#), details are to be further indexed by using the

indexing codes chosen from [H01L 2223/66](#) and subgroups

24/00

{Arrangements for connecting or disconnecting semiconductor or solid-state bodies; Methods or apparatus related thereto}

NOTES

1. This group does not cover:

- details of semiconductor bodies or of electrodes of devices provided for in group [H01L 29/00](#), which details are covered by that group;
- details peculiar to devices provided for in a single main group of groups [H01L 31/00](#) - [H01L 51/00](#), which details are covered by those groups.
- printed circuits, which are covered by groups [H05K 1/00](#) - [H05K 1/189](#);
- apparatus or manufacturing processes for printed circuits, which are covered by groups [H05K 3/00](#) - [H05K 3/4685](#);
- manufacture or treatment of parts, which are covered by group [H01L 21/48](#) and subgroups except [H01L 21/4885](#) - [H01L 21/4896](#);
- assemblies of semiconductor devices, which are covered by groups [H01L 21/50](#) - [H01L 21/568](#);
- applying interconnections to be used for carrying current between separate components within a device, which is covered by group [H01L 21/768](#) and subgroups;
- containers or seals, which are covered by groups [H01L 23/02](#) - [H01L 23/10](#);
- mountings, which are covered by groups [H01L 23/12](#) - [H01L 23/15](#) and subgroups;
- arrangements for cooling, heating, ventilating or temperature compensation, which are covered by groups [H01L 23/34](#) - [H01L 23/4735](#);
- arrangements for conducting electric current, which are covered by groups [H01L 23/48](#) - [H01L 23/50](#), and by groups [H01L 23/52](#) - [H01L 23/5389](#);
- structural electrical arrangements, which are covered by groups [H01L 24/80](#) - [H01L 23/66](#);
- assemblies of semiconductor or other solid state devices, which are covered by groups [H01L 25/00](#) - [H01L 25/18](#).

2. In this group the following indexing codes are used : [H01L 24/00](#), [H01L 2224/00](#), [H01L 2924/00](#), and subgroups thereof

24/01

- {Means for bonding being attached to, or being formed on, the surface to be connected, e.g. chip-to-package, die-attach, "first-level" interconnects; Manufacturing methods related thereto}

- 24/02 . . . {Bonding areas (on insulating substrates, e.g. chip carriers, [H01L 23/49816](#), [H01L 23/49838](#), [H01L 23/5389](#)); Manufacturing methods related thereto}
- WARNING**
- Groups [H01L 24/02](#) – [H01L 24/09](#) are incomplete pending reclassification of documents from groups [H01L 24/02](#) and [H01L 24/10](#).
- Groups [H01L 24/02](#) – [H01L 24/09](#) and [H01L 24/10](#) should be considered in order to perform a complete search.
- 24/03 . . . {Manufacturing methods}
- 24/04 . . . {Structure, shape, material or disposition of the bonding areas prior to the connecting process}
- 24/05 {of an individual bonding area}
- 24/06 {of a plurality of bonding areas}
- 24/07 . . . {Structure, shape, material or disposition of the bonding areas after the connecting process}
- 24/08 {of an individual bonding area}
- 24/09 {of a plurality of bonding areas}
- 24/10 . . {Bump connectors (bumps on insulating substrates, e.g. chip carriers, [H01L 23/49816](#)); Manufacturing methods related thereto}
- 24/11 . . . {Manufacturing methods (for bumps on insulating substrates [H01L 21/4853](#))}
- 24/12 . . . {Structure, shape, material or disposition of the bump connectors prior to the connecting process}
- 24/13 {of an individual bump connector}
- 24/14 {of a plurality of bump connectors}
- 24/15 . . . {Structure, shape, material or disposition of the bump connectors after the connecting process}
- 24/16 {of an individual bump connector}
- 24/17 {of a plurality of bump connectors}
- 24/18 . . {High density interconnect [HDI] connectors; Manufacturing methods related thereto (interconnection structure between a plurality of semiconductor chips [H01L 23/5389](#))}
- WARNING**
- Groups [H01L 24/18](#) – [H01L 24/25](#) are incomplete pending reclassification of documents from groups [H01L 24/18](#) and [H01L 24/82](#).
- Groups [H01L 24/18](#) – [H01L 24/25](#) and [H01L 24/82](#) should be considered in order to perform a complete search.
- 24/19 . . . {Manufacturing methods of high density interconnect preforms}
- 24/20 . . . {Structure, shape, material or disposition of high density interconnect preforms}
- 24/23 . . . {Structure, shape, material or disposition of the high density interconnect connectors after the connecting process}
- 24/24 {of an individual high density interconnect connector}
- 24/25 {of a plurality of high density interconnect connectors}
- 24/26 . . {Layer connectors, e.g. plate connectors, solder or adhesive layers; Manufacturing methods related thereto}
- 24/27 . . . {Manufacturing methods}
- 24/28 . . . {Structure, shape, material or disposition of the layer connectors prior to the connecting process}
- 24/29 {of an individual layer connector}
- 24/30 {of a plurality of layer connectors}
- 24/31 . . . {Structure, shape, material or disposition of the layer connectors after the connecting process}
- 24/32 {of an individual layer connector}
- 24/33 {of a plurality of layer connectors}
- 24/34 . . {Strap connectors, e.g. copper straps for grounding power devices; Manufacturing methods related thereto}
- WARNING**
- Groups [H01L 24/34](#) – [H01L 24/41](#) are incomplete pending reclassification of documents from groups [H01L 24/34](#), [H01L 24/01](#), [H01L 24/42](#), and [H01L 24/85](#).
- Groups [H01L 24/34](#) – [H01L 24/41](#) and [H01L 24/01](#), [H01L 24/42](#), [H01L 24/85](#) should be considered in order to perform a complete search.
- 24/35 . . . {Manufacturing methods}
- 24/36 . . . {Structure, shape, material or disposition of the strap connectors prior to the connecting process}
- 24/37 {of an individual strap connector}
- 24/38 {of a plurality of strap connectors}
- 24/39 . . . {Structure, shape, material or disposition of the strap connectors after the connecting process}
- 24/40 {of an individual strap connector}
- 24/41 {of a plurality of strap connectors}
- 24/42 . . {Wire connectors; Manufacturing methods related thereto}
- 24/43 . . . {Manufacturing methods}
- WARNING**
- Group [H01L 24/43](#) is incomplete pending reclassification of documents from groups [H01L 21/4885](#) and [H01L 24/42](#), [H01L 24/85](#).
- Groups [H01L 24/43](#) and [H01L 21/4885](#), [H01L 24/42](#), [H01L 24/85](#) should be considered in order to perform a complete search.
- 24/44 . . . {Structure, shape, material or disposition of the wire connectors prior to the connecting process}
- WARNING**
- Group [H01L 24/44](#) is incomplete pending reclassification of documents from groups [H01L 24/42](#) and [H01L 24/85](#).
- Groups [H01L 24/44](#) and [H01L 24/42](#), [H01L 24/85](#) should be considered in order to perform a complete search.
- 24/45 {of an individual wire connector}
- 24/46 {of a plurality of wire connectors}

- 24/47 . . . {Structure, shape, material or disposition of the wire connectors after the connecting process}
- WARNING**
- Group [H01L 24/47](#) is incomplete pending reclassification of documents from groups [H01L 24/42](#) and [H01L 24/85](#).
- Groups [H01L 24/47](#) and [H01L 24/42](#), [H01L 24/85](#) should be considered in order to perform a complete search.
- 24/48 {of an individual wire connector}
- 24/49 {of a plurality of wire connectors}
- 24/50 . . {Tape automated bonding [TAB] connectors, i.e. film carriers; Manufacturing methods related thereto (thin flexible metallic tape with or without a film carrier [H01L 23/49572](#), flexible insulating substrates [H01L 23/4985](#), [H01L 23/5387](#))}
- WARNING**
- Group [H01L 24/50](#) is incomplete pending reclassification of documents from group [H01L 24/86](#).
- Groups [H01L 24/50](#) and [H01L 24/86](#) should be considered in order to perform a complete search.
- 24/63 . . {Connectors not provided for in any of the groups [H01L 24/10](#) - [H01L 24/50](#) and subgroups; Manufacturing methods related thereto}
- 24/64 . . . {Manufacturing methods}
- 24/65 . . . {Structure, shape, material or disposition of the connectors prior to the connecting process}
- 24/66 {of an individual connector}
- 24/67 {of a plurality of connectors}
- 24/68 . . . {Structure, shape, material or disposition of the connectors after the connecting process}
- 24/69 {of an individual connector}
- 24/70 {of a plurality of connectors}
- 24/71 . {Means for bonding not being attached to, or not being formed on, the surface to be connected (holders for supporting the complete device in operation [H01L 23/32](#))}
- 24/72 . . {Detachable connecting means consisting of mechanical auxiliary parts connecting the device, e.g. pressure contacts using springs or clips}
- 24/73 . {Means for bonding being of different types provided for in two or more of groups [H01L 24/10](#), [H01L 24/18](#), [H01L 24/26](#), [H01L 24/34](#), [H01L 24/42](#), [H01L 24/50](#), [H01L 24/63](#), [H01L 24/71](#)}
- 24/74 . {Apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies}
- 24/741 . . {Apparatus for manufacturing means for bonding, e.g. connectors}
- 24/742 . . . {Apparatus for manufacturing bump connectors}
- 24/743 . . . {Apparatus for manufacturing layer connectors}
- 24/744 . . . {Apparatus for manufacturing strap connectors}
- 24/745 . . . {Apparatus for manufacturing wire connectors}
- 24/75 . . {Apparatus for connecting with bump connectors or layer connectors}
- 24/76 . . {Apparatus for connecting with build-up interconnects}
- 24/77 . . {Apparatus for connecting with strap connectors}
- 24/78 . . {Apparatus for connecting with wire connectors}
- 24/79 . . {Apparatus for Tape Automated Bonding [TAB]}
- 24/799 . . {Apparatus for disconnecting}
- 24/80 . {Methods for connecting semiconductor or other solid state bodies using means for bonding being attached to, or being formed on, the surface to be connected}
- 24/81 . . {using a bump connector}
- 24/82 . . {by forming build-up interconnects at chip-level, e.g. for high density interconnects [HDI] (interconnection structure between a plurality of semiconductor chips [H01L 23/5389](#))}
- 24/83 . . {using a layer connector}
- 24/84 . . {using a strap connector}
- WARNING**
- Group [H01L 24/84](#) is incomplete pending reclassification of documents from group [H01L 24/85](#).
- Group [H01L 24/84](#) and [H01L 24/85](#) should be considered in order to perform a complete search.
- 24/85 . . {using a wire connector (wire bonding in general [B23K 20/004](#))}
- 24/86 . . {using tape automated bonding [TAB]}
- 24/89 . . {using at least one connector not provided for in any of the groups [H01L 24/81](#) - [H01L 24/86](#)}
- 24/90 . {Methods for connecting semiconductor or solid state bodies using means for bonding not being attached to, or not being formed on, the body surface to be connected, e.g. pressure contacts using springs or clips}
- 24/91 . {Methods for connecting semiconductor or solid state bodies including different methods provided for in two or more of groups [H01L 24/80](#) - [H01L 24/90](#)}
- 24/92 . . {Specific sequence of method steps}
- 24/93 . {Batch processes}
- WARNING**
- Group [H01L 24/93](#) is incomplete pending reclassification of documents from groups [H01L 24/80](#) - [H01L 24/90](#).
- Groups [H01L 24/93](#) and [H01L 24/80](#) - [H01L 24/90](#) should be considered in order to perform a complete search.
- 24/94 . . {at wafer-level, i.e. with connecting carried out on a wafer comprising a plurality of undiced individual devices}
- 24/95 . . {at chip-level, i.e. with connecting carried out on a plurality of singulated devices, i.e. on diced chips}
- 24/96 . . . {the devices being encapsulated in a common layer, e.g. neo-wafer or pseudo-wafer, said common layer being separable into individual assemblies after connecting}
- 24/97 . . . {the devices being connected to a common substrate, e.g. interposer, said common substrate being separable into individual assemblies after connecting}

24/98	• {Methods for disconnecting semiconductor or solid-state bodies}	25/105	• . . . {the devices being of a type provided for in group H01L 27/00 }
25/00	Assemblies consisting of a plurality of individual semiconductor or other solid state devices {; Multistep manufacturing processes thereof} (devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00 ; photovoltaic modules or arrays of photovoltaic cells H01L 31/042 {; panels or arrays of photo electrochemical cells H01G 9/2068 })		NOTE When classifying in group H01L 25/105 , details of the assemblies are to be further indexed by using the indexing codes chosen from H01L 2225/1005 and subgroups
25/03	• all the devices being of a type provided for in the same subgroup of groups H01L 27/00 - H01L 51/00 , e.g. assemblies of rectifier diodes	25/11	• . . . the devices being of a type provided for in group H01L 29/00
25/04	• . the devices not having separate containers		NOTE Group H01L 25/112 takes precedence over groups H01L 25/115 and H01L 25/117
25/041	• . . . {the devices being of a type provided for in group H01L 31/00 }	25/112	• {Mixed assemblies}
25/042	• {the devices being arranged next to each other (solar cells H01L 31/042)}	25/115	• {the devices being arranged next to each other}
25/043	• {Stacked arrangements of devices}	25/117	• {Stacked arrangements of devices}
25/046	• . . . {the devices being of a type provided for in group H01L 51/00 }	25/13	• . . . the devices being of a type provided for in group H01L 33/00
25/047	• {the devices being of a type provided for in group H01L 51/42 , e.g. photovoltaic modules based on organic solar cells}	25/16	• the devices being of types provided for in two or more different main groups of H01L 27/00 - H01L 49/00 {and H01L 51/00 }, e.g. forming hybrid circuits {(interconnections for hybrid circuits H01L 23/5389)}
25/048	• {the devices being of a type provided for in group H01L 51/50 , e.g. assembly of organic light emitting devices}	25/162	• . {the devices being mounted on two or more different substrates}
25/065	• . . . the devices being of a type provided for in group H01L 27/00	25/165	• . {Containers}
	NOTE Group H01L 25/0652 takes precedence over groups H01L 25/0655 and H01L 25/0657	25/167	• . {comprising optoelectronic devices, e.g. LED, photodiodes}
25/0652	• {the devices being arranged next and on each other, i.e. mixed assemblies}	25/18	• the devices being of types provided for in two or more different subgroups of the same main group of groups H01L 27/00 - H01L 51/00 {(comprising devices provided for in H01L 27/144 and subgroups, see H01L 27/144 and subgroups)}
25/0655	• {the devices being arranged next to each other}	25/50	• {Multistep manufacturing processes of assemblies consisting of devices, each device being of a type provided for in group H01L 27/00 or H01L 29/00 (H01L 21/50 takes precedence)}
25/0657	• {Stacked arrangements of devices}		
25/07	• . . . the devices being of a type provided for in group H01L 29/00	27/00	Devices consisting of a plurality of semiconductor or other solid-state components formed in or on a common substrate (details thereof H01L 23/00 , H01L 29/00 - H01L 51/00 ; assemblies consisting of a plurality of individual solid state devices H01L 25/00)
	NOTE Group H01L 25/071 takes precedence over groups H01L 25/072 - H01L 25/074		NOTES
25/071	• {the devices being arranged next and on each other, i.e. mixed assemblies}		1. In this group, with the exception of groups H01L 27/115 - H01L 27/11597 , the last place priority rule is applied, i.e. at each hierarchical level, in the absence of an indication to the contrary, classification is made in the last appropriate place.
25/072	• {the devices being arranged next to each other}		2. When classifying in this group, subject matter relating to electrically programmable read-only memories is classified in group H01L 27/115 , irrespective of the last place priority rule.
25/073	• {Apertured devices mounted on one or more rods passed through the apertures}		
25/074	• {Stacked arrangements of non-apertured devices}		
25/075	• . . . the devices being of a type provided for in group H01L 33/00		
25/0753	• {the devices being arranged next to each other}		
25/0756	• {Stacked arrangements of devices}		
25/10	• . the devices having separate containers		

27/01	<ul style="list-style-type: none"> comprising only passive thin-film or thick-film elements formed on a common insulating substrate {passive two-terminal components without a potential-jump or surface barrier for integrated circuits, details thereof and multistep manufacturing processes therefor H01L 28/00} <p>NOTE</p> <p>In groups H01L 27/01 - H01L 27/26, in the absence of an indication to the contrary, classification is made in the last appropriate place.</p>	27/0277	<ul style="list-style-type: none"> {involving a parasitic bipolar transistor triggered by the local electrical biasing of the layer acting as base of said parasitic bipolar transistor}
27/013	<ul style="list-style-type: none"> {Thick-film circuits} 	27/0281	<ul style="list-style-type: none"> {field effect transistors in a "Darlington-like" configuration}
27/016	<ul style="list-style-type: none"> {Thin-film circuits} 	27/0285	<ul style="list-style-type: none"> {bias arrangements for gate electrode of field effect transistors, e.g. RC networks, voltage partitioning circuits (H01L 27/0281 takes precedence)}
27/02	<ul style="list-style-type: none"> including semiconductor components specially adapted for rectifying, oscillating, amplifying or switching and having at least one potential-jump barrier or surface barrier; including integrated passive circuit elements with at least one potential-jump barrier or surface barrier 	27/0288	<ul style="list-style-type: none"> {using passive elements as protective elements, e.g. resistors, capacitors, inductors, spark-gaps}
27/0203	<ul style="list-style-type: none"> {Particular design considerations for integrated circuits} 	27/0292	<ul style="list-style-type: none"> {using a specific configuration of the conducting means connecting the protective devices, e.g. ESD buses}
27/0207	<ul style="list-style-type: none"> {Geometrical layout of the components, e.g. computer aided design; custom LSI, semi-custom LSI, standard cell technique} 	27/0296	<ul style="list-style-type: none"> {involving a specific disposition of the protective devices}
27/0211	<ul style="list-style-type: none"> {adapted for requirements of temperature} 	27/04	<ul style="list-style-type: none"> the substrate being a semiconductor body
27/0214	<ul style="list-style-type: none"> {for internal polarisation, e.g. I2L} 	27/06	<ul style="list-style-type: none"> including a plurality of individual components in a non-repetitive configuration
27/0218	<ul style="list-style-type: none"> {of field effect structures} 	27/0605	<ul style="list-style-type: none"> {integrated circuits made of compound material, e.g. A_{III}B_V}
27/0222	<ul style="list-style-type: none"> {Charge pumping, substrate bias generation structures} 	27/0611	<ul style="list-style-type: none"> {integrated circuits having a two-dimensional layout of components without a common active region}
27/0225	<ul style="list-style-type: none"> {Charge injection in static induction transistor logic structures [SITL]} 	27/0617	<ul style="list-style-type: none"> {comprising components of the field-effect type (H01L 27/0251 takes precedence)}
27/0229	<ul style="list-style-type: none"> {of bipolar structures} 	27/0623	<ul style="list-style-type: none"> {in combination with bipolar transistors}
27/0233	<ul style="list-style-type: none"> {Integrated injection logic structures [I2L]} 	27/0629	<ul style="list-style-type: none"> {in combination with diodes, or resistors, or capacitors}
27/0237	<ul style="list-style-type: none"> {using vertical injector structures} 	27/0635	<ul style="list-style-type: none"> {in combination with bipolar transistors and diodes, or resistors, or capacitors}
27/024	<ul style="list-style-type: none"> {using field effect injector structures} 	27/0641	<ul style="list-style-type: none"> {without components of the field effect type}
27/0244	<ul style="list-style-type: none"> {I2L structures integrated in combination with analog structures} 	27/0647	<ul style="list-style-type: none"> {Bipolar transistors in combination with diodes, or capacitors, or resistors, e.g. vertical bipolar transistor and bipolar lateral transistor and resistor}
27/0248	<ul style="list-style-type: none"> {for electrical or thermal protection, e.g. electrostatic discharge [ESD] protection} 	27/0652	<ul style="list-style-type: none"> {Vertical bipolar transistor in combination with diodes, or capacitors, or resistors}
27/0251	<ul style="list-style-type: none"> {for MOS devices} 	27/0658	<ul style="list-style-type: none"> {Vertical bipolar transistor in combination with resistors or capacitors}
27/0255	<ul style="list-style-type: none"> {using diodes as protective elements} 	27/0664	<ul style="list-style-type: none"> {Vertical bipolar transistor in combination with diodes}
27/0259	<ul style="list-style-type: none"> {using bipolar transistors as protective elements} 	27/067	<ul style="list-style-type: none"> {Lateral bipolar transistor in combination with diodes, or capacitors, or resistors}
27/0262	<ul style="list-style-type: none"> {including a PNP transistor and a NPN transistor, wherein each of said transistors has its base coupled to the collector of the other transistor, e.g. silicon controlled rectifier [SCR] devices} 	27/0676	<ul style="list-style-type: none"> {comprising combinations of diodes, or capacitors or resistors}
27/0266	<ul style="list-style-type: none"> {using field effect transistors as protective elements} 	27/0682	<ul style="list-style-type: none"> {comprising combinations of capacitors and resistors}
27/027	<ul style="list-style-type: none"> {specially adapted to provide an electrical current path other than the field effect induced current path} 	27/0688	<ul style="list-style-type: none"> {Integrated circuits having a three-dimensional layout}
27/0274	<ul style="list-style-type: none"> {involving a parasitic bipolar transistor triggered by the electrical biasing of the gate electrode of the field effect transistor, e.g. gate coupled transistors} 	27/0694	<ul style="list-style-type: none"> {comprising components formed on opposite sides of a semiconductor substrate}
		27/07	<ul style="list-style-type: none"> the components having an active region in common

27/0705 {comprising components of the field effect type}	27/0886 {including transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
27/0711 {in combination with bipolar transistors and diodes, or capacitors, or resistors}	27/092 complementary MIS field-effect transistors
27/0716 {in combination with vertical bipolar transistors and diodes, or capacitors, or resistors}	27/0921 {Means for preventing a bipolar, e.g. thyristor, action between the different transistor regions, e.g. Latchup prevention}
27/0722 {in combination with lateral bipolar transistors and diodes, or capacitors, or resistors}	27/0922 {Combination of complementary transistors having a different structure, e.g. stacked CMOS, high-voltage and low-voltage CMOS}
27/0727 {in combination with diodes, or capacitors or resistors}	27/0924 {including transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
27/0733 {in combination with capacitors only}	27/0925 {comprising an N-well only in the substrate}
27/0738 {in combination with resistors only}	27/0927 {comprising a P-well only in the substrate}
27/0744 {without components of the field effect type}	27/0928 {comprising both N- and P- wells in the substrate, e.g. twin-tub}
27/075 {Bipolar transistors in combination with diodes, or capacitors, or resistors, e.g. lateral bipolar transistor, and vertical bipolar transistor and resistor}	27/095 the components being Schottky barrier gate field-effect transistors
27/0755 {Vertical bipolar transistor in combination with diodes, or capacitors, or resistors}	27/098 the components being PN junction gate field-effect transistors
27/0761 {Vertical bipolar transistor in combination with diodes only}	27/10	. . . including a plurality of individual components in a repetitive configuration
27/0766 {with Schottky diodes only}	27/101 {including resistors or capacitors only}
27/0772 {Vertical bipolar transistor in combination with resistors only}	27/102 including bipolar components
27/0777 {Vertical bipolar transistor in combination with capacitors only}	27/1021 {including diodes only}
27/0783 {Lateral bipolar transistors in combination with diodes, or capacitors, or resistors}	27/1022 {including bipolar transistors}
27/0788 {comprising combinations of diodes or capacitors or resistors}	27/1023 {Bipolar dynamic random access memory structures}
27/0794 {Combinations of capacitors and resistors}	27/1024 {Arrays of single bipolar transistors only, e.g. read only memory structures}
27/08	. . . including only semiconductor components of a single kind	27/1025 {Static bipolar memory cell structures}
27/0802 {Resistors only}	27/1026 {Bipolar electrically programmable memory structures (using fuses H01L 23/525)}
27/0805 {Capacitors only}	27/1027 {Thyristors}
27/0808 {Varactor diodes}	27/1028 {Double base diodes}
27/0811 {MIS diodes}	27/105 including field-effect components
27/0814 {Diodes only}		
27/0817 {Thyristors only}		
27/082 including bipolar components only		
27/0821 {Combination of lateral and vertical transistors only}		
27/0823 {including vertical bipolar transistors only}		
27/0825 {Combination of vertical direct transistors of the same conductivity type having different characteristics,(e.g. Darlington transistors)}	27/1052 {Memory structures and multistep manufacturing processes therefor not provided for in groups H01L 27/1055 - H01L 27/112 }
27/0826 {Combination of vertical complementary transistors}	27/1055 {comprising charge coupled devices of the so-called bucket brigade type}
27/0828 {Combination of direct and inverse vertical transistors}	27/1057 {comprising charge coupled devices [CCD] or charge injection devices [CID]}
27/085 including field-effect components only		
27/088 the components being field-effect transistors with insulated gate		
27/0883 {Combination of depletion and enhancement field effect transistors}		

NOTE

In this group and its subgroups classification is made in any appropriate place

27/108	Dynamic random access memory structures	27/10876	{the transistor having a trench structure in the substrate (vertical transistor in combination with a capacitor formed in a substrate trench H01L 27/10864)}
		NOTE			
		In this group and its subgroups classification is made in any appropriate place	27/10879	{the transistor being of the FinFET type}
27/10802	{comprising floating-body transistors, e.g. floating-body cells}	27/10882	{with at least one step of making a data line}
27/10805	{with one-transistor one-capacitor memory cells}	27/10885	{with at least one step of making a bit line}
27/10808	{the storage electrode stacked over transistor}	27/10888	{with at least one step of making a bit line contact}
27/10811	{with bit line higher than capacitor}	27/10891	{with at least one step of making a word line}
27/10814	{with capacitor higher than bit line level}	27/10894	{with simultaneous manufacture of periphery and memory cells}
27/10817	{the storage electrode having multiple wings}	27/10897	{Peripheral structures}
27/1082	{the capacitor extending under transfer transistor area}	27/11	Static random access memory structures
27/10823	{the transistor having a trench structure in the substrate}	27/1104	{the load element being a MOSFET transistor}
27/10826	{the transistor being of the FinFET type}	27/1108	{the load element being a thin film transistor}
27/10829	{the capacitor being in a substrate trench}	27/1112	{the load element being a resistor (resistors for integrated circuits H01L 28/20, H01L 29/8605)}
27/10832	{the capacitor extending under or around transfer transistor area}	27/1116	{Peripheral circuit region}
27/10835	{having storage electrode extension stacked over transistor}	27/112	Read-only memory structures {[ROM] and multistep manufacturing processes therefor}
27/10838	{the capacitor and the transistor being in one trench}	27/11206	{Programmable ROM [PROM], e.g. memory cells comprising a transistor and a fuse or an antifuse}
27/10841	{the transistor being vertical}	27/11213	{ROM only}
27/10844	{Multistep manufacturing methods}	27/1122	{with source and drain on the same level, e.g. lateral transistors}
27/10847	{for structures comprising one transistor one-capacitor memory cells}	27/11226	{Source or drain contact programmed}
27/1085	{with at least one step of making the capacitor or connections thereto}	27/11233	{Gate programmed, e.g. different gate material or no gate}
27/10852	{the capacitor extending over the access transistor}	27/1124	{Gate contact programmed}
27/10855	{with at least one step of making a connection between transistor and capacitor, e.g. plug}	27/11246	{Gate dielectric programmed, e.g. different thickness}
27/10858	{the capacitor extending under the access transistor area}	27/11253	{Doping programmed, e.g. mask ROM}
27/10861	{the capacitor being in a substrate trench}	27/1126	{Entire channel doping programmed}
27/10864	{in combination with a vertical transistor}	27/11266	{Source or drain doping programmed}
27/10867	{with at least one step of making a connection between transistor and capacitor, e.g. buried strap}	27/11273	{with source and drain on different levels, e.g. vertical channel}
27/1087	{with at least one step of making the trench}	27/1128	{with transistors on different levels, e.g. 3D ROM}
27/10873	{with at least one step of making the transistor}	27/11286	{Peripheral circuit regions}
			27/11293	{of memory structures of the ROM-only type}
			27/115	Electrically programmable read-only memories; Multistep manufacturing processes therefor
			27/11502	with ferroelectric memory capacitors
			27/11504	characterised by the top-view layout
			27/11507	characterised by the memory core region

27/11509	characterised by the peripheral circuit region	27/11573	characterised by the peripheral circuit region
27/11512	characterised by the boundary region between the core and peripheral circuit regions	27/11575	characterised by the boundary region between the core and peripheral circuit regions
27/11514	characterised by the three-dimensional arrangements, e.g. with cells on different height levels	27/11578	characterised by three-dimensional arrangements, e.g. with cells on different height levels
27/11517	with floating gate	27/1158	with source and drain on different levels, e.g. with sloping channels
27/11519	characterised by the top-view layout	27/11582	the channels comprising vertical portions, e.g. U-shaped channels
27/11521	characterised by the memory core region (three-dimensional arrangements H01L 27/11551)	27/11585	with the gate electrodes comprising a layer used for its ferroelectric memory properties, e.g. metal-ferroelectric-semiconductor [MFS] or metal-ferroelectric-metal-insulator-semiconductor [MFMIS]
27/11524	with cell select transistors, e.g. NAND	27/11587	characterised by the top-view layout
27/11526	characterised by the peripheral circuit region	27/1159	characterised by the memory core region
27/11529	of memory regions comprising cell select transistors, e.g. NAND	27/11592	characterised by the peripheral circuit region
27/11531	Simultaneous manufacturing of periphery and memory cells	27/11595	characterised by the boundary region between core and peripheral circuit regions
27/11534	including only one type of peripheral transistor	27/11597	characterised by three-dimensional arrangements, e.g. cells on different height levels
27/11536	with a control gate layer also being used as part of the peripheral transistor	27/118	Masterslice integrated circuits
27/11539	with an inter-gate dielectric layer also being used as part of the peripheral transistor	27/11801	{using bipolar technology}
27/11541	with a floating-gate layer also being used as part of the peripheral transistor	27/11803	{using field effect technology}
27/11543	with a tunnel dielectric layer also being used as part of the peripheral transistor	2027/11805	{A3B5 or A3B6 gate arrays}
27/11546	including different types of peripheral transistor	27/11807	{CMOS gate arrays}
27/11548	characterised by the boundary region between the core and peripheral circuit regions	2027/11809	{Microarchitecture}
27/11551	characterised by three-dimensional arrangements, e.g. with cells on different height levels	2027/11811	{Basic cell P to N transistor count}
27/11553	with source and drain on different levels, e.g. with sloping channels	2027/11812	{4-T CMOS basic cell}
27/11556	the channels comprising vertical portions, e.g. U-shaped channels	2027/11814	{5-T CMOS basic cell}
27/11558	the control gate being a doped region, e.g. single-poly memory cells	2027/11816	{6-T CMOS basic cell}
27/1156	the floating gate being an electrode shared by two or more components	2027/11818	{7-T CMOS basic cell}
27/11563	with charge-trapping gate insulators, e.g. MNOS or NROM	2027/1182	{8-T CMOS basic cell}
27/11565	characterised by the top-view layout	2027/11822	{relative P to N transistor sizes}
27/11568	characterised by the memory core region (three-dimensional arrangements H01L 27/11578)	2027/11824	{for current drive capability}
27/1157	with cell select transistors, e.g. NAND	2027/11825	{for delay time adaptation}
		2027/11827	{for capacitive loading}
		2027/11829	{Isolation techniques}
		2027/11831	{FET isolation}
		2027/11833	{LOCOS}
		2027/11835	{Degree of specialisation for implementing specific functions}
		2027/11837	{Implementation of digital circuits}
		2027/11838	{Implementation of memory functions}
		2027/1184	{Implementation of analog circuits}
		2027/11842	{Resistors and capacitors}
		2027/11844	{Hybrid analog or digital}
		2027/11846	{Embedded IO cells}
		2027/11848	{Transmission gate}

2027/1185	{Porous cells, i.e. pass-through elements}	27/1222	{with a particular composition, shape or crystalline structure of the active layer}
2027/11851	{Technology used, i.e. design rules}	27/1225	{with semiconductor materials not belonging to the group IV of the periodic table, e.g. InGaZnO}
2027/11853	{Sub-micron technology}	27/1229	{with different crystal properties within a device or between different devices}
2027/11855	{Twin-tub technology}	27/1233	{with different thicknesses of the active layer in different devices}
2027/11857	{SOS, SOI technology}	27/1237	{with a different composition, shape, layout or thickness of the gate insulator in different devices}
2027/11859	{Connectivity characteristics, i.e. diffusion and polysilicon geometries}	27/124	{with a particular composition, shape or layout of the wiring layers specially adapted to the circuit arrangement, e.g. scanning lines in LCD pixel circuits (wiring structures per se H01L 23/52)}
2027/11861	{Substrate and well contacts}	27/1244	{for preventing breakage, peeling or short circuiting}
2027/11862	{Horizontal or vertical grid line density}	27/1248	{with a particular composition or shape of the interlayer dielectric specially adapted to the circuit arrangement}
2027/11864	{Yield or reliability}	27/1251	{comprising TFTs having a different architecture, e.g. top- and bottom gate TFTs}
2027/11866	{Gate electrode terminals or contacts}	27/1255	{integrated with passive devices, e.g. auxiliary capacitors}
2027/11868	{Macro-architecture}	27/1259	{Multistep manufacturing methods}
2027/1187	{Number of core or basic cells in the macro (RAM, ROM)}	27/1262	{with a particular formation, treatment or coating of the substrate}
2027/11872	{Distribution function, e.g. Sea of Gates}	27/1266	{the substrate on which the devices are formed not being the final device substrate, e.g. using a temporary substrate}
2027/11874	{Layout specification, i.e. inner core region}	27/127	{with a particular formation, treatment or patterning of the active layer specially adapted to the circuit arrangement}
2027/11875	{Wiring region, routing}	27/1274	{using crystallisation of amorphous semiconductor or recrystallisation of crystalline semiconductor}
2027/11877	{Avoiding clock-skew or clock-delay}	27/1277	{using a crystallisation promoting species, e.g. local introduction of Ni catalyst}
2027/11879	{Data lines (buses)}	27/1281	{by using structural features to control crystal growth, e.g. placement of grain filters}
2027/11881	{Power supply lines}	27/1285	{using control of the annealing or irradiation parameters, e.g. using different scanning direction or intensity for different transistors}
2027/11883	{Levels of metallisation}	27/1288	{employing particular masking sequences or specially adapted masks, e.g. half-tone mask}
2027/11885	{Two levels of metal}	27/1292	{using liquid deposition, e.g. printing}
2027/11887	{Three levels of metal}	27/1296	{adapted to increase the uniformity of device parameters}
2027/11888	{More than 3 levels of metal}	27/13	combined with thin-film or thick-film passive components
2027/1189	{Latch-up prevention}			
2027/11892	{Noise prevention (crosstalk)}			
2027/11894	{Radiation hardened circuits}			
27/11896	{using combined field effect/bipolar technology}			
27/11898	{Input and output buffer/driver structures}			
27/12	. .	the substrate being other than a semiconductor body, e.g. an insulating body			
27/1203	. . .	{the substrate comprising an insulating body on a semiconductor body, e.g. SOI (three-dimensional layout H01L 27/0688)}			
27/1207	{combined with devices in contact with the semiconductor body, i.e. bulk/SOI hybrid circuits}			
27/1211	{combined with field-effect transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}			
27/1214	. . .	{comprising a plurality of TFTs formed on a non-semiconducting substrate, e.g. driving circuits for AMLCDs}			
WARNING					
Group H01L 27/1218 – H01L 27/1296 are incomplete pending reclassification of documents from group H01L 27/1214 .					
Groups H01L 27/1218 – H01L 27/1296 and H01L 27/1214 should be considered in order to perform a complete search.					
27/1218	{with a particular composition or structure of the substrate}			

- 27/14 . . . including semiconductor components sensitive to infra-red radiation, light, electromagnetic radiation of shorter wavelength, or corpuscular radiation and specially adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation ([radiation-sensitive components structurally associated with one or more electric light sources only H01L 31/14](#); couplings of light guides with optoelectronic elements [G02B 6/42](#))
- 27/142 . . . Energy conversion devices ([photovoltaic modules or arrays of single photovoltaic cells comprising bypass diodes integrated or directly associated with the devices H01L 31/0443](#); photovoltaic modules composed of a plurality of thin film solar cells deposited on the same substrate [H01L 31/046](#))
- 27/1421 . . . {comprising bypass diodes integrated or directly associated with the device, e.g. bypass diode integrated or formed in or on the same substrate as the solar cell}
- 27/144 . . . Devices controlled by radiation
- 27/1443 . . . {with at least one potential jump or surface barrier}
- 27/1446 . . . {in a repetitive configuration}
- 27/146 . . . Imager structures
- WARNING**
- Groups [H01L 27/146](#) – [H01L 27/14893](#) are incomplete pending reclassification of documents from groups [H04N 5/3696](#) and [H04N 9/045](#).
- Groups [H04N 5/3696](#), [H04N 9/045](#), and [H01L 27/146](#) – [H01L 27/14893](#) should be considered in order to perform a complete search.
- 27/14601 {Structural or functional details thereof}
- 27/14603 {Special geometry or disposition of pixel-elements, address-lines or gate-electrodes}
- 27/14605 {Structural or functional details relating to the position of the pixel elements, e.g. smaller pixel elements in the center of the imager compared to pixel elements at the periphery}
- 27/14607 {Geometry of the photosensitive area}
- 27/14609 {Pixel-elements with integrated switching, control, storage or amplification elements ([scanning details of imagers H04N 3/15](#); [circuitry of imagers H04N 5/369](#))}
- 27/1461 {characterised by the photosensitive area}
- 27/14612 {involving a transistor}
- 27/14614 {having a special gate structure}
- 27/14616 {characterised by the channel of the transistor, e.g. channel having a doping gradient}
- 27/14618 {Containers}
- 27/1462 {Coatings}
- 27/14621 {Colour filter arrangements}
- 27/14623 {Optical shielding}
- 27/14625 {Optical elements or arrangements associated with the device}
- 27/14627 {Microlenses}
- 27/14629 {Reflectors}
- 27/1463 {Pixel isolation structures}
- 27/14632 {Wafer-level processed structures}
- 27/14634 {Assemblies, i.e. Hybrid structures}
- 27/14636 {Interconnect structures}
- 27/14638 {Structures specially adapted for transferring the charges across the imager perpendicular to the imaging plane}
- 27/1464 {Back illuminated imager structures}
- 27/14641 {Electronic components shared by two or more pixel-elements, e.g. one amplifier shared by two pixel elements}
- 27/14643 {Photodiode arrays; MOS imagers}
- 27/14645 {Colour imagers}
- 27/14647 {Multicolour imagers having a stacked pixel-element structure, e.g. npn, npnpn or MQW elements}
- 27/14649 {Infra-red imagers}
- 27/1465 {of the hybrid type}
- 27/14652 {Multispectral infra-red imagers, having a stacked pixel-element structure, e.g. npn, npnpn or MQW structures}
- 27/14654 {Blooming suppression}
- 27/14656 {Overflow drain structures}
- 27/14658 {X-ray, gamma-ray or corpuscular radiation imagers ([measuring X-, gamma- or corpuscular radiation G01T 1/00](#))}
- 27/14659 {Direct radiation imagers structures}
- 27/14661 {of the hybrid type}
- 27/14663 {Indirect radiation imagers, e.g. using luminescent members}
- 27/14665 {Imagers using a photoconductor layer}
- 27/14667 {Colour imagers}
- 27/14669 {Infra-red imagers}
- 27/1467 {of the hybrid type}
- 27/14672 {Blooming suppression}
- 27/14674 {Overflow drain structures}
- 27/14676 {X-ray, gamma-ray or corpuscular radiation imagers ([measuring X-, gamma- or corpuscular radiation G01T 1/00](#))}
- 27/14678 {Contact-type imagers}
- 27/14679 {Junction field effect transistor [JFET] imagers; static induction transistor [SIT] imagers}
- 27/14681 {Bipolar transistor imagers}
- 27/14683 {Processes or apparatus peculiar to the manufacture or treatment of these devices or parts thereof ([not peculiar thereto H01L 21/00](#))}
- 27/14685 {Process for coatings or optical elements}
- 27/14687 {Wafer level processing}
- 27/14689 {MOS based technologies}
- 27/1469 {Assemblies, i.e. hybrid integration}
- 27/14692 {Thin film technologies, e.g. amorphous, poly, micro- or nanocrystalline silicon}
- 27/14694 {The active layers comprising only $A_{III}B_V$ compounds, e.g. GaAs, InP}
- 27/14696 {The active layers comprising only $A_{II}B_{VI}$ compounds, e.g. CdS, ZnS, CdTe}
- 27/14698 {Post-treatment for the devices, e.g. annealing, impurity-gettering, short-circuit elimination, recrystallisation}
- 27/148 Charge coupled imagers ([individual charge coupled devices H01L 29/765](#))

- 27/14806 {Structural or functional details thereof}
 - 27/14812 {Special geometry or disposition of pixel-elements, address lines or gate-electrodes}
 - 27/14818 {Optical shielding}
 - 27/14825 {Linear CCD imagers}
 - 27/14831 {Area CCD imagers}
 - 27/14837 {Frame-interline transfer}
 - 27/14843 {Interline transfer}
 - 27/1485 {Frame transfer}
 - 27/14856 {Time-delay and integration}
 - 27/14862 {CID imagers}
 - 27/14868 {CCD or CID colour imagers}
 - 27/14875 {Infra-red CCD or CID imagers}
 - 27/14881 {of the hybrid type}
 - 27/14887 {Blooming suppression}
 - 27/14893 {comprising a photoconductive layer deposited on the CCD structure}
 - 27/15 including semiconductor components with at least one potential-jump barrier or surface barrier specially adapted for light emission {[monolithically integrated components including semiconductor laser components H01S 5/026](#)}
 - 27/153 {in a repetitive configuration, e.g. LED bars}
 - 27/156 {two-dimensional arrays}
 - 27/16 including thermoelectric components with or without a junction of dissimilar materials; including thermomagnetic components [\(using the Peltier effect only for cooling of semiconductor or other solid state devices H01L 23/38\)](#)
 - 27/18 including components exhibiting superconductivity
 - 27/20 including piezo-electric components; including electrostrictive components; including magnetostrictive components
 - 27/22 including components using galvano-magnetic effects, e.g. Hall effects; using similar magnetic field effects
 - 27/222 {Magnetic non-volatile memory structures, e.g. MRAM}
 - 27/224 {comprising two-terminal components, e.g. diodes, MIM elements}
 - 27/226 {comprising multi-terminal components, e.g. transistors}
 - 27/228 {of the field-effect transistor type}
 - 27/24 including solid state components for rectifying, amplifying or switching without a potential-jump barrier or surface barrier, {e.g. resistance switching non-volatile memory structures}
 - 27/2409 {comprising two-terminal selection components, e.g. diodes}
 - 27/2418 {of the metal-insulator-metal type}
 - 27/2427 {of the Ovonic threshold switching type}
 - 27/2436 {comprising multi-terminal selection components, e.g. transistors}
 - 27/2445 {of the bipolar type}
 - 27/2454 {of the vertical channel field-effect transistor type}
 - 27/2463 {Arrangements comprising multiple bistable or multistable switching components of the same type on a plane parallel to the substrate, e.g. cross-point arrays, details of the horizontal layout}
 - 27/2472 {the switching components having a common active material layer}
 - 27/2481 {arranged in a direction perpendicular to the substrate, e.g. 3D cell arrays, details of the vertical layout}
 - 27/249 {the switching components being connected to a common vertical conductor}
 - 27/26 including bulk negative resistance effect components
 - 27/265 {Gunn effect devices}
 - 27/28 including components using organic materials as the active part, or using a combination of organic materials with other materials as the active part
 - 27/281 {Integrated circuits having a three-dimensional layout}
 - 27/283 {comprising components of the field-effect type}
 - 27/285 {Integrated circuits with a common active layer, e.g. cross point devices}
 - 27/286 {with an active region comprising an inorganic semiconductor}
 - 27/288 {Combination of organic light sensitive components with organic light emitting components, e.g. optocoupler}
 - 27/30 with components specially adapted for sensing infra-red radiation, light, electromagnetic radiation of shorter wavelength, or corpuscular radiation; with components specially adapted for either the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation [{\(combination of organic light sensitive components with organic light emitting components, e.g. optocoupler H01L 27/288\)}](#)
 - 27/301 {Energy conversion devices}
 - 27/302 {comprising multiple junctions, e.g. tandem cells}
 - 27/304 {in form of a fiber or a tube, e.g. photovoltaic fibers}
 - 27/305 {Devices controlled by radiation}
 - 27/307 {Imager structures}
- WARNING**
- Group [H01L 27/307](#) is incomplete pending reclassification of documents from groups [H04N 5/3696](#) and [H04N 9/045](#).
- Groups [H04N 5/3696](#), [H04N 9/045](#), and [H01L 27/307](#) should be considered in order to perform a complete search.
- 27/308 {Devices specially adapted for detecting X-ray radiation [\(measuring X-radiation G01T 1/00\)](#)}
 - 27/32 with components specially adapted for light emission, e.g. flat-panel displays using organic light-emitting diodes [OLED] [{\(combination of organic light sensitive components with organic light emitting components, e.g. optocoupler H01L 27/288\)}](#)
 - 27/3202 {OLEDs electrically connected in parallel}
 - 27/3204 {OLEDs electrically connected in series}
 - 27/3206 {Multi-colour light emission}
 - 27/3209 {using stacked OLED}

27/3211 {using RGB sub-pixels}	27/3269 {Including photosensors to control luminance}
	WARNING	27/3272 {Shielding, e.g. of TFT}
	Groups H01L 27/3213 – H01L 27/3218 are incomplete pending reclassification of documents from group H01L 27/3211 .	27/3274 {including organic thin film transistors [OTFT]}
	Groups H01L 27/3213 – H01L 27/3218 and H01L 27/3211 should be considered in order to perform a complete search.	27/3276 {Wiring lines}
27/3213 {using more than three sub-pixels, e.g. RGBW}	27/3279 {comprising structures specially adapted for lowering the resistance}
27/3216 {the areas of RGB sub-pixels being different}	27/3281 {Passive matrix displays}
27/3218 {characterised by the geometrical arrangement of the RGB sub-pixels}	27/3283 {Including banks or shadow masks}
27/322 {using colour filters or colour changing media [CCM]}	27/3286 {Dual display, i.e. having two independent displays}
27/3223	. . . {combined with dummy elements, i.e. non-functional features}	27/3288 {Wiring lines}
27/3225	. . . {OLED integrated with another component (H01L 27/3223 takes precedence)}	27/329 {comprising structures specially adapted for lowering the resistance}
27/3227 {the other component being a light sensitive element, e.g. inorganic solar cell, inorganic photodiode (H01L 27/288 takes precedence)}	27/3293 {Tiled displays}
27/323 {the other component being a touch screen}	27/3295 {including banks or shadow masks}
27/3232 {the other component being a light modulating element, e.g. electrochromic element, photochromic element, liquid crystal element}	27/3297 {Wiring lines, e.g. power supply lines}
27/3234 {the other component being an imager structure (H01L 27/146 takes precedence)}	28/00	{Passive two-terminal components without a potential-jump or surface barrier for integrated circuits; Details thereof; Multistep manufacturing processes therefor (testing or measuring during manufacture H01L 22/00; integration methods H01L 21/70; integrated circuits H01L 27/00; two-terminal components with a potential-jump or surface barrier H01L 29/00; resistors in general H01C; inductors in general H01F; capacitors in general H01G)}
27/3237	. . . {Displays not provided for in group H01L 27/3241 and subgroups, e.g. segment-type displays}	28/10	. {Inductors}
27/3239 {Light emitting logos}	28/20	. {Resistors}
27/3241	. . . {Matrix-type displays}	28/22	. . {with an active material comprising carbon, e.g. diamond or diamond-like carbon [DLC]}
	WARNING	28/24	. . {with an active material comprising a refractory, transition or noble metal, metal compound or metal alloy, e.g. silicides, oxides, nitrides}
	From 1.2.2012 onwards, groups H01L 27/3295 and H01L 27/3297 are no longer used for classification of new documents. The backfile is being reclassified to H01L 27/3244 and H01L 27/3281 and subgroups thereof	28/26	. . {with an active material comprising an organic conducting material, e.g. conducting polymers}
27/3244 {Active matrix displays}	28/40	. {Capacitors}
27/3246 {Banks, i.e. pixel defining layers}	28/55	. . {with a dielectric comprising a perovskite structure material}
27/3248 {Connection of the pixel electrode to the TFT}	28/56	. . . {the dielectric comprising two or more layers, e.g. comprising buffer layers, seed layers, gradient layers}
27/3251 {Double substrate, i.e. with OLED and TFT on different substrates}	28/57	. . . {comprising a barrier layer to prevent diffusion of hydrogen or oxygen}
27/3253 {Electrical connection of the two substrates}	28/60	. . {Electrodes}
27/3255 {Chiplets}	28/65	. . . {comprising a noble metal or a noble metal oxide, e.g. platinum (Pt), ruthenium (Ru), ruthenium dioxide (RuO ₂), iridium (Ir), iridium dioxide (IrO ₂)}
27/3258 {Insulating layers formed between TFT elements and OLED elements}	28/75	. . . {comprising two or more layers, e.g. comprising a barrier layer and a metal layer}
27/326 {special geometry or disposition of pixel-elements}	28/82	. . . {with an enlarged surface, e.g. formed by texturisation}
27/3262 {of TFT}	28/84 {being a rough surface, e.g. using hemispherical grains}
27/3265 {of capacitor}	28/86 {having horizontal extensions}
27/3267 {Dual display, i.e. having two independent displays}	28/87 {made by depositing layers, e.g. by depositing alternating conductive and insulating layers}
		28/88 {made by patterning layers, e.g. by etching conductive layers}
		28/90 {having vertical extensions}

28/91 {made by depositing layers, e.g. by depositing alternating conductive and insulating layers}	29/0619 {with a supplementary region doped oppositely to or in rectifying contact with the semiconductor containing or contacting region, e.g. guard rings with PN or Schottky junction}
28/92 {made by patterning layers, e.g. by etching conductive layers}	29/0623 {Buried supplementary region, e.g. buried guard ring (multi-RESURF H01L 29/0634)}
29/00	Semiconductor devices adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential-jump barrier or surface barrier, e.g. PN junction depletion layer or carrier concentration layer; Details of semiconductor bodies or of electrodes thereof; {Multistep manufacturing processes therefor} (H01L 31/00 - H01L 47/00, H01L 51/05 take precedence; processes or apparatus adapted for the manufacture or treatment thereof or of parts thereof H01L 21/00; details other than of semiconductor bodies or of electrodes thereof H01L 23/00; devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00; {passive two-terminal components without a potential-jump or surface barrier for integrated circuits, details thereof and multistep manufacturing processes therefor H01L 28/00; } resistors in general H01C; capacitors in general H01G, {e.g. ceramic barrier-layer capacitors H01G 4/1272}) NOTE In this main group, classification is made both in groups H01L 29/02 - H01L 29/51 and in groups H01L 29/66 - H01L 29/94 if both of these sets of groups are relevant.	29/0626 {with a localised breakdown region, e.g. built-in avalanching region (in self-protected thyristors H01L 29/7424)}
		29/063 {Reduced surface field [RESURF] pn-junction structures}
		29/0634 {Multiple reduced surface field (multi-RESURF) structures, e.g. double RESURF, charge compensation, cool, superjunction (SJ), 3D-RESURF, composite buffer (CB) structures}
		29/0638 {for preventing surface leakage due to surface inversion layer, e.g. with channel stopper (channel stoppers in combination with isolation region for integrated circuits H01L 21/762)}
		29/0642 {Isolation within the component, i.e. internal isolation}
		29/0646 {PN junctions}
		29/0649 {Dielectric regions, e.g. SiO ₂ regions, air gaps}
		29/0653 {adjoining the input or output region of a field-effect device, e.g. the source or drain region}
29/02	. Semiconductor bodies {; Multistep manufacturing processes therefor}	29/0657	. . . {characterised by the shape of the body}
29/04	. . characterised by their crystalline structure, e.g. polycrystalline, cubic or particular orientation of crystalline planes (characterised by physical imperfections H01L 29/30)	29/0661 {specially adapted for altering the breakdown voltage by removing semiconductor material at, or in the neighbourhood of, a reverse biased junction, e.g. by bevelling, moat etching, depletion etching}
29/045	. . . {by their particular orientation of crystalline planes}	29/0665 {the shape of the body defining a nanostructure (nanotechnology per se B82B)}
29/06	. . characterised by their shape; characterised by the shapes, relative sizes, or dispositions of the semiconductor regions {; characterised by the concentration or distribution of impurities within semiconductor regions}	29/0669 {Nanowires or nanotubes (carbon nanotubes as material of solid-state device active part H01L 51/0048)}
29/0603	. . . {characterised by particular constructional design considerations, e.g. for preventing surface leakage, for controlling electric field concentration or for internal isolations regions (isolation regions between components H01L 21/76 ; design considerations for integrated circuits H01L 27/00 ; geometrical design considerations for devices H01L 29/0657)}	29/0673 {oriented parallel to a substrate}
		29/0676 {oriented perpendicular or at an angle to a substrate}
29/0607 {for preventing surface leakage or controlling electric field concentration}	29/068 {comprising a junction}
29/0611 {for increasing or controlling the breakdown voltage of reverse biased devices (H01L 29/0661 takes precedence)}	29/0684 {characterised by the shape, relative sizes or dispositions of the semiconductor regions or junctions between the regions}
29/0615 {by the doping profile or the shape or the arrangement of the PN junction, or with supplementary regions, e.g. junction termination extension [JTE] (LDD or drain offset regions H01L 29/7833)}	29/0688 {characterised by the particular shape of a junction between semiconductor regions}
		29/0692 {Surface layout}
		29/0696 {of cellular field-effect devices, e.g. multicellular DMOS transistors or IGBTs}
		29/08	. . . with semiconductor regions connected to an electrode carrying current to be rectified, amplified or switched and such electrode being part of a semiconductor device which comprises three or more electrodes
		29/0804 {Emitter regions of bipolar transistors}
		29/0808 {of lateral transistors}

29/0813	{Non-interconnected multi-emitter structures}	29/1033	{with insulated gate, e.g. characterised by the length, the width, the geometric contour or the doping structure (with channel and gate aligned in the lengthwise direction H01L 29/42376 ; with buried channel H01L 29/7838)}
29/0817	{of heterojunction bipolar transistors (H01L 29/7375 takes precedence)}	29/1037	{and non-planar channel (resulting from the gate electrode disposition, e.g. within a trench, H01L 29/42356)}
29/0821	{Collector regions of bipolar transistors}	29/1041	{with a non-uniform doping structure in the channel region surface}
29/0826	{Pedestal collectors}	29/1045	{the doping structure being parallel to the channel length, e.g. DMOS like}
29/083	{Anode or cathode regions of thyristors or gated bipolar-mode devices}	29/105	{with vertical doping variation (H01L 29/7827 takes precedence)}
29/0834	{Anode regions of thyristors or gated bipolar-mode devices, e.g. supplementary regions surrounding anode regions}	29/1054	{with a variation of the composition, e.g. channel with strained layer for increasing the mobility}
29/0839	{Cathode regions of thyristors}	29/1058	{with PN junction gate}
29/0843	{Source or drain regions of field-effect devices}	29/1062	{of charge coupled devices}
29/0847	{of field-effect transistors with insulated gate (H01L 29/0653 takes precedence; with a passive supplementary region related to punch-through, capacity or isolation phenomena H01L 29/1079 ; with LDD or DDD structure H01L 29/7833 ; for thin film transistors H01L 29/78618)}	29/1066	{Gate region of field-effect devices with PN junction gate}
29/0852	{of DMOS transistors}	29/107	{Substrate region of field-effect devices}
WARNING			29/1075	{of field-effect transistors}
Groups H01L 29/0852 – H01L 29/0886 are incomplete pending reclassification of documents from group H01L 29/0847 and H01L 29/7801 .			29/1079	{with insulated gate}
Groups H01L 29/0852 – H01L 29/0886 and H01L 29/0847 , H01L 29/7801 should be considered in order to perform a complete search.			29/1083	{with an inactive supplementary region, e.g. for preventing punch-through, improving capacity effect or leakage current}
29/0856	{Source regions}	29/1087	{characterised by the contact structure of the substrate region, e.g. for controlling or preventing bipolar effect}
29/086	{Impurity concentration or distribution}	29/1091	{of charge coupled devices}
29/0865	{Disposition}	29/1095	{Body region, i.e. base region, of DMOS transistors or IGBTs (cell layout H01L 29/0696)}
29/0869	{Shape (cell layout H01L 29/0696)}	29/12	characterised by the materials of which they are formed
29/0873	{Drain regions}	29/122	{Single quantum well structures (single heterojunctions, couples of materials H01L 29/165 , H01L 29/205 , H01L 29/225 , H01L 29/267)}
29/0878	{Impurity concentration or distribution}	29/125	{Quantum wire structures}
29/0882	{Disposition}	29/127	{Quantum box structures}
29/0886	{Shape}	29/15	Structures with periodic or quasi periodic potential variation, e.g. multiple quantum wells, superlattices (such structures applied for the control of light G02F 1/017 , applied in semiconductor lasers H01S 5/34)
29/0891	{of field-effect transistors with Schottky gate}	NOTE		
29/0895	{Tunnel injectors}	Group H01L 29/15 takes precedence over groups H01L 29/16 - H01L 29/26 .		
29/10	with semiconductor regions connected to an electrode not carrying current to be rectified, amplified or switched and such electrode being part of a semiconductor device which comprises three or more electrodes	29/151	{Compositional structures (H01L 29/157 and H01L 29/158 take precedence)}
29/1004	{Base region of bipolar transistors}	29/152	{with quantum effects only in vertical direction, i.e. layered structures with quantum effects solely resulting from vertical potential variation}
29/1008	{of lateral transistors}			
29/1012	{Base regions of thyristors (H01L 29/083 takes precedence)}			
29/1016	{Anode base regions of thyristors}			
29/102	{Cathode base regions of thyristors}			
29/1025	{Channel region of field-effect devices}			
29/1029	{of field-effect transistors}			

- 29/154 {comprising at least one long range structurally disordered material, e.g. one-dimensional vertical amorphous superlattices}
- 29/155 {Comprising only semiconductor materials ([H01L 29/154](#) takes precedence)}
- 29/157 {Doping structures, e.g. doping superlattices, nipi superlattices ([delta doping in general H01L 29/365](#))}
- 29/158 {Structures without potential periodicity in a direction perpendicular to a major surface of the substrate, i.e. vertical direction, e.g. lateral superlattices, lateral surface superlattices [LSS]}
- 29/16 . . . including, apart from doping materials or other impurities, only elements of Group IV of the Periodic System
- 29/1602 {Diamond}
- 29/1604 {Amorphous materials}
- 29/1606 {Graphene}
- 29/1608 {Silicon carbide}
- 29/161 including two or more of the elements provided for in group [H01L 29/16](#) {, e.g. alloys ([H01L 29/1604](#) takes precedence)}
- 29/165 in different semiconductor regions {, e.g. heterojunctions}
- 29/167 further characterised by the doping material {([H01L 29/1604](#) takes precedence)}
- 29/18 . . . Selenium or tellurium only, apart from doping materials or other impurities
- 29/185 {Amorphous materials}
- 29/20 . . . including, apart from doping materials or other impurities, only $A_{III}B_V$ compounds
- 29/2003 {Nitride compounds}
- 29/2006 {Amorphous materials}
- 29/201 including two or more compounds {, e.g. alloys ([H01L 29/2006](#) takes precedence)}
- 29/205 in different semiconductor regions {, e.g. heterojunctions}
- 29/207 further characterised by the doping material {([H01L 29/2006](#) takes precedence)}
- 29/22 . . . including, apart from doping materials or other impurities, only $A_{II}B_{VI}$ compounds
- 29/2203 {Cd X compounds being one element of the 6th group of the Periodic System ([H01L 29/2206](#) takes precedence)}
- 29/2206 {Amorphous materials}
- 29/221 including two or more compounds {, e.g. alloys ([H01L 29/2206](#) takes precedence)}
- 29/225 in different semiconductor regions {, e.g. heterojunctions}
- 29/227 further characterised by the doping material {([H01L 29/2206](#) takes precedence)}
- 29/24 . . . including, apart from doping materials or other impurities, only semiconductor materials not provided for in groups [H01L 29/16](#), [H01L 29/18](#), [H01L 29/20](#), [H01L 29/22](#) (including organic materials [H01L 51/00](#))
- 29/242 { $A_{IB_{VI}}$ or $A_{IB_{VII}}$ compounds, e.g. Cu_2O , Cu I ([H01L 29/247](#) takes precedence)}
- 29/245 {Pb compounds, e.g. PbO ([H01L 29/247](#) takes precedence)}
- 29/247 {Amorphous materials}
- 29/26 . . . including, apart from doping materials or other impurities, elements provided for in two or more of the groups [H01L 29/16](#), [H01L 29/18](#), [H01L 29/20](#), [H01L 29/22](#), [H01L 29/24](#) {, e.g. alloys}
- 29/263 {Amorphous materials}
- 29/267 in different semiconductor regions {, e.g. heterojunctions ([H01L 29/263](#) takes precedence)}
- 29/30 . . characterised by physical imperfections; having polished or roughened surface
- 29/32 . . . the imperfections being within the semiconductor body
- 29/34 . . . the imperfections being on the surface
- 29/36 . . characterised by the concentration or distribution of impurities {in the bulk material (within semiconductor regions [H01L 29/06](#))}
- 29/365 . . . {Planar doping, e.g. atomic-plane doping, delta-doping}
- 29/40 . Electrodes {; Multistep manufacturing processes therefor}
- 29/401 . . {Multistep manufacturing processes}
- 29/402 . . {Field plates}
- 29/404 . . . {Multiple field plate structures}
- 29/405 . . . {Resistive arrangements, e.g. resistive or semi-insulating field plates}
- 29/407 . . . {Recessed field plates, e.g. trench field plates, buried field plates}
- 29/408 . . {with an insulating layer with a particular dielectric or electrostatic property, e.g. with static charges or for controlling trapped charges or moving ions, or with a plate acting on the insulator potential or the insulator charges, e.g. for controlling charges effect or potential distribution in the insulating layer, or with a semi-insulating layer contacting directly the semiconductor surface}
- 29/41 . . characterised by their shape, relative sizes or dispositions
- 29/413 . . . {Nanosized electrodes, e.g. nanowire electrodes comprising one or a plurality of nanowires (transparent electrodes comprising carbon nano-tubes [H01L 51/444](#), nanotechnology [per se B82B](#); nanosized carbon materials, e.g. carbon nanotubes, [per se C01B 32/15](#))}
- 29/417 . . . carrying the current to be rectified, amplified or switched
- 29/41708 {Emitter or collector electrodes for bipolar transistors}
- 29/41716 {Cathode or anode electrodes for thyristors}
- 29/41725 {Source or drain electrodes for field effect devices (with monocrystalline semiconductor on source/drain region [H01L 29/0843](#))}
- 29/41733 {for thin film transistors with insulated gate}
- 29/41741 {for vertical or pseudo-vertical devices}

NOTE

A pseudo-vertical device is a device with the drain and source electrodes on the same main surface and where the main current is vertical at least in a part of its path

29/4175	{for lateral devices where the connection to the source or drain region is done through at least one part of the semiconductor substrate thickness, e.g. with connecting sink or with via-hole}	29/42344	{with at least one additional gate, e.g. program gate, erase gate or select gate}
		NOTE The sink or via-hole leading to the source or drain region is considered to form part of the source or drain electrode	29/42348	{with trapping site formed by at least two separated sites, e.g. multi-particles trapping site}
29/41758	{for lateral devices with structured layout for source or drain region, i.e. the source or drain region having cellular, interdigitated or ring structure or being curved or angular (H01L 29/41733 - H01L 29/4175 take precedence)}	29/42352	{with the gate at least partly formed in a trench}
		NOTE Interdigitated structure means that at least one of the source or drain region has two or more fingers	29/42356	{Disposition, e.g. buried gate electrode (H01L 29/42324 and H01L 29/4234 take precedence)}
29/41766	{with at least part of the source or drain electrode having contact below the semiconductor surface, e.g. the source or drain electrode formed at least partially in a groove or with inclusions of conductor inside the semiconductor (H01L 29/41733 - H01L 29/41758 take precedence)}	29/4236	{within a trench, e.g. trench gate electrode, groove gate electrode}
29/41775	{characterised by the proximity or the relative position of the source or drain electrode and the gate electrode, e.g. the source or drain electrode separated from the gate electrode by side-walls or spreading around or above the gate electrode}	29/42364	{characterised by the insulating layer, e.g. thickness or uniformity (H01L 29/42324 and H01L 29/4234 take precedence)}
29/41783	{Raised source or drain electrodes self aligned with the gate}	29/42368	{the thickness being non-uniform}
29/41791	{for transistors with a horizontal current flow in a vertical sidewall, e.g. FinFET, MuGFET}	29/42372	{characterised by the conducting layer, e.g. the length, the sectional shape or the lay-out (H01L 29/42324 takes precedence)}
29/423	not carrying the current to be rectified, amplified or switched	29/42376	{characterised by the length or the sectional shape}
29/42304	{Base electrodes for bipolar transistors}	29/4238	{characterised by the surface lay-out}
29/42308	{Gate electrodes for thyristors}	29/42384	{for thin film field effect transistors, e.g. characterised by the thickness or the shape of the insulator or the dimensions, the shape or the lay-out of the conductor}
29/42312	{Gate electrodes for field effect devices}	2029/42388	{characterised by the shape of the insulating material}
29/42316	{for field-effect transistors}	29/42392	{fully surrounding the channel, e.g. gate-all-around}
29/4232	{with insulated gate}	29/42396	{for charge coupled devices}
29/42324	{Gate electrodes for transistors with a floating gate}	29/43	characterised by the materials of which they are formed
29/42328	{with at least one additional gate other than the floating gate and the control gate, e.g. program gate, erase gate or select gate}	29/432	{Heterojunction gate for field effect devices}
29/42332	{with the floating gate formed by two or more non connected parts, e.g. multi-particles flating gate}	29/435	{Resistive materials for field effect devices, e.g. resistive gate for MOSFET or MESFET}
29/42336	{with one gate at least partly formed in a trench}	29/437	{Superconductor materials}
29/4234	{Gate electrodes for transistors with charge trapping gate insulator}	29/45	Ohmic electrodes
			29/452	{on AIII-BV compounds}
			29/454	{on thin film AIII-BV compounds}
			29/456	{on silicon}
			29/458	{for thin film silicon, e.g. source or drain electrode}
			29/47	Schottky barrier electrodes (H01L 29/435 takes precedence)}
			29/475	{on AIII-BV compounds}
			29/49	Metal-insulator-semiconductor electrodes, {e.g. gates of MOSFET (H01L 29/435 takes precedence)}
					NOTE This group covers also devices using any other conductor material in place of metal
			29/4908	{for thin film semiconductor, e.g. gate of TFT}

- 29/4916 {the conductor material next to the insulator being a silicon layer, e.g. polysilicon doped with boron, phosphorus or nitrogen ([H01L 29/4908](#), [H01L 29/4983](#) take precedence)}
- 29/4925 {with a multiple layer structure, e.g. several silicon layers with different crystal structure or grain arrangement (with only a vertical doping structure or vertical doping variation [H01L 29/4916](#))}
- 29/4933 {with a silicide layer contacting the silicon layer, e.g. Polycide gate (with a barrier layer between the silicide and silicon layers [H01L 29/4941](#))}
- 29/4941 {with a barrier layer between the silicon and the metal or metal silicide upper layer, e.g. Silicide/TiN/Polysilicon}
- 29/495 {the conductor material next to the insulator being a simple metal, e.g. W, Mo ([H01L 29/4908](#), [H01L 29/4983](#) take precedence)}
- 29/4958 {with a multiple layer structure}
- 29/4966 {the conductor material next to the insulator being a composite material, e.g. organic material, TiN, MoSi₂ ([H01L 29/4908](#), [H01L 29/4983](#) take precedence)}
- 29/4975 {being a silicide layer, e.g. TiSi₂}
- 29/4983 {with a lateral structure, e.g. a Polysilicon gate with a lateral doping variation or with a lateral composition variation or characterised by the sidewalls being composed of conductive, resistive or dielectric material}
- 29/4991 {comprising an air gap}
- WARNING**
- Group [H01L 29/4991](#) is incomplete pending reclassification of documents from group [H01L 29/4983](#).
- Groups [H01L 29/4991](#) and [H01L 29/4983](#) should be considered in order to perform a complete search.
- 29/51 Insulating materials associated therewith {for MIS structures on thin film semiconductor [H01L 29/4908](#)}
- 29/511 {with a compositional variation, e.g. multilayer structures ([H01L 29/516](#) takes precedence)}
- 29/512 {the variation being parallel to the channel plane}
- 29/513 {the variation being perpendicular to the channel plane}
- 29/515 {with cavities, e.g. containing a gas}
- 29/516 {with at least one ferroelectric layer}
- 29/517 {the insulating material comprising a metallic compound, e.g. metal oxide, metal silicate ([H01L 29/518](#) takes precedence)}
- 29/518 {the insulating material containing nitrogen, e.g. nitride, oxynitride, nitrogen-doped material}
- 29/66 . . Types of semiconductor device {; Multistep manufacturing processes therefor}
- 29/66007 . . {Multistep manufacturing processes}
- 29/66015 {of devices having a semiconductor body comprising semiconducting carbon, e.g. diamond, diamond-like carbon, graphene}
- 29/66022 {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 29/6603 {Diodes}
- 29/66037 {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}
- 29/66045 {Field-effect transistors}
- 29/66053 {of devices having a semiconductor body comprising crystalline silicon carbide}
- 29/6606 {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 29/66068 {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}
- 29/66075 {of devices having semiconductor bodies comprising group 14 or group 13/15 materials (comprising semiconducting carbon [H01L 29/66015](#); comprising crystalline silicon carbide [H01L 29/66053](#))}
- 29/66083 {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 29/6609 {Diodes}
- 29/66098 {Breakdown diodes}
- 29/66106 {Zener diodes}
- 29/66113 {Avalanche diodes}
- 29/66121 {Multilayer diodes, e.g. PNP diodes}
- 29/66128 {Planar diodes}
- 29/66136 {PN junction diodes}
- 29/66143 {Schottky diodes}
- 29/66151 {Tunnel diodes (group 13/15 resonant tunneling diodes [H01L 29/66219](#))}
- 29/66159 {Transit time diodes, e.g. IMPATT, TRAPATT diodes}
- 29/66166 {Resistors with PN junction}
- 29/66174 {Capacitors with PN or Schottky junction, e.g. varactors (capacitors with PN junction combined with MOS control [H01L 29/66189](#))}
- 29/66181 {Conductor-insulator-semiconductor capacitors, e.g. trench capacitors}
- 29/66189 {with PN junction, e.g. hybrid capacitors}
- 29/66196 {with an active layer made of a group 13/15 material}

29/66204	{Diodes}	29/66416	{Static induction transistors [SIT] (with an active layer made of a group 13/15 material H01L 29/66454)}
29/66212	{Schottky diodes}	29/66424	{Permeable base transistors [PBT]}
29/66219	{with a heterojunction, e.g. resonant tunneling diodes [RTD]}	29/66431	{with a heterojunction interface channel or gate, e.g. HFET, HIGFET, SISFET, HJFET, HEMT (with an active layer made of a group 13/15 material H01L 29/66462)}
29/66227	{the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}	29/66439	{with a one- or zero-dimensional channel, e.g. quantum wire FET, in-plane gate transistor [IPG], single electron transistor [SET], striped channel transistor, Coulomb blockade transistor (with an active layer made of a group 13/15 material H01L 29/66469)}
29/66234	{Bipolar junction transistors [BJT]}	29/66446	{with an active layer made of a group 13/15 material, e.g. group 13/15 velocity modulation transistor [VMT], group 13/15 negative resistance FET [NERFET]}
29/66242	{Heterojunction transistors [HBT] (with an active layer made of a group 13/15 material H01L 29/66318)}	29/66454	{Static induction transistors [SIT], e.g. permeable base transistors [PBT]}
29/6625	{Lateral transistors (H01L 29/66242 and H01L 29/66265 take precedence)}	29/66462	{with a heterojunction interface channel or gate, e.g. HFET, HIGFET, SISFET, HJFET, HEMT}
29/66257	{Schottky transistors}	29/66469	{with one- or zero-dimensional channel, e.g. quantum wire field-effect transistors, in-plane gate transistors [IPG], single electron transistors [SET], Coulomb blockade transistors, striped channel transistors}
29/66265	{Thin film bipolar transistors (H01L 29/66242 takes precedence)}	29/66477	{with an insulated gate, i.e. MISFET}
29/66272	{Silicon vertical transistors (H01L 29/66242 , H01L 29/66257 and H01L 29/66265 take precedence)}	29/66484	{with multiple gate, at least one gate being an insulated gate (H01L 29/66742 takes precedence)}
29/6628	{Inverse transistors}	29/66492	{with a pocket or a lightly doped drain selectively formed at the side of the gate}
29/66287	{with a single crystalline emitter, collector or base including extrinsic, link or graft base formed on the silicon substrate, e.g. by epitaxy, recrystallisation, after insulating device isolation (H01L 29/6628 takes precedence)}	29/665	{using self aligned silicidation, i.e. silicide (formation of conductive layers comprising silicides H01L 21/28518)}
29/66295	{with main current going through the whole silicon substrate, e.g. power bipolar transistor}	29/66507	{providing different silicide thicknesses on the gate and on source or drain}
29/66303	{with multi-emitter, e.g. interdigitated, multi-cellular or distributed emitter}	29/66515	{using self aligned selective metal deposition simultaneously on the gate and on source or drain}
29/6631	{with an active layer made of a group 13/15 material}	29/66522	{with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence)}
29/66318	{Heterojunction transistors}	29/6653	{using the removal of at least part of spacer, e.g. disposable spacer}
29/66325	{controlled by field-effect, e.g. insulated gate bipolar transistors [IGBT]}	29/66537	{using a self aligned punch through stopper or threshold implant under the gate region (H01L 29/66606 takes precedence)}
29/66333	{Vertical insulated gate bipolar transistors}	29/66545	{using a dummy, i.e. replacement gate in a process wherein at least a part of the final gate is self aligned to the dummy gate}
29/6634	{with a recess formed by etching in the source/emitter contact region (H01L 29/66348 takes precedence; etching of semiconductor bodies H01L 21/302)}		
29/66348	{with a recessed gate}		
29/66356	{Gated diodes, e.g. field controlled diodes [FCD], static induction thyristors [SITh], field controlled thyristors [FCTh]}		
29/66363	{Thyristors}		
29/66371	{structurally associated with another device, e.g. built-in diode (making integrated circuits H01L 21/82)}		
29/66378	{the other device being a controlling field-effect device}		
29/66386	{Bidirectional thyristors}		
29/66393	{Lateral or planar thyristors}		
29/66401	{with an active layer made of a group 13/15 material}		
29/66409	{Unipolar field-effect transistors}		

29/66553	{using inside spacers, permanent or not}	29/66674	{DMOS transistors, i.e. MISFETs with a channel accommodating body or base region adjoining a drain drift region (making lateral high-voltage MISFETs with channel well and drain offset region H01L 29/66659)}
29/6656	{using multiple spacer layers, e.g. multiple sidewall spacers}	29/66681	{Lateral DMOS transistors, i.e. LDMOS transistors}
29/66568	{Lateral single gate silicon transistors}	29/66689	{with a step of forming an insulating sidewall spacer (forming insulating material on a substrate H01L 21/02107)}
29/66575	{where the source and drain or source and drain extensions are self-aligned to the sides of the gate (H01L 29/66606 takes precedence)}	29/66696	{with a step of recessing the source electrode}
29/66583	{with initial gate mask or masking layer complementary to the prospective gate location, e.g. with dummy source and drain contacts}	29/66704	{with a step of recessing the gate electrode, e.g. to form a trench gate electrode}
29/6659	{with both lightly doped source and drain extensions and source and drain self-aligned to the sides of the gate, e.g. lightly doped drain [LDD] MOSFET, double diffused drain [DDD] MOSFET}	29/66712	{Vertical DMOS transistors, i.e. VDMOS transistors}
29/66598	{forming drain [D] and lightly doped drain [LDD] simultaneously, e.g. using implantation through the wings a T-shaped layer, or through a specially shaped layer}	29/66719	{With a step of forming an insulating sidewall spacer}
29/66606	{with final source and drain contacts formation strictly before final or dummy gate formation, e.g. contact first technology (H01L 29/66621 takes precedence)}	29/66727	{with a step of recessing the source electrode}
29/66613	{with a gate recessing step, e.g. using local oxidation (making recessed gate LDMOS transistors H01L 29/66704)}	29/66734	{with a step of recessing the gate electrode, e.g. to form a trench gate electrode}
29/66621	{using etching to form a recess at the gate location (etching of semiconductor bodies H01L 21/302)}	29/66742	{Thin film unipolar transistors}
29/66628	{recessing the gate by forming single crystalline semiconductor material at the source or drain location}	29/6675	{Amorphous silicon or polysilicon transistors}
29/66636	{with source or drain recessed by etching or first recessed by etching and then refilled}	29/66757	{Lateral single gate single channel transistors with non-inverted structure, i.e. the channel layer is formed before the gate}
29/66643	{with source or drain regions formed by a Schottky barrier or a conductor-insulator-semiconductor structure}	29/66765	{Lateral single gate single channel transistors with inverted structure, i.e. the channel layer is formed after the gate}
29/66651	{with a single crystalline channel formed on the silicon substrate after insulating device isolation}	29/66772	{Monocrystalline silicon transistors on insulating substrates, e.g. quartz substrates (H01L 29/66666 takes precedence; thin film FinFETs H01L 29/66795)}
29/66659	{with asymmetry in the channel direction, e.g. lateral high-voltage MISFETs with drain offset region, extended drain MISFETs}	29/6678	{on sapphire substrates, e.g. SOS transistors}
29/66666	{Vertical transistors (H01L 29/66712, H01L 29/66742 take precedence)}	29/66787	{with a gate at the side of the channel}
			29/66795	{with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
			29/66803	{with a step of doping the vertical sidewall, e.g. using tilted or multi-angled implants}
			29/6681	{using dummy structures having essentially the same shape as the semiconductor body, e.g. to provide stability}
			29/66818	{the channel being thinned after patterning, e.g. sacrificial oxidation on fin}
			29/66825	{with a floating gate (H01L 29/6684 takes precedence)}
			29/66833	{with a charge trapping gate insulator, e.g. MNOS transistors}

29/6684	{ with a ferroelectric gate insulator }	29/7302	{ structurally associated with other devices (assemblies of devices H01L 25/00 ; integrated circuits H01L 27/00 ; IGBT H01L 29/7393) }
29/66848	{ with a Schottky gate, i.e. MESFET }	29/7304	{ the device being a resistive element, e.g. ballasting resistor (transistors integrated with resistors H01L 27/075) }
29/66856	{ with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence) }	29/7306	{ Point contact transistors }
29/66863	{ Lateral single gate transistors }	29/7308	{ Schottky transistors }
29/66871	{ Processes wherein the final gate is made after the formation of the source and drain regions in the active layer, e.g. dummy-gate processes }	29/7311	{ Tunnel transistors }
29/66878	{ Processes wherein the final gate is made before the formation, e.g. activation anneal, of the source and drain regions in the active layer }	29/7313	{ Avalanche transistors }
29/66886	{ Lateral transistors with two or more independent gates }	29/7315	{ Transistors with hook collector }
29/66893	{ with a PN junction gate, i.e. JFET }	29/7317	{ Bipolar thin film transistors }
29/66901	{ with a PN homojunction gate }	29/732	Vertical transistors
29/66909	{ Vertical transistors, e.g. tecnetrans }	29/7322	{ having emitter-base and base-collector junctions leaving at the same surface of the body, e.g. planar transistor }
29/66916	{ with a PN heterojunction gate }	29/7325	{ having an emitter-base junction leaving at a main surface and a base-collector junction leaving at a peripheral surface of the body, e.g. mesa planar transistor }
29/66924	{ with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence) }	29/7327	{ Inverse vertical transistors }
29/66931	{ BJT-like unipolar transistors, e.g. hot electron transistors [HET], metal base transistors [MBT], resonant tunneling transistor [RTT], bulk barrier transistor [BBT], planar doped barrier transistor [PDBT], charge injection transistor [CHINT] }	29/735	Lateral transistors
29/66939	{ with an active layer made of a group 13/15 material }	29/737	Hetero-junction transistors
29/66946	{ Charge transfer devices }	29/7371	{ Vertical transistors }
29/66954	{ with an insulated gate }	29/7373	{ having a two-dimensional base, e.g. modulation-doped base, inversion layer base, delta-doped base }
29/66962	{ with a Schottky gate }	29/7375	{ having an emitter comprising one or more non-monocrystalline elements of group IV, e.g. amorphous silicon, alloys comprising group IV elements }
29/66969	. . .	{ of devices having semiconductor bodies not comprising group 14 or group 13/15 materials (comprising selenium or tellurium in uncombined form other than as impurities in semiconductor bodies of other materials, comprising cuprous oxide or cuprous iodide H01L 21/02365) }	29/7376	{ Resonant tunnelling transistors }
29/66977	. .	{ Quantum effect devices, e.g. using quantum reflection, diffraction or interference effects, i.e. Bragg- or Aharonov-Bohm effects }	29/7378	{ comprising lattice mismatched active layers, e.g. SiGe strained layer transistors }
29/66984	. .	{ Devices using spin polarized carriers }	29/739	controlled by field-effect, {e.g. bipolar static induction transistors [BSIT] (unijunction transistors H01L 29/705) }
29/66992	. .	{ controllable only by the variation of applied heat (controllable by IR radiation H01L 31/00 ; measuring quantity of heat G01K 17/00) }	29/7391	{ Gated diode structures }
29/68	. .	controllable by only the electric current supplied, or only the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched	29/7392	{ with PN junction gate, e.g. field controlled thyristors (FCTh), static induction thyristors (SITh) }
29/685	. . .	{ Hi-Lo semiconductor devices, e.g. memory devices }	29/7393	{ Insulated gate bipolar mode transistors, i.e. IGBT; IGT; COMFET }
29/70	. . .	Bipolar devices	29/7394	{ on an insulating layer or substrate, e.g. thin film device or device isolated from the bulk substrate (H01L 29/7398 takes precedence) }
29/705	{ Double base diodes }	29/7395	{ Vertical transistors, e.g. vertical IGBT }
29/72	Transistor-type devices, i.e. able to continuously respond to applied control signals			NOTE
29/73	Bipolar junction transistors			The transistor is called vertical if the emitter and the collector are not on the same main surface or, if they are on the same main surface, at least a part of the main current

H01L

H01L 29/7395

(continued)

		has a component substantially not parallel to the main surface	29/76825	{Structures for regeneration, refreshing, leakage compensation or the like}
29/7396	{with a non planar surface, e.g. with a non planar gate or with a trench or recess or pillar in the surface of the emitter, base or collector region for improving current density or short circuiting the emitter and base regions (H01L 29/7398 takes precedence)}	29/76833	{Buried channel CCD}
			29/76841	{Two-Phase CCD}
			29/7685	{Three-Phase CCD}
			29/76858	{Four-Phase CCD}
			29/76866	{Surface Channel CCD}
			29/76875	{Two-Phase CCD}
			29/76883	{Three-Phase CCD}
29/7397	{and a gate structure lying on a slanted or vertical surface or formed in a groove, e.g. trench gate IGBT}	29/76891	{Four-Phase CCD}
			29/772	Field effect transistors
			29/7722	{using static field induced regions, e.g. SIT, PBT}
29/7398	{with both emitter and collector contacts in the same substrate side}	29/7725	{with delta-doped channel (H01L 29/778 takes precedence)}
29/74	Thyristor-type devices, e.g. having four-zone regenerative action {(two-terminal thyristors H01L 29/87)}	29/7727	{Velocity modulation transistors, i.e. VMT}
29/7404	{structurally associated with at least one other device (assemblies H01L 25/00; integrated circuits H01L 27/00)}	29/775	with one dimensional charge carrier gas channel, e.g. quantum wire FET
29/7408	{the device being a capacitor or a resistor}	29/778	with two-dimensional charge carrier gas channel, e.g. HEMT {; with two-dimensional charge-carrier layer formed at a heterojunction interface (H01L 29/803 takes precedence)}
29/7412	{the device being a diode}	29/7781	{with inverted single heterostructure, i.e. with active layer formed on top of wide bandgap layer, e.g. IHEMT}
29/7416	{the device being an antiparallel diode, e.g. RCT (shorted anode structures enabling reverse conduction H01L 29/0834)}	29/7782	{with confinement of carriers by at least two heterojunctions, e.g. DHHEMT, quantum well HEMT, DHMODFET}
29/742	{the device being a field effect transistor (for turn-on or turn-off by field effect H01L 29/745, H01L 29/749)}	29/7783	{using III-V semiconductor material}
29/7424	{having a built-in localised breakdown/breakover region, e.g. self-protected against destructive spontaneous, e.g. voltage breakover, firing}	29/7784	{with delta or planar doped donor layer (H01L 29/7785 takes precedence)}
29/7428	{having an amplifying gate structure, e.g. cascade (Darlington) configuration}	29/7785	{with more than one donor layer}
29/7432	{Asymmetrical thyristors (with a particular shorted anode structure H01L 29/0834)}	29/7786	{with direct single heterostructure, i.e. with wide bandgap layer formed on top of active layer, e.g. direct single heterostructure MIS-like HEMT}
29/7436	{Lateral thyristors}	29/7787	{with wide bandgap charge-carrier supplying layer, e.g. direct single heterostructure MODFET}
29/744	Gate-turn-off devices	29/7788	{Vertical transistors}
29/745	with turn-off by field effect	29/7789	{the two-dimensional charge carrier gas being at least partially not parallel to a main surface of the semiconductor body}
29/7455	{produced by an insulated gate structure}	29/78	with field effect produced by an insulated gate {(H01L 29/7725, H01L 29/775, H01L 29/778 take precedence)}
29/747	Bidirectional devices, e.g. triacs	29/7801	{DMOS transistors, i.e. MISFETs with a channel accommodating body or base region adjoining a drain drift region (lateral high-voltage MISFETs with channel well and drain offset region H01L 29/7835)}
29/749	with turn-on by field effect	29/7802	{Vertical DMOS transistors, i.e. VDMOS transistors}
29/76	Unipolar devices {, e.g. field effect transistors}			
29/7606	{Transistor-like structures, e.g. hot electron transistor [HET]; metal base transistor [MBT]}			
29/7613	{Single electron transistors; Coulomb blockade devices (H01L 29/7888 takes precedence)}			
29/762	Charge transfer devices			
29/765	Charge-coupled devices {(peripheral circuits for CCD storage devices G11C 19/285)}			
29/768	with field effect produced by an insulated gate			
29/76808	{Input structures}			
29/76816	{Output structures}			

29/7803	{structurally associated with at least one other device (assemblies H01L 25/00 ; integrated circuits H01L 27/00)}	29/7816	{Lateral DMOS transistors, i.e. LDMOS transistors}
		WARNING	29/7817	{structurally associated with at least one other device (assemblies H01L 25/00 ; integrated circuits H01L 27/00)}
		Groups H01L 29/7803 – H01L 29/7808 are incomplete pending reclassification of documents from group H01L 29/7802 .	29/7818	{the other device being a pn-junction diode}
		Groups H01L 29/7803 – H01L 29/7808 and H01L 29/7802 should be considered in order to perform a complete search.	29/7819	{in antiparallel, e.g. freewheel diode}
29/7804	{the other device being a pn-junction diode}	29/782	{the other device being a Schottky barrier diode}
29/7805	{in antiparallel, e.g. freewheel diode}	29/7821	{the other device being a breakdown diode, e.g. Zener diode}
29/7806	{the other device being a Schottky barrier diode}	29/7823	{with an edge termination structure (guard regions per se H01L 29/0619 ; field plates per se H01L 29/402)}
29/7808	{the other device being a breakdown diode, e.g. Zener diode}	29/7824	{with a substrate comprising an insulating layer, e.g. SOI-LDMOS transistors}
29/7809	{having both source and drain contacts on the same surface, i.e. Up-Drain VDMOS transistors}	29/7825	{with trench gate electrode (trench gate electrodes per se H01L 29/4236)}
29/781	{Inverted VDMOS transistors, i.e. Source-Down VDMOS transistors}	29/7826	{with voltage or current sensing structure, e.g. emulator section, overcurrent sensing cell}
29/7811	{with an edge termination structure (guard regions per se H01L 29/0619 ; field plates per se H01L 29/402)}	29/7827	{Vertical transistors (H01L 29/7802 , H01L 29/78642 take precedence)}
		WARNING	29/7828	{without inversion channel, e.g. vertical ACCUFETs, normally-on vertical MISFETs}
		Group H01L 29/7811 is incomplete pending reclassification of documents from group H01L 29/7802 .	29/783	{comprising a gate to body connection, i.e. bulk dynamic threshold voltage MOSFET (for thin film transistors H01L 29/78612 , H01L 29/78696)}
		Groups H01L 29/7811 and H01L 29/7802 should be considered in order to perform a complete search.	29/7831	{with multiple gate structure (FinFETs or MuGFETs H01L 29/7855 , thin film transistors H01L 29/78645)}
29/7812	{with a substrate comprising an insulating layer, e.g. SOI-VDMOS transistors}	29/7832	{the structure comprising a MOS gate and at least one non-MOS gate, e.g. JFET or MESFET gate}
29/7813	{with trench gate electrode, e.g. UMOS transistors (trench gate electrodes per se H01L 29/4236)}	29/7833	{with lightly doped drain or source extension, e.g. LDD MOSFET's; DDD MOSFET's (for thin film transistors H01L 29/78618)}
29/7815	{with voltage or current sensing structure, e.g. emulator section, overcurrent sensing cell}	29/7834	{with a non-planar structure, e.g. the gate or the source or the drain being non-planar}
		WARNING			NOTE
		Group H01L 29/7815 is incomplete pending reclassification of documents from group H01L 29/7802 .			Field oxide sunken in the substrate and not filling a groove is not an element characterising a non-planar structure
		Groups H01L 29/7815 and H01L 29/7802 should be considered in order to perform a complete search.	29/7835	{with asymmetrical source and drain regions, e.g. lateral high-voltage MISFETs with drain offset region, extended drain MISFETs}
			29/7836	{with a significant overlap between the lightly doped extension and the gate electrode (H01L 29/7834 , H01L 29/7835 take precedence)}

29/7838	{ without inversion channel, e.g. buried channel lateral MISFETs, normally-on lateral MISFETs, depletion-mode lateral MISFETs }	29/78609	{ for preventing leakage current (H01L 29/78618 takes precedence) }
29/7839	{ with Schottky drain or source contact }	29/78612	{ for preventing the kink- or the snapback effect, e.g. discharging the minority carriers of the channel region for preventing bipolar effect }
29/78391	{ the gate comprising a layer which is used for its ferroelectric properties }	29/78615	{ with a body contact }
29/7841	{ with floating body, e.g. programmable transistors }	29/78618	{ characterised by the drain or the source properties, e.g. the doping structure, the composition, the sectional shape or the contact structure (silicide contacts, electrodes in general H01L 29/458) }
29/7842	{ means for exerting mechanical stress on the crystal lattice of the channel region, e.g. using a flexible substrate (variation of the composition of the channel H01L 29/1054) }	29/78621	{ with LDD structure or an extension or an offset region or characterised by the doping profile }
29/7843	{ the means being an applied insulating layer }	29/78624	{ the source and the drain regions being asymmetrical }
29/7845	{ the means being a conductive material, e.g. silicided S/D or Gate }	29/78627	{ with a significant overlap between the lightly doped drain and the gate electrode, e.g. GOLDD }
29/7846	{ the means being located in the lateral device isolation region, e.g. STI }	2029/7863	{ with an LDD consisting of more than one lightly doped zone or having a non-homogeneous dopant distribution, e.g. graded LDD }
29/7847	{ using a memorization technique, e.g. re-crystallization under strain, bonding on a substrate having a thermal expansion coefficient different from the one of the region }	29/78633	{ with a light shield }
29/7848	{ the means being located in the source/drain region, e.g. SiGe source and drain }	29/78636	{ with supplementary region or layer for improving the flatness of the device }
29/7849	{ the means being provided under the channel }	29/78639	{ with a drain or source connected to a bulk conducting substrate }
29/785	{ having a channel with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET }	29/78642	{ Vertical transistors }
29/7851	{ with the body tied to the substrate }	29/78645	{ with multiple gate }
29/7853	{ the body having a non-rectangular crosssection }	NOTE In groups H01L 29/78651 - H01L 29/78696 , the materials specified for the transistors are the material of the channel region		
29/7854	{ with rounded corners }			
29/7855	{ with at least two independent gates }	29/78648	{ arranged on opposing sides of the channel }
29/7856	{ with an non-uniform gate, e.g. varying doping structure, shape or composition on different sides of the fin, or different gate insulator thickness or composition on opposing fin sides (H01L 29/7855 takes precedence) }	29/78651	{ Silicon transistors (H01L 29/78606 - H01L 29/78645 take precedence) }
2029/7857	{ of the accumulation type }	29/78654	{ Monocrystalline silicon transistors }
2029/7858	{ having contacts specially adapted to the FinFET geometry, e.g. wrap-around contacts }	29/78657	{ SOS transistors }
29/786	Thin film transistors, { i.e. transistors with a channel being at least partly a thin film (transistors having only the source or the drain region on an insulator layer H01L 29/0653 ; thin film FinFETs H01L 29/785) }	29/7866	{ Non-monocrystalline silicon transistors }
29/78603	{ characterised by the insulating substrate or support (H01L 29/78657 takes precedence) }	29/78663	{ Amorphous silicon transistors }
29/78606	{ with supplementary region or layer in the thin film or in the insulated bulk substrate supporting it for controlling or increasing the safety of the device (H01L 29/78642 , H01L 29/78645 take precedence) }	29/78666	{ with normal-type structure, e.g. with top gate }
			29/78669	{ with inverted-type structure, e.g. with bottom gate }
			29/78672	{ Polycrystalline or microcrystalline silicon transistor }

29/78675	{with normal-type structure, e.g. with top gate}	29/80	with field effect produced by a PN or other rectifying junction gate {, i.e. potential-jump barrier}
29/78678	{with inverted-type structure, e.g. with bottom gate}	29/802	{with heterojunction gate, e.g. transistors with semiconductor layer acting as gate insulating layer, MIS-like transistors (H01L 29/806 takes precedence; with one dimensional electron gas H01L 29/775 ; with dimensional electron gas H01L 29/778)}
29/78681	{having a semiconductor body comprising $A_{III}B_V$ or $A_{II}B_{VI}$ or $A_{IV}B_{VI}$ semiconductor materials, or Se or Te}	29/803	{Programmable transistors, e.g. with charge-trapping quantum well}
29/78684	{having a semiconductor body comprising semiconductor materials of Group IV not being silicon, or alloys including an element of the group IV, e.g. Ge, SiN alloys, SiC alloys (H01L 29/7869 takes precedence)}	29/806	{with Schottky drain or source contact}
29/78687	{with a multilayer structure or superlattice structure}	29/808	with a PN junction gate {, e.g. PN homojunction gate (H01L 29/7725 , H01L 29/775 , H01L 29/778 , H01L 29/806 take precedence)}
29/7869	{having a semiconductor body comprising an oxide semiconductor material, e.g. zinc oxide, copper aluminium oxide, cadmium stannate}	29/8083	{Vertical transistors (SIT H01L 29/7722)}
29/78693	{the semiconducting oxide being amorphous}	29/8086	{Thin film JFET's}
29/78696	{characterised by the structure of the channel, e.g. multichannel, transverse or longitudinal shape, length or width, doping structure, or the overlap or alignment between the channel and the gate, the source or the drain, or the contacting structure of the channel (H01L 29/78612 takes precedence; transistors having a drain offset region or a lightly doped drain [LDD] H01L 29/78621)}	29/812	with a Schottky gate {(H01L 29/7725 , H01L 29/775 , H01L 29/778 , H01L 29/806 take precedence; with Schottky contact on top of heterojunction gate H01L 29/802)}
29/788	with floating gate {(H01L 29/78391 takes precedence)}	29/8122	{Vertical transistors (SIT, PBT H01L 29/7722)}
29/7881	{Programmable transistors with only two possible levels of programming (H01L 29/7888 takes precedence)}	29/8124	{with multiple gate}
29/7882	{charging by injection of carriers through a conductive insulator, e.g. Poole-Frankel conduction}	29/8126	{Thin film MESFET's}
29/7883	{charging by tunnelling of carriers, e.g. Fowler-Nordheim tunnelling}	29/8128	{with recessed gate}
29/7884	{charging by hot carrier injection}	29/82	. . .	controllable by variation of the magnetic field applied to the device
29/7885	{Hot carrier injection from the channel}	29/84	. . .	controllable by variation of applied mechanical force, e.g. of pressure
29/7886	{Hot carrier produced by avalanche breakdown of a PN junction, e.g. FAMOS}	29/86	. . .	controllable only by variation of the electric current supplied, or only the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched
29/7887	{Programmable transistors with more than two possible different levels of programming}	29/8605	. . .	Resistors with PN junctions
29/7888	{Transistors programmable by two single electrons}	29/861	. . .	Diodes
29/7889	{Vertical transistors, i.e. transistors having source and drain not in the same horizontal plane}	29/8611	{Planar PN junction diodes}
29/792	with charge trapping gate insulator, e.g. MNOS-memory transistors	29/8613	{Mesa PN junction diodes}
29/7923	{Programmable transistors with more than two possible different levels of programming}	29/8615	{Hi-lo semiconductor devices, e.g. memory devices}
29/7926	{Vertical transistors, i.e. transistors having source and drain not in the same horizontal plane}	29/8616	{Charge trapping diodes}
			29/8618	{Diodes with bulk potential barrier, e.g. Camel diodes, Planar Doped Barrier diodes, Graded bandgap diodes}
			29/862	Point contact diodes
			29/864	Transit-time diodes, e.g. IMPATT, TRAPATT diodes
			29/866	Zener diodes
			29/868	PIN diodes
			29/87	Thyristor diodes, e.g. Shockley diodes, break-over diodes
			29/872	Schottky diodes
			29/8725	{of the trench MOS barrier type [TMBS]}
			29/88	Tunnel-effect diodes
			29/882	{Resonant tunneling diodes, i.e. RTD, RTBD}
			29/885	Esaki diodes
			29/92	. . .	Capacitors with potential-jump barrier or surface barrier

- 29/93 Variable capacitance diodes, e.g. varactors
 29/94 Metal-insulator-semiconductors, e.g. MOS
 29/945 {Trench capacitors}
- 31/00** **Semiconductor devices sensitive to infra-red radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation and adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof; Details thereof** ([H01L 51/42](#) takes precedence; devices consisting of a plurality of solid state components formed in, or on, a common substrate, other than combinations of radiation-sensitive components with one or more electric light sources, [H01L 27/00](#); measurement of X-radiation, gamma radiation, corpuscular radiation or cosmic radiation with semiconductor detectors [G01T 1/24](#), with resistance detectors [G01T 1/26](#); measurement of neutron radiation with semiconductor detectors [G01T 3/08](#); couplings of light guides with optoelectronic elements [G02B 6/42](#); obtaining energy from radioactive sources [G21H](#))
- 31/02 . Details
 31/02002 . . {Arrangements for conducting electric current to or from the device in operations}
 31/02005 . . . {for device characterised by at least one potential jump barrier or surface barrier}
 31/02008 {for solar cells or solar cell modules}
 31/0201 {comprising specially adapted module bus-bar structures}
 31/02013 {comprising output lead wires elements}
 31/02016 . . {Circuit arrangements of general character for the devices}
 31/02019 . . . {for devices characterised by at least one potential jump barrier or surface barrier}
 31/02021 {for solar cells (electrical connection means, e.g. junction boxes, specially adapted for structural association with photovoltaic modules [H02S 40/34](#))}
 31/02024 {Position sensitive and lateral effect photodetectors; Quadrant photodiodes}
 31/02027 {for devices working in avalanche mode}
 31/0203 . . Containers; Encapsulations {, e.g. encapsulation of photodiodes} (for photovoltaic devices [H01L 31/048](#); for organic photosensitive devices [H01L 51/44](#))
 31/0216 . . Coatings ([H01L 31/041](#) takes precedence)
 31/02161 . . . {for devices characterised by at least one potential jump barrier or surface barrier}
 31/02162 {for filtering or shielding light, e.g. multicolour filters for photodetectors}
 31/02164 {for shielding light, e.g. light blocking layers, cold shields for infra-red detectors}
 31/02165 {using interference filters, e.g. multilayer dielectric filters (interference filters [G02B 5/28](#))}
 31/02167 {for solar cells}
 31/02168 {the coatings being antireflective or having enhancing optical properties for the solar cells}
 31/0224 . . Electrodes
- 31/022408 . . . {for devices characterised by at least one potential jump barrier or surface barrier}
 31/022416 {comprising ring electrodes}
 31/022425 {for solar cells}
 31/022433 {Particular geometry of the grid contacts}
 31/022441 {Electrode arrangements specially adapted for back-contact solar cells}
 31/02245 {for metallisation wrap-through [MWT] type solar cells}
 31/022458 {for emitter wrap-through [EWT] type solar cells, e.g. interdigitated emitter-base back-contacts}
 31/022466 . . . {made of transparent conductive layers, e.g. TCO, ITO layers}
 31/022475 {composed of indium tin oxide [ITO]}
 31/022483 {composed of zinc oxide [ZnO]}
 31/022491 {composed of a thin transparent metal layer, e.g. gold}
 31/0232 . . Optical elements or arrangements associated with the device ([H01L 31/0236](#) takes precedence; for photovoltaic cells [H01L 31/054](#); for photovoltaic modules [H02S 40/20](#))
 31/02322 . . . {comprising luminescent members, e.g. fluorescent sheets upon the device}
 31/02325 . . . {the optical elements not being integrated nor being directly associated with the device}
 31/02327 . . . {the optical elements being integrated or being directly associated to the device, e.g. back reflectors (optical coatings [H01L 31/0216](#))}
 31/0236 . . Special surface textures
 31/02363 . . . {of the semiconductor body itself, e.g. textured active layers}
 31/02366 . . . {of the substrate or of a layer on the substrate, e.g. textured ITO/glass substrate or superstrate, textured polymer layer on glass substrate}
 31/024 . . Arrangements for cooling, heating, ventilating or temperature compensation (for photovoltaic devices [H01L 31/052](#))
 31/0248 . characterised by their semiconductor bodies
 31/0256 . . characterised by the material
 31/0264 . . . Inorganic materials
 31/0272 Selenium or tellurium
 31/02725 {characterised by the doping material}
 31/028 including, apart from doping material or other impurities, only elements of Group IV of the Periodic System
 31/0284 {comprising porous silicon as part of the active layer(s) (porous silicon as antireflective layer for photodiodes [H01L 31/0216](#); for solar cells [H01L 31/02168](#))}
 31/0288 characterised by the doping material
 31/0296 including, apart from doping material or other impurities, only $A_{II}B_{VI}$ compounds, e.g. CdS, ZnS, HgCdTe
 31/02963 {characterised by the doping material}
 31/02966 {including ternary compounds, e.g. HgCdTe}
 31/0304 including, apart from doping materials or other impurities, only $A_{III}B_V$ compounds
 31/03042 {characterised by the doping material}
 31/03044 {comprising a nitride compounds, e.g. GaN}

- 31/03046 {including ternary or quaternary compounds, e.g. GaAlAs, InGaAs, InGaAsP}
- 31/03048 {comprising a nitride compounds, e.g. InGaN}
- 31/0312 including, apart from doping materials or other impurities, only $A_{IV}B_{IV}$ compounds, e.g. SiC
- 31/03125 {characterised by the doping material}
- 31/032 including, apart from doping materials or other impurities, only compounds not provided for in groups [H01L 31/0272](#) - [H01L 31/0312](#)
- 31/0321 {characterised by the doping material ([H01L 31/0323](#), [H01L 31/0325](#) take precedence)}
- 31/0322 {comprising only $A_{IV}B_{III}C_{VI}$ chalcopyrite compounds, e.g. Cu In Se₂, Cu Ga Se₂, Cu In Ga Se₂}
- 31/0323 {characterised by the doping material}
- 31/0324 {comprising only $A_{IV}B_{VI}$ or $A_{II}B_{IV}C_{VI}$ chalcogenide compounds, e.g. Pb Sn Te}
- 31/0325 {characterised by the doping material}
- 31/0326 {comprising $A_{IV}B_{II}C_{IV}D_{VI}$ kesterite compounds, e.g. Cu₂ZnSnSe₄, Cu₂ZnSnS₄}
- 31/0327 {characterised by the doping material}
- 31/0328 including, apart from doping materials or other impurities, semiconductor materials provided for in two or more of groups [H01L 31/0272](#) - [H01L 31/032](#)
- 31/0336 in different semiconductor regions, e.g. Cu₂X/CdX hetero-junctions, X being an element of Group VI of the Periodic System
- 31/03365 {comprising only Cu₂X / CdX heterojunctions, X being an element of Group VI of the Periodic System}
- 2031/0344 {Organic materials}
- 31/0352 characterised by their shape or by the shapes, relative sizes or disposition of the semiconductor regions
- 31/035209 {comprising a quantum structures}
- 31/035218 {the quantum structure being quantum dots}
- 31/035227 {the quantum structure being quantum wires, or nanorods ([carbon nanotubes](#) [H01L 51/0048](#))}
- 31/035236 {Superlattices; Multiple quantum well structures}
- 31/035245 {characterised by amorphous semiconductor layers}
- 31/035254 {including, apart from doping materials or other impurities, only elements of Group IV of the Periodic System, e.g. Si-SiGe superlattices}
- 31/035263 {Doping superlattices, e.g. nipi superlattices}
- 31/035272 {characterised by at least one potential jump barrier or surface barrier}
- 31/035281 {Shape of the body}
- 31/03529 {Shape of the potential jump barrier or surface barrier}
- 31/036 characterised by their crystalline structure or particular orientation of the crystalline planes
- 31/0368 including polycrystalline semiconductors ([H01L 31/0392](#) takes precedence)
- 31/03682 {including only elements of Group IV of the Periodic System}
- 31/03685 {including microcrystalline silicon, uc-Si}
- 31/03687 {including microcrystalline $A_{IV}B_{IV}$ alloys, e.g. uc-SiGe, uc-SiC}
- 31/0376 including amorphous semiconductors ([H01L 31/0392](#) takes precedence)
- 31/03762 {including only elements of Group IV of the Periodic System}
- 31/03765 {including $A_{IV}B_{IV}$ compounds or alloys, e.g. SiGe, SiC}
- 31/03767 {presenting light-induced characteristic variations, e.g. Staebler-Wronski effect}
- 31/0384 including other non-monocrystalline materials, e.g. semiconductor particles embedded in an insulating material ([H01L 31/0392](#) takes precedence)
- 31/03845 {comprising semiconductor nanoparticles embedded in a semiconductor matrix ([in insulating matrix](#) [H01L 31/0384](#))}
- 31/0392 including thin films deposited on metallic or insulating substrates {; characterised by specific substrate materials or substrate features or by the presence of intermediate layers, e.g. barrier layers, on the substrate ([textured substrates](#) [H01L 31/02366](#))}
- 31/03921 {including only elements of Group IV of the Periodic System}
- 31/03923 {including $A_{IV}B_{III}C_{VI}$ compound materials, e.g. CIS, CIGS}
- 31/03925 {including $A_{II}B_{VI}$ compound materials, e.g. CdTe, CdS}
- 31/03926 {comprising a flexible substrate}
- 31/03928 {including $A_{IV}B_{III}C_{VI}$ compound, e.g. CIS, CIGS deposited on metal or polymer foils}
- 31/04 adapted as photovoltaic [PV] conversion devices ([testing thereof during manufacture](#) {[H01L 22/00](#)}; [testing thereof after manufacture](#) [H02S 50/10](#))
- 31/041 Provisions for preventing damage caused by corpuscular radiation, e.g. for space applications
- 31/042 PV modules or arrays of single PV cells ([supporting structures for PV modules](#) [H02S 20/00](#))
- 31/043 Mechanically stacked PV cells
- 31/044 including bypass diodes ([bypass diodes in the junction box](#) [H02S 40/34](#))
- 31/0443 comprising bypass diodes integrated or directly associated with the devices, e.g. bypass diodes integrated or formed in or on the same substrate as the photovoltaic cells
- 31/0445 including thin film solar cells, e.g. single thin film a-Si, CIS or CdTe solar cells
- 31/046 PV modules composed of a plurality of thin film solar cells deposited on the same substrate
- 31/0463 characterised by special patterning methods to connect the PV cells in a module, e.g. laser cutting of the conductive or active layers
- 31/0465 comprising particular structures for the electrical interconnection of adjacent PV cells in the module ([H01L 31/0463](#) takes precedence)

- 31/0468 comprising specific means for obtaining partial light transmission through the module, e.g. partially transparent thin film solar modules for windows
- 31/047 . . . PV cell arrays including PV cells having multiple vertical junctions or multiple V-groove junctions formed in a semiconductor substrate
- 31/0475 . . . PV cell arrays made by cells in a planar, e.g. repetitive, configuration on a single semiconductor substrate; PV cell microarrays (PV modules composed of a plurality of thin film solar cells deposited on the same substrate [H01L 31/046](#))
- 31/048 . . . Encapsulation of modules
- 31/0481 {characterised by the composition of the encapsulation material}
- 31/0488 {Double glass encapsulation, e.g. photovoltaic cells arranged between front and rear glass sheets}
- 31/049 Protective back sheets
- 31/05 . . . Electrical interconnection means between PV cells inside the PV module, e.g. series connection of PV cells (electrodes [H01L 31/0224](#); electrical interconnection of thin film solar cells formed on a common substrate [H01L 31/046](#); particular structures for electrical interconnecting of adjacent thin film solar cells in the module [H01L 31/0465](#); electrical interconnection means specially adapted for electrically connecting two or more PV modules [H02S 40/36](#))
- 31/0504 {specially adapted for series or parallel connection of solar cells in a module}
- 31/0508 {the interconnection means having a particular shape}
- 31/0512 {made of a particular material or composition of materials}
- 31/0516 {specially adapted for interconnection of back-contact solar cells}
- 31/052 . . Cooling means directly associated or integrated with the PV cell, e.g. integrated Peltier elements for active cooling or heat sinks directly associated with the PV cells (cooling means in combination with the PV module [H02S 40/42](#))
- 31/0521 . . . {using a gaseous or a liquid coolant, e.g. air flow ventilation, water circulation}
- 31/0525 . . . including means to utilise heat energy directly associated with the PV cell, e.g. integrated Seebeck elements
- 31/053 . . Energy storage means directly associated or integrated with the PV cell, e.g. a capacitor integrated with a PV cell (energy storage means associated with the PV module [H02S 40/38](#))
- 31/054 . . Optical elements directly associated or integrated with the PV cell, e.g. light-reflecting means or light-concentrating means
- 31/0543 . . . {comprising light concentrating means of the refractive type, e.g. lenses}
- 31/0547 . . . {comprising light concentrating means of the reflecting type, e.g. parabolic mirrors, concentrators using total internal reflection}
- 31/0549 . . . {comprising spectrum splitting means, e.g. dichroic mirrors}
- 31/055 . . . where light is absorbed and re-emitted at a different wavelength by the optical element directly associated or integrated with the PV cell, e.g. by using luminescent material, fluorescent concentrators or up-conversion arrangements
- 31/056 . . . the light-reflecting means being of the back surface reflector [BSR] type
- 31/06 . . characterised by at least one potential-jump barrier or surface barrier
- 31/061 . . . the potential barriers being of the point-contact type ([H01L 31/07](#) takes precedence)
- 31/062 . . . the potential barriers being only of the metal-insulator-semiconductor type
- 31/065 . . . the potential barriers being only of the graded gap type
- 31/068 . . . the potential barriers being only of the PN homojunction type, e.g. bulk silicon PN homojunction solar cells or thin film polycrystalline silicon PN homojunction solar cells
- 31/0682 {back-junction, i.e. rearside emitter, solar cells, e.g. interdigitated base-emitter regions back-junction cells}
- 31/0684 {double emitter cells, e.g. bifacial solar cells}
- 31/0687 Multiple junction or tandem solar cells
- 31/06875 {inverted grown metamorphic [IMM] multiple junction solar cells, e.g. III-V compounds inverted metamorphic multi-junction cells}
- 31/0693 the devices including, apart from doping material or other impurities, only $A_{III}B_V$ compounds, e.g. GaAs or InP solar cells
- 31/07 . . . the potential barriers being only of the Schottky type
- 31/072 . . . the potential barriers being only of the PN heterojunction type
- 31/0725 Multiple junction or tandem solar cells
- 31/073 comprising only $A_{II}B_{VI}$ compound semiconductors, e.g. CdS/CdTe solar cells
- 31/0735 comprising only $A_{III}B_V$ compound semiconductors, e.g. GaAs/AlGaAs or InP/GaInAs solar cells
- 31/074 comprising a heterojunction with an element of Group IV of the Periodic System, e.g. ITO/Si, GaAs/Si or CdTe/Si solar cells
- 31/0745 comprising a $A_{IV}B_{IV}$ heterojunction, e.g. Si/Ge, SiGe/Si or Si/SiC solar cells
- 31/0747 comprising a heterojunction of crystalline and amorphous materials, e.g. heterojunction with intrinsic thin layer or HIT® solar cells; solar cells
- 31/0749 including a $A_{I}B_{III}C_{VI}$ compound, e.g. CdS/CuInSe₂ [CIS] heterojunction solar cells
- 31/075 . . . the potential barriers being only of the PIN type
- 31/076 Multiple junction or tandem solar cells
- 31/077 the devices comprising monocrystalline or polycrystalline materials
- 31/078 . . . including different types of potential barriers provided for in two or more of groups [H01L 31/062](#) - [H01L 31/075](#)
- 31/08 . . in which radiation controls flow of current through the device, e.g. photoresistors

- 31/085 . . {the device being sensitive to very short wavelength, e.g. X-ray, Gamma-rays}
- 31/09 . . Devices sensitive to infra-red, visible or ultraviolet radiation ([H01L 31/101 takes precedence](#))
- 31/095 . . . {comprising amorphous semiconductors}
- 31/10 . . characterised by at least one potential-jump barrier or surface barrier, e.g. phototransistors
- 31/101 . . . Devices sensitive to infra-red, visible or ultra-violet radiation
- 31/1013 {devices sensitive to two or more wavelengths, e.g. multi-spectrum radiation detection devices}
- 31/1016 {comprising transparent or semitransparent devices}
- 31/102 characterised by only one potential barrier or surface barrier
- 31/1025 {the potential barrier being of the point contact type}
- 31/103 the potential barrier being of the PN homojunction type
- 31/1032 {the devices comprising active layers formed only by $A_{II}B_{VI}$ compounds, e.g. HgCdTe IR photodiodes}
- 31/1035 {the devices comprising active layers formed only by $A_{III}B_V$ compounds}
- 31/1037 {the devices comprising active layers formed only by $A_{IV}B_{VI}$ compounds}
- 31/105 the potential barrier being of the PIN type
- 31/1055 {the devices comprising amorphous materials of Group IV of the Periodic System}
- 31/107 the potential barrier working in avalanche mode, e.g. avalanche photodiode
- 31/1075 {in which the active layers, e.g. absorption or multiplication layers, form an heterostructure, e.g. SAM structure}
- 31/108 the potential barrier being of the Schottky type
- 31/1085 {the devices being of the Metal-Semiconductor-Metal [MSM] Schottky barrier type}
- 31/109 the potential barrier being of the PN heterojunction type
- 31/11 characterised by two potential barriers or surface barriers, e.g. bipolar phototransistor
- 31/1105 {the device being a bipolar phototransistor}
- 31/111 characterised by at least three potential barriers, e.g. photothyristor
- 31/1113 {the device being a photothyristor}
- 31/1116 {of the static induction type}
- 31/112 characterised by field-effect operation, e.g. junction field-effect phototransistor
- 31/1121 {Devices with Schottky gate}
- 31/1122 {the device being a CCD device}
- 31/1123 {the device being a photo MESFET}
- 31/1124 {Devices with PN homojunction gate}
- 31/1125 {the device being a CCD device}
- 31/1126 {the device being a field-effect phototransistor}
- 31/1127 {Devices with PN heterojunction gate}
- 31/1128 {the device being a CCD device}
- 31/1129 {the device being a field-effect phototransistor}
- 31/113 being of the conductor-insulator-semiconductor type, e.g. metal-insulator-semiconductor field-effect transistor
- 31/1133 {the device being a conductor-insulator-semiconductor diode or a CCD device}
- 31/1136 {the device being a metal-insulator-semiconductor field-effect transistor}
- 31/115 . . . Devices sensitive to very short wavelength, e.g. X-rays, gamma-rays or corpuscular radiation
- 31/117 of the bulk effect radiation detector type, e.g. Ge-Li compensated PIN gamma-ray detectors
- 31/1175 {Li compensated PIN gamma-ray detectors}
- 31/118 of the surface barrier or shallow PN junction detector type, e.g. surface barrier alpha-particle detectors
- 31/1185 {of the shallow PN junction detector type}
- 31/119 characterised by field-effect operation, e.g. MIS type detectors
- 31/12 . . structurally associated with, e.g. formed in or on a common substrate with, one or more electric light sources, e.g. electroluminescent light sources, and electrically or optically coupled thereto ([semiconductor devices with at least one potential barrier or surface barrier adapted for light emission H01L 33/00; amplifiers using electroluminescent element and photocell H03F 17/00; electroluminescent light sources per se H05B 33/00](#))
- 31/125 . . {Composite devices with photosensitive elements and electroluminescent elements within one single body}
- 31/14 . . the light source or sources being controlled by the semiconductor device sensitive to radiation, e.g. image converters, image amplifiers, image storage devices
- 31/141 . . . {the semiconductor device sensitive to radiation being without a potential-jump barrier or surface barrier}
- 31/143 {the light source being a semiconductor device with at least one potential-jump barrier or surface barrier, e.g. light emitting diode}
- 31/145 . . . {the semiconductor device sensitive to radiation being characterised by at least one potential-jump barrier or surface barrier}
- 31/147 . . . the light sources and the devices sensitive to radiation all being semiconductor devices characterised by at least one potential or surface barrier
- 31/153 formed in, or on, a common substrate
- 31/16 . . the semiconductor device sensitive to radiation being controlled by the light source or sources
- 31/161 . . . {Semiconductor device sensitive to radiation without a potential-jump or surface barrier, e.g. photoresistors}
- 31/162 {the light source being a semiconductor device with at least one potential-jump barrier or surface barrier, e.g. a light emitting diode}
- 31/164 {Optical potentiometers}

- 31/165 . . . {the semiconductor sensitive to radiation being characterised by at least one potential-jump or surface barrier}
- 31/167 . . . the light sources and the devices sensitive to radiation all being semiconductor devices characterised by at least one potential or surface barrier
- 31/173 formed in, or on, a common substrate
- 31/18 . . . Processes or apparatus peculiar to the manufacture or treatment of these devices or of parts thereof (not peculiar thereto [H01L 21/00](#))
- 31/1804 . . {comprising only elements of Group IV of the Periodic System}
- 31/1808 . . . {including only Ge}
- 31/1812 . . . {including only $A_{IV}B_{IV}$ alloys, e.g. SiGe}
- 31/1816 {Special manufacturing methods for microcrystalline layers, e.g. uc-SiGe, uc-SiC}
- 31/182 . . . {Special manufacturing methods for polycrystalline Si, e.g. Si ribbon, poly Si ingots, thin films of polycrystalline Si}
- 31/1824 {Special manufacturing methods for microcrystalline Si, uc-Si}
- 31/1828 . . {the active layers comprising only $A_{II}B_{VI}$ compounds, e.g. CdS, ZnS, CdTe}
- 31/1832 . . . {comprising ternary compounds, e.g. Hg Cd Te}
- 31/1836 . . . {comprising a growth substrate not being an $A_{II}B_{VI}$ compound}
- 31/184 . . {the active layers comprising only $A_{III}B_V$ compounds, e.g. GaAs, InP}
- 31/1844 . . . {comprising ternary or quaternary compounds, e.g. Ga Al As, In Ga As P}
- 31/1848 {comprising nitride compounds, e.g. InGa_N, InGaAl_N}
- 31/1852 . . . {comprising a growth substrate not being an $A_{III}B_V$ compound}
- 31/1856 . . . {comprising nitride compounds, e.g. GaN}
- 31/186 . . {Particular post-treatment for the devices, e.g. annealing, impurity gettering, short-circuit elimination, recrystallisation}
- 31/1864 . . . {Annealing}
- 31/1868 . . . {Passivation}
- 31/1872 . . . {Recrystallisation}
- 31/1876 . . {Particular processes or apparatus for batch treatment of the devices}
- 31/188 . . . {Apparatus specially adapted for automatic interconnection of solar cells in a module}
- 31/1884 . . {Manufacture of transparent electrodes, e.g. TCO, ITO}
- 31/1888 . . . {methods for etching transparent electrodes}
- 31/1892 . . {methods involving the use of temporary, removable substrates}
- 31/1896 . . . {for thin-film semiconductors}
- 31/20 . . such devices or parts thereof comprising amorphous semiconductor materials
- 31/202 . . . {including only elements of Group IV of the Periodic System}
- 31/204 {including $A_{IV}B_{IV}$ alloys, e.g. SiGe, SiC}
- 31/206 . . . {Particular processes or apparatus for continuous treatment of the devices, e.g. roll-to roll processes, multi-chamber deposition}
- 31/208 . . . {Particular post-treatment of the devices, e.g. annealing, short-circuit elimination}
- 33/00** **Semiconductor devices with at least one potential-jump barrier or surface barrier specially adapted for light emission; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof; Details thereof** ([H01L 51/50](#) takes precedence; devices consisting of a plurality of semiconductor components formed in or on a common substrate and including semiconductor components with at least one potential-jump barrier or surface barrier, specially adapted for light emission [H01L 27/15](#); semiconductor lasers [H01S 5/00](#))
- NOTES**
1. This group covers light emitting diodes [LEDs] or superluminescent diodes [SLDs], including LEDs or SLDs emitting infra-red [IR] light or ultra-violet [UV] light.
 2. In this group, the first place priority rule is applied, i.e. at each hierarchical level, in the absence of an indication to the contrary, classification is made in the first appropriate place.
- 33/0004 . {Devices characterised by their operation}
- 33/0008 . . {having p-n or hi-lo junctions}
- 33/0012 . . . {p-i-n devices}
- 33/0016 . . . {having at least two p-n junctions}
- 33/002 . . {having heterojunctions or graded gap}
- 33/0025 . . . {comprising only $A_{III}B_V$ compounds}
- 33/0029 . . . {comprising only $A_{II}B_{VI}$ compounds}
- 33/0033 . . {having Schottky barriers}
- 33/0037 . . {having a MIS barrier layer}
- 33/0041 . . {characterised by field-effect operation}
- 33/0045 . . {the devices being superluminescent diodes}
- 33/005 . {Processes}
- 33/0054 . . {for devices with an active region comprising only group IV elements}
- 33/0058 . . . {comprising amorphous semiconductors}
- 33/0062 . . {for devices with an active region comprising only III-V compounds}
- 33/0066 . . . {with a substrate not being a III-V compound}
- 33/007 {comprising nitride compounds}
- 33/0075 . . . {comprising nitride compounds}
- 33/0079 . . . {wafer bonding or at least partial removal of the growth substrate}
- 33/0083 . . {for devices with an active region comprising only II-VI compounds}
- 33/0087 . . . {with a substrate not being a II-VI compound}
- 33/0091 . . {for devices with an active region comprising only IV-VI compounds}
- 33/0095 . . {Post-treatments of the devices, e.g. annealing, recrystallisation, short-circuit elimination}
- 33/02 . characterised by the semiconductor bodies
- 33/025 . . {Physical imperfections, e.g. particular concentration or distribution of impurities}
- 33/04 . . with a quantum effect structure or superlattice, e.g. tunnel junction
- 33/06 . . . within the light emitting region, e.g. quantum confinement structure or tunnel barrier

33/08	<ul style="list-style-type: none"> with a plurality of light emitting regions, e.g. laterally discontinuous light emitting layer or photoluminescent region integrated within the semiconductor body (H01L 27/15 takes precedence) 	33/48	<ul style="list-style-type: none"> characterised by the semiconductor body packages
33/10	<ul style="list-style-type: none"> with a light reflecting structure, e.g. semiconductor Bragg reflector 		
33/105	<ul style="list-style-type: none"> {with a resonant cavity structure} 	33/483	<ul style="list-style-type: none"> {Containers}
33/12	<ul style="list-style-type: none"> with a stress relaxation structure, e.g. buffer layer 	33/486	<ul style="list-style-type: none"> {adapted for surface mounting}
33/14	<ul style="list-style-type: none"> with a carrier transport control structure, e.g. highly-doped semiconductor layer or current-blocking structure 	33/50	<ul style="list-style-type: none"> Wavelength conversion elements
33/145	<ul style="list-style-type: none"> {with a current-blocking structure} 	33/501	<ul style="list-style-type: none"> {characterised by the materials, e.g. binder}
33/16	<ul style="list-style-type: none"> with a particular crystal structure or orientation, e.g. polycrystalline, amorphous or porous 	33/502	<ul style="list-style-type: none"> {Wavelength conversion materials}
33/18	<ul style="list-style-type: none"> within the light emitting region 	33/504	<ul style="list-style-type: none"> {Elements with two or more wavelength conversion materials}
	<p>NOTE</p> <p>When classifying in this group, classification is also made in group H01L 33/26 or one of its subgroups in order to identify the chemical composition of the light emitting region</p>	33/505	<ul style="list-style-type: none"> {characterised by the shape, e.g. plate or foil}
33/20	<ul style="list-style-type: none"> with a particular shape, e.g. curved or truncated substrate 	33/507	<ul style="list-style-type: none"> {the elements being in intimate contact with parts other than the semiconductor body or integrated with parts other than the semiconductor body}
33/22	<ul style="list-style-type: none"> Roughened surfaces, e.g. at the interface between epitaxial layers 	33/508	<ul style="list-style-type: none"> {having a non-uniform spatial arrangement or non-uniform concentration, e.g. patterned wavelength conversion layer, wavelength conversion layer with a concentration gradient of the wavelength conversion material}
33/24	<ul style="list-style-type: none"> of the light emitting region, e.g. non-planar junction 	33/52	<ul style="list-style-type: none"> Encapsulations
33/26	<ul style="list-style-type: none"> Materials of the light emitting region 	33/54	<ul style="list-style-type: none"> having a particular shape
33/28	<ul style="list-style-type: none"> containing only elements of group II and group VI of the periodic system 	33/56	<ul style="list-style-type: none"> Materials, e.g. epoxy or silicone resin
33/285	<ul style="list-style-type: none"> {characterised by the doping materials} 	33/58	<ul style="list-style-type: none"> Optical field-shaping elements
33/30	<ul style="list-style-type: none"> containing only elements of group III and group V of the periodic system 	33/60	<ul style="list-style-type: none"> Reflective elements
33/305	<ul style="list-style-type: none"> {characterised by the doping materials} 	33/62	<ul style="list-style-type: none"> Arrangements for conducting electric current to or from the semiconductor body, e.g. lead-frames, wire-bonds or solder balls
33/32	<ul style="list-style-type: none"> containing nitrogen 	33/64	<ul style="list-style-type: none"> Heat extraction or cooling elements
33/325	<ul style="list-style-type: none"> {characterised by the doping materials} 	33/641	<ul style="list-style-type: none"> {characterized by the materials}
33/34	<ul style="list-style-type: none"> containing only elements of group IV of the periodic system 	33/642	<ul style="list-style-type: none"> {characterized by the shape}
33/343	<ul style="list-style-type: none"> {characterised by the doping materials} 	33/644	<ul style="list-style-type: none"> {in intimate contact or integrated with parts of the device other than the semiconductor body}
33/346	<ul style="list-style-type: none"> {containing porous silicon} 	33/645	<ul style="list-style-type: none"> {the elements being electrically controlled, e.g. Peltier elements}
33/36	<ul style="list-style-type: none"> characterised by the electrodes 	33/647	<ul style="list-style-type: none"> {the elements conducting electric current to or from the semiconductor body}
33/38	<ul style="list-style-type: none"> with a particular shape 	33/648	<ul style="list-style-type: none"> {the elements comprising fluids, e.g. heat-pipes}
33/382	<ul style="list-style-type: none"> {the electrode extending partially in or entirely through the semiconductor body} 	35/00	<p>Thermoelectric devices comprising a junction of dissimilar materials, i.e. exhibiting Seebeck or Peltier effect with or without other thermoelectric effects or thermomagnetic effects; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof; Details thereof (devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00; refrigerating machines using electric or magnetic effects F25B 21/00; thermometers using thermoelectric or thermomagnetic elements G01K 7/00; obtaining energy from radioactive sources G21H)</p>
33/385	<ul style="list-style-type: none"> {the electrode extending at least partially onto a side surface of the semiconductor body} 	35/02	<ul style="list-style-type: none"> Details
33/387	<ul style="list-style-type: none"> {with a plurality of electrode regions in direct contact with the semiconductor body and being electrically interconnected by another electrode layer} 	35/04	<ul style="list-style-type: none"> Structural details of the junction; Connections of leads
33/40	<ul style="list-style-type: none"> Materials therefor 	35/06	<ul style="list-style-type: none"> detachable, e.g. using a spring
33/405	<ul style="list-style-type: none"> {Reflective materials} 	35/08	<ul style="list-style-type: none"> non-detachable, e.g. cemented, sintered, soldered {, e.g. thin films}
33/42	<ul style="list-style-type: none"> Transparent materials 	35/10	<ul style="list-style-type: none"> Connections of leads
33/44	<ul style="list-style-type: none"> characterised by the coatings, e.g. passivation layer or anti-reflective coating 	35/12	<ul style="list-style-type: none"> Selection of the material for the legs of the junction
33/46	<ul style="list-style-type: none"> Reflective coating, e.g. dielectric Bragg reflector 		
33/465	<ul style="list-style-type: none"> {with a resonant cavity structure} 		

- 35/14 . . using inorganic compositions
- 35/16 . . . comprising tellurium or selenium or sulfur
- 35/18 . . . comprising arsenic or antimony or bismuth ([H01L 35/16 takes precedence](#)), {e.g. $A_{III}B_V$ compounds}
- 35/20 . . . comprising metals only ([H01L 35/16](#), [H01L 35/18 take precedence](#))
- 35/22 . . . comprising compounds containing boron, carbon, oxygen or nitrogen {or germanium or silicon, e.g. superconductors}
- 35/225 {Superconducting materials}
- 35/24 . . using organic compositions
- 35/26 . . using compositions changing continuously or discontinuously inside the material
- 35/28 . operating with Peltier or Seebeck effect only
- 35/30 . . characterised by the heat-exchanging means at the junction
- 35/32 . . characterised by the structure or configuration of the cell or thermo-couple forming the device {including details about, e.g., housing, insulation, geometry, module}
- 35/325 . . . {Cascades of thermo-couples}
- 35/34 . Processes or apparatus peculiar to the manufacture or treatment of these devices or of parts thereof (not peculiar thereto [H01L 21/00](#))
- 37/00 Thermoelectric devices without a junction of dissimilar materials; Thermomagnetic devices, e.g. using Nernst-Ettinghausen effect; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); {radiation pyrometers using pyroelectric detectors [G01J 5/34](#)} thermometers using thermo-electric or thermomagnetic elements [G01K 7/00](#); selection of materials for magnetography, e.g. for Curie-point writing [G03G 5/00](#))**
- 37/02 . using thermal change of dielectric constant, e.g. working above and below Curie point {, e.g. pyroelectric devices}
- 37/025 . . {Selection of materials}
- 37/04 . using thermal change of magnetic permeability, e.g. working above and below the Curie point {, e.g. pyromagnetic devices}
- 39/00 Devices using superconductivity; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); {light detection [G01J](#), [G02F 2/00](#); application to memories [G11C 11/44](#), [G11C 15/00](#), [G11C 19/32](#)} ; superconducting conductors cables or transmission lines [H01B 12/00](#); {microwaves [H01P 7/00](#), [H01P 11/00](#)} ; superconductive coils or windings [H01F](#); amplifiers using superconductivity [H03F 19/00](#); {impulse generators and logic circuits [H03K 3/38](#), [H03K 17/92](#), [H03K 19/195](#); lasers [H01S 3/00](#), [H01S 5/00](#)})**
- NOTE**
- In this group, in the absence of an indication to the contrary, an invention is classified in the last appropriate place
- 39/005 . {Alleged superconductivity}
- 39/02 . Details
- 39/025 . . {for Josephson devices}
- 39/04 . . Containers; Mountings
- 39/045 . . . {for Josephson devices}
- 39/06 . . characterised by the current path
- 39/08 . . characterised by the shape of the element
- 39/10 . . characterised by the means for switching {between superconductive and normal states}
- 39/12 . . characterised by the material
- 39/121 . . . {Organic materials}
- 39/123 {Fullerene superconductors, e.g. soccerball-shaped allotrope of carbon, e.g. C_{60} , C_{94} ([fullerenes in general C07C 13/00](#))}
- 39/125 . . . {Ceramic materials}
- 39/126 {comprising copper oxide}
- 39/128 {Multi-layered structures, e.g. super lattices}
- 39/14 . Permanent superconductor devices
- 39/141 . . {comprising metal borides, e.g. MgB_2 }
- 39/143 . . {comprising high T_c ceramic materials}
- 39/145 . . {Three or more electrode devices ([H01L 39/228 takes precedence](#))}
- 39/146 . . . {Field effect devices}
- 39/148 . . {Abrikosov vortex devices}
- 39/16 . Devices switchable between superconductive and normal states {, e.g. switches, current limiters (circuits for current limitation using superconductor elements [H02H 9/023](#))}
- 39/18 . . Cryotrons
- 39/20 . . . Power cryotrons
- 39/22 . Devices comprising a junction of dissimilar materials, e.g. Josephson-effect devices
- 39/221 . . {Single electron tunnelling devices}
- 39/223 . . {Josephson-effect devices}
- 39/225 . . . {comprising high T_c ceramic materials}
- 39/226 . . . {comprising metal borides, e.g. MgB_2 }
- 39/228 . . {three or more electrode devices, e.g. transistor-like structures}
- 39/24 . Processes or apparatus peculiar to the manufacture or treatment of devices provided for in [H01L 39/00](#) or of parts thereof
- 39/2403 . . {Processes peculiar to the manufacture or treatment of composite superconductor filaments (comprising copper oxide [H01L 39/2419](#))}
- 39/2406 . . {of devices comprising Nb or an alloy of Nb with one or more of the elements of group 4, e.g. Ti, Zr, Hf}
- 39/2409 . . {of devices comprising an intermetallic compound of type A-15, e.g. Nb_3Sn }
- 39/2412 . . {of devices comprising molybdenum chalcogenides}
- 39/2416 . . {of devices comprising nitrides or carbonitrides}
- 39/2419 . . {the superconducting material comprising copper oxide}
- 39/2422 . . . {Processes for depositing or forming superconductor layers}
- 39/2425 {from a solution}
- 39/2429 {from a suspension or slurry, e.g. screen printing; doctor blade casting}
- 39/2432 {by evaporation independent of heat source, e.g. MBE}
- 39/2435 {by sputtering}

- 39/2438 {by chemical vapour deposition [CVD]}
- 39/2441 {by metalloorganic chemical vapour deposition [MOCVD]}
- 39/2445 {by thermal spraying, e.g. plasma deposition}
- 39/2448 {Pulsed laser deposition, e.g. laser sputtering; laser ablation}
- 39/2451 {Precursor deposition followed by after-treatment, e.g. oxidation}
- 39/2454 {characterised by the substrate}
- 39/2458 {Monocrystalline substrates, e.g. epitaxial growth}
- 39/2461 {Intermediate layers, e.g. for growth control}
- 39/2464 . . . {After-treatment, e.g. patterning}
- 39/2467 {Etching}
- 39/247 {Passivation}
- 39/2474 . . . {Manufacture or deposition of contacts or electrodes}
- 39/2477 . . . {Processes including the use of precursors}
- 39/248 . . . {Processes peculiar to the manufacture or treatment of filaments or composite wires}
- 39/2483 . . . {Introducing flux pinning centres}
- 39/2487 . . {of devices comprising metal borides, e.g. MgB₂}
- 39/249 . . {Treatment of superconductive layers by irradiation, e.g. ion-beam, electron-beam, laser beam, X-rays (irradiation devices [G21K](#), [H01J](#))}
- 39/2493 . . {for Josephson devices}
- 39/2496 . . . {comprising high T_c ceramic materials}
- 41/00 Piezo-electric devices in general; Electrostrictive devices in general; Magnetostrictive devices in general; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof; Details thereof (devices consisting of a plurality of solid-state components formed in or on a common substrate [H01L 27/00](#))**
- WARNING**
- Groups [H01L 41/23-H01L 41/47](#) are incomplete pending reclassification of documents from group [H01L 41/22](#).
- Groups [H01L 41/23-H01L 41/47](#) and [H01L 41/22](#) should be considered in order to perform a complete search.
- 41/02 . Details
- 41/04 . . of piezo-electric or electrostrictive devices
- 41/042 . . . {Drive or control circuitry or methods for piezo-electric or electrostrictive devices not otherwise provided for}
- 41/044 {for piezoelectric transformers (conversion of DC or AC power [H02M](#); for operating discharge lamps [H05B 41/282](#))}
- 41/047 . . . Electrodes {or electrical connection arrangements}
- 41/0471 {Individual layer electrodes of multilayer piezo-electric or electrostrictive devices, e.g. internal electrodes}
- 41/0472 {Connection electrodes of multilayer piezo-electric or electrostrictive devices, e.g. external electrodes}
- 41/0474 {embedded within piezo-electric or electrostrictive material, e.g. via connections}
- 41/0475 {Further connection or lead arrangements, e.g. flexible wiring boards, terminal pins}
- 41/0477 {Conductive materials (in general [H01B 1/00](#))}
- 41/0478 {the principal material being non-metallic, e.g. oxide or carbon based}
- 41/053 . . . Mounts, supports, enclosures or casings
- 41/0533 {Further insulation means against electrical, physical or chemical damage, e.g. protective coatings}
- 41/0536 {Mechanical prestressing means, e.g. springs (in general [F16F 1/00](#))}
- 41/06 . . of magnetostrictive devices
- 41/08 . Piezo-electric or electrostrictive devices
- 41/0805 . . {based on piezo-electric or electrostrictive films or coatings}
- 41/081 . . . {characterised by the underlying base, e.g. substrates}
- 41/0815 {Intermediate layers, e.g. barrier, adhesion or growth control buffer layers}
- 41/082 . . {based on piezo-electric or electrostrictive fibres}
- 41/0825 . . {with electrical and mechanical input and output, e.g. having combined actuator and sensor parts}
- 41/083 . . having a stacked or multilayer structure
- 41/0831 . . . {with non-rectangular cross-section in stacking direction, e.g. polygonal, trapezoidal}
- 41/0833 . . . {with non-rectangular cross-section orthogonal to the stacking direction, e.g. polygonal, circular}
- 41/0835 {Annular cross-section}
- 41/0836 . . . {of cylindrical shape with stacking in radial direction, e.g. coaxial or spiral type rolls}
- 41/0838 . . . {adapted for alleviating internal stress, e.g. cracking control layers ("Sollbruchstellen")}
- 41/087 . . formed as coaxial cables
- 41/09 . . with electrical input and mechanical output {, e.g. actuators, vibrators (in frequency selective networks [H03H 9/00](#))}
- 41/0906 . . . {using longitudinal or thickness displacement combined with bending, shear or torsion displacement}
- 41/0913 {with polygonal or rectangular shape}
- 41/092 {with cylindrical or annular shape}
- 41/0926 . . . {using bending displacement, e.g. unimorph, bimorph or multimorph cantilever or membrane benders}
- 41/0933 {Beam type}
- 41/094 {Cantilevers, i.e. having one fixed end}
- 41/0946 {connected at their free ends, e.g. parallelogram type}
- 41/0953 {with multiple segments mechanically connected in series, e.g. zig-zag type}
- 41/096 {adapted for in-plane bending displacement}
- 41/0966 {adapted for multi-directional bending displacement}
- 41/0973 {Membrane type}
- 41/098 {with non-planar shape}
- 41/0986 . . . {using longitudinal or thickness displacement only, e.g. d33 or d31 type devices}
- 41/0993 . . . {using shear or torsion displacement, e.g. d15 type devices}
- 41/107 . . with electrical input and electrical output {, e.g. transformers}

- 41/113 . . with mechanical input and electrical output {, e.g. generators, sensors}
- 41/1132 . . . {Sensors}
- 41/1134 . . . {Beam type}
- 41/1136 {Cantilevers}
- 41/1138 . . . {Membrane type}
- 41/12 . Magnetostrictive devices
- 41/125 . . {with mechanical input and electrical output, e.g. generators, sensors}
- 41/16 . Selection of materials
- 41/18 . . for piezo-electric or electrostrictive devices {, e.g. bulk piezo-electric crystals}
- 41/183 . . . {Composite materials, e.g. having 1-3 or 2-2 type connectivity}
- 41/187 . . . Ceramic compositions {, i.e. synthetic inorganic polycrystalline compounds incl. epitaxial, quasi-crystalline materials}
- 41/1871 {Alkaline earth metal based oxides, e.g. barium titanates}
- 41/1873 {Alkali metal based oxides, e.g. lithium, sodium or potassium niobates}
- 41/1875 {Lead based oxides}
- 41/1876 {Lead zirconate titanate based}
- 41/1878 {Bismuth based oxides}
- 41/193 . . . Macromolecular compositions {, e.g. piezo-electric polymers}
- 41/20 . . for magnetostrictive devices
- 41/22 . Processes or apparatus specially adapted for the assembly, manufacture or treatment of piezo-electric or electrostrictive devices or of parts thereof
- 41/23 . . Forming enclosures or casings
- 41/25 . . Assembling devices that include piezo-electric or electrostrictive parts
- 41/253 . . Treating devices or parts thereof to modify a piezo-electric or electrostrictive property, e.g. polarisation characteristics, vibration characteristics or mode tuning
- 41/257 . . . by polarising
- 41/27 . . Manufacturing multilayered piezo-electric or electrostrictive devices or parts thereof, e.g. by stacking piezo-electric bodies and electrodes
- 41/273 . . . by integrally sintering piezo-electric or electrostrictive bodies and electrodes
- 41/277 . . . by stacking bulk piezo-electric or electrostrictive bodies and electrodes
- 41/29 . . Forming electrodes, leads or terminal arrangements
- 41/293 . . . Connection electrodes of multilayered piezo-electric or electrostrictive parts
- NOTE**
Integral individual layer electrode and connection electrode are classified in both [H01L 41/293](#) and [H01L 41/297](#)
- 41/297 . . . Individual layer electrodes of multilayered piezo-electric or electrostrictive parts
- NOTE**
Integral individual layer electrode and connection electrode are classified in both [H01L 41/293](#) and [H01L 41/297](#)
- 41/31 . . Applying piezo-electric or electrostrictive parts or bodies onto an electrical element or another base
- 41/311 . . . Mounting of piezo-electric or electrostrictive parts together with semiconductor elements, or other circuit elements, on a common substrate
- 41/312 . . . by laminating or bonding of piezo-electric or electrostrictive bodies
- 41/313 by metal fusing or with adhesives
- 41/314 . . . by depositing piezo-electric or electrostrictive layers, e.g. aerosol or screen printing
- 41/316 by vapour phase deposition
- 41/317 by liquid phase deposition
- 41/318 by sol-gel deposition
- 41/319 using intermediate layers, e.g. for growth control
- 41/33 . . Shaping or machining of piezo-electric or electrostrictive bodies
- 41/331 . . . by coating or depositing using masks, e.g. lift-off
- 41/332 . . . by etching, e.g. lithography
- 41/333 . . . by moulding or extrusion
- 41/335 . . . by machining
- 41/337 by polishing or grinding
- 41/338 by cutting or dicing
- 41/339 by punching
- 41/35 . . Forming piezo-electric or electrostrictive materials
- 41/37 . . . Composite materials
- 41/39 . . . Inorganic materials
- 41/41 by melting
- 41/43 by sintering
- 41/45 . . . Organic materials
- 41/47 . Processes or apparatus specially adapted for the assembly, manufacture or treatment of magnetostrictive devices or of parts thereof
- 43/00 Devices using galvano-magnetic or similar magnetic effects; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); devices with potential-jump barrier, or surface barrier controllable by variation of a magnetic field [H01L 29/82](#))**
- 43/02 . Details
- 43/04 . . of Hall-effect devices
- 43/06 . Hall-effect devices
- 43/065 . . {Semiconductor Hall-effect devices}
- 43/08 . Magnetic-field-controlled resistors
- 43/10 . Selection of materials
- 43/12 . Processes or apparatus peculiar to the manufacture or treatment of these devices or of parts thereof ([not peculiar thereto \[H01L 21/00\]\(#\)](#))
- 43/14 . . for Hall-effect devices

- 45/00** Solid state devices adapted for rectifying, amplifying, oscillating or switching without a potential-jump barrier or surface barrier, e.g. dielectric triodes; Ovshinsky-effect devices; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); devices using superconductivity [H01L 39/00](#); piezo-electric devices [H01L 41/00](#); bulk negative resistance effect devices [H01L 47/00](#); {memories [G11C 11/34](#); [G11C 13/0002](#); amplifying circuits [H03F 11/00](#); pulse generation [H03K 3/02](#); electronic switching circuits [H03K 17/00](#); logic circuits [H03K 19/00](#)})
- 45/005 . {Charge density wave transport devices}
- 45/02 . Solid state travelling-wave devices
- 45/04 . {Bistable or multistable switching devices, e.g. for resistance switching non-volatile memory}
- 45/06 . . {based on solid-state phase change, e.g. between amorphous and crystalline phases, Ovshinsky effect}
- 45/065 . . . {between different crystalline phases, e.g. cubic and hexagonal}
- 45/08 . . {based on migration or redistribution of ionic species, e.g. anions, vacancies}
- 45/085 . . . {the species being metal cations, e.g. programmable metallization cells}
- 45/10 . . {based on bulk electronic defects, e.g. trapping of electrons}
- 45/12 . . {Details}
- 45/1206 . . . {Three or more terminal devices, e.g. transistor like devices}
- 45/1213 . . . {Radiation or particle beam assisted switching devices, e.g. optically controlled devices}
- 45/122 . . . {Device geometry}
- 45/1226 {adapted for essentially horizontal current flow, e.g. bridge type devices}
- 45/1233 {adapted for essentially vertical current flow, e.g. sandwich or pillar type devices}
- 45/124 {on sidewalls of dielectric structures, e.g. mesa or cup type devices}
- 45/1246 {Further means within the switching material region to limit current flow, e.g. constrictions}
- 45/1253 . . . {Electrodes}
- 45/126 {adapted for resistive heating}
- 45/1266 {adapted for supplying ionic species}
- 45/1273 {adapted for electric field or current focusing, e.g. tip shaped}
- 45/128 . . . {Thermal details}
- 45/1286 {Heating or cooling means other than resistive heating electrodes, e.g. heater in parallel}
- 45/1293 {Thermal insulation means}
- 45/14 . . {Selection of switching materials}
- 45/141 . . . {Compounds of sulfur, selenium or tellurium, e.g. chalcogenides}
- 45/142 {Sulfides, e.g. CuS}
- 45/143 {Selenides, e.g. GeSe}
- 45/144 {Tellurides, e.g. GeSbTe}
- 45/145 . . . {Oxides or nitrides}
- 45/146 {Binary metal oxides, e.g. TaOx}
- 45/147 {Complex metal oxides, e.g. perovskites, spinels}
- 45/148 . . . {Other compounds of groups 13-15, e.g. elemental or compound semiconductors}
- 45/149 {Carbon or carbides}
- 45/16 . . {Manufacturing}
- 45/1608 . . . {Formation of the switching material, e.g. layer deposition}
- 45/1616 {by chemical vapor deposition, e.g. MOCVD, ALD}
- 45/1625 {by physical vapor deposition, e.g. sputtering}
- 45/1633 {by conversion of electrode material, e.g. oxidation}
- 45/1641 . . . {Modification of the switching material, e.g. post-treatment, doping}
- 45/165 {by implantation}
- 45/1658 {by diffusion, e.g. photo-dissolution}
- 45/1666 . . . {Patterning of the switching material}
- 45/1675 {by etching of pre-deposited switching material layers, e.g. lithography}
- 45/1683 {by filling of openings, e.g. damascene method}
- 45/1691 {Patterning process specially adapted for achieving sub-lithographic dimensions, e.g. using spacers}
- 47/00** Bulk negative resistance effect devices, e.g. Gunn-effect devices; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#))
- 47/005 . {Processes or apparatus peculiar to the manufacture or treatment of these devices or of parts thereof (not peculiar thereto [H01L 21/00](#))}
- 47/02 . Gunn-effect devices {or transferred electron devices}
- 47/023 . . {controlled by electromagnetic radiation}
- 47/026 . . {Gunn diodes ([H01L 47/02](#) takes precedence)}
- 49/00** Solid state devices not provided for in groups [H01L 27/00](#) - [H01L 47/00](#) and [H01L 51/00](#) and not provided for in any other subclass; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof
- 49/003 . {Devices using Mott metal-insulator transition, e.g. field effect transistors}
- 49/006 . {Quantum devices, e.g. Quantum Interference Devices, Metal Single Electron Transistor (using semiconductors in the active part [H01L 29/00](#))}
- 49/02 . Thin-film or thick-film devices
- 51/00** Solid state devices using organic materials as the active part, or using a combination of organic materials with other materials as the active part; Processes or apparatus specially adapted for the manufacture or treatment of such devices, or of parts thereof (devices consisting of a plurality of components formed in or on a common substrate [H01L 27/28](#); thermoelectric devices using organic material [H01L 35/00](#), [H01L 37/00](#); piezoelectric, electrostrictive or magnetostrictive elements using organic material [H01L 41/00](#))

- 51/0001 . {Processes specially adapted for the manufacture or treatment of devices or of parts thereof ([multistep processes H01L 51/0098](#), [H01L 51/05](#), [H01L 51/42](#), [H01L 51/50](#))}
- 51/0002 . . {Deposition of organic semiconductor materials on a substrate}
- 51/0003 . . . {using liquid deposition, e.g. spin coating}
- 51/0004 {using printing techniques, e.g. ink-jet printing, screen printing}
- 51/0005 {ink-jet printing}
- 51/0006 {Electrolytic deposition using an external electrical current, e.g. in-situ electropolymerisation}
- 51/0007 {characterised by the solvent}
- 51/0008 . . . {using physical deposition, e.g. sublimation, sputtering}
- 51/0009 {using laser ablation}
- 51/001 {Vacuum deposition}
- 51/0011 {selective deposition, e.g. using a mask}
- 51/0012 . . . {special provisions for the orientation or alignment of the layer to be deposited}
- 51/0013 . . . {using non liquid printing techniques, e.g. thermal transfer printing from a donor sheet}
- 51/0014 . . {for changing the shape of the device layer, e.g. patterning}
- 51/0015 . . . {by selective transformation of an existing layer}
- 51/0016 . . . {lift off techniques}
- 51/0017 . . . {etching of an existing layer}
- 51/0018 {using photolithographic techniques}
- 51/0019 {using printing techniques, e.g. applying the etch liquid using an ink jet printer}
- 51/002 . . {Making n- or p-doped regions}
- 51/0021 . . {Formation of conductors}
- 51/0022 . . . {using printing techniques, e.g. ink jet printing}
- 51/0023 . . . {Patterning of conductive layers}
- 51/0024 . . {for forming devices by joining two substrates together, e.g. lamination technique}
- 51/0025 . . {Purification process of the organic semiconductor material}
- 51/0026 . . {Thermal treatment of the active layer, e.g. annealing}
- 51/0027 . . . {using coherent electromagnetic radiation, e.g. laser annealing}
- 51/0028 . . . {Thermal treatment in the presence of solvent vapors, e.g. solvent annealing}
- 51/0029 . . {Special provisions for controlling the atmosphere during processing ([H01L 51/0026 takes precedence](#))}
- 51/003 . . {using a temporary substrate}
- 51/0031 . . {Testing, e.g. accelerated lifetime tests of photoelectric devices}
- 51/0032 . {Selection of organic semiconducting materials, e.g. organic light sensitive or organic light emitting materials}
- NOTE**
- This group only covers the selection of organic materials for their electrical or other properties insofar as they are specific for their use in devices covered by the group [H01L 51/00](#).
- For the materials [per se](#), [see](#) the relevant subclasses.
- Attention is drawn to the following places:
- organic materials in general [C07C](#), [C07D](#), [C07E](#), [C08L](#);
- organic materials as electrical conductors [H01B 1/12](#);
- organic materials as electrical insulators [H01B 3/18](#)
- 51/0034 . . {Organic polymers or oligomers ([organic macromolecular compounds or compositions per se C08](#))}
- 51/0035 . . . {comprising aromatic, heteroaromatic, or aryl chains, e.g. polyaniline ([per se C08G 73/026](#)), polyphenylene ([per se C08G 61/10](#)), polyphenylene vinylene ([per se C08G 61/02](#))}
- 51/0036 {Heteroaromatic compounds comprising sulfur or selen, e.g. polythiophene ([per se C08G 61/126](#))}
- 51/0037 {Polyethylene dioxythiophene [PEDOT] and derivatives}
- 51/0038 {Poly-phenylenevinylene and derivatives ([per se C08G 61/10](#))}
- 51/0039 {Polyfluorene and derivatives}
- 51/004 . . . {comprising aliphatic or olefinic chains, e.g. poly N-vinylcarbazol, PVC, PTFE}
- 51/0041 {Poly acetylene ([per se C08G 61/04](#), [C08F 38/02](#), [C08F 138/02](#), [C08F 238/02](#)) or derivatives}
- 51/0042 {poly N-vinylcarbazol and derivatives}
- 51/0043 . . . {Copolymers}
- 51/0044 . . . {Ladder-type polymers}
- 51/0045 . . {Carbon containing materials, e.g. carbon nanotubes, fullerenes ([per se C01B 32/15](#))}
- 51/0046 . . . {Fullerenes, e.g. C₆₀, C₇₀}
- 51/0047 {comprising substituents, e.g. PCBM}
- 51/0048 . . . {Carbon nanotubes}
- 51/0049 {comprising substituents}
- 51/005 . . {Macromolecular systems with low molecular weight, e.g. cyanine dyes, coumarine dyes, tetrathiafulvalene ([H01L 51/0045](#), [H01L 51/0077](#), [H01L 51/0093](#), [H01L 51/0094 take precedence](#))}
- 51/0051 . . . {Charge transfer complexes}
- 51/0052 . . . {Polycyclic condensed aromatic hydrocarbons, e.g. anthracene}
- 51/0053 {Aromatic anhydride or imide compounds, e.g. perylene tetra-carboxylic dianhydride, perylene tetracarboxylic diimide}
- 51/0054 {containing four rings, e.g. pyrene}
- 51/0055 {containing five rings, e.g. pentacene}
- 51/0056 {containing six or more rings}
- 51/0057 {containing at least one aromatic ring having 7 or more carbon atoms, e.g. azulene}
- 51/0058 {containing more than one polycyclic condensed aromatic rings, e.g. bis-anthracene}
- 51/0059 . . . {Amine compounds having at least two aryl rest on at least one amine-nitrogen atom, e.g. triphenylamine ([per se C07C 211/00](#))}
- 51/006 {comprising polycyclic condensed aromatic hydrocarbons as substituents on the nitrogen atom}
- 51/0061 {comprising heteroaromatic hydrocarbons as substituents on the nitrogen atom}

- 51/0062 . . . {aromatic compounds comprising a heteroatom, e.g.: N,P,S}
- 2051/0063 {Oxadiazole Compounds}
- 51/0064 {Cyanine Dyes}
- 51/0065 {comprising only oxygen as heteroatom}
- 51/0067 {comprising only nitrogen as heteroatom ([H01L 51/0064 takes precedence](#))}
- 51/0068 {comprising only sulfur as heteroatom}
- 51/0069 {comprising two or more different heteroatoms per ring, e.g. S and N ([H01L 51/0064 takes precedence](#))}
- 51/007 {oxadiazole compounds}
- 51/0071 {Polycyclic condensed heteroaromatic hydrocarbons}
- 51/0072 {comprising only nitrogen in the heteroaromatic polycondensed ringsystem, e.g. phenanthroline, carbazole}
- 51/0073 {comprising only oxygen in the heteroaromatic polycondensed ringsystem, e.g. cumarine dyes}
- 51/0074 {comprising only sulfur in the heteroaromatic polycondensed ringsystem, e.g. benzothiophene}
- 51/0075 . . {Langmuir Blodgett films ([per se B05D 1/202](#))}
- 51/0076 . . {Liquid crystalline materials ([per se C09K 19/00](#))}
- 51/0077 . . {Coordination compounds, e.g. porphyrin}
- 51/0078 . . . {Phthalocyanine ([per se C09B 47/04](#))}
- 51/0079 . . . {Metal complexes comprising a IIIB-metal (B, Al, Ga, In or Tl), e.g. Tris (8-hydroxyquinoline) gallium (Ga_q3)}
- 51/008 {comprising boron}
- 51/0081 {comprising aluminium, e.g. Al_q3}
- 51/0082 {comprising gallium}
- 51/0083 . . . {Metal complexes comprising an iron-series metal, e.g. Fe, Co, Ni}
- 51/0084 . . . {Transition metal complexes, e.g. Ru(II)polypyridine complexes}
- 51/0085 {comprising Iridium}
- 51/0086 {comprising Ruthenium}
- 51/0087 {comprising platinum}
- 51/0088 {comprising osmium}
- 51/0089 . . . {Metal complexes comprising Lanthanides or Actinides, e.g. Eu}
- 51/009 . . . {Polynuclear complexes, i.e. complexes having two or more metal centers}
- 51/0091 . . . {Metal complexes comprising a IB-metal (Cu, Ag, Au)}
- 51/0092 . . . {Metal complexes comprising a IIB-metal (Zn, Cd, Hg)}
- 51/0093 . . {Biomolecules or bio-macromolecules, e.g. proteines, ATP, chlorophyl, beta-carotene, lipids, enzymes}
- 51/0094 . . {Silicon-containing organic semiconductors}
- 51/0095 . . {Starburst compounds}
- 51/0096 . {Substrates}
- 51/0097 . . {flexible substrates}
- 51/0098 . {Molecular electronic devices ([molecular computers G06F 15/80; molecular memories G11C 11/00, G11C 13/02](#))}
- 51/05 . . specially adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential- jump barrier or surface barrier {multistep processes for their manufacture}
- 51/0504 . . {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or swiched, e.g. three-terminal devices}
- 51/0508 . . . {Field-effect devices, e.g. TFTs}
- 51/0512 {insulated gate field effect transistors}
- 51/0516 {characterised by the gate dielectric}
- 51/052 {the gate dielectric comprising only organic materials}
- 51/0525 {the gate dielectric comprising only inorganic materials}
- 51/0529 {the gate dielectric having a multilayered structure}
- 51/0533 {Combinations of organic and inorganic layers}
- 51/0537 {the gate dielectric comprising composite materials, e.g. TiO₂ particles in a polymer matrix}
- 51/0541 {Lateral single gate single channel transistors with non inverted structure, i.e. the organic semiconductor layer is formed before the gate electrode}
- 51/0545 {Lateral single gate single channel transistors with inverted structure, i.e. the organic semiconductor layer is formed after the gate electrode}
- 51/055 {characterised by the gate conductor}
- 51/0554 {the transistor having two or more gate electrodes}
- 51/0558 {characterised by the channel of the transistor}
- 51/0562 {the channel comprising two or more active layers, e.g. forming pn - hetero junction}
- 51/0566 {the channel comprising a composite layer, e.g. a mixture of donor and acceptor moieties, forming pn - bulk hetero junction}
- 51/057 {having a vertical structure, e.g. vertical carbon nanotube field effect transistors [CNT-FETs]}
- 51/0575 . . {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 51/0579 . . . {Schottky diodes}
- 51/0583 . . . {comprising an organic/organic junction, e.g. hetero-junction}
- 51/0587 . . . {comprising an organic/inorganic hetero-junction, e.g. hetero-junction}
- 51/0591 . . . {Bi-stable switching devices}
- 51/0595 . . . {molecular electronic devices ([molecular computers G06F 15/80; molecular memories G11C 11/00, G11C 13/02](#))}
- 51/10 . . Details of devices
- 51/102 . . . {Electrodes}
- 51/105 {Ohmic contacts, e.g. source and drain electrodes}
- 51/107 . . . {Passivation, containers, encapsulations}

- 51/42 . . specially adapted for sensing infra-red radiation, light, electro-magnetic radiation of shorter wavelength or corpuscular radiation and adapted for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation {using organic materials as the active part, or using a combination of organic materials with other material as the active part; Multistep processes for their manufacture}
 - 51/4206 . . {Metal-organic semiconductor-metal devices}
 - 51/4213 . . {Comprising organic semiconductor-inorganic semiconductor hetero-junctions ([H01L 51/4253](#) takes precedence)}
 - 51/422 . . . {Majority carrier devices using sensitisation of widebandgap semiconductors, e.g. TiO₂ (photoelectrochemical devices with a liquid or solid electrolyte [H01G 9/20](#))}
 - 51/4226 {the wideband gap semiconductor comprising titanium oxide, e.g. TiO₂}
 - 51/4233 {the wideband gap semiconductor comprising zinc oxide, e.g. ZnO}
 - 51/424 . . {comprising organic semiconductor-organic semiconductor hetero-junctions ([H01L 51/4253](#) takes precedence)}
 - 51/4246 . . . {comprising multi-junctions, e.g. double hetero-junctions}
 - 51/4253 . . {comprising bulk hetero-junctions, e.g. interpenetrating networks}
 - 51/426 . . . {comprising inorganic nanostructures, e.g. CdSe nanoparticles}
 - 51/4266 {the inorganic nanostructures being nanotubes or nanowires, e.g. CdTe nanotubes in P3HT}
 - 51/4273 . . . {comprising blocking layers, e.g. exciton blocking layers}
 - 51/428 . . {light sensitive field effect devices}
 - 51/4286 . . {Devices having a m-i-s structure}
 - 51/4293 . . {Devices having a p-i-n structure}
 - 51/44 . . Details of devices
 - 51/441 . . . {Electrodes}
 - 51/442 {transparent electrodes, e.g. ITO, TCO}
 - 51/444 {comprising carbon nanotubes}
 - 51/445 {comprising arrangements for extracting the current from the cell, e.g. metal finger grid systems to reduce the serial resistance of transparent electrodes}
 - 51/447 . . . {Light trapping means}
 - 51/448 . . . {Passivation, containers, encapsulations}
 - 51/50 . . specially adapted for light emission, e.g. organic light emitting diodes [OLED] or polymer light emitting devices [PLED]; (organic semiconductor lasers [H01S 5/36](#); {circuit arrangements for OLED or PLED [H05B 33/0896](#); control arrangements for organic electroluminescent displays [G09G 3/3208](#)})
 - 51/5004 . . {characterised by the interrelation between parameters of constituting active layers, e.g. HOMO-LUMO relation}
 - 51/5008 . . {Intermediate layers comprising a mixture of materials of the adjoining active layers}
 - 51/5012 . . {Electroluminescent [EL] layer}
 - 51/5016 . . . {Triplet emission}
 - 51/502 . . . {comprising active inorganic nanostructures, e.g. luminescent quantum dots}
 - 51/5024 {having a host comprising an emissive dopant and further additive materials, e.g. for improving the dispersability, for improving the stabilisation, for assisting energy transfer}
 - 51/5028 {for assisting energy transfer, e.g. sensitization}
 - 51/5032 . . . {Light emitting electrochemical cells [LEC], i.e. with mobile ions in the active layer}
 - 51/5036 . . . {Multi-colour light emission, e.g. colour tuning, polymer blend, stack of electroluminescent layers}
 - 51/504 {Stack of electroluminescent layers}
 - 51/5044 {with spacer layers between the emissive layers}
 - 51/5048 . . {Carrier transporting layer}
 - 51/5052 . . . {Doped transporting layer}
 - 51/5056 . . . {Hole transporting layer}
 - 51/506 {comprising a dopant}
 - 51/5064 {having a multilayered structure}
 - 51/5068 {arranged between the light emitting layer and the cathode}
 - 51/5072 . . . {Electron transporting layer}
 - 51/5076 {comprising a dopant}
 - 51/508 {having a multilayered structure}
 - 51/5084 {arranged between the light emitting layer and the anode}
 - 51/5088 . . {Carrier injection layer}
 - 51/5092 . . . {Electron injection layer}
 - 51/5096 . . {Carrier blocking layer}
 - 51/52 . . Details of devices
 - 51/5203 . . . {Electrodes}
 - 51/5206 {Anodes, i.e. with high work-function material}
- WARNING**
- Groups [H01L 51/5209](#) – [H01L 51/5218](#) are incomplete pending reclassification of documents from group [H01L 51/5206](#).
- Groups [H01L 51/5209](#) – [H01L 51/5218](#) and [H01L 51/5206](#) should be considered in order to perform a complete search.
- 51/5209 {characterised by the shape}
 - 51/5212 {combined with auxiliary electrode, e.g. ITO layer combined with metal lines}
 - 51/5215 {composed of transparent multilayers}
 - 51/5218 {Reflective anodes, e.g. ITO combined with thick metallic layer}
 - 51/5221 {Cathodes, i.e. with low work-function material}
- WARNING**
- Groups [H01L 51/5225](#) – [H01L 51/5234](#) are incomplete pending reclassification of documents from group [H01L 51/5221](#).
- Groups [H01L 51/5225](#) – [H01L 51/5234](#) and [H01L 51/5221](#) should be considered in order to perform a complete search.
- 51/5225 {characterised by the shape}
 - 51/5228 {combined with auxiliary electrodes}
 - 51/5231 {composed of opaque multilayers}
 - 51/5234 {Transparent, e.g. including thin metal film}

51/5237	. . . {Passivation; Containers; Encapsulation, e.g. against humidity}	2221/1042	. . . the dielectric comprising air gaps
	WARNING	2221/1047 the air gaps being formed by pores in the dielectric
	Groups H01L 51/524 – H01L 51/5259 are incomplete pending reclassification of documents from group H01L 51/5237 .	2221/1052	. . . Formation of thin functional dielectric layers
	Groups H01L 51/524 – H01L 51/5259 and H01L 51/5237 should be considered in order to perform a complete search.	2221/1057 in via holes or trenches
51/524 {Sealing arrangements having a self-supporting structure, e.g. containers}	2221/1063 Sacrificial or temporary thin dielectric films in openings in a dielectric
51/5243 {the sealing arrangements being made of metallic material}	2221/1068	. . Formation and after-treatment of conductors
51/5246 {characterised by the peripheral sealing arrangements, e.g. adhesives, sealants}	2221/1073	. . . Barrier, adhesion or liner layers
51/525 {Vertical spacers, e.g. arranged between the sealing arrangement and the OLED}	2221/1078 Multiple stacked thin films not being formed in openings in dielectrics
51/5253 {Protective coatings}	2221/1084 Layers specifically deposited to enhance or enable the nucleation of further layers, i.e. seed layers
51/5256 {having repetitive multilayer structures}	2221/1089 Stacks of seed layers
51/5259 {including getter material or desiccant}	2221/1094	. . . Conducting structures comprising nanotubes or nanowires
51/5262	. . . {Arrangements for extracting light from the device}	2221/67	. Apparatus for handling semiconductor or electric solid state devices during manufacture or treatment thereof; Apparatus for handling wafers during manufacture or treatment of semiconductor or electric solid state devices or components; Apparatus not specifically provided for elsewhere
51/5265 {comprising a resonant cavity structure, e.g. Bragg reflector pair}	2221/683	. . for supporting or gripping
51/5268 {Scattering means}	2221/68304	. . . using temporarily an auxiliary support
51/5271 {Reflective means}	2221/68309 Auxiliary support including alignment aids
51/5275 {Refractive means, e.g. lens}	2221/68313 Auxiliary support including a cavity for storing a finished device, e.g. IC package, or a partly finished device, e.g. die, during manufacturing or mounting
51/5278 {comprising a repetitive electroluminescent unit between one set of electrodes}	2221/68318 Auxiliary support including means facilitating the separation of a device or wafer from the auxiliary support
51/5281	. . . {Arrangements for contrast improvement, e.g. preventing reflection of ambient light}	2221/68322 Auxiliary support including means facilitating the selective separation of some of a plurality of devices from the auxiliary support
51/5284 {comprising a light absorbing layer, e.g. black layer}	2221/68327 used during dicing or grinding
51/5287	. . . {OLED having a fiber structure}	2221/68331 of passive members, e.g. die mounting substrate
51/529	. . . {Arrangements for heating or cooling}	2221/68336 involving stretching of the auxiliary support post dicing
51/5293	. . . {Arrangements for polarized light emission (H01L 51/5281 takes precedence)}	2221/6834 used to protect an active side of a device or wafer
51/5296	. . . {Light emitting organic transistors}	2221/68345 used as a support during the manufacture of self supporting substrates
51/56	. . Processes or apparatus specially adapted for the manufacture or treatment of such devices or of parts thereof	2221/6835 used as a support during build up manufacturing of active devices
2221/00	Processes or apparatus adapted for the manufacture or treatment of semiconductor or solid state devices or of parts thereof covered by H01L 21/00	2221/68354 used to support diced chips prior to mounting
2221/10	. Applying interconnections to be used for carrying current between separate components within a device	2221/68359 used as a support during manufacture of interconnect decals or build up layers
2221/1005	. . Formation and after-treatment of dielectrics	2221/68363 used in a transfer process involving transfer directly from an origin substrate to a target substrate without use of an intermediate handle substrate
2221/101	. . . Forming openings in dielectrics	2221/68368 used in a transfer process involving at least two transfer steps, i.e. including an intermediate handle substrate
2221/1015 for dual damascene structures	2221/68372 used to support a device or wafer when forming electrical connections thereto (when forming bonding pads H01L 24/03; when forming bump connectors H01L 24/11; when forming layer connectors H01L 24/27)
2221/1021 Pre-forming the dual damascene structure in a resist layer		
2221/1026 the via being formed by burying a sacrificial pillar in the dielectric and removing the pillar		
2221/1031 Dual damascene by forming vias in the via-level dielectric prior to deposition of the trench-level dielectric		
2221/1036 Dual damascene with different via-level and trench-level dielectrics		

2221/68377	with parts of the auxiliary support remaining in the finished device	2223/6688	Mixed frequency adaptations, i.e. for operation at different frequencies
2221/68381	Details of chemical or physical process used for separating the auxiliary support from a device or wafer	2223/6694	Optical signal interface included within high-frequency semiconductor device housing
2221/68386	Separation by peeling	2224/00 Indexing scheme for arrangements for connecting or disconnecting semiconductor or solid-state bodies and methods related thereto as covered by H01L 24/00		
2221/6839	using peeling wedge or knife or bar	2224/01	Means for bonding being attached to, or being formed on, the surface to be connected, e.g. chip-to-package, die-attach, "first-level" interconnects; Manufacturing methods related thereto
2221/68395	using peeling wheel	2224/02	. .	Bonding areas; Manufacturing methods related thereto
2223/00 Details relating to semiconductor or other solid state devices covered by the group H01L 23/00			2224/0212	. . .	Auxiliary members for bonding areas, e.g. spacers
2223/544	. .	Marks applied to semiconductor devices or parts	2224/02122	being formed on the semiconductor or solid-state body
2223/54406	. .	comprising alphanumeric information	2224/02123	inside the bonding area
2223/54413	. .	comprising digital information, e.g. bar codes, data matrix	2224/02125	Reinforcing structures
2223/5442	. .	comprising non digital, non alphanumeric information, e.g. symbols	2224/02126	Collar structures
2223/54426	. .	for alignment	2224/0213	Alignment aids
2223/54433	. .	containing identification or tracking information	2224/02135	Flow barrier
2223/5444	. . .	for electrical read out	2224/0214	Structure of the auxiliary member
2223/54446	Wireless electrical read out	2224/02141	Multilayer auxiliary member
2223/54453	. .	for use prior to dicing	2224/02145	Shape of the auxiliary member
2223/5446	. . .	Located in scribe lines	2224/0215	Material of the auxiliary member
2223/54466	. . .	Located in a dummy or reference die	2224/02163	on the bonding area
2223/54473	. .	for use after dicing	2224/02165	Reinforcing structures
2223/5448	. . .	Located on chip prior to dicing and remaining on chip after dicing	2224/02166	Collar structures
2223/54486	. . .	Located on package parts, e.g. encapsulation, leads, package substrate	2224/0217	Alignment aids
2223/54493	. .	Peripheral marks on wafers, e.g. orientation flats, notches, lot number	2224/02175	Flow barrier
2223/58	. .	Structural electrical arrangements for semiconductor devices not otherwise provided for	2224/0218	Structure of the auxiliary member
2223/64	. .	Impedance arrangements	2224/02181	Multilayer auxiliary member
2223/66	. . .	High-frequency adaptations	2224/02185	Shape of the auxiliary member
2223/6605	High-frequency electrical connections	2224/0219	Material of the auxiliary member
2223/6611	Wire connections	2224/022	Protective coating, i.e. protective bond-through coating
2223/6616	Vertical connections, e.g. vias	2224/02205	Structure of the protective coating
2223/6622	Coaxial feed-throughs in active or passive substrates	2224/02206	Multilayer protective coating
2223/6627	Waveguides, e.g. microstrip line, strip line, coplanar line	2224/0221	Shape of the protective coating
2223/6633	Transition between different waveguide types	2224/02215	Material of the protective coating
2223/6638	Differential pair signal lines	2224/02233	not in direct contact with the bonding area
2223/6644	Packaging aspects of high-frequency amplifiers (amplifiers per se H03F)	2224/02235	Reinforcing structures
2223/665	Bias feed arrangements	2224/0224	Alignment aids
2223/6655	Matching arrangements, e.g. arrangement of inductive and capacitive components	2224/02245	Flow barrier
2223/6661	for passive devices (passive components per se H01L 28/00)	2224/0225	Structure of the auxiliary member
2223/6666	for decoupling, e.g. bypass capacitors	2224/02251	Multilayer auxiliary member
2223/6672	for integrated passive components, e.g. semiconductor device with passive components only (integrated circuits with passive components only per se H01L 27/01)	2224/02255	Shape of the auxiliary member
2223/6677	for antenna, e.g. antenna included within housing of semiconductor device (antennas per se H01Q)	2224/0226	Material of the auxiliary member
2223/6683	for monolithic microwave integrated circuit [MMIC]	2224/023	. . .	Redistribution layers [RDL] for bonding areas
			2224/0231	Manufacturing methods of the redistribution layers
			2224/02311	Additive methods
			2224/02313	Subtractive methods
			2224/02315	Self-assembly processes
			2224/02317	by local deposition
			2224/02319	by using a preform
			2224/02321	Reworking
			2224/0233	Structure of the redistribution layers
			2224/02331	Multilayer structure
			2224/02333	being a bump

2224/02335	Free-standing redistribution layers	2224/03426	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/0235	Shape of the redistribution layers	2224/03428	Wave coating
2224/02351	comprising interlocking features	2224/0343	in solid form
2224/0236	Shape of the insulating layers therebetween	2224/03436	Lamination of a preform, e.g. foil, sheet or layer
2224/0237	Disposition of the redistribution layers	2224/03438	the preform being at least partly pre-patterned
2224/02371	connecting the bonding area on a surface of the semiconductor or solid-state body with another surface of the semiconductor or solid-state body	2224/0344	by transfer printing
2224/02372	connecting to a via connection in the semiconductor or solid-state body	2224/03442	using a powder
2224/02373	Layout of the redistribution layers	2224/03444	in gaseous form
2224/02375	Top view	2224/0345	Physical vapour deposition [PVD], e.g. evaporation, or sputtering
2224/02377	Fan-in arrangement	2224/03452	Chemical vapour deposition [CVD], e.g. laser CVD
2224/02379	Fan-out arrangement	2224/0346	Plating
2224/02381	Side view	2224/03462	Electroplating
2224/0239	Material of the redistribution layers	2224/03464	Electroless plating
2224/024	Material of the insulating layers therebetween	2224/03466	Conformal deposition, i.e. blanket deposition of a conformal layer on a patterned surface
2224/03	Manufacturing methods	2224/0347	using a lift-off mask
2224/03001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate	2224/03472	Profile of the lift-off mask
2224/03002	for supporting the semiconductor or solid-state body	2224/03474	Multilayer masks
2224/03003	for holding or transferring a preform	2224/0348	Permanent masks, i.e. masks left in the finished device, e.g. passivation layers
2224/03005	for aligning the bonding area, e.g. marks, spacers	2224/035	by chemical or physical modification of a pre-existing or pre-deposited material
2224/03009	for protecting parts during manufacture	2224/03502	Pre-existing or pre-deposited material
2224/03011	Involving a permanent auxiliary member, i.e. a member which is left at least partly in the finished device, e.g. coating, dummy feature	2224/03505	Sintering
2224/03013	for holding or confining the bonding area, e.g. solder flow barrier	2224/0351	Anodisation
2224/03015	for aligning the bonding area, e.g. marks, spacers	2224/03515	Curing and solidification, e.g. of a photosensitive material
2224/03019	for protecting parts during the process	2224/0352	Self-assembly, e.g. self-agglomeration of the material in a fluid
2224/031	Manufacture and pre-treatment of the bonding area preform	2224/03522	Auxiliary means therefor, e.g. for self-assembly activation
2224/0311	Shaping	2224/03524	with special adaptation of the surface of the body to be connected or of an auxiliary substrate, e.g. surface shape specially adapted for the self-assembly process
2224/0312	Applying permanent coating	2224/0355	Selective modification
2224/033	by local deposition of the material of the bonding area	2224/03552	using a laser or a focussed ion beam [FIB]
2224/0331	in liquid form	2224/03554	Stereolithography, i.e. solidification of a pattern defined by a laser trace in a photosensitive resin
2224/03312	Continuous flow, e.g. using a microsyringe, a pump, a nozzle or extrusion	2224/036	by patterning a pre-deposited material (treatment of parts prior to assembly of the devices H01L 21/48)
2224/03318	by dispensing droplets	2224/03602	Mechanical treatment, e.g. polishing, grinding
2224/0332	Screen printing, i.e. using a stencil	2224/0361	Physical or chemical etching
2224/0333	in solid form	2224/03612	by physical means only
2224/03332	using a powder	2224/03614	by chemical means only
2224/03334	using a preform	2224/03616	Chemical mechanical polishing [CMP]
2224/034	by blanket deposition of the material of the bonding area	2224/03618	with selective exposure, development and removal of a photosensitive material, e.g. of a photosensitive conductive resin
2224/0341	in liquid form	2224/0362	Photolithography
2224/03416	Spin coating	2224/03622	using masks
2224/03418	Spray coating	2224/0363	using a laser or a focused ion beam [FIB]
2224/0342	Curtain coating			
2224/03422	by dipping, e.g. in a solder bath (hot-dipping C23C 2/00)			
2224/03424	Immersion coating, e.g. in a solder bath (immersion processes C23C 2/00)			

2224/03632	Ablation by means of a laser or focused ion beam [FIB]	2224/0405	Bonding areas specifically adapted for tape automated bonding [TAB] connectors
2224/037	involving monitoring, e.g. feedback loop	2224/04073	Bonding areas specifically adapted for connectors of different types
2224/038	Post-treatment of the bonding area	2224/04105	Bonding areas formed on an encapsulation of the semiconductor or solid-state body, e.g. bonding areas on chip-scale packages
2224/0381	Cleaning, e.g. oxide removal step, desmearing	2224/05	of an individual bonding area
2224/0382	Applying permanent coating, e.g. in-situ coating	2224/05001	Internal layers
2224/03821	Spray coating	2224/05005	Structure
2224/03822	by dipping, e.g. in a solder bath	2224/05006	Dual damascene structure
2224/03823	Immersion coating, e.g. in a solder bath	2224/05007	comprising a core and a coating
2224/03824	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/05008	Bonding area integrally formed with a redistribution layer on the semiconductor or solid-state body, e.g.
2224/03825	Plating, e.g. electroplating, electroless plating	2224/05009	Bonding area integrally formed with a via connection of the semiconductor or solid-state body
2224/03826	Physical vapour deposition [PVD], e.g. evaporation, or sputtering	2224/0501	Shape
2224/03827	Chemical vapour deposition [CVD], e.g. laser CVD	2224/05011	comprising apertures or cavities
2224/03828	Applying flux	2224/05012	in top view
2224/03829	Applying a precursor material	2224/05013	being rectangular
2224/0383	Reworking, e.g. shaping (reflowing H01L 2224/03849)	2224/05014	being square
2224/03831	involving a chemical process, e.g. etching the bonding area	2224/05015	being circular or elliptic
2224/0384	involving a mechanical process, e.g. planarising the bonding area	2224/05016	in side view
2224/03845	Chemical mechanical polishing [CMP]	2224/05017	comprising protrusions or indentations
2224/03848	Thermal treatments, e.g. annealing, controlled cooling	2224/05018	being a conformal layer on a patterned surface
2224/03849	Reflowing	2224/05019	being a non conformal layer on a patterned surface
2224/039	Methods of manufacturing bonding areas involving a specific sequence of method steps	2224/0502	Disposition
2224/03901	with repetition of the same manufacturing step	2224/05022	the internal layer being at least partially embedded in the surface
2224/03902	Multiple masking steps	2224/05023	the whole internal layer protruding from the surface
2224/03903	using different masks	2224/05024	the internal layer being disposed on a redistribution layer on the semiconductor or solid-state body
2224/03906	with modification of the same mask	2224/05025	the internal layer being disposed on a via connection of the semiconductor or solid-state body
2224/0391	Forming a passivation layer after forming the bonding area	2224/05026	the internal layer being disposed in a recess of the surface
2224/03912	the bump being used as a mask for patterning the bonding area	2224/05027	the internal layer extending out of an opening
2224/03914	the bonding area, e.g. under bump metallisation [UBM], being used as a mask for patterning other parts	2224/05073	Single internal layer
2224/03916	a passivation layer being used as a mask for patterning the bonding area	2224/05075	Plural internal layers
2224/0392	specifically adapted to include a probing step	2224/05076	being mutually engaged together, e.g. through inserts
2224/03921	by repairing the bonding area damaged by the probing step	2224/05078	being disposed next to each other, e.g. side-to-side arrangements
2224/04	. . .	Structure, shape, material or disposition of the bonding areas prior to the connecting process	2224/0508	being stacked
2224/0401	Bonding areas specifically adapted for bump connectors, e.g. under bump metallisation [UBM]	2224/05082	Two-layer arrangements
2224/04026	Bonding areas specifically adapted for layer connectors	2224/05083	Three-layer arrangements
2224/04034	Bonding areas specifically adapted for strap connectors	2224/05084	Four-layer arrangements
2224/04042	Bonding areas specifically adapted for wire connectors, e.g. wirebond pads	2224/05085	with additional elements, e.g. vias arrays, interposed between the stacked layers
			2224/05086	Structure of the additional element

2224/05087	being a via with at least a lining layer	2224/05157	Cobalt [Co] as principal constituent
2224/05088	Shape of the additional element	2224/0516	Iron [Fe] as principal constituent
2224/05089	Disposition of the additional element	2224/05163	the principal constituent melting at a temperature of greater than 1550°C
2224/0509	of a single via	2224/05164	Palladium [Pd] as principal constituent
2224/05091	at the center of the internal layers	2224/05166	Titanium [Ti] as principal constituent
2224/05092	at the periphery of the internal layers	2224/05169	Platinum [Pt] as principal constituent
2224/05093	of a plurality of vias	2224/0517	Zirconium [Zr] as principal constituent
2224/05094	at the center of the internal layers	2224/05171	Chromium [Cr] as principal constituent
2224/05095	at the periphery of the internal layers	2224/05172	Vanadium [V] as principal constituent
2224/05096	Uniform arrangement, i.e. array	2224/05173	Rhodium [Rh] as principal constituent
2224/05097	Random arrangement	2224/05176	Ruthenium [Ru] as principal constituent
2224/05098	Material of the additional element	2224/05178	Iridium [Ir] as principal constituent
2224/05099	Material	2224/05179	Niobium [Nb] as principal constituent
2224/051	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/0518	Molybdenum [Mo] as principal constituent
2224/05101	the principal constituent melting at a temperature of less than 400°C	2224/05181	Tantalum [Ta] as principal constituent
2224/05105	Gallium [Ga] as principal constituent	2224/05183	Rhenium [Re] as principal constituent
2224/05109	Indium [In] as principal constituent	2224/05184	Tungsten [W] as principal constituent
2224/05111	Tin [Sn] as principal constituent	2224/05186	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05113	Bismuth [Bi] as principal constituent	2224/05187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05188)
2224/05114	Thallium [Tl] as principal constituent	2224/05188	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05116	Lead [Pb] as principal constituent	2224/0519	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05118	Zinc [Zn] as principal constituent	2224/05193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/051 - H01L 2224/05191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/0512	Antimony [Sb] as principal constituent	2224/05194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/051 - H01L 2224/05191
2224/05123	Magnesium [Mg] as principal constituent	2224/05195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/051 - H01L 2224/05191
2224/05124	Aluminium [Al] as principal constituent		
2224/05138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C		
2224/05139	Silver [Ag] as principal constituent		
2224/05144	Gold [Au] as principal constituent		
2224/05147	Copper [Cu] as principal constituent		
2224/05149	Manganese [Mn] as principal constituent		
2224/05155	Nickel [Ni] as principal constituent		

2224/05198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/05266	Titanium [Ti] as principal constituent
2224/05199	Material of the matrix	2224/05269	Platinum [Pt] as principal constituent
2224/052	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/0527	Zirconium [Zr] as principal constituent
2224/05201	the principal constituent melting at a temperature of less than 400°C	2224/05271	Chromium [Cr] as principal constituent
2224/05205	Gallium [Ga] as principal constituent	2224/05272	Vanadium [V] as principal constituent
2224/05209	Indium [In] as principal constituent	2224/05273	Rhodium [Rh] as principal constituent
2224/05211	Tin [Sn] as principal constituent	2224/05276	Ruthenium [Ru] as principal constituent
2224/05213	Bismuth [Bi] as principal constituent	2224/05278	Iridium [Ir] as principal constituent
2224/05214	Thallium [Tl] as principal constituent	2224/05279	Niobium [Nb] as principal constituent
2224/05216	Lead [Pb] as principal constituent	2224/0528	Molybdenum [Mo] as principal constituent
2224/05217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05281	Tantalum [Ta] as principal constituent
2224/05218	Zinc [Zn] as principal constituent	2224/05283	Rhenium [Re] as principal constituent
2224/0522	Antimony [Sb] as principal constituent	2224/05284	Tungsten [W] as principal constituent
2224/05223	Magnesium [Mg] as principal constituent	2224/05286	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05224	Aluminium [Al] as principal constituent	2224/05287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05288)
2224/05238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05288	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05239	Silver [Ag] as principal constituent	2224/0529	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05244	Gold [Au] as principal constituent	2224/05291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05247	Copper [Cu] as principal constituent	2224/05293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/052 - H01L 2224/05291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05249	Manganese [Mn] as principal constituent	2224/05294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/052 - H01L 2224/05291
2224/05255	Nickel [Ni] as principal constituent	2224/05295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/052 - H01L 2224/05291
2224/05257	Cobalt [Co] as principal constituent	2224/05298	Fillers
2224/0526	Iron [Fe] as principal constituent	2224/05299	Base material
2224/05263	the principal constituent melting at a temperature of greater than 1550°C		
2224/05264	Palladium [Pd] as principal constituent		

2224/053	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/05371	Chromium [Cr] as principal constituent
2224/05301	the principal constituent melting at a temperature of less than 400°C	2224/05372	Vanadium [V] as principal constituent
2224/05305	Gallium [Ga] as principal constituent	2224/05373	Rhodium [Rh] as principal constituent
2224/05309	Indium [In] as principal constituent	2224/05376	Ruthenium [Ru] as principal constituent
2224/05311	Tin [Sn] as principal constituent	2224/05378	Iridium [Ir] as principal constituent
2224/05313	Bismuth [Bi] as principal constituent	2224/05379	Niobium [Nb] as principal constituent
2224/05314	Thallium [Tl] as principal constituent	2224/0538	Molybdenum [Mo] as principal constituent
2224/05316	Lead [Pb] as principal constituent	2224/05381	Tantalum [Ta] as principal constituent
2224/05317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05383	Rhenium [Re] as principal constituent
2224/05318	Zinc [Zn] as principal constituent	2224/05384	Tungsten [W] as principal constituent
2224/0532	Antimony [Sb] as principal constituent	2224/05386	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05323	Magnesium [Mg] as principal constituent	2224/05387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05388)
2224/05324	Aluminium [Al] as principal constituent	2224/05388	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/0539	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05339	Silver [Ag] as principal constituent	2224/05391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05344	Gold [Au] as principal constituent	2224/05393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/053 - H01L 2224/05391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05347	Copper [Cu] as principal constituent	2224/05394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/053 - H01L 2224/05391
2224/05349	Manganese [Mn] as principal constituent	2224/05395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/053 - H01L 2224/05391
2224/05355	Nickel [Ni] as principal constituent	2224/05398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05357	Cobalt [Co] as principal constituent	2224/05399	Coating material
2224/0536	Iron [Fe] as principal constituent		
2224/05363	the principal constituent melting at a temperature of greater than 1550°C		
2224/05364	Palladium [Pd] as principal constituent		
2224/05366	Titanium [Ti] as principal constituent		
2224/05369	Platinum [Pt] as principal constituent		
2224/0537	Zirconium [Zr] as principal constituent		

2224/054	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/05471	Chromium [Cr] as principal constituent
2224/05401	the principal constituent melting at a temperature of less than 400°C	2224/05472	Vanadium [V] as principal constituent
2224/05405	Gallium [Ga] as principal constituent	2224/05473	Rhodium [Rh] as principal constituent
2224/05409	Indium [In] as principal constituent	2224/05476	Ruthenium [Ru] as principal constituent
2224/05411	Tin [Sn] as principal constituent	2224/05478	Iridium [Ir] as principal constituent
2224/05413	Bismuth [Bi] as principal constituent	2224/05479	Niobium [Nb] as principal constituent
2224/05414	Thallium [Tl] as principal constituent	2224/0548	Molybdenum [Mo] as principal constituent
2224/05416	Lead [Pb] as principal constituent	2224/05481	Tantalum [Ta] as principal constituent
2224/05417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05483	Rhenium [Re] as principal constituent
2224/05418	Zinc [Zn] as principal constituent	2224/05484	Tungsten [W] as principal constituent
2224/0542	Antimony [Sb] as principal constituent	2224/05486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05423	Magnesium [Mg] as principal constituent	2224/05487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05488)
2224/05424	Aluminium [Al] as principal constituent	2224/05488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/0549	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05439	Silver [Ag] as principal constituent	2224/05491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05444	Gold [Au] as principal constituent	2224/05493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/054 - H01L 2224/05491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05447	Copper [Cu] as principal constituent	2224/05494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/054 - H01L 2224/05491
2224/05449	Manganese [Mn] as principal constituent	2224/05495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/054 - H01L 2224/05491
2224/05455	Nickel [Ni] as principal constituent	2224/05498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05457	Cobalt [Co] as principal constituent	2224/05499	Shape or distribution of the fillers
2224/0546	Iron [Fe] as principal constituent	2224/0554	External layer
2224/05463	the principal constituent melting at a temperature of greater than 1550°C	2224/05541	Structure
2224/05464	Palladium [Pd] as principal constituent	2224/05546	Dual damascene structure
2224/05466	Titanium [Ti] as principal constituent	2224/05547	comprising a core and a coating
2224/05469	Platinum [Pt] as principal constituent		
2224/0547	Zirconium [Zr] as principal constituent		

2224/05548	Bonding area integrally formed with a redistribution layer on the semiconductor or solid-state body	2224/05609	Indium [In] as principal constituent
2224/05555	Shape	2224/05611	Tin [Sn] as principal constituent
2224/05551	comprising apertures or cavities	2224/05613	Bismuth [Bi] as principal constituent
2224/05552	in top view	2224/05614	Thallium [Tl] as principal constituent
2224/05553	being rectangular	2224/05616	Lead [Pb] as principal constituent
2224/05554	being square	2224/05617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/05555	being circular or elliptic	2224/05618	Zinc [Zn] as principal constituent
2224/05556	in side view	2224/0562	Antimony [Sb] as principal constituent
2224/05557	comprising protrusions or indentations	2224/05623	Magnesium [Mg] as principal constituent
2224/05558	conformal layer on a patterned surface	2224/05624	Aluminium [Al] as principal constituent
2224/05559	non conformal layer on a patterned surface	2224/05638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/0556	Disposition	2224/05639	Silver [Ag] as principal constituent
2224/05561	On the entire surface of the internal layer	2224/05644	Gold [Au] as principal constituent
2224/05562	On the entire exposed surface of the internal layer	2224/05647	Copper [Cu] as principal constituent
2224/05563	Only on parts of the surface of the internal layer	2224/05649	Manganese [Mn] as principal constituent
2224/05564	Only on the bonding interface of the bonding area	2224/05655	Nickel [Ni] as principal constituent
2224/05565	Only outside the bonding interface of the bonding area	2224/05657	Cobalt [Co] as principal constituent
2224/05566	Both on and outside the bonding interface of the bonding area	2224/0566	Iron [Fe] as principal constituent
2224/05567	the external layer being at least partially embedded in the surface	2224/05663	the principal constituent melting at a temperature of greater than 1550°C
2224/05568	the whole external layer protruding from the surface	2224/05664	Palladium [Pd] as principal constituent
2224/05569	the external layer being disposed on a redistribution layer on the semiconductor or solid-state body	2224/05666	Titanium [Ti] as principal constituent
2224/0557	the external layer being disposed on a via connection of the semiconductor or solid-state body	2224/05669	Platinum [Pt] as principal constituent
2224/05571	the external layer being disposed in a recess of the surface	2224/0567	Zirconium [Zr] as principal constituent
2224/05572	the external layer extending out of an opening	2224/05671	Chromium [Cr] as principal constituent
2224/05573	Single external layer	2224/05672	Vanadium [V] as principal constituent
2224/05575	Plural external layers	2224/05673	Rhodium [Rh] as principal constituent
2224/05576	being mutually engaged together, e.g. through inserts	2224/05676	Ruthenium [Ru] as principal constituent
2224/05578	being disposed next to each other, e.g. side-to-side arrangements	2224/05678	Iridium [Ir] as principal constituent
2224/0558	being stacked	2224/05679	Niobium [Nb] as principal constituent
2224/05582	Two-layer coating	2224/0568	Molybdenum [Mo] as principal constituent
2224/05583	Three-layer coating	2224/05681	Tantalum [Ta] as principal constituent
2224/05584	Four-layer coating	2224/05683	Rhenium [Re] as principal constituent
2224/05599	Material			
2224/056	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof			
2224/05601	the principal constituent melting at a temperature of less than 400°C			
2224/05605	Gallium [Ga] as principal constituent			

2224/05684	• • • • • Tungsten [W] as principal constituent	2224/05718	• • • • • Zinc [Zn] as principal constituent
2224/05686	• • • • • with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/0572	• • • • • Antimony [Sb] as principal constituent
2224/05687	• • • • • Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05688)	2224/05723	• • • • • Magnesium [Mg] as principal constituent
2224/05688	• • • • • Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/05724	• • • • • Aluminium [Al] as principal constituent
2224/0569	• • • • • with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/05738	• • • • • the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/05691	• • • • • The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/05739	• • • • • Silver [Ag] as principal constituent
2224/05693	• • • • • with a principal constituent of the material being a solid not provided for in groups H01L 2224/056 - H01L 2224/05691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/05744	• • • • • Gold [Au] as principal constituent
2224/05694	• • • • • with a principal constituent of the material being a liquid not provided for in groups H01L 2224/056 - H01L 2224/05691	2224/05747	• • • • • Copper [Cu] as principal constituent
2224/05695	• • • • • with a principal constituent of the material being a gas not provided for in groups H01L 2224/056 - H01L 2224/05691	2224/05749	• • • • • Manganese [Mn] as principal constituent
2224/05698	• • • • • with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/05755	• • • • • Nickel [Ni] as principal constituent
2224/05699	• • • • • Material of the matrix	2224/05757	• • • • • Cobalt [Co] as principal constituent
2224/057	• • • • • with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/0576	• • • • • Iron [Fe] as principal constituent
2224/05701	• • • • • the principal constituent melting at a temperature of less than 400°C	2224/05763	• • • • • the principal constituent melting at a temperature of greater than 1550°C
2224/05705	• • • • • Gallium [Ga] as principal constituent	2224/05764	• • • • • Palladium [Pd] as principal constituent
2224/05709	• • • • • Indium [In] as principal constituent	2224/05766	• • • • • Titanium [Ti] as principal constituent
2224/05711	• • • • • Tin [Sn] as principal constituent	2224/05769	• • • • • Platinum [Pt] as principal constituent
2224/05713	• • • • • Bismuth [Bi] as principal constituent	2224/0577	• • • • • Zirconium [Zr] as principal constituent
2224/05714	• • • • • Thallium [Tl] as principal constituent	2224/05771	• • • • • Chromium [Cr] as principal constituent
2224/05716	• • • • • Lead [Pb] as principal constituent	2224/05772	• • • • • Vanadium [V] as principal constituent
2224/05717	• • • • • the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05773	• • • • • Rhodium [Rh] as principal constituent
		2224/05776	• • • • • Ruthenium [Ru] as principal constituent
		2224/05778	• • • • • Iridium [Ir] as principal constituent
		2224/05779	• • • • • Niobium [Nb] as principal constituent
		2224/0578	• • • • • Molybdenum [Mo] as principal constituent
		2224/05781	• • • • • Tantalum [Ta] as principal constituent
		2224/05783	• • • • • Rhenium [Re] as principal constituent
		2224/05784	• • • • • Tungsten [W] as principal constituent
		2224/05786	• • • • • with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/05787	• • • • • Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05788)

2224/05788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/05839	Silver [Ag] as principal constituent
2224/0579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/05844	Gold [Au] as principal constituent
2224/05791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/05847	Copper [Cu] as principal constituent
2224/05793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/057 - H01L 2224/05791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/05849	Manganese [Mn] as principal constituent
2224/05794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/057 - H01L 2224/05791	2224/05855	Nickel [Ni] as principal constituent
2224/05795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/057 - H01L 2224/05791	2224/05857	Cobalt [Co] as principal constituent
2224/05798	Fillers	2224/0586	Iron [Fe] as principal constituent
2224/05799	Base material	2224/05863	the principal constituent melting at a temperature of greater than 1550°C
2224/058	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/05864	Palladium [Pd] as principal constituent
2224/05801	the principal constituent melting at a temperature of less than 400°C	2224/05866	Titanium [Ti] as principal constituent
2224/05805	Gallium [Ga] as principal constituent	2224/05869	Platinum [Pt] as principal constituent
2224/05809	Indium [In] as principal constituent	2224/0587	Zirconium [Zr] as principal constituent
2224/05811	Tin [Sn] as principal constituent	2224/05871	Chromium [Cr] as principal constituent
2224/05813	Bismuth [Bi] as principal constituent	2224/05872	Vanadium [V] as principal constituent
2224/05814	Thallium [Tl] as principal constituent	2224/05873	Rhodium [Rh] as principal constituent
2224/05816	Lead [Pb] as principal constituent	2224/05876	Ruthenium [Ru] as principal constituent
2224/05817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05878	Iridium [Ir] as principal constituent
2224/05818	Zinc [Zn] as principal constituent	2224/05879	Niobium [Nb] as principal constituent
2224/0582	Antimony [Sb] as principal constituent	2224/0588	Molybdenum [Mo] as principal constituent
2224/05823	Magnesium [Mg] as principal constituent	2224/05881	Tantalum [Ta] as principal constituent
2224/05824	Aluminium [Al] as principal constituent	2224/05883	Rhenium [Re] as principal constituent
2224/05838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05884	Tungsten [W] as principal constituent
		2224/05886	with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/05887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05888)
		2224/05888	Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/0589	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/05891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene

2224/05893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/058 - H01L 2224/05891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/05947	Copper [Cu] as principal constituent
2224/05894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/058 - H01L 2224/05891	2224/05949	Manganese [Mn] as principal constituent
2224/05895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/058 - H01L 2224/05891	2224/05955	Nickel [Ni] as principal constituent
2224/05898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/05957	Cobalt [Co] as principal constituent
2224/05899	Coating material	2224/0596	Iron [Fe] as principal constituent
2224/059	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/05963	the principal constituent melting at a temperature of greater than 1550°C
2224/05901	the principal constituent melting at a temperature of less than 400°C	2224/05964	Palladium [Pd] as principal constituent
2224/05905	Gallium [Ga] as principal constituent	2224/05966	Titanium [Ti] as principal constituent
2224/05909	Indium [In] as principal constituent	2224/05969	Platinum [Pt] as principal constituent
2224/05911	Tin [Sn] as principal constituent	2224/0597	Zirconium [Zr] as principal constituent
2224/05913	Bismuth [Bi] as principal constituent	2224/05971	Chromium [Cr] as principal constituent
2224/05914	Thallium [Tl] as principal constituent	2224/05972	Vanadium [V] as principal constituent
2224/05916	Lead [Pb] as principal constituent	2224/05973	Rhodium [Rh] as principal constituent
2224/05917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05976	Ruthenium [Ru] as principal constituent
2224/05918	Zinc [Zn] as principal constituent	2224/05978	Iridium [Ir] as principal constituent
2224/0592	Antimony [Sb] as principal constituent	2224/05979	Niobium [Nb] as principal constituent
2224/05923	Magnesium [Mg] as principal constituent	2224/0598	Molybdenum [Mo] as principal constituent
2224/05924	Aluminium [Al] as principal constituent	2224/05981	Tantalum [Ta] as principal constituent
2224/05938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05983	Rhenium [Re] as principal constituent
2224/05939	Silver [Ag] as principal constituent	2224/05984	Tungsten [W] as principal constituent
2224/05944	Gold [Au] as principal constituent	2224/05986	with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/05987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05988)
		2224/05988	Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/0599	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/05991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/05993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/059 - H01L 2224/05991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/05994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/059 - H01L 2224/05991	2224/06147	with specially adapted redistribution layers [RDL]
2224/05995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/059 - H01L 2224/05991	2224/06148	being disposed in a single wiring level, i.e. planar layout
2224/05998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/06149	being disposed in different wiring levels, i.e. resurf layout
2224/05999	Shape or distribution of the fillers	2224/0615	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry
2224/06	of a plurality of bonding areas	2224/06151	being uniform, i.e. having a uniform pitch across the array
2224/0601	Structure	2224/06152	being non uniform, i.e. having a non uniform pitch across the array
2224/0603	Bonding areas having different sizes, e.g. different heights or widths	2224/06153	with a staggered arrangement, e.g. depopulated array
2224/0605	Shape	2224/06154	covering only portions of the surface to be connected
2224/06051	Bonding areas having different shapes	2224/06155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/061	Disposition	2224/06156	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/06102	the bonding areas being at different heights	2224/06157	with specially adapted redistribution layers [RDL]
2224/0612	Layout	2224/06158	being disposed in a single wiring level, i.e. planar layout
2224/0613	Square or rectangular array	2224/06159	being disposed in different wiring levels, i.e. resurf layout
2224/06131	being uniform, i.e. having a uniform pitch across the array	2224/0616	Random array, i.e. array with no symmetry
2224/06132	being non uniform, i.e. having a non uniform pitch across the array	2224/06163	with a staggered arrangement
2224/06133	with a staggered arrangement, e.g. depopulated array	2224/06164	covering only portions of the surface to be connected
2224/06134	covering only portions of the surface to be connected	2224/06165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/06135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/06166	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/06136	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/06167	with specially adapted redistribution layers [RDL]
2224/06137	with specially adapted redistribution layers [RDL]	2224/06168	being disposed in a single wiring level, i.e. planar layout
2224/06138	being disposed in a single wiring level, i.e. planar layout	2224/06169	being disposed in different wiring levels, i.e. resurf layout
2224/06139	being disposed in different wiring levels, i.e. resurf layout	2224/06177	Combinations of arrays with different layouts
2224/0614	Circular array, i.e. array with radial symmetry	2224/06179	Corner adaptations, i.e. disposition of the bonding areas at the corners of the semiconductor or solid-state body
2224/06141	being uniform, i.e. having a uniform pitch across the array	2224/0618	being disposed on at least two different sides of the body, e.g. dual array
2224/06142	being non uniform, i.e. having a non uniform pitch across the array	2224/06181	On opposite sides of the body
2224/06143	with a staggered arrangement, e.g. depopulated array	2224/06182	with specially adapted redistribution layers [RDL]
2224/06144	covering only portions of the surface to be connected	2224/06183	On contiguous sides of the body
2224/06145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/06187	with specially adapted redistribution layers [RDL]
2224/06146	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/06188	being disposed in a single wiring level, i.e. planar layout
		2224/06189	being disposed in different wiring levels, i.e. resurf layout
		2224/065	Material

2224/06505	Bonding areas having different materials	2224/08155	the item being non-metallic, e.g. being an insulating substrate with or without metallisation
2224/0651	Function			
2224/06515	Bonding areas having different functions	2224/0816	the bonding area connecting to a pin of the item
2224/06517	including bonding areas providing primarily mechanical bonding	2224/08163	the bonding area connecting to a potential ring of the item
2224/06519	including bonding areas providing primarily thermal dissipation	2224/08165	the bonding area connecting to a via metallisation of the item
2224/07	. . .	Structure, shape, material or disposition of the bonding areas after the connecting process	2224/08167	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08	of an individual bonding area	2224/08168	the bonding area connecting to a bonding area protruding from the surface of the item
2224/0801	Structure			
2224/0805	Shape	2224/08175	the item being metallic
2224/08052	in top view	2224/08183	the bonding area connecting to a potential ring of the item
2224/08053	being non uniform along the bonding area	2224/08187	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08054	being rectangular			
2224/08055	being square	2224/08188	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08056	being circular or elliptic	2224/08195	the item being a discrete passive component
2224/08057	in side view	2224/08197	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08058	being non uniform along the bonding area	2224/08198	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08059	comprising protrusions or indentations			
2224/0807	of bonding interfaces, e.g. interlocking features	2224/08221	the body and the item being stacked
2224/081	Disposition	2224/08225	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/08111	the bonding area being disposed in a recess of the surface of the body	2224/0823	the bonding area connecting to a pin of the item
2224/08112	the bonding area being at least partially embedded in the surface of the body	2224/08233	the bonding area connecting to a potential ring of the item
2224/08113	the whole bonding area protruding from the surface of the body	2224/08235	the bonding area connecting to a via metallisation of the item
2224/0812	the bonding area connecting directly to another bonding area, i.e. connectorless bonding, e.g. bumpless bonding	2224/08237	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08121	the connected bonding areas being not aligned with respect to each other	2224/08238	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08123	the bonding area connecting directly to at least two bonding areas	2224/08245	the item being metallic
2224/08135	the bonding area connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip	2224/08253	the bonding area connecting to a potential ring of the item
2224/08137	the bodies being arranged next to each other, e.g. on a common substrate	2224/08257	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08145	the bodies being stacked	2224/08258	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08146	the bonding area connecting to a via connection in the body	2224/08265	the item being a discrete passive component
2224/08147	the bonding area connecting to a bonding area disposed in a recess of the surface of the body			
2224/08148	the bonding area connecting to a bonding area protruding from the surface of the body			
2224/08151	the bonding area connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive			
2224/08153	the body and the item being arranged next to each other, e.g. on a common substrate			

2224/08267	the bonding area connecting to a bonding area disposed in a recess of the surface of the item	2224/09155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/08268	the bonding area connecting to a bonding area protruding from the surface of the item	2224/09156	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/085	Material	2224/0916	Random array, i.e. array with no symmetry
2224/08501	at the bonding interface	2224/09163	with a staggered arrangement
2224/08502	comprising an eutectic alloy	2224/09164	covering only portions of the surface to be connected
2224/08503	comprising an intermetallic compound	2224/09165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/08505	outside the bonding interface	2224/09177	Combinations of arrays with different layouts
2224/08506	comprising an eutectic alloy	2224/09179	Corner adaptations, i.e. disposition of the bonding areas at the corners of the semiconductor or solid-state body
2224/09	of a plurality of bonding areas	2224/0918	being disposed on at least two different sides of the body, e.g. dual array
2224/0901	Structure	2224/09181	On opposite sides of the body
2224/0903	Bonding areas having different sizes, e.g. different diameters, heights or widths	2224/09183	On contiguous sides of the body
2224/0905	Shape	2224/095	Material
2224/09051	Bonding areas having different shapes	2224/09505	Bonding areas having different materials
2224/09055	of their bonding interfaces	2224/0951	Function
2224/091	Disposition	2224/09515	Bonding areas having different functions
2224/09102	the bonding areas being at different heights	2224/09517	including bonding areas providing primarily mechanical support
2224/09103	on the semiconductor or solid-state body	2224/09519	including bonding areas providing primarily thermal dissipation
2224/09104	outside the semiconductor or solid-state body	2224/10	Bump connectors; Manufacturing methods related thereto
2224/0912	Layout (layout of bonding areas prior to the connecting process H01L 2224/0612)	2224/1012	Auxiliary members for bump connectors, e.g. spacers
2224/0913	Square or rectangular array	2224/10122	being formed on the semiconductor or solid-state body to be connected
2224/09132	being non uniform, i.e. having a non uniform pitch across the array	2224/10125	Reinforcing structures
2224/09133	with a staggered arrangement, e.g. depopulated array	2224/10126	Bump collar
2224/09134	covering only portions of the surface to be connected	2224/10135	Alignment aids
2224/09135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/10145	Flow barriers
2224/0914	Circular array, i.e. array with radial symmetry	2224/10152	being formed on an item to be connected not being a semiconductor or solid-state body
2224/09142	being non uniform, i.e. having a non uniform pitch across the array	2224/10155	Reinforcing structures
2224/09143	with a staggered arrangement	2224/10156	Bump collar
2224/09144	covering only portions of the surface to be connected	2224/10165	Alignment aids
2224/09145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/10175	Flow barriers
2224/0915	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/11	Manufacturing methods
2224/09151	being uniform, i.e. having a uniform pitch across the array	2224/11001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate
2224/09152	being non uniform, i.e. having a non uniform pitch across the array	2224/11002	for supporting the semiconductor or solid-state body
2224/09153	with a staggered arrangement, e.g. depopulated array	2224/11003	for holding or transferring the bump preform
2224/09154	covering only portions of the surface to be connected	2224/11005	for aligning the bump connector, e.g. marks, spacers
			2224/11009	for protecting parts during manufacture
			2224/11011	Involving a permanent auxiliary member, i.e. a member which is left at least partly in the finished device, e.g. coating, dummy feature

2224/11013	for holding or confining the bump connector, e.g. solder flow barrier	2224/11515	Curing and solidification, e.g. of a photosensitive bump material
2224/11015	for aligning the bump connector, e.g. marks, spacers	2224/1152	Self-assembly, e.g. self-agglomeration of the bump material in a fluid
2224/11019	for protecting parts during the process	2224/11522	Auxiliary means therefor, e.g. for self-assembly activation
2224/111	Manufacture and pre-treatment of the bump connector preform	2224/11524	with special adaptation of the surface or of an auxiliary substrate, e.g. surface shape specially adapted for the self-assembly process
2224/1111	Shaping	2224/11526	involving the material of the bonding area, e.g. bonding pad or under bump metallisation [UBM]
2224/1112	Applying permanent coating	2224/1155	Selective modification
2224/113	by local deposition of the material of the bump connector	2224/11552	using a laser or a focussed ion beam [FIB]
2224/1131	in liquid form	2224/11554	Stereolithography, i.e. solidification of a pattern defined by a laser trace in a photosensitive resin
2224/11312	Continuous flow, e.g. using a microsyringe, a pump, a nozzle or extrusion	2224/116	by patterning a pre-deposited material (treatment of parts prior to assembly of the devices H01L 21/48)
2224/11318	by dispensing droplets	2224/11602	Mechanical treatment, e.g. polishing, grinding
2224/1132	Screen printing, i.e. using a stencil	2224/1161	Physical or chemical etching
2224/1133	in solid form	2224/11612	by physical means only
2224/11332	using a powder	2224/11614	by chemical means only
2224/11334	using preformed bumps	2224/11616	Chemical mechanical polishing [CMP]
2224/1134	Stud bumping, i.e. using a wire-bonding apparatus	2224/11618	with selective exposure, development and removal of a photosensitive bump material, e.g. of a photosensitive conductive resin
2224/114	by blanket deposition of the material of the bump connector	2224/1162	using masks
2224/1141	in liquid form	2224/11622	Photolithography
2224/11416	Spin coating	2224/1163	using a laser or a focused ion beam [FIB]
2224/11418	Spray coating	2224/11632	Ablation by means of a laser or focused ion beam [FIB]
2224/1142	Curtain coating	2224/117	involving monitoring, e.g. feedback loop
2224/11422	by dipping, e.g. in a solder bath (hot-dipping C23C 2/00)	2224/118	Post-treatment of the bump connector
2224/11424	Immersion coating, e.g. in a solder bath (immersion processes C23C 2/00)	2224/1181	Cleaning, e.g. oxide removal step, desmearing
2224/11426	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/1182	Applying permanent coating, e.g. in-situ coating
2224/11428	Wave coating	2224/11821	Spray coating
2224/1143	in solid form	2224/11822	by dipping, e.g. in a solder bath
2224/11436	Lamination of a preform, e.g. foil, sheet or layer	2224/11823	Immersion coating, e.g. in a solder bath
2224/11438	the preform being at least partly pre-patterned	2224/11824	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/1144	by transfer printing	2224/11825	Plating, e.g. electroplating, electroless plating
2224/11442	using a powder	2224/11826	Physical vapour deposition [PVD], e.g. evaporation, or sputtering
2224/11444	in gaseous form	2224/11827	Chemical vapour deposition [CVD], e.g. laser CVD
2224/1145	Physical vapour deposition [PVD], e.g. evaporation, or sputtering	2224/1183	Reworking, e.g. shaping (reflowing H01L 2224/11849)
2224/11452	Chemical vapour deposition [CVD], e.g. laser CVD	2224/11831	involving a chemical process, e.g. etching the bump connector
2224/1146	Plating	2224/1184	involving a mechanical process, e.g. planarising the bump connector
2224/11462	Electroplating	2224/11845	Chemical mechanical polishing [CMP]
2224/11464	Electroless plating	2224/11848	Thermal treatments, e.g. annealing, controlled cooling
2224/11466	Conformal deposition, i.e. blanket deposition of a conformal layer on a patterned surface	2224/11849	Reflowing
2224/1147	using a lift-off mask			
2224/11472	Profile of the lift-off mask			
2224/11474	Multilayer masks			
2224/1148	Permanent masks, i.e. masks left in the finished device, e.g. passivation layers			
2224/115	by chemical or physical modification of a pre-existing or pre-deposited material			
2224/11502	Pre-existing or pre-deposited material			
2224/11505	Sintering			
2224/1151	Anodisation			

2224/119	Methods of manufacturing bump connectors involving a specific sequence of method steps	2224/13024	the bump connector being disposed on a redistribution layer on the semiconductor or solid-state body
2224/11901	with repetition of the same manufacturing step	2224/13025	the bump connector being disposed on a via connection of the semiconductor or solid-state body
2224/11902	Multiple masking steps	2224/13026	relative to the bonding area, e.g. bond pad, of the semiconductor or solid-state body
2224/11903	using different masks	2224/13027	the bump connector being offset with respect to the bonding area, e.g. bond pad
2224/11906	with modification of the same mask	2224/13028	the bump connector being disposed on at least two separate bonding areas, e.g. bond pads
2224/1191	Forming a passivation layer after forming the bump connector	2224/13075	Plural core members
2224/11912	the bump being used as a mask for patterning other parts	2224/13076	being mutually engaged together, e.g. through inserts
2224/11914	the under bump metallisation [UBM] being used as a mask for patterning other parts	2224/13078	being disposed next to each other, e.g. side-to-side arrangements
2224/11916	a passivation layer being used as a mask for patterning other parts	2224/1308	being stacked
2224/12	. . .	Structure, shape, material or disposition of the bump connectors prior to the connecting process	2224/13082	Two-layer arrangements
2224/12105	Bump connectors formed on an encapsulation of the semiconductor or solid-state body, e.g. bumps on chip-scale packages	2224/13083	Three-layer arrangements
2224/13	of an individual bump connector	2224/13084	Four-layer arrangements
2224/13001	Core members of the bump connector	2224/13099	Material
2224/13005	Structure	2224/131	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13006	Bump connector larger than the underlying bonding area, e.g. than the under bump metallisation [UBM]	2224/13101	the principal constituent melting at a temperature of less than 400°C
2224/13007	Bump connector smaller than the underlying bonding area, e.g. than the under bump metallisation [UBM]	2224/13105	Gallium [Ga] as principal constituent
2224/13008	Bump connector integrally formed with a redistribution layer on the semiconductor or solid-state body	2224/13109	Indium [In] as principal constituent
2224/13009	Bump connector integrally formed with a via connection of the semiconductor or solid-state body	2224/13111	Tin [Sn] as principal constituent
2224/1301	Shape	2224/13113	Bismuth [Bi] as principal constituent
2224/13011	comprising apertures or cavities, e.g. hollow bump	2224/13114	Thallium [Tl] as principal constituent
2224/13012	in top view	2224/13116	Lead [Pb] as principal constituent
2224/13013	being rectangular or square	2224/13117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13014	being circular or elliptic	2224/13118	Zinc [Zn] as principal constituent
2224/13015	comprising protrusions or indentations	2224/1312	Antimony [Sb] as principal constituent
2224/13016	in side view	2224/13123	Magnesium [Mg] as principal constituent
2224/13017	being non uniform along the bump connector	2224/13124	Aluminium [Al] as principal constituent
2224/13018	comprising protrusions or indentations	2224/13138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13019	at the bonding interface of the bump connector, i.e. on the surface of the bump connector	2224/13139	Silver [Ag] as principal constituent
2224/1302	Disposition	2224/13144	Gold [Au] as principal constituent
2224/13021	the bump connector being disposed in a recess of the surface	2224/13147	Copper [Cu] as principal constituent
2224/13022	the bump connector being at least partially embedded in the surface			
2224/13023	the whole bump connector protruding from the surface			

2224/13149	Manganese [Mn] as principal constituent	2224/13195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/131 - H01L 2224/13191
2224/13155	Nickel [Ni] as principal constituent	2224/13198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/13157	Cobalt [Co] as principal constituent	2224/13199	Material of the matrix
2224/1316	Iron [Fe] as principal constituent	2224/132	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13163	the principal constituent melting at a temperature of greater than 1550°C	2224/13201	the principal constituent melting at a temperature of less than 400°C
2224/13164	Palladium [Pd] as principal constituent	2224/13205	Gallium [Ga] as principal constituent
2224/13166	Titanium [Ti] as principal constituent	2224/13209	Indium [In] as principal constituent
2224/13169	Platinum [Pt] as principal constituent	2224/13211	Tin [Sn] as principal constituent
2224/1317	Zirconium [Zr] as principal constituent	2224/13213	Bismuth [Bi] as principal constituent
2224/13171	Chromium [Cr] as principal constituent	2224/13214	Thallium [Tl] as principal constituent
2224/13172	Vanadium [V] as principal constituent	2224/13216	Lead [Pb] as principal constituent
2224/13173	Rhodium [Rh] as principal constituent	2224/13217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13176	Ruthenium [Ru] as principal constituent	2224/13218	Zinc [Zn] as principal constituent
2224/13178	Iridium [Ir] as principal constituent	2224/1322	Antimony [Sb] as principal constituent
2224/13179	Niobium [Nb] as principal constituent	2224/13223	Magnesium [Mg] as principal constituent
2224/1318	Molybdenum [Mo] as principal constituent	2224/13224	Aluminium [Al] as principal constituent
2224/13181	Tantalum [Ta] as principal constituent	2224/13238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13183	Rhenium [Re] as principal constituent	2224/13239	Silver [Ag] as principal constituent
2224/13184	Tungsten [W] as principal constituent	2224/13244	Gold [Au] as principal constituent
2224/13186	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/13247	Copper [Cu] as principal constituent
2224/13187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13188)	2224/13249	Manganese [Mn] as principal constituent
2224/13188	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13255	Nickel [Ni] as principal constituent
2224/1319	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13257	Cobalt [Co] as principal constituent
2224/13191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/1326	Iron [Fe] as principal constituent
2224/13193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/131 - H01L 2224/13191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond		
2224/13194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/131 - H01L 2224/13191		

2224/13263	the principal constituent melting at a temperature of greater than 1550°C	2224/133	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13264	Palladium [Pd] as principal constituent	2224/13301	the principal constituent melting at a temperature of less than 400°C
2224/13266	Titanium [Ti] as principal constituent	2224/13305	Gallium [Ga] as principal constituent
2224/13269	Platinum [Pt] as principal constituent	2224/13309	Indium [In] as principal constituent
2224/1327	Zirconium [Zr] as principal constituent	2224/13311	Tin [Sn] as principal constituent
2224/13271	Chromium [Cr] as principal constituent	2224/13313	Bismuth [Bi] as principal constituent
2224/13272	Vanadium [V] as principal constituent	2224/13314	Thallium [Tl] as principal constituent
2224/13273	Rhodium [Rh] as principal constituent	2224/13316	Lead [Pb] as principal constituent
2224/13276	Ruthenium [Ru] as principal constituent	2224/13317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13278	Iridium [Ir] as principal constituent	2224/13318	Zinc [Zn] as principal constituent
2224/13279	Niobium [Nb] as principal constituent	2224/1332	Antimony [Sb] as principal constituent
2224/1328	Molybdenum [Mo] as principal constituent	2224/13323	Magnesium [Mg] as principal constituent
2224/13281	Tantalum [Ta] as principal constituent	2224/13324	Aluminium [Al] as principal constituent
2224/13283	Rhenium [Re] as principal constituent	2224/13338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13284	Tungsten [W] as principal constituent	2224/13339	Silver [Ag] as principal constituent
2224/13286	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/13344	Gold [Au] as principal constituent
2224/13287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13288)	2224/13347	Copper [Cu] as principal constituent
2224/13288	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13349	Manganese [Mn] as principal constituent
2224/1329	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13355	Nickel [Ni] as principal constituent
2224/13291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13357	Cobalt [Co] as principal constituent
2224/13293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/132 - H01L 2224/13291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/1336	Iron [Fe] as principal constituent
2224/13294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/132 - H01L 2224/13291	2224/13363	the principal constituent melting at a temperature of greater than 1550°C
2224/13295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/132 - H01L 2224/13291	2224/13364	Palladium [Pd] as principal constituent
2224/13298	Fillers	2224/13366	Titanium [Ti] as principal constituent
2224/13299	Base material	2224/13369	Platinum [Pt] as principal constituent
		2224/1337	Zirconium [Zr] as principal constituent

2224/13371	Chromium [Cr] as principal constituent	2224/134	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13372	Vanadium [V] as principal constituent	2224/13401	the principal constituent melting at a temperature of less than 400°C
2224/13373	Rhodium [Rh] as principal constituent	2224/13405	Gallium [Ga] as principal constituent
2224/13376	Ruthenium [Ru] as principal constituent	2224/13409	Indium [In] as principal constituent
2224/13378	Iridium [Ir] as principal constituent	2224/13411	Tin [Sn] as principal constituent
2224/13379	Niobium [Nb] as principal constituent	2224/13413	Bismuth [Bi] as principal constituent
2224/1338	Molybdenum [Mo] as principal constituent	2224/13414	Thallium [Tl] as principal constituent
2224/13381	Tantalum [Ta] as principal constituent	2224/13416	Lead [Pb] as principal constituent
2224/13383	Rhenium [Re] as principal constituent	2224/13417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13384	Tungsten [W] as principal constituent	2224/13418	Zinc [Zn] as principal constituent
2224/13386	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/1342	Antimony [Sb] as principal constituent
2224/13387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13388)	2224/13423	Magnesium [Mg] as principal constituent
2224/13388	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13424	Aluminium [Al] as principal constituent
2224/1339	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13439	Silver [Ag] as principal constituent
2224/13393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/133 - H01L 2224/13391	2224/13444	Gold [Au] as principal constituent
2224/13394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/133 - H01L 2224/13391	2224/13447	Copper [Cu] as principal constituent
2224/13395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/133 - H01L 2224/13391	2224/13449	Manganese [Mn] as principal constituent
2224/13398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13455	Nickel [Ni] as principal constituent
2224/13399	Coating material	2224/13457	Cobalt [Co] as principal constituent
		2224/1346	Iron [Fe] as principal constituent
		2224/13463	the principal constituent melting at a temperature of greater than 1550°C
		2224/13464	Palladium [Pd] as principal constituent
		2224/13466	Titanium [Ti] as principal constituent
		2224/13469	Platinum [Pt] as principal constituent
		2224/1347	Zirconium [Zr] as principal constituent

2224/13471	Chromium [Cr] as principal constituent	2224/13552	comprising protrusions or indentations
2224/13472	Vanadium [V] as principal constituent	2224/13553	at the bonding interface of the bump connector, i.e. on the surface of the bump connector
2224/13473	Rhodium [Rh] as principal constituent	2224/1356	Disposition
2224/13476	Ruthenium [Ru] as principal constituent	2224/13561	On the entire surface of the core, i.e. integral coating
2224/13478	Iridium [Ir] as principal constituent	2224/13562	On the entire exposed surface of the core
2224/13479	Niobium [Nb] as principal constituent	2224/13563	Only on parts of the surface of the core, i.e. partial coating
2224/1348	Molybdenum [Mo] as principal constituent	2224/13564	Only on the bonding interface of the bump connector
2224/13481	Tantalum [Ta] as principal constituent	2224/13565	Only outside the bonding interface of the bump connector
2224/13483	Rhenium [Re] as principal constituent	2224/13566	Both on and outside the bonding interface of the bump connector
2224/13484	Tungsten [W] as principal constituent	2224/1357	Single coating layer
2224/13486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/13575	Plural coating layers
2224/13487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13488)	2224/13576	being mutually engaged together, e.g. through inserts
2224/13488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13578	being disposed next to each other, e.g. side-to-side arrangements
2224/1349	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/1358	being stacked
2224/13491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13582	Two-layer coating
2224/13493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/134 - H01L 2224/13491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/13583	Three-layer coating
2224/13494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/134 - H01L 2224/13491	2224/13584	Four-layer coating
2224/13495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/134 - H01L 2224/13491	2224/13599	Material
2224/13498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/136	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13499	Shape or distribution of the fillers	2224/13601	the principal constituent melting at a temperature of less than 400°C
2224/1354	Coating	2224/13605	Gallium [Ga] as principal constituent
2224/13541	Structure	2224/13609	Indium [In] as principal constituent
2224/1355	Shape	2224/13611	Tin [Sn] as principal constituent
2224/13551	being non uniform	2224/13613	Bismuth [Bi] as principal constituent
		2224/13614	Thallium [Tl] as principal constituent
		2224/13616	Lead [Pb] as principal constituent
		2224/13617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
		2224/13618	Zinc [Zn] as principal constituent
		2224/1362	Antimony [Sb] as principal constituent
		2224/13623	Magnesium [Mg] as principal constituent
		2224/13624	Aluminium [Al] as principal constituent
		2224/13638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
		2224/13639	Silver [Ag] as principal constituent

2224/13644	Gold [Au] as principal constituent	2224/13694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/136 - H01L 2224/13691
2224/13647	Copper [Cu] as principal constituent	2224/13695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/136 - H01L 2224/13691
2224/13649	Manganese [Mn] as principal constituent	2224/13698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/13655	Nickel [Ni] as principal constituent	2224/13699	Material of the matrix
2224/13657	Cobalt [Co] as principal constituent	2224/137	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/1366	Iron [Fe] as principal constituent	2224/13701	the principal constituent melting at a temperature of less than 400°C
2224/13663	the principal constituent melting at a temperature of greater than 1550°C	2224/13705	Gallium [Ga] as principal constituent
2224/13664	Palladium [Pd] as principal constituent	2224/13709	Indium [In] as principal constituent
2224/13666	Titanium [Ti] as principal constituent	2224/13711	Tin [Sn] as principal constituent
2224/13669	Platinum [Pt] as principal constituent	2224/13713	Bismuth [Bi] as principal constituent
2224/1367	Zirconium [Zr] as principal constituent	2224/13714	Thallium [Tl] as principal constituent
2224/13671	Chromium [Cr] as principal constituent	2224/13716	Lead [Pb] as principal constituent
2224/13672	Vanadium [V] as principal constituent	2224/13717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13673	Rhodium [Rh] as principal constituent	2224/13718	Zinc [Zn] as principal constituent
2224/13676	Ruthenium [Ru] as principal constituent	2224/1372	Antimony [Sb] as principal constituent
2224/13678	Iridium [Ir] as principal constituent	2224/13723	Magnesium [Mg] as principal constituent
2224/13679	Niobium [Nb] as principal constituent	2224/13724	Aluminium [Al] as principal constituent
2224/1368	Molybdenum [Mo] as principal constituent	2224/13738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13681	Tantalum [Ta] as principal constituent	2224/13739	Silver [Ag] as principal constituent
2224/13683	Rhenium [Re] as principal constituent	2224/13744	Gold [Au] as principal constituent
2224/13684	Tungsten [W] as principal constituent	2224/13747	Copper [Cu] as principal constituent
2224/13686	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/13749	Manganese [Mn] as principal constituent
2224/13687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13688)	2224/13755	Nickel [Ni] as principal constituent
2224/13688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13757	Cobalt [Co] as principal constituent
2224/1369	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		
2224/13691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		
2224/13693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/136 - H01L 2224/13691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond		

2224/1376	Iron [Fe] as principal constituent	2224/13799	Base material
2224/13763	the principal constituent melting at a temperature of greater than 1550°C	2224/138	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13764	Palladium [Pd] as principal constituent	2224/13801	the principal constituent melting at a temperature of less than 400°C
2224/13766	Titanium [Ti] as principal constituent	2224/13805	Gallium [Ga] as principal constituent
2224/13769	Platinum [Pt] as principal constituent	2224/13809	Indium [In] as principal constituent
2224/1377	Zirconium [Zr] as principal constituent	2224/13811	Tin [Sn] as principal constituent
2224/13771	Chromium [Cr] as principal constituent	2224/13813	Bismuth [Bi] as principal constituent
2224/13772	Vanadium [V] as principal constituent	2224/13814	Thallium [Tl] as principal constituent
2224/13773	Rhodium [Rh] as principal constituent	2224/13816	Lead [Pb] as principal constituent
2224/13776	Ruthenium [Ru] as principal constituent	2224/13817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13778	Iridium [Ir] as principal constituent	2224/13818	Zinc [Zn] as principal constituent
2224/13779	Niobium [Nb] as principal constituent	2224/1382	Antimony [Sb] as principal constituent
2224/1378	Molybdenum [Mo] as principal constituent	2224/13823	Magnesium [Mg] as principal constituent
2224/13781	Tantalum [Ta] as principal constituent	2224/13824	Aluminium [Al] as principal constituent
2224/13783	Rhenium [Re] as principal constituent	2224/13838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13784	Tungsten [W] as principal constituent	2224/13839	Silver [Ag] as principal constituent
2224/13786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/13844	Gold [Au] as principal constituent
2224/13787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13788)	2224/13847	Copper [Cu] as principal constituent
2224/13788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13849	Manganese [Mn] as principal constituent
2224/1379	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13855	Nickel [Ni] as principal constituent
2224/13791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13857	Cobalt [Co] as principal constituent
2224/13793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/137 - H01L 2224/13791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/1386	Iron [Fe] as principal constituent
2224/13794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/137 - H01L 2224/13791	2224/13863	the principal constituent melting at a temperature of greater than 1550°C
2224/13795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/137 - H01L 2224/13791	2224/13864	Palladium [Pd] as principal constituent
2224/13798	Fillers	2224/13866	Titanium [Ti] as principal constituent
		2224/13869	Platinum [Pt] as principal constituent
		2224/1387	Zirconium [Zr] as principal constituent

2224/13871	Chromium [Cr] as principal constituent	2224/139	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/13872	Vanadium [V] as principal constituent	2224/13901	the principal constituent melting at a temperature of less than 400°C
2224/13873	Rhodium [Rh] as principal constituent	2224/13905	Gallium [Ga] as principal constituent
2224/13876	Ruthenium [Ru] as principal constituent	2224/13909	Indium [In] as principal constituent
2224/13878	Iridium [Ir] as principal constituent	2224/13911	Tin [Sn] as principal constituent
2224/13879	Niobium [Nb] as principal constituent	2224/13913	Bismuth [Bi] as principal constituent
2224/1388	Molybdenum [Mo] as principal constituent	2224/13914	Thallium [Tl] as principal constituent
2224/13881	Tantalum [Ta] as principal constituent	2224/13916	Lead [Pb] as principal constituent
2224/13883	Rhenium [Re] as principal constituent	2224/13917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13884	Tungsten [W] as principal constituent	2224/13918	Zinc [Zn] as principal constituent
2224/13886	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/1392	Antimony [Sb] as principal constituent
2224/13887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13888)	2224/13923	Magnesium [Mg] as principal constituent
2224/13888	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13924	Aluminium [Al] as principal constituent
2224/1389	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13939	Silver [Ag] as principal constituent
2224/13893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/138 - H01L 2224/13891	2224/13944	Gold [Au] as principal constituent
2224/13894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/138 - H01L 2224/13891	2224/13947	Copper [Cu] as principal constituent
2224/13895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/138 - H01L 2224/13891	2224/13949	Manganese [Mn] as principal constituent
2224/13898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13955	Nickel [Ni] as principal constituent
2224/13899	Coating material	2224/13957	Cobalt [Co] as principal constituent
		2224/1396	Iron [Fe] as principal constituent
		2224/13963	the principal constituent melting at a temperature of greater than 1550°C
		2224/13964	Palladium [Pd] as principal constituent
		2224/13966	Titanium [Ti] as principal constituent
		2224/13969	Platinum [Pt] as principal constituent
		2224/1397	Zirconium [Zr] as principal constituent

2224/13971	Chromium [Cr] as principal constituent	2224/1405	Shape
2224/13972	Vanadium [V] as principal constituent	2224/14051	Bump connectors having different shapes
2224/13973	Rhodium [Rh] as principal constituent	2224/141	Disposition
2224/13976	Ruthenium [Ru] as principal constituent	2224/14104	relative to the bonding areas, e.g. bond pads, of the semiconductor or solid-state body
2224/13978	Iridium [Ir] as principal constituent	2224/1411	the bump connectors being bonded to at least one common bonding area
2224/13979	Niobium [Nb] as principal constituent	2224/1412	Layout
2224/1398	Molybdenum [Mo] as principal constituent	2224/1413	Square or rectangular array
2224/13981	Tantalum [Ta] as principal constituent	2224/14131	being uniform, i.e. having a uniform pitch across the array
2224/13983	Rhenium [Re] as principal constituent	2224/14132	being non uniform, i.e. having a non uniform pitch across the array
2224/13984	Tungsten [W] as principal constituent	2224/14133	with a staggered arrangement, e.g. depopulated array
2224/13986	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/14134	covering only portions of the surface to be connected
2224/13987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13988)	2224/14135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/13988	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/14136	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/1399	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/1414	Circular array, i.e. array with radial symmetry
2224/13991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/14141	being uniform, i.e. having a uniform pitch across the array
2224/13993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/139 - H01L 2224/13991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/14142	being non uniform, i.e. having a non uniform pitch across the array
2224/13994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/139 - H01L 2224/13991	2224/14143	with a staggered arrangement, e.g. depopulated array
2224/13995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/139 - H01L 2224/13991	2224/14144	covering only portions of the surface to be connected
2224/13998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/14145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/13999	Shape or distribution of the fillers	2224/14146	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/14	of a plurality of bump connectors	2224/1415	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry
2224/1401	Structure	2224/14151	being uniform, i.e. having a uniform pitch across the array
2224/1403	Bump connectors having different sizes, e.g. different diameters, heights or widths	2224/14152	being non uniform, i.e. having a non uniform pitch across the array
		2224/14153	with a staggered arrangement, e.g. depopulated array
		2224/14154	covering only portions of the surface to be connected
		2224/14155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
		2224/14156	Covering only the central area of the surface to be connected, i.e. central arrangements
		2224/1416	Random layout, i.e. layout with no symmetry
		2224/14163	with a staggered arrangement
		2224/14164	covering only portions of the surface to be connected

2224/14165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/16113	the whole bump connector protruding from the surface
2224/14166	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/1613	the bump connector connecting within a semiconductor or solid-state body, i.e. connecting two bonding areas on the same semiconductor or solid-state body
2224/14177	Combinations of arrays with different layouts	2224/16135	the bump connector connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip
2224/14179	Corner adaptations, i.e. disposition of the bump connectors at the corners of the semiconductor or solid-state body	2224/16137	the bodies being arranged next to each other, e.g. on a common substrate
2224/1418	being disposed on at least two different sides of the body, e.g. dual array	2224/16141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
2224/14181	On opposite sides of the body	2224/16145	the bodies being stacked
2224/14183	On contiguous sides of the body	2224/16146	the bump connector connecting to a via connection in the semiconductor or solid-state body
2224/145	Material	2224/16147	the bump connector connecting to a bonding area disposed in a recess of the surface
2224/14505	Bump connectors having different materials	2224/16148	the bump connector connecting to a bonding area protruding from the surface
2224/1451	Function	2224/16151	the bump connector connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive
2224/14515	Bump connectors having different functions	2224/16153	the body and the item being arranged next to each other, e.g. on a common substrate
2224/14517	including bump connectors providing primarily mechanical bonding	2224/16155	the item being non-metallic, e.g. being an insulating substrate with or without metallisation
2224/14519	including bump connectors providing primarily thermal dissipation	2224/16157	the bump connector connecting to a bond pad of the item
2224/15	Structure, shape, material or disposition of the bump connectors after the connecting process	2224/1616	the bump connector connecting to a pin of the item
2224/16	of an individual bump connector	2224/16163	the bump connector connecting to a potential ring of the item
2224/1601	Structure	2224/16165	the bump connector connecting to a via metallisation of the item
2224/16012	relative to the bonding area, e.g. bond pad	2224/16167	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16013	the bump connector being larger than the bonding area, e.g. bond pad	2224/16168	the bump connector connecting to a bonding area protruding from the surface of the item
2224/16014	the bump connector being smaller than the bonding area, e.g. bond pad	2224/16175	the item being metallic
2224/1605	Shape	2224/16183	the bump connector connecting to a potential ring of the item
2224/16052	in top view	2224/16187	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16054	being rectangular or square	2224/16188	the bump connector connecting to a bonding area protruding from the surface of the item
2224/16055	being circular or elliptic	2224/16195	the item being a discrete passive component
2224/16056	comprising protrusions or indentations	2224/16197	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16057	in side view			
2224/16058	being non uniform along the bump connector			
2224/16059	comprising protrusions or indentations			
2224/1607	of bonding interfaces, e.g. interlocking features			
2224/161	Disposition			
2224/16104	relative to the bonding area, e.g. bond pad			
2224/16105	the bump connector connecting bonding areas being not aligned with respect to each other			
2224/16106	the bump connector connecting one bonding area to at least two respective bonding areas			
2224/16108	the bump connector not being orthogonal to the surface			
2224/16111	the bump connector being disposed in a recess of the surface			
2224/16112	the bump connector being at least partially embedded in the surface			

2224/16198	the bump connector connecting to a bonding area protruding from the surface of the item	2224/17055	of their bonding interfaces
2224/16221	the body and the item being stacked	2224/171	Disposition
2224/16225	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/17104	relative to the bonding areas, e.g. bond pads
2224/16227	the bump connector connecting to a bond pad of the item	2224/17106	the bump connectors being bonded to at least one common bonding area
2224/1623	the bump connector connecting to a pin of the item	2224/17107	the bump connectors connecting two common bonding areas
2224/16233	the bump connector connecting to a potential ring of the item	2224/1712	Layout (layout of bump connectors prior to the connecting process H01L 2224/1412)
2224/16235	the bump connector connecting to a via metallisation of the item	2224/1713	Square or rectangular array
2224/16237	the bump connector connecting to a bonding area disposed in a recess of the surface of the item	2224/17132	being non uniform, i.e. having a non uniform pitch across the array
2224/16238	the bump connector connecting to a bonding area protruding from the surface of the item	2224/17133	with a staggered arrangement, e.g. depopulated array
2224/1624	the bump connector connecting between the body and an opposite side of the item with respect to the body	2224/17134	covering only portions of the surface to be connected
2224/16245	the item being metallic	2224/17135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/16253	the bump connector connecting to a potential ring of the item	2224/17136	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/16257	the bump connector connecting to a bonding area disposed in a recess of the surface of the item	2224/1714	Circular array, i.e. array with radial symmetry
2224/16258	the bump connector connecting to a bonding area protruding from the surface of the item	2224/17142	being non uniform, i.e. having a non uniform pitch across the array
2224/1626	the bump connector connecting between the body and an opposite side of the item with respect to the body	2224/17143	with a staggered arrangement
2224/16265	the item being a discrete passive component	2224/17144	covering only portions of the surface to be connected
2224/16267	the bump connector connecting to a bonding area disposed in a recess of the surface of the item	2224/17145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/16268	the bump connector connecting to a bonding area protruding from the surface of the item	2224/17146	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/165	Material	2224/1715	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry
2224/16501	at the bonding interface	2224/17151	being uniform, i.e. having a uniform pitch across the array
2224/16502	comprising an eutectic alloy	2224/17152	being non uniform, i.e. having a non uniform pitch across the array
2224/16503	comprising an intermetallic compound	2224/17153	with a staggered arrangement, e.g. depopulated array
2224/16505	outside the bonding interface, e.g. in the bulk of the bump connector	2224/17154	covering only portions of the surface to be connected
2224/16506	comprising an eutectic alloy	2224/17155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/16507	comprising an intermetallic compound	2224/17156	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/17	of a plurality of bump connectors	2224/1716	Random layout, i.e. layout with no symmetry
2224/1701	Structure	2224/17163	with a staggered arrangement
2224/1703	Bump connectors having different sizes, e.g. different diameters, heights or widths	2224/17164	covering only portions of the surface to be connected
2224/1705	Shape	2224/17165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/17051	Bump connectors having different shapes			

2224/17166	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/24137	the bodies being arranged next to each other, e.g. on a common substrate
2224/17177	Combinations of arrays with different layouts	2224/24141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
2224/17179	Corner adaptations, i.e. disposition of the bump connectors at the corners of the semiconductor or solid-state body	2224/24145	the bodies being stacked
2224/1718	being disposed on at least two different sides of the body, e.g. dual array	2224/24146	the HDI interconnect connecting to the same level of the lower semiconductor or solid-state body at which the upper semiconductor or solid-state body is mounted
2224/17181	On opposite sides of the body	2224/24147	the HDI interconnect not connecting to the same level of the lower semiconductor or solid-state body at which the upper semiconductor or solid-state body is mounted, e.g. the upper semiconductor or solid-state body being mounted in a cavity or on a protrusion of the lower semiconductor or solid-state body
2224/17183	On contiguous sides of the body	2224/24151	Connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive
2224/175	Material	2224/24153	the body and the item being arranged next to each other, e.g. on a common substrate
2224/17505	Bump connectors having different materials	2224/24155	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/1751	Function	2224/24175	the item being metallic
2224/17515	Bump connectors having different functions	2224/24195	the item being a discrete passive component
2224/17517	including bump connectors providing primarily mechanical support	2224/24221	the body and the item being stacked
2224/17519	including bump connectors providing primarily thermal dissipation	2224/24225	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/18	. .	High density interconnect [HDI] connectors; Manufacturing methods related thereto	2224/24226	the HDI interconnect connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the item being planar
2224/19	. . .	Manufacturing methods of high density interconnect preforms	2224/24227	the HDI interconnect not connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the semiconductor or solid-state body being mounted in a cavity or on a protrusion of the item
2224/20	. . .	Structure, shape, material or disposition of high density interconnect preforms	2224/24245	the item being metallic
2224/21	of an individual HDI interconnect	2224/24246	the HDI interconnect connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the item being planar
2224/2101	Structure	2224/24247	the HDI interconnect not connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the semiconductor or solid-state body being mounted in a cavity or on a protrusion of the item
2224/2105	Shape			
2224/211	Disposition			
2224/214	Connecting portions			
2224/215	Material			
2224/22	of a plurality of HDI interconnects			
2224/2201	Structure			
2224/2205	Shape			
2224/221	Disposition			
2224/224	Connecting portions			
2224/225	Material			
2224/22505	HDI interconnects having different materials			
2224/23	. . .	Structure, shape, material or disposition of the high density interconnect connectors after the connecting process			
2224/24	of an individual high density interconnect connector			
2224/2401	Structure			
2224/24011	Deposited, e.g. MCM-D type			
2224/2402	Laminated, e.g. MCM-L type			
2224/2405	Shape			
2224/24051	Conformal with the semiconductor or solid-state device			
2224/241	Disposition			
2224/24101	Connecting bonding areas at the same height			
2224/24105	Connecting bonding areas at different heights			
2224/2413	Connecting within a semiconductor or solid-state body			
2224/24135	Connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip			

2224/24265	the item being a discrete passive component	2224/27001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate
2224/244	Connecting portions	2224/27002	for supporting the semiconductor or solid-state body
2224/245	Material	2224/27003	for holding or transferring the layer preform
2224/2499	Auxiliary members for HDI interconnects, e.g. spacers, alignment aids	2224/27005	for aligning the layer connector, e.g. marks, spacers
2224/24991	being formed on the semiconductor or solid-state body to be connected	2224/27009	for protecting parts during manufacture
2224/24992	Flow barrier	2224/27011	Involving a permanent auxiliary member, i.e. a member which is left at least partly in the finished device, e.g. coating, dummy feature
2224/24996	being formed on an item to be connected not being a semiconductor or solid-state body	2224/27013	for holding or confining the layer connector, e.g. solder flow barrier
2224/24997	Flow barrier	2224/27015	for aligning the layer connector, e.g. marks, spacers
2224/24998	Reinforcing structures, e.g. ramp-like support	2224/27019	for protecting parts during the process
2224/25	of a plurality of high density interconnect connectors	2224/271	Manufacture and pre-treatment of the layer connector preform
2224/2501	Structure	2224/2711	Shaping
2224/2505	Shape	2224/2712	Applying permanent coating
2224/251	Disposition	2224/273	by local deposition of the material of the layer connector
2224/25105	Connecting at different heights	2224/2731	in liquid form
2224/2511	the connectors being bonded to at least one common bonding area	2224/27312	Continuous flow, e.g. using a microsyringe, a pump, a nozzle or extrusion
2224/25111	the connectors connecting two common bonding areas	2224/27318	by dispensing droplets
2224/25112	the connectors connecting a common bonding area on the semiconductor or solid-state body to different bonding areas outside the body	2224/2732	Screen printing, i.e. using a stencil
2224/25113	the connectors connecting different bonding areas on the semiconductor or solid-state body to a common bonding area outside the body	2224/2733	in solid form
2224/2512	Layout	2224/27332	using a powder
2224/25171	Fan-out arrangements	2224/27334	using preformed layer
2224/25174	Stacked arrangements	2224/274	by blanket deposition of the material of the layer connector
2224/25175	Parallel arrangements	2224/2741	in liquid form
2224/25177	Combinations of a plurality of arrangements	2224/27416	Spin coating
2224/2518	being disposed on at least two different sides of the body, e.g. dual array	2224/27418	Spray coating
2224/254	Connecting portions	2224/2742	Curtain coating
2224/2541	the connecting portions being stacked	2224/27422	by dipping, e.g. in a solder bath (hot-dipping C23C 2/00)
2224/2543	the connecting portions being staggered	2224/27424	Immersion coating, e.g. in a solder bath (immersion processes C23C 2/00)
2224/255	Material	2224/27426	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/26	Layer connectors, e.g. plate connectors, solder or adhesive layers; Manufacturing methods related thereto	2224/27428	Wave coating
2224/2612	Auxiliary members for layer connectors, e.g. spacers	2224/2743	in solid form
2224/26122	being formed on the semiconductor or solid-state body to be connected	2224/27436	Lamination of a preform, e.g. foil, sheet or layer
2224/26125	Reinforcing structures	2224/27438	the preform being at least partly pre-patterned
2224/26135	Alignment aids	2224/2744	by transfer printing
2224/26145	Flow barriers	2224/27442	using a powder
2224/26152	being formed on an item to be connected not being a semiconductor or solid-state body	2224/27444	in gaseous form
2224/26155	Reinforcing structures	2224/2745	Physical vapour deposition [PVD], e.g. evaporation, or sputtering
2224/26165	Alignment aids	2224/27452	Chemical vapour deposition [CVD], e.g. laser CVD
2224/26175	Flow barriers	2224/2746	Plating
2224/27	Manufacturing methods	2224/27462	Electroplating
			2224/27464	Electroless plating

2224/27466	Conformal deposition, i.e. blanket deposition of a conformal layer on a patterned surface	2224/27827	Chemical vapour deposition [CVD], e.g. laser CVD
2224/2747	using a lift-off mask	2224/2783	Reworking, e.g. shaping (reflowing H01L 2224/27849)
2224/27472	Profile of the lift-off mask	2224/27831	involving a chemical process, e.g. etching the layer connector
2224/27474	Multilayer masks	2224/2784	involving a mechanical process, e.g. planarising the layer connector
2224/2748	Permanent masks, i.e. masks left in the finished device, e.g. passivation layers	2224/27845	Chemical mechanical polishing [CMP]
2224/275	by chemical or physical modification of a pre-existing or pre-deposited material	2224/27848	Thermal treatments, e.g. annealing, controlled cooling
2224/27502	Pre-existing or pre-deposited material	2224/27849	Reflowing
2224/27505	Sintering	2224/279	Methods of manufacturing layer connectors involving a specific sequence of method steps
2224/2751	Anodisation	2224/27901	with repetition of the same manufacturing step
2224/27515	Curing and solidification, e.g. of a photosensitive layer material	2224/27902	Multiple masking steps
2224/2752	Self-assembly, e.g. self-agglomeration of the layer material in a fluid	2224/27903	using different masks
2224/27522	Auxiliary means therefor, e.g. for self-assembly activation	2224/27906	with modification of the same mask
2224/27524	with special adaptation of the surface or of an auxiliary substrate, e.g. surface shape specially adapted for the self-assembly process	2224/2791	Forming a passivation layer after forming the layer connector
2224/27526	involving the material of the bonding area, e.g. bonding pad	2224/27912	the layer being used as a mask for patterning other parts
2224/2755	Selective modification	2224/27916	a passivation layer being used as a mask for patterning other parts
2224/27552	using a laser or a focussed ion beam [FIB]	2224/28	Structure, shape, material or disposition of the layer connectors prior to the connecting process
2224/27554	Stereolithography, i.e. solidification of a pattern defined by a laser trace in a photosensitive resin	2224/28105	Layer connectors formed on an encapsulation of the semiconductor or solid-state body, e.g. layer connectors on chip-scale packages
2224/276	by patterning a pre-deposited material (treatment of parts prior to assembly of the devices H01L 21/48)	2224/29	of an individual layer connector
2224/27602	Mechanical treatment, e.g. polishing, grinding	2224/29001	Core members of the layer connector
2224/2761	Physical or chemical etching	2224/29005	Structure
2224/27612	by physical means only	2224/29006	Layer connector larger than the underlying bonding area
2224/27614	by chemical means only	2224/29007	Layer connector smaller than the underlying bonding area
2224/27616	Chemical mechanical polishing [CMP]	2224/29008	Layer connector integrally formed with a redistribution layer on the semiconductor or solid-state body
2224/27618	with selective exposure, development and removal of a photosensitive layer material, e.g. of a photosensitive conductive resin	2224/29009	Layer connector integrally formed with a via connection of the semiconductor or solid-state body
2224/2762	using masks	2224/2901	Shape
2224/27622	Photolithography	2224/29011	comprising apertures or cavities
2224/2763	using a laser or a focused ion beam [FIB]	2224/29012	in top view
2224/27632	Ablation by means of a laser or focused ion beam [FIB]	2224/29013	being rectangular or square
2224/277	involving monitoring, e.g. feedback loop	2224/29014	being circular or elliptic
2224/278	Post-treatment of the layer connector	2224/29015	comprising protrusions or indentations
2224/2781	Cleaning, e.g. oxide removal step, desmearing	2224/29016	in side view
2224/2782	Applying permanent coating, e.g. in-situ coating	2224/29017	being non uniform along the layer connector
2224/27821	Spray coating	2224/29018	comprising protrusions or indentations
2224/27822	by dipping, e.g. in a solder bath	2224/29019	at the bonding interface of the layer connector, i.e. on the surface of the layer connector
2224/27823	Immersion coating, e.g. in a solder bath	2224/2902	Disposition
2224/27824	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/29021	the layer connector being disposed in a recess of the surface (embedded layer connector H01L 2224/29022)
2224/27825	Plating, e.g. electroplating, electroless plating			
2224/27826	Physical vapour deposition [PVD], e.g. evaporation, or sputtering			

2224/29022	the layer connector being at least partially embedded in the surface	2224/29138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/29023	the whole layer connector protruding from the surface	2224/29139	Silver [Ag] as principal constituent
2224/29024	the layer connector being disposed on a redistribution layer on the semiconductor or solid-state body	2224/29144	Gold [Au] as principal constituent
2224/29025	the layer connector being disposed on a via connection of the semiconductor or solid-state body	2224/29147	Copper [Cu] as principal constituent
2224/29026	relative to the bonding area, e.g. bond pad, of the semiconductor or solid-state body	2224/29149	Manganese [Mn] as principal constituent
2224/29027	the layer connector being offset with respect to the bonding area, e.g. bond pad	2224/29155	Nickel [Ni] as principal constituent
2224/29028	the layer connector being disposed on at least two separate bonding areas, e.g. bond pads	2224/29157	Cobalt [Co] as principal constituent
2224/29034	the layer connector covering only portions of the surface to be connected	2224/2916	Iron [Fe] as principal constituent
2224/29035	covering only the peripheral area of the surface to be connected	2224/29163	the principal constituent melting at a temperature of greater than 1550°C
2224/29036	covering only the central area of the surface to be connected	2224/29164	Palladium [Pd] as principal constituent
2224/29075	Plural core members	2224/29166	Titanium [Ti] as principal constituent
2224/29076	being mutually engaged together, e.g. through inserts	2224/29169	Platinum [Pt] as principal constituent
2224/29078	being disposed next to each other, e.g. side-to-side arrangements	2224/2917	Zirconium [Zr] as principal constituent
2224/2908	being stacked	2224/29171	Chromium [Cr] as principal constituent
2224/29082	Two-layer arrangements	2224/29172	Vanadium [V] as principal constituent
2224/29083	Three-layer arrangements	2224/29173	Rhodium [Rh] as principal constituent
2224/29084	Four-layer arrangements	2224/29176	Ruthenium [Ru] as principal constituent
2224/29099	Material	2224/29178	Iridium [Ir] as principal constituent
2224/291	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/29179	Niobium [Nb] as principal constituent
2224/29101	the principal constituent melting at a temperature of less than 400°C	2224/2918	Molybdenum [Mo] as principal constituent
2224/29105	Gallium [Ga] as principal constituent	2224/29181	Tantalum [Ta] as principal constituent
2224/29109	Indium [In] as principal constituent	2224/29183	Rhenium [Re] as principal constituent
2224/29111	Tin [Sn] as principal constituent	2224/29184	Tungsten [W] as principal constituent
2224/29113	Bismuth [Bi] as principal constituent	2224/29186	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29114	Thallium [Tl] as principal constituent	2224/29187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29188)
2224/29116	Lead [Pb] as principal constituent	2224/29188	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/2919	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29118	Zinc [Zn] as principal constituent	2224/29191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/2912	Antimony [Sb] as principal constituent		
2224/29123	Magnesium [Mg] as principal constituent		
2224/29124	Aluminium [Al] as principal constituent		

2224/29193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/291 - H01L 2224/29191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/29249	Manganese [Mn] as principal constituent
2224/29194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/291 - H01L 2224/29191	2224/29255	Nickel [Ni] as principal constituent
2224/29195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/291 - H01L 2224/29191	2224/29257	Cobalt [Co] as principal constituent
2224/29198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/2926	Iron [Fe] as principal constituent
2224/29199	Material of the matrix	2224/29263	the principal constituent melting at a temperature of greater than 1550°C
2224/292	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/29264	Palladium [Pd] as principal constituent
2224/29201	the principal constituent melting at a temperature of less than 400°C	2224/29266	Titanium [Ti] as principal constituent
2224/29205	Gallium [Ga] as principal constituent	2224/29269	Platinum [Pt] as principal constituent
2224/29209	Indium [In] as principal constituent	2224/2927	Zirconium [Zr] as principal constituent
2224/29211	Tin [Sn] as principal constituent	2224/29271	Chromium [Cr] as principal constituent
2224/29213	Bismuth [Bi] as principal constituent	2224/29272	Vanadium [V] as principal constituent
2224/29214	Thallium [Tl] as principal constituent	2224/29273	Rhodium [Rh] as principal constituent
2224/29216	Lead [Pb] as principal constituent	2224/29276	Ruthenium [Ru] as principal constituent
2224/29217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29278	Iridium [Ir] as principal constituent
2224/29218	Zinc [Zn] as principal constituent	2224/29279	Niobium [Nb] as principal constituent
2224/2922	Antimony [Sb] as principal constituent	2224/2928	Molybdenum [Mo] as principal constituent
2224/29223	Magnesium [Mg] as principal constituent	2224/29281	Tantalum [Ta] as principal constituent
2224/29224	Aluminium [Al] as principal constituent	2224/29283	Rhenium [Re] as principal constituent
2224/29238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29284	Tungsten [W] as principal constituent
2224/29239	Silver [Ag] as principal constituent	2224/29286	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29244	Gold [Au] as principal constituent	2224/29287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29288)
2224/29247	Copper [Cu] as principal constituent	2224/29288	Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/2929	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/29291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/29293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/292 - H01L 2224/29291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/29294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/292 - H01L 2224/29291	2224/29364	Palladium [Pd] as principal constituent
2224/29295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/292 - H01L 2224/29291	2224/29366	Titanium [Ti] as principal constituent
2224/29298	Fillers	2224/29369	Platinum [Pt] as principal constituent
2224/29299	Base material	2224/2937	Zirconium [Zr] as principal constituent
2224/293	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/29371	Chromium [Cr] as principal constituent
2224/29301	the principal constituent melting at a temperature of less than 400°C	2224/29372	Vanadium [V] as principal constituent
2224/29305	Gallium [Ga] as principal constituent	2224/29373	Rhodium [Rh] as principal constituent
2224/29309	Indium [In] as principal constituent	2224/29376	Ruthenium [Ru] as principal constituent
2224/29311	Tin [Sn] as principal constituent	2224/29378	Iridium [Ir] as principal constituent
2224/29313	Bismuth [Bi] as principal constituent	2224/29379	Niobium [Nb] as principal constituent
2224/29314	Thallium [Tl] as principal constituent	2224/2938	Molybdenum [Mo] as principal constituent
2224/29316	Lead [Pb] as principal constituent	2224/29381	Tantalum [Ta] as principal constituent
2224/29317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29383	Rhenium [Re] as principal constituent
2224/29318	Zinc [Zn] as principal constituent	2224/29384	Tungsten [W] as principal constituent
2224/2932	Antimony [Sb] as principal constituent	2224/29386	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29323	Magnesium [Mg] as principal constituent	2224/29387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29388)
2224/29324	Aluminium [Al] as principal constituent	2224/29388	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/2939	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29339	Silver [Ag] as principal constituent	2224/29391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29344	Gold [Au] as principal constituent	2224/29393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/293 - H01L 2224/29391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29347	Copper [Cu] as principal constituent	2224/29394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/293 - H01L 2224/29391
2224/29349	Manganese [Mn] as principal constituent	2224/29395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/293 - H01L 2224/29391
2224/29355	Nickel [Ni] as principal constituent		
2224/29357	Cobalt [Co] as principal constituent		
2224/2936	Iron [Fe] as principal constituent		
2224/29363	the principal constituent melting at a temperature of greater than 1550°C		

2224/29398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/29466	Titanium [Ti] as principal constituent
2224/29399	Coating material	2224/29469	Platinum [Pt] as principal constituent
2224/294	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/2947	Zirconium [Zr] as principal constituent
2224/29401	the principal constituent melting at a temperature of less than 400°C	2224/29471	Chromium [Cr] as principal constituent
2224/29405	Gallium [Ga] as principal constituent	2224/29472	Vanadium [V] as principal constituent
2224/29409	Indium [In] as principal constituent	2224/29473	Rhodium [Rh] as principal constituent
2224/29411	Tin [Sn] as principal constituent	2224/29476	Ruthenium [Ru] as principal constituent
2224/29413	Bismuth [Bi] as principal constituent	2224/29478	Iridium [Ir] as principal constituent
2224/29414	Thallium [Tl] as principal constituent	2224/29479	Niobium [Nb] as principal constituent
2224/29416	Lead [Pb] as principal constituent	2224/2948	Molybdenum [Mo] as principal constituent
2224/29417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29481	Tantalum [Ta] as principal constituent
2224/29418	Zinc [Zn] as principal constituent	2224/29483	Rhenium [Re] as principal constituent
2224/2942	Antimony [Sb] as principal constituent	2224/29484	Tungsten [W] as principal constituent
2224/29423	Magnesium [Mg] as principal constituent	2224/29486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29424	Aluminium [Al] as principal constituent	2224/29487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29488)
2224/29438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29439	Silver [Ag] as principal constituent	2224/2949	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29444	Gold [Au] as principal constituent	2224/29491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29447	Copper [Cu] as principal constituent	2224/29493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/294 - H01L 2224/29491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29449	Manganese [Mn] as principal constituent	2224/29494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/294 - H01L 2224/29491
2224/29455	Nickel [Ni] as principal constituent	2224/29495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/294 - H01L 2224/29491
2224/29457	Cobalt [Co] as principal constituent	2224/29498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/2946	Iron [Fe] as principal constituent		
2224/29463	the principal constituent melting at a temperature of greater than 1550°C		
2224/29464	Palladium [Pd] as principal constituent		

2224/29499	Shape or distribution of the fillers	2224/29638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/2954	Coating	2224/29639	Silver [Ag] as principal constituent
2224/29541	Structure	2224/29644	Gold [Au] as principal constituent
2224/2955	Shape	2224/29647	Copper [Cu] as principal constituent
2224/29551	being non uniform	2224/29649	Manganese [Mn] as principal constituent
2224/29552	comprising protrusions or indentations	2224/29655	Nickel [Ni] as principal constituent
2224/29553	at the bonding interface of the layer connector, i.e. on the surface of the layer connector	2224/29657	Cobalt [Co] as principal constituent
2224/2956	Disposition	2224/2966	Iron [Fe] as principal constituent
2224/29561	On the entire surface of the core, i.e. integral coating	2224/29663	the principal constituent melting at a temperature of greater than 1550°C
2224/29562	On the entire exposed surface of the core	2224/29664	Palladium [Pd] as principal constituent
2224/29563	Only on parts of the surface of the core, i.e. partial coating	2224/29666	Titanium [Ti] as principal constituent
2224/29564	Only on the bonding interface of the layer connector	2224/29669	Platinum [Pt] as principal constituent
2224/29565	Only outside the bonding interface of the layer connector	2224/2967	Zirconium [Zr] as principal constituent
2224/29566	Both on and outside the bonding interface of the layer connector	2224/29671	Chromium [Cr] as principal constituent
2224/2957	Single coating layer	2224/29672	Vanadium [V] as principal constituent
2224/29575	Plural coating layers	2224/29673	Rhodium [Rh] as principal constituent
2224/29576	being mutually engaged together, e.g. through inserts	2224/29676	Ruthenium [Ru] as principal constituent
2224/29578	being disposed next to each other, e.g. side-to-side arrangements	2224/29678	Iridium [Ir] as principal constituent
2224/2958	being stacked	2224/29679	Niobium [Nb] as principal constituent
2224/29582	Two-layer coating	2224/2968	Molybdenum [Mo] as principal constituent
2224/29583	Three-layer coating	2224/29681	Tantalum [Ta] as principal constituent
2224/29584	Four-layer coating	2224/29683	Rhenium [Re] as principal constituent
2224/29599	Material	2224/29684	Tungsten [W] as principal constituent
2224/296	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/29686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29601	the principal constituent melting at a temperature of less than 400°C	2224/29687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29688)
2224/29605	Gallium [Ga] as principal constituent	2224/29688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29609	Indium [In] as principal constituent	2224/2969	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29611	Tin [Sn] as principal constituent	2224/29691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29613	Bismuth [Bi] as principal constituent		
2224/29614	Thallium [Tl] as principal constituent		
2224/29616	Lead [Pb] as principal constituent		
2224/29617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C		
2224/29618	Zinc [Zn] as principal constituent		
2224/2962	Antimony [Sb] as principal constituent		
2224/29623	Magnesium [Mg] as principal constituent		
2224/29624	Aluminium [Al] as principal constituent		

2224/29693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/296 - H01L 2224/29691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/29749	Manganese [Mn] as principal constituent
2224/29694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/296 - H01L 2224/29691	2224/29755	Nickel [Ni] as principal constituent
2224/29695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/296 - H01L 2224/29691	2224/29757	Cobalt [Co] as principal constituent
2224/29698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/2976	Iron [Fe] as principal constituent
2224/29699	Material of the matrix	2224/29763	the principal constituent melting at a temperature of greater than 1550°C
2224/297	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/29764	Palladium [Pd] as principal constituent
2224/29701	the principal constituent melting at a temperature of less than 400°C	2224/29766	Titanium [Ti] as principal constituent
2224/29705	Gallium [Ga] as principal constituent	2224/29769	Platinum [Pt] as principal constituent
2224/29709	Indium [In] as principal constituent	2224/2977	Zirconium [Zr] as principal constituent
2224/29711	Tin [Sn] as principal constituent	2224/29771	Chromium [Cr] as principal constituent
2224/29713	Bismuth [Bi] as principal constituent	2224/29772	Vanadium [V] as principal constituent
2224/29714	Thallium [Tl] as principal constituent	2224/29773	Rhodium [Rh] as principal constituent
2224/29716	Lead [Pb] as principal constituent	2224/29776	Ruthenium [Ru] as principal constituent
2224/29717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29778	Iridium [Ir] as principal constituent
2224/29718	Zinc [Zn] as principal constituent	2224/29779	Niobium [Nb] as principal constituent
2224/2972	Antimony [Sb] as principal constituent	2224/2978	Molybdenum [Mo] as principal constituent
2224/29723	Magnesium [Mg] as principal constituent	2224/29781	Tantalum [Ta] as principal constituent
2224/29724	Aluminium [Al] as principal constituent	2224/29783	Rhenium [Re] as principal constituent
2224/29738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29784	Tungsten [W] as principal constituent
2224/29739	Silver [Ag] as principal constituent	2224/29786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29744	Gold [Au] as principal constituent	2224/29787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29788)
2224/29747	Copper [Cu] as principal constituent	2224/29788	Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/2979	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/29791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/29793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/297 - H01L 2224/29791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/29794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/297 - H01L 2224/29791	2224/29864	Palladium [Pd] as principal constituent
2224/29795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/297 - H01L 2224/29791	2224/29866	Titanium [Ti] as principal constituent
2224/29798	Fillers	2224/29869	Platinum [Pt] as principal constituent
2224/29799	Base material	2224/2987	Zirconium [Zr] as principal constituent
2224/298	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/29871	Chromium [Cr] as principal constituent
2224/29801	the principal constituent melting at a temperature of less than 400°C	2224/29872	Vanadium [V] as principal constituent
2224/29805	Gallium [Ga] as principal constituent	2224/29873	Rhodium [Rh] as principal constituent
2224/29809	Indium [In] as principal constituent	2224/29876	Ruthenium [Ru] as principal constituent
2224/29811	Tin [Sn] as principal constituent	2224/29878	Iridium [Ir] as principal constituent
2224/29813	Bismuth [Bi] as principal constituent	2224/29879	Niobium [Nb] as principal constituent
2224/29814	Thallium [Tl] as principal constituent	2224/2988	Molybdenum [Mo] as principal constituent
2224/29816	Lead [Pb] as principal constituent	2224/29881	Tantalum [Ta] as principal constituent
2224/29817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29883	Rhenium [Re] as principal constituent
2224/29818	Zinc [Zn] as principal constituent	2224/29884	Tungsten [W] as principal constituent
2224/2982	Antimony [Sb] as principal constituent	2224/29886	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29823	Magnesium [Mg] as principal constituent	2224/29887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29888)
2224/29824	Aluminium [Al] as principal constituent	2224/2989	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29891	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29839	Silver [Ag] as principal constituent	2224/29893	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29844	Gold [Au] as principal constituent	2224/29894	with a principal constituent of the material being a solid not provided for in groups H01L 2224/298 - H01L 2224/29891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29847	Copper [Cu] as principal constituent	2224/29895	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/298 - H01L 2224/29891
2224/29849	Manganese [Mn] as principal constituent		
2224/29855	Nickel [Ni] as principal constituent		
2224/29857	Cobalt [Co] as principal constituent		
2224/2986	Iron [Fe] as principal constituent		
2224/29863	the principal constituent melting at a temperature of greater than 1550°C		

2224/29898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/29966	Titanium [Ti] as principal constituent
2224/29899	Coating material	2224/29969	Platinum [Pt] as principal constituent
2224/299	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/2997	Zirconium [Zr] as principal constituent
2224/29901	the principal constituent melting at a temperature of less than 400°C	2224/29971	Chromium [Cr] as principal constituent
2224/29905	Gallium [Ga] as principal constituent	2224/29972	Vanadium [V] as principal constituent
2224/29909	Indium [In] as principal constituent	2224/29973	Rhodium [Rh] as principal constituent
2224/29911	Tin [Sn] as principal constituent	2224/29976	Ruthenium [Ru] as principal constituent
2224/29913	Bismuth [Bi] as principal constituent	2224/29978	Iridium [Ir] as principal constituent
2224/29914	Thallium [Tl] as principal constituent	2224/29979	Niobium [Nb] as principal constituent
2224/29916	Lead [Pb] as principal constituent	2224/2998	Molybdenum [Mo] as principal constituent
2224/29917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29981	Tantalum [Ta] as principal constituent
2224/29918	Zinc [Zn] as principal constituent	2224/29983	Rhenium [Re] as principal constituent
2224/2992	Antimony [Sb] as principal constituent	2224/29984	Tungsten [W] as principal constituent
2224/29923	Magnesium [Mg] as principal constituent	2224/29986	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29924	Aluminium [Al] as principal constituent	2224/29987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29988)
2224/29938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29988	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29939	Silver [Ag] as principal constituent	2224/2999	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29944	Gold [Au] as principal constituent	2224/29991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29947	Copper [Cu] as principal constituent	2224/29993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/299 - H01L 2224/29991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29949	Manganese [Mn] as principal constituent	2224/29994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/299 - H01L 2224/29991
2224/29955	Nickel [Ni] as principal constituent	2224/29995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/299 - H01L 2224/29991
2224/29957	Cobalt [Co] as principal constituent	2224/29998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/2996	Iron [Fe] as principal constituent		
2224/29963	the principal constituent melting at a temperature of greater than 1550°C		
2224/29964	Palladium [Pd] as principal constituent		

2224/29999	Shape or distribution of the fillers	2224/30164	covering only portions of the surface to be connected
2224/30	of a plurality of layer connectors	2224/30165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/3001	Structure	2224/30166	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/3003	Layer connectors having different sizes, e.g. different heights or widths	2224/30177	Combinations of arrays with different layouts
2224/3005	Shape	2224/30179	Corner adaptations, i.e. disposition of the layer connectors at the corners of the semiconductor or solid-state body
2224/30051	Layer connectors having different shapes	2224/3018	being disposed on at least two different sides of the body, e.g. dual array
2224/301	Disposition	2224/30181	On opposite sides of the body
2224/30104	relative to the bonding areas, e.g. bond pads, of the semiconductor or solid-state body	2224/30183	On contiguous sides of the body
2224/3011	the layer connectors being bonded to at least one common bonding area	2224/305	Material
2224/3012	Layout	2224/30505	Layer connectors having different materials
2224/3013	Square or rectangular array	2224/3051	Function
2224/30131	being uniform, i.e. having a uniform pitch across the array	2224/30515	Layer connectors having different functions
2224/30132	being non uniform, i.e. having a non uniform pitch across the array	2224/30517	including layer connectors providing primarily mechanical bonding
2224/30133	with a staggered arrangement, e.g. depopulated array	2224/30519	including layer connectors providing primarily thermal dissipation
2224/30134	covering only portions of the surface to be connected	2224/31	Structure, shape, material or disposition of the layer connectors after the connecting process
2224/30135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/32	of an individual layer connector
2224/30136	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/3201	Structure
2224/3014	Circular array, i.e. array with radial symmetry	2224/32012	relative to the bonding area, e.g. bond pad
2224/30141	being uniform, i.e. having a uniform pitch across the array	2224/32013	the layer connector being larger than the bonding area, e.g. bond pad
2224/30142	being non uniform, i.e. having a non uniform pitch across the array	2224/32014	the layer connector being smaller than the bonding area, e.g. bond pad
2224/30143	covering only portions of the surface to be connected	2224/3205	Shape
2224/30145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/32052	in top view
2224/30146	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/32053	being non uniform along the layer connector
2224/3015	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/32054	being rectangular or square
2224/30151	being uniform, i.e. having a uniform pitch across the array	2224/32055	being circular or elliptic
2224/30152	being non uniform, i.e. having a non uniform pitch across the array	2224/32056	comprising protrusions or indentations
2224/30153	with a staggered arrangement, e.g. depopulated array	2224/32057	in side view
2224/30154	covering only portions of the surface to be connected	2224/32058	being non uniform along the layer connector
2224/30155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/32059	comprising protrusions or indentations
2224/30156	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/3207	of bonding interfaces, e.g. interlocking features
2224/3016	Random layout, i.e. layout with no symmetry	2224/321	Disposition
2224/30163	with a staggered arrangement	2224/32104	relative to the bonding area, e.g. bond pad
		2224/32105	the layer connector connecting bonding areas being not aligned with respect to each other
		2224/32106	the layer connector connecting one bonding area to at least two respective bonding areas
		2224/32111	the layer connector being disposed in a recess of the surface

2224/32112	the layer connector being at least partially embedded in the surface	2224/32198	the layer connector connecting to a bonding area protruding from the surface of the item
2224/32113	the whole layer connector protruding from the surface	2224/32221	the body and the item being stacked
2224/3213	the layer connector connecting within a semiconductor or solid-state body, i.e. connecting two bonding areas on the same semiconductor or solid-state body	2224/32225	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/32135	the layer connector connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip	2224/32227	the layer connector connecting to a bond pad of the item
2224/32137	the bodies being arranged next to each other, e.g. on a common substrate	2224/3223	the layer connector connecting to a pin of the item
2224/32141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements	2224/32233	the layer connector connecting to a potential ring of the item
2224/32145	the bodies being stacked	2224/32235	the layer connector connecting to a via metallisation of the item
2224/32146	the layer connector connecting to a via connection in the semiconductor or solid-state body	2224/32237	the layer connector connecting to a bonding area disposed in a recess of the surface of the item
2224/32147	the layer connector connecting to a bonding area disposed in a recess of the surface	2224/32238	the layer connector connecting to a bonding area protruding from the surface of the item
2224/32148	the layer connector connecting to a bonding area protruding from the surface	2224/3224	the layer connector connecting between the body and an opposite side of the item with respect to the body
2224/32151	the layer connector connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive	2224/32245	the item being metallic
2224/32153	the body and the item being arranged next to each other, e.g. on a common substrate	2224/32253	the layer connector connecting to a potential ring of the item
2224/32155	the item being non-metallic, e.g. being an insulating substrate with or without metallisation	2224/32257	the layer connector connecting to a bonding area disposed in a recess of the surface of the item
2224/32157	the layer connector connecting to a bond pad of the item	2224/32258	the layer connector connecting to a bonding area protruding from the surface of the item
2224/3216	the layer connector connecting to a pin of the item	2224/3226	the layer connector connecting between the body and an opposite side of the item with respect to the body
2224/32163	the layer connector connecting to a potential ring of the item	2224/32265	the item being a discrete passive component
2224/32165	the layer connector connecting to a via metallisation of the item	2224/32267	the layer connector connecting to a bonding area disposed in a recess of the surface of the item
2224/32167	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/32268	the layer connector connecting to a bonding area protruding from the surface of the item
2224/32168	the layer connector connecting to a bonding area protruding from the surface of the item	2224/325	Material
2224/32175	the item being metallic	2224/32501	at the bonding interface
2224/32183	the layer connector connecting to a potential ring of the item	2224/32502	comprising an eutectic alloy
2224/32187	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/32503	comprising an intermetallic compound
2224/32188	the layer connector connecting to a bonding area protruding from the surface of the item	2224/32505	outside the bonding interface, e.g. in the bulk of the layer connector
2224/32195	the item being a discrete passive component	2224/32506	comprising an eutectic alloy
2224/32197	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/32507	comprising an intermetallic compound
			2224/33	of a plurality of layer connectors
			2224/3301	Structure
			2224/3303	Layer connectors having different sizes, e.g. different heights or widths
			2224/3305	Shape
			2224/33051	Layer connectors having different shapes
			2224/33055	of their bonding interfaces

2224/331	Disposition	2224/335	Material
2224/33104	relative to the bonding areas, e.g. bond pads	2224/33505	Layer connectors having different materials
2224/33106	the layer connectors being bonded to at least one common bonding area	2224/3351	Function
2224/33107	the layer connectors connecting two common bonding areas	2224/33515	Layer connectors having different functions
2224/3312	Layout (layout of layer connectors prior to the connecting process H01L 2224/3012)	2224/33517	including layer connectors providing primarily mechanical support
2224/3313	Square or rectangular array	2224/33519	including layer connectors providing primarily thermal dissipation
2224/33132	being non uniform, i.e. having a non uniform pitch across the array	2224/34	. . .	Strap connectors, e.g. copper straps for grounding power devices; Manufacturing methods related thereto
2224/33133	with a staggered arrangement, e.g. depopulated array	2224/35	. . .	Manufacturing methods
2224/33134	covering only portions of the surface to be connected	2224/35001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate
2224/33135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/351	Pre-treatment of the preform connector
2224/3314	Circular array, i.e. array with radial symmetry	2224/3512	Applying permanent coating, e.g. in-situ coating
2224/33142	being non uniform, i.e. having a non uniform pitch across the array	2224/35125	Plating, e.g. electroplating, electroless plating
2224/33143	with a staggered arrangement	2224/352	Mechanical processes
2224/33144	covering only portions of the surface to be connected	2224/3521	Pulling
2224/33145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/355	Modification of a pre-existing material
2224/3315	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/3551	Sintering
2224/33151	being uniform, i.e. having a uniform pitch across the array	2224/3552	Anodisation
2224/33152	being non uniform, i.e. having a non uniform pitch across the array	2224/357	Involving monitoring, e.g. feedback loop
2224/33153	with a staggered arrangement, e.g. depopulated array	2224/358	Post-treatment of the connector
2224/33154	covering only portions of the surface to be connected	2224/3581	Cleaning, e.g. oxide removal step, desmearing
2224/33155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/3582	Applying permanent coating, e.g. in-situ coating
2224/33156	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/35821	Spray coating
2224/3316	Random layout, i.e. layout with no symmetry	2224/35822	Dip coating
2224/33163	with a staggered arrangement	2224/35823	Immersion coating, e.g. solder bath
2224/33164	covering only portions of the surface to be connected	2224/35824	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/33165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/35825	Plating, e.g. electroplating, electroless plating
2224/33177	Combinations of arrays with different layouts	2224/35826	Physical vapour deposition [PVD], e.g. evaporation, sputtering
2224/33179	Corner adaptations, i.e. disposition of the layer connectors at the corners of the semiconductor or solid-state body	2224/35827	Chemical vapour deposition [CVD], e.g. laser CVD
2224/3318	being disposed on at least two different sides of the body, e.g. dual array	2224/3583	Reworking
2224/33181	On opposite sides of the body	2224/35831	etching with a chemical process, e.g. with etching of the connector
2224/33183	On contiguous sides of the body	2224/35847	with a mechanical process, e.g. with flattening of the connector
			2224/35848	Thermal treatments, e.g. annealing, controlled cooling
			2224/35985	Methods of manufacturing strap connectors involving a specific sequence of method steps
			2224/35986	with repetition of the same manufacturing step
			2224/36	. . .	Structure, shape, material or disposition of the strap connectors prior to the connecting process
			2224/37	of an individual strap connector
			2224/37001	Core members of the connector
			2224/37005	Structure
			2224/3701	Shape

2224/37011	comprising apertures or cavities	2224/37166	Titanium [Ti] as principal constituent
2224/37012	Cross-sectional shape	2224/37169	Platinum [Pt] as principal constituent
2224/37013	being non uniform along the connector	2224/3717	Zirconium [Zr] as principal constituent
2224/3702	Disposition	2224/37171	Chromium [Cr] as principal constituent
2224/37025	Plural core members	2224/37172	Vanadium [V] as principal constituent
2224/37026	being mutually engaged together, e.g. through inserts	2224/37173	Rhodium [Rh] as principal constituent
2224/37028	Side-to-side arrangements	2224/37176	Ruthenium [Ru] as principal constituent
2224/3703	Stacked arrangements	2224/37178	Iridium [Ir] as principal constituent
2224/37032	Two-layer arrangements	2224/37179	Niobium [Nb] as principal constituent
2224/37033	Three-layer arrangements	2224/3718	Molybdenum [Mo] as principal constituent
2224/37034	Four-layer arrangements	2224/37181	Tantalum [Ta] as principal constituent
2224/37099	Material	2224/37183	Rhenium [Re] as principal constituent
2224/371	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/37184	Tungsten [W] as principal constituent
2224/37101	the principal constituent melting at a temperature of less than 400°C	2224/37186	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/37105	Gallium [Ga] as principal constituent	2224/37187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37188)
2224/37109	Indium [In] as principal constituent	2224/37188	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/37111	Tin [Sn] as principal constituent	2224/3719	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/37113	Bismuth [Bi] as principal constituent	2224/37191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37114	Thallium [Tl] as principal constituent	2224/37193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/371 - H01L 2224/37191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37116	Lead [Pb] as principal constituent	2224/37194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/371 - H01L 2224/37191
2224/37117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/37195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/371 - H01L 2224/37191
2224/37118	Zinc [Zn] as principal constituent	2224/37198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/3712	Antimony [Sb] as principal constituent	2224/37199	Material of the matrix
2224/37123	Magnesium [Mg] as principal constituent		
2224/37124	Aluminium [Al] as principal constituent		
2224/37138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C		
2224/37139	Silver [Ag] as principal constituent		
2224/37144	Gold [Au] as principal constituent		
2224/37147	Copper [Cu] as principal constituent		
2224/37149	Manganese [Mn] as principal constituent		
2224/37155	Nickel [Ni] as principal constituent		
2224/37157	Cobalt [Co] as principal constituent		
2224/3716	Iron [Fe] as principal constituent		
2224/37163	the principal constituent melting at a temperature of greater than 1550°C		
2224/37164	Palladium [Pd] as principal constituent		

2224/372	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/37271	Chromium [Cr] as principal constituent
2224/37201	the principal constituent melting at a temperature of less than 400°C	2224/37272	Vanadium [V] as principal constituent
2224/37205	Gallium [Ga] as principal constituent	2224/37273	Rhodium [Rh] as principal constituent
2224/37209	Indium [In] as principal constituent	2224/37276	Ruthenium [Ru] as principal constituent
2224/37211	Tin [Sn] as principal constituent	2224/37278	Iridium [Ir] as principal constituent
2224/37213	Bismuth [Bi] as principal constituent	2224/37279	Niobium [Nb] as principal constituent
2224/37214	Thallium [Tl] as principal constituent	2224/3728	Molybdenum [Mo] as principal constituent
2224/37216	Lead [Pb] as principal constituent	2224/37281	Tantalum [Ta] as principal constituent
2224/37217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/37283	Rhenium [Re] as principal constituent
2224/37218	Zinc [Zn] as principal constituent	2224/37284	Tungsten [W] as principal constituent
2224/3722	Antimony [Sb] as principal constituent	2224/37286	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/37223	Magnesium [Mg] as principal constituent	2224/37287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37288)
2224/37224	Aluminium [Al] as principal constituent	2224/37288	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/37238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/3729	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/37239	Silver [Ag] as principal constituent	2224/37291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37244	Gold [Au] as principal constituent	2224/37293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/372 - H01L 2224/37291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37247	Copper [Cu] as principal constituent	2224/37294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/372 - H01L 2224/37291
2224/37249	Manganese [Mn] as principal constituent	2224/37295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/372 - H01L 2224/37291
2224/37255	Nickel [Ni] as principal constituent	2224/37298	Fillers
2224/37257	Cobalt [Co] as principal constituent	2224/37299	Base material
2224/3726	Iron [Fe] as principal constituent	2224/373	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37263	the principal constituent melting at a temperature of greater than 1550°C	2224/37301	the principal constituent melting at a temperature of less than 400°C
2224/37264	Palladium [Pd] as principal constituent	2224/37305	Gallium [Ga] as principal constituent
2224/37266	Titanium [Ti] as principal constituent		
2224/37269	Platinum [Pt] as principal constituent		
2224/3727	Zirconium [Zr] as principal constituent		

2224/37309	Indium [In] as principal constituent	2224/3738	Molybdenum [Mo] as principal constituent
2224/37311	Tin [Sn] as principal constituent	2224/37381	Tantalum [Ta] as principal constituent
2224/37313	Bismuth [Bi] as principal constituent	2224/37383	Rhenium [Re] as principal constituent
2224/37314	Thallium [Tl] as principal constituent	2224/37384	Tungsten [W] as principal constituent
2224/37316	Lead [Pb] as principal constituent	2224/37386	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/37317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/37387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37388)
2224/37318	Zinc [Zn] as principal constituent	2224/37388	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/3732	Antimony [Sb] as principal constituent	2224/3739	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/37323	Magnesium [Mg] as principal constituent	2224/37391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37324	Aluminium [Al] as principal constituent	2224/37393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/373 - H01L 2224/37391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/37394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/373 - H01L 2224/37391
2224/37339	Silver [Ag] as principal constituent	2224/37395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/373 - H01L 2224/37391
2224/37344	Gold [Au] as principal constituent	2224/37398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/37347	Copper [Cu] as principal constituent	2224/37399	Coating material
2224/37349	Manganese [Mn] as principal constituent	2224/374	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37355	Nickel [Ni] as principal constituent	2224/37401	the principal constituent melting at a temperature of less than 400°C
2224/37357	Cobalt [Co] as principal constituent	2224/37405	Gallium [Ga] as principal constituent
2224/3736	Iron [Fe] as principal constituent	2224/37409	Indium [In] as principal constituent
2224/37363	the principal constituent melting at a temperature of greater than 1550°C	2224/37411	Tin [Sn] as principal constituent
2224/37364	Palladium [Pd] as principal constituent		
2224/37366	Titanium [Ti] as principal constituent		
2224/37369	Platinum [Pt] as principal constituent		
2224/3737	Zirconium [Zr] as principal constituent		
2224/37371	Chromium [Cr] as principal constituent		
2224/37372	Vanadium [V] as principal constituent		
2224/37373	Rhodium [Rh] as principal constituent		
2224/37376	Ruthenium [Ru] as principal constituent		
2224/37378	Iridium [Ir] as principal constituent		
2224/37379	Niobium [Nb] as principal constituent		

2224/37413	Bismuth [Bi] as principal constituent	2224/37483	Rhenium [Re] as principal constituent
2224/37414	Thallium [Tl] as principal constituent	2224/37484	Tungsten [W] as principal constituent
2224/37416	Lead [Pb] as principal constituent	2224/37486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/37417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/37487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37488)
2224/37418	Zinc [Zn] as principal constituent	2224/37488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/3742	Antimony [Sb] as principal constituent	2224/3749	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/37423	Magnesium [Mg] as principal constituent	2224/37491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37424	Aluminium [Al] as principal constituent	2224/37493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/374 - H01L 2224/37491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/37494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/374 - H01L 2224/37491
2224/37439	Silver [Ag] as principal constituent	2224/37495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/374 - H01L 2224/37491
2224/37444	Gold [Au] as principal constituent	2224/37498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/37447	Copper [Cu] as principal constituent	2224/37499	Shape or distribution of the fillers
2224/37449	Manganese [Mn] as principal constituent	2224/3754	Coating
2224/37455	Nickel [Ni] as principal constituent	2224/37541	Structure
2224/37457	Cobalt [Co] as principal constituent	2224/3755	Shape
2224/3746	Iron [Fe] as principal constituent	2224/3756	Disposition, e.g. coating on a part of the core
2224/37463	the principal constituent melting at a temperature of greater than 1550°C	2224/37565	Single coating layer
2224/37464	Palladium [Pd] as principal constituent	2224/3757	Plural coating layers
2224/37466	Titanium [Ti] as principal constituent	2224/37572	Two-layer stack coating
2224/37469	Platinum [Pt] as principal constituent	2224/37573	Three-layer stack coating
2224/3747	Zirconium [Zr] as principal constituent	2224/37574	Four-layer stack coating
2224/37471	Chromium [Cr] as principal constituent	2224/37576	being mutually engaged together, e.g. through inserts
2224/37472	Vanadium [V] as principal constituent	2224/37578	being disposed next to each other, e.g. side-to-side arrangements
2224/37473	Rhodium [Rh] as principal constituent	2224/37599	Material
2224/37476	Ruthenium [Ru] as principal constituent	2224/376	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37478	Iridium [Ir] as principal constituent		
2224/37479	Niobium [Nb] as principal constituent		
2224/3748	Molybdenum [Mo] as principal constituent		
2224/37481	Tantalum [Ta] as principal constituent		

2224/37601	the principal constituent melting at a temperature of less than 400°C	2224/37681	Tantalum [Ta] as principal constituent
2224/37605	Gallium [Ga] as principal constituent	2224/37683	Rhenium [Re] as principal constituent
2224/37609	Indium [In] as principal constituent	2224/37684	Tungsten [W] as principal constituent
2224/37611	Tin [Sn] as principal constituent	2224/37686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/37613	Bismuth [Bi] as principal constituent	2224/37687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37688)
2224/37614	Thallium [Tl] as principal constituent	2224/37688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/37616	Lead [Pb] as principal constituent	2224/3769	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/37617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/37691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37618	Zinc [Zn] as principal constituent	2224/37693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/376 - H01L 2224/37691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/3762	Antimony [Sb] as principal constituent	2224/37694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/376 - H01L 2224/37691
2224/37623	Magnesium [Mg] as principal constituent	2224/37695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/376 - H01L 2224/37691
2224/37624	Aluminium [Al] as principal constituent	2224/37698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/37638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/37699	Material of the matrix
2224/37639	Silver [Ag] as principal constituent	2224/377	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37644	Gold [Au] as principal constituent	2224/37701	the principal constituent melting at a temperature of less than 400°C
2224/37647	Copper [Cu] as principal constituent	2224/37705	Gallium [Ga] as principal constituent
2224/37649	Manganese [Mn] as principal constituent	2224/37709	Indium [In] as principal constituent
2224/37655	Nickel [Ni] as principal constituent	2224/37711	Tin [Sn] as principal constituent
2224/37657	Cobalt [Co] as principal constituent	2224/37713	Bismuth [Bi] as principal constituent
2224/3766	Iron [Fe] as principal constituent	2224/37714	Thallium [Tl] as principal constituent
2224/37663	the principal constituent melting at a temperature of greater than 1550°C	2224/37716	Lead [Pb] as principal constituent
2224/37664	Palladium [Pd] as principal constituent		
2224/37666	Titanium [Ti] as principal constituent		
2224/37669	Platinum [Pt] as principal constituent		
2224/3767	Zirconium [Zr] as principal constituent		
2224/37671	Chromium [Cr] as principal constituent		
2224/37672	Vanadium [V] as principal constituent		
2224/37673	Rhodium [Rh] as principal constituent		
2224/37676	Ruthenium [Ru] as principal constituent		
2224/37678	Iridium [Ir] as principal constituent		
2224/37679	Niobium [Nb] as principal constituent		
2224/3768	Molybdenum [Mo] as principal constituent		

2224/37717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/37787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37788)
2224/37718	Zinc [Zn] as principal constituent	2224/37788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/3772	Antimony [Sb] as principal constituent	2224/3779	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/37723	Magnesium [Mg] as principal constituent	2224/37791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37724	Aluminium [Al] as principal constituent	2224/37793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/377 - H01L 2224/37791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/37794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/377 - H01L 2224/37791
2224/37739	Silver [Ag] as principal constituent	2224/37795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/377 - H01L 2224/37791
2224/37744	Gold [Au] as principal constituent	2224/37798	Fillers
2224/37747	Copper [Cu] as principal constituent	2224/37799	Base material
2224/37749	Manganese [Mn] as principal constituent	2224/378	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37755	Nickel [Ni] as principal constituent	2224/37801	the principal constituent melting at a temperature of less than 400°C
2224/37757	Cobalt [Co] as principal constituent	2224/37805	Gallium [Ga] as principal constituent
2224/3776	Iron [Fe] as principal constituent	2224/37809	Indium [In] as principal constituent
2224/37763	the principal constituent melting at a temperature of greater than 1550°C	2224/37811	Tin [Sn] as principal constituent
2224/37764	Palladium [Pd] as principal constituent	2224/37813	Bismuth [Bi] as principal constituent
2224/37766	Titanium [Ti] as principal constituent	2224/37814	Thallium [Tl] as principal constituent
2224/37769	Platinum [Pt] as principal constituent	2224/37816	Lead [Pb] as principal constituent
2224/3777	Zirconium [Zr] as principal constituent	2224/37817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37771	Chromium [Cr] as principal constituent	2224/37818	Zinc [Zn] as principal constituent
2224/37772	Vanadium [V] as principal constituent	2224/3782	Antimony [Sb] as principal constituent
2224/37773	Rhodium [Rh] as principal constituent	2224/37823	Magnesium [Mg] as principal constituent
2224/37776	Ruthenium [Ru] as principal constituent	2224/37824	Aluminium [Al] as principal constituent
2224/37778	Iridium [Ir] as principal constituent		
2224/37779	Niobium [Nb] as principal constituent		
2224/3778	Molybdenum [Mo] as principal constituent		
2224/37781	Tantalum [Ta] as principal constituent		
2224/37783	Rhenium [Re] as principal constituent		
2224/37784	Tungsten [W] as principal constituent		
2224/37786	with a principal constituent of the material being a non metallic, non metalloid inorganic material		

2224/37838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/37891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/37839	Silver [Ag] as principal constituent	2224/37893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/378 - H01L 2224/37891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37844	Gold [Au] as principal constituent	2224/37894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/378 - H01L 2224/37891
2224/37847	Copper [Cu] as principal constituent	2224/37895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/378 - H01L 2224/37891
2224/37849	Manganese [Mn] as principal constituent	2224/37898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/37855	Nickel [Ni] as principal constituent	2224/37899	Coating material
2224/37857	Cobalt [Co] as principal constituent	2224/379	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/3786	Iron [Fe] as principal constituent	2224/37901	the principal constituent melting at a temperature of less than 400°C
2224/37863	the principal constituent melting at a temperature of greater than 1550°C	2224/37905	Gallium [Ga] as principal constituent
2224/37864	Palladium [Pd] as principal constituent	2224/37909	Indium [In] as principal constituent
2224/37866	Titanium [Ti] as principal constituent	2224/37911	Tin [Sn] as principal constituent
2224/37869	Platinum [Pt] as principal constituent	2224/37913	Bismuth [Bi] as principal constituent
2224/3787	Zirconium [Zr] as principal constituent	2224/37914	Thallium [Tl] as principal constituent
2224/37871	Chromium [Cr] as principal constituent	2224/37916	Lead [Pb] as principal constituent
2224/37872	Vanadium [V] as principal constituent	2224/37917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37873	Rhodium [Rh] as principal constituent	2224/37918	Zinc [Zn] as principal constituent
2224/37876	Ruthenium [Ru] as principal constituent	2224/3792	Antimony [Sb] as principal constituent
2224/37878	Iridium [Ir] as principal constituent	2224/37923	Magnesium [Mg] as principal constituent
2224/37879	Niobium [Nb] as principal constituent	2224/37924	Aluminium [Al] as principal constituent
2224/3788	Molybdenum [Mo] as principal constituent	2224/37938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37881	Tantalum [Ta] as principal constituent		
2224/37883	Rhenium [Re] as principal constituent		
2224/37884	Tungsten [W] as principal constituent		
2224/37886	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/37887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37888)		
2224/37888	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/3789	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		

2224/37939	...	Silver [Ag] as principal constituent	2224/37993	...	with a principal constituent of the material being a solid not provided for in groups H01L 2224/379 - H01L 2224/37991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/37944	...	Gold [Au] as principal constituent	2224/37994	...	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/379 - H01L 2224/37991
2224/37947	...	Copper [Cu] as principal constituent	2224/37995	...	with a principal constituent of the material being a gas not provided for in groups H01L 2224/379 - H01L 2224/37991
2224/37949	...	Manganese [Mn] as principal constituent	2224/37998	...	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/37955	...	Nickel [Ni] as principal constituent	2224/37999	...	Shape or distribution of the fillers
2224/37957	...	Cobalt [Co] as principal constituent	2224/38	...	of a plurality of strap connectors
2224/3796	...	Iron [Fe] as principal constituent	2224/39	...	Structure, shape, material or disposition of the strap connectors after the connecting process
2224/37963	...	the principal constituent melting at a temperature of greater than 1550°C	2224/40	...	of an individual strap connector
2224/37964	...	Palladium [Pd] as principal constituent	2224/4001	...	Structure
2224/37966	...	Titanium [Ti] as principal constituent	2224/4005	...	Shape
2224/37969	...	Platinum [Pt] as principal constituent	2224/4007	...	of bonding interfaces, e.g. interlocking features
2224/3797	...	Zirconium [Zr] as principal constituent	2224/4009	...	Loop shape
2224/37971	...	Chromium [Cr] as principal constituent	2224/40091	...	Arched
2224/37972	...	Vanadium [V] as principal constituent	2224/40095	...	Kinked
2224/37973	...	Rhodium [Rh] as principal constituent	2224/401	...	Disposition
2224/37976	...	Ruthenium [Ru] as principal constituent	2224/40101	...	Connecting bonding areas at the same height, e.g. horizontal bond
2224/37978	...	Iridium [Ir] as principal constituent	2224/40105	...	Connecting bonding areas at different heights
2224/37979	...	Niobium [Nb] as principal constituent	2224/40106	...	the connector being orthogonal to a side surface of the semiconductor or solid-state body, e.g. parallel layout
2224/3798	...	Molybdenum [Mo] as principal constituent	2224/40108	...	the connector not being orthogonal to a side surface of the semiconductor or solid-state body, e.g. fanned-out connectors, radial layout
2224/37981	...	Tantalum [Ta] as principal constituent	2224/40111	...	the strap connector extending above another semiconductor or solid-state body
2224/37983	...	Rhenium [Re] as principal constituent	2224/4013	...	Connecting within a semiconductor or solid-state body, i.e. fly strap, bridge strap
2224/37984	...	Tungsten [W] as principal constituent	2224/40132	...	with an intermediate bond, e.g. continuous strap daisy chain
2224/37986	...	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/40135	...	Connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip
2224/37987	...	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37988)	2224/40137	...	the bodies being arranged next to each other, e.g. on a common substrate
2224/37988	...	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/40139	...	with an intermediate bond, e.g. continuous strap daisy chain
2224/3799	...	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/40141	...	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
2224/37991	...	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene			

2224/40145	the bodies being stacked	2224/40248	the bond pad being disposed in a recess of the surface of the item
2224/40147	with an intermediate bond, e.g. continuous strap daisy chain	2224/40249	the bond pad protruding from the surface of the item
2224/40151	Connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive	2224/40253	Connecting the strap to a potential ring of the item
2224/40153	the body and the item being arranged next to each other, e.g. on a common substrate	2224/40257	Connecting the strap to a die pad of the item
2224/40155	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/4026	Connecting between the body and an opposite side of the item with respect to the body
2224/40157	Connecting the strap to a bond pad of the item	2224/40265	the item being a discrete passive component
2224/40158	the bond pad being disposed in a recess of the surface of the item	2224/404	Connecting portions
2224/40159	the bond pad protruding from the surface of the item	2224/4046	with multiple bonds on the same bonding area
2224/4016	Connecting the strap to a pin of the item	2224/40475	connected to auxiliary connecting means on the bonding areas
2224/40163	Connecting the strap to a potential ring of the item	2224/40477	being a pre-ball (i.e. a ball formed by capillary bonding)
2224/40165	Connecting the strap to a via metallisation of the item	2224/40479	on the semiconductor or solid-state body
2224/40175	the item being metallic	2224/4048	outside the semiconductor or solid-state body
2224/40177	Connecting the strap to a bond pad of the item	2224/40484	being a plurality of pre-balls disposed side-to-side
2224/40178	the bond pad being disposed in a recess of the surface of the item	2224/40486	on the semiconductor or solid-state body
2224/40179	the bond pad protruding from the surface of the item	2224/40487	outside the semiconductor or solid-state body
2224/40183	Connecting the strap to a potential ring of the item	2224/40491	being an additional member attached to the bonding area through an adhesive or solder, e.g. buffer pad
2224/40195	the item being a discrete passive component	2224/40496	not being interposed between the connector and the bonding area
2224/40221	the body and the item being stacked	2224/40499	Material of the auxiliary connecting means
2224/40225	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/405	Material
2224/40227	Connecting the strap to a bond pad of the item	2224/40505	at the bonding interface
2224/40228	the bond pad being disposed in a recess of the surface of the item	2224/40506	comprising an eutectic alloy
2224/40229	the bond pad protruding from the surface of the item	2224/40507	comprising an intermetallic compound
2224/4023	Connecting the strap to a pin of the item	2224/4051	Morphology of the connecting portion, e.g. grain size distribution
2224/40233	Connecting the strap to a potential ring of the item	2224/4052	Bonding interface between the connecting portion and the bonding area
2224/40235	Connecting the strap to a via metallisation of the item	2224/4099	Auxiliary members for strap connectors, e.g. flow-barriers, spacers
2224/40237	Connecting the strap to a die pad of the item	2224/40991	being formed on the semiconductor or solid-state body to be connected
2224/4024	Connecting between the body and an opposite side of the item with respect to the body	2224/40992	Reinforcing structures
2224/40245	the item being metallic	2224/40993	Alignment aids
2224/40247	Connecting the strap to a bond pad of the item	2224/40996	being formed on an item to be connected not being a semiconductor or solid-state body
			2224/40997	Reinforcing structures
			2224/40998	Alignment aids
			2224/41	of a plurality of strap connectors
			2224/4101	Structure
			2224/4103	Connectors having different sizes
			2224/4105	Shape
			2224/41051	Connectors having different shapes

2224/41052	Different loop heights	2224/437	Involving monitoring, e.g. feedback loop
2224/411	Disposition	2224/438	Post-treatment of the connector
2224/41105	Connecting at different heights	2224/4381	Cleaning, e.g. oxide removal step, desmearing
2224/41107	on the semiconductor or solid-state body being	2224/4382	Applying permanent coating, e.g. in-situ coating
2224/41109	outside the semiconductor or solid-state body	2224/43821	Spray coating
2224/4111	the connectors being bonded to at least one common bonding area, e.g. daisy chain	2224/43822	Dip coating
2224/41111	the connectors connecting two common bonding areas	2224/43823	Immersion coating, e.g. solder bath
2224/41112	the connectors connecting a common bonding area on the semiconductor or solid-state body to different bonding areas outside the body, e.g. diverging straps	2224/43824	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/41113	the connectors connecting different bonding areas on the semiconductor or solid-state body to a common bonding area outside the body, e.g. converging straps	2224/43825	Plating, e.g. electroplating, electroless plating
2224/4112	Layout	2224/43826	Physical vapour deposition [PVD], e.g. evaporation, sputtering
2224/4117	Crossed straps	2224/43827	Chemical vapour deposition [CVD], e.g. laser CVD
2224/41171	Fan-out arrangements	2224/4383	Reworking
2224/41173	Radial fan-out arrangements	2224/43831	with a chemical process, e.g. with etching of the connector
2224/41174	Stacked arrangements	2224/43847	with a mechanical process, e.g. with flattening of the connector
2224/41175	Parallel arrangements	2224/43848	Thermal treatments, e.g. annealing, controlled cooling
2224/41176	Strap connectors having the same loop shape and height	2224/43985	Methods of manufacturing wire connectors involving a specific sequence of method steps
2224/41177	Combinations of different arrangements	2224/43986	with repetition of the same manufacturing step
2224/41179	Corner adaptations, i.e. disposition of the strap connectors at the corners of the semiconductor or solid-state body	2224/44	. . .	Structure, shape, material or disposition of the wire connectors prior to the connecting process
2224/4118	being disposed on at least two different sides of the body, e.g. dual array	2224/45	of an individual wire connector
2224/414	Connecting portions	2224/45001	Core members of the connector
2224/4141	the connecting portions being stacked	2224/45005	Structure
2224/41421	on the semiconductor or solid-state body	2224/4501	Shape
2224/41422	outside the semiconductor or solid-state body	2224/45012	Cross-sectional shape
2224/4143	the connecting portions being staggered	2224/45013	being non uniform along the connector
2224/415	Material	2224/45014	Ribbon connectors, e.g. rectangular cross-section
2224/41505	Connectors having different materials	2224/45015	being circular
2224/42	. .	Wire connectors; Manufacturing methods related thereto	2224/45016	being elliptic
2224/43	. . .	Manufacturing methods	2224/4502	Disposition
2224/43001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate	2224/45025	Plural core members
2224/431	Pre-treatment of the preform connector	2224/45026	being mutually engaged together, e.g. through inserts
2224/4312	Applying permanent coating, e.g. in-situ coating	2224/45028	Side-to-side arrangements
2224/43125	Plating, e.g. electroplating, electroless plating	2224/4503	Stacked arrangements
2224/432	Mechanical processes	2224/45032	Two-layer arrangements
2224/4321	Pulling	2224/45033	Three-layer arrangements
2224/435	Modification of a pre-existing material	2224/45034	Four-layer arrangements
2224/4351	Sintering	2224/45099	Material
2224/4352	Anodisation	2224/451	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
			2224/45101	the principal constituent melting at a temperature of less than 400°C
			2224/45105	Gallium (Ga) as principal constituent

2224/45109	Indium (In) as principal constituent	2224/45184	Tungsten (W) as principal constituent
2224/45111	Tin (Sn) as principal constituent	2224/45186	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/45113	Bismuth (Bi) as principal constituent	2224/45187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45188)
2224/45114	Thallium (Tl) as principal constituent	2224/45188	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/45116	Lead (Pb) as principal constituent	2224/4519	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/45117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/45191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/45118	Zinc (Zn) as principal constituent	2224/45193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/451 - H01L 2224/45191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/4512	Antimony (Sb) as principal constituent	2224/45194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/451 - H01L 2224/45191
2224/45123	Magnesium (Mg) as principal constituent	2224/45195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/451 - H01L 2224/45191
2224/45124	Aluminium (Al) as principal constituent	2224/45198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/45138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/45199	Material of the matrix
2224/45139	Silver (Ag) as principal constituent	2224/452	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/45144	Gold (Au) as principal constituent	2224/45201	the principal constituent melting at a temperature of less than 400°C
2224/45147	Copper (Cu) as principal constituent	2224/45205	Gallium (Ga) as principal constituent
2224/45149	Manganese (Mn) as principal constituent	2224/45209	Indium (In) as principal constituent
2224/45155	Nickel (Ni) as principal constituent	2224/45211	Tin (Sn) as principal constituent
2224/45157	Cobalt (Co) as principal constituent	2224/45213	Bismuth (Bi) as principal constituent
2224/4516	Iron (Fe) as principal constituent	2224/45214	Thallium (Tl) as principal constituent
2224/45163	the principal constituent melting at a temperature of greater than 1550°C	2224/45216	Lead (Pb) as principal constituent
2224/45164	Palladium (Pd) as principal constituent	2224/45217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45166	Titanium (Ti) as principal constituent		
2224/45169	Platinum (Pt) as principal constituent		
2224/4517	Zirconium (Zr) as principal constituent		
2224/45171	Chromium (Cr) as principal constituent		
2224/45172	Vanadium (V) as principal constituent		
2224/45173	Rhodium (Rh) as principal constituent		
2224/45176	Ruthenium (Ru) as principal constituent		
2224/45178	Iridium (Ir) as principal constituent		
2224/45179	Niobium (Nb) as principal constituent		
2224/4518	Molybdenum (Mo) as principal constituent		
2224/45181	Tantalum (Ta) as principal constituent		
2224/45183	Rhenium (Re) as principal constituent		

2224/45218	Zinc (Zn) as principal constituent	2224/45288	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/4522	Antimony (Sb) as principal constituent	2224/4529	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/45223	Magnesium (Mg) as principal constituent	2224/45291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/45224	Aluminium (Al) as principal constituent	2224/45293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/452 - H01L 2224/45291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/45238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/45294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/452 - H01L 2224/45291
2224/45239	Silver (Ag) as principal constituent	2224/45295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/452 - H01L 2224/45291
2224/45244	Gold (Au) as principal constituent	2224/45298	Fillers
2224/45247	Copper (Cu) as principal constituent	2224/45299	Base material
2224/45249	Manganese (Mn) as principal constituent	2224/453	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/45255	Nickel (Ni) as principal constituent	2224/45301	the principal constituent melting at a temperature of less than 400°C
2224/45257	Cobalt (Co) as principal constituent	2224/45305	Gallium (Ga) as principal constituent
2224/4526	Iron (Fe) as principal constituent	2224/45309	Indium (In) as principal constituent
2224/45263	the principal constituent melting at a temperature of greater than 1550°C	2224/45311	Tin (Sn) as principal constituent
2224/45264	Palladium (Pd) as principal constituent	2224/45313	Bismuth (Bi) as principal constituent
2224/45266	Titanium (Ti) as principal constituent	2224/45314	Thallium (Tl) as principal constituent
2224/45269	Platinum (Pt) as principal constituent	2224/45316	Lead (Pb) as principal constituent
2224/4527	Zirconium (Zr) as principal constituent	2224/45317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45271	Chromium (Cr) as principal constituent	2224/45318	Zinc (Zn) as principal constituent
2224/45272	Vanadium (V) as principal constituent	2224/4532	Antimony (Sb) as principal constituent
2224/45273	Rhodium (Rh) as principal constituent	2224/45323	Magnesium (Mg) as principal constituent
2224/45276	Ruthenium (Ru) as principal constituent	2224/45324	Aluminium (Al) as principal constituent
2224/45278	Iridium (Ir) as principal constituent	2224/45338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45279	Niobium (Nb) as principal constituent			
2224/4528	Molybdenum (Mo) as principal constituent			
2224/45281	Tantalum (Ta) as principal constituent			
2224/45283	Rhenium (Re) as principal constituent			
2224/45284	Tungsten (W) as principal constituent			
2224/45286	with a principal constituent of the material being a non metallic, non metalloid inorganic material			
2224/45287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45288)			

2224/45339	Silver (Ag) as principal constituent	2224/45393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/453 - H01L 2224/45391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/45344	Gold (Au) as principal constituent	2224/45394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/453 - H01L 2224/45391
2224/45347	Copper (Cu) as principal constituent	2224/45395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/453 - H01L 2224/45391
2224/45349	Manganese (Mn) as principal constituent	2224/45398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/45355	Nickel (Ni) as principal constituent	2224/45399	Coating material
2224/45357	Cobalt (Co) as principal constituent	2224/454	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/4536	Iron (Fe) as principal constituent	2224/45401	the principal constituent melting at a temperature of less than 400°C
2224/45363	the principal constituent melting at a temperature of greater than 1550°C	2224/45405	Gallium (Ga) as principal constituent
2224/45364	Palladium (Pd) as principal constituent	2224/45409	Indium (In) as principal constituent
2224/45366	Titanium (Ti) as principal constituent	2224/45411	Tin (Sn) as principal constituent
2224/45369	Platinum (Pt) as principal constituent	2224/45413	Bismuth (Bi) as principal constituent
2224/4537	Zirconium (Zr) as principal constituent	2224/45414	Thallium (Tl) as principal constituent
2224/45371	Chromium (Cr) as principal constituent	2224/45416	Lead (Pb) as principal constituent
2224/45372	Vanadium (V) as principal constituent	2224/45417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45373	Rhodium (Rh) as principal constituent	2224/45418	Zinc (Zn) as principal constituent
2224/45376	Ruthenium (Ru) as principal constituent	2224/4542	Antimony (Sb) as principal constituent
2224/45378	Iridium (Ir) as principal constituent	2224/45423	Magnesium (Mg) as principal constituent
2224/45379	Niobium (Nb) as principal constituent	2224/45424	Aluminium (Al) as principal constituent
2224/4538	Molybdenum (Mo) as principal constituent	2224/45438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45381	Tantalum (Ta) as principal constituent	2224/45439	Silver (Ag) as principal constituent
2224/45383	Rhenium (Re) as principal constituent	2224/45444	Gold (Au) as principal constituent
2224/45384	Tungsten (W) as principal constituent		
2224/45386	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/45387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45388)		
2224/45388	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/4539	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		
2224/45391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		

2224/45447	Copper (Cu) as principal constituent	2224/45494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/454 - H01L 2224/45491
2224/45449	Manganese (Mn) as principal constituent	2224/45495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/454 - H01L 2224/45491
2224/45455	Nickel (Ni) as principal constituent	2224/45498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/45457	Cobalt (Co) as principal constituent	2224/45499	Shape or distribution of the fillers
2224/4546	Iron (Fe) as principal constituent	2224/4554	Coating
2224/45463	the principal constituent melting at a temperature of greater than 1550°C	2224/45541	Structure
2224/45464	Palladium (Pd) as principal constituent	2224/4555	Shape
2224/45466	Titanium (Ti) as principal constituent	2224/4556	Disposition, e.g. coating on a part of the core
2224/45469	Platinum (Pt) as principal constituent	2224/45565	Single coating layer
2224/4547	Zirconium (Zr) as principal constituent	2224/4557	Plural coating layers
2224/45471	Chromium (Cr) as principal constituent	2224/45572	Two-layer stack coating
2224/45472	Vanadium (V) as principal constituent	2224/45573	Three-layer stack coating
2224/45473	Rhodium (Rh) as principal constituent	2224/45574	Four-layer stack coating
2224/45476	Ruthenium (Ru) as principal constituent	2224/45576	being mutually engaged together, e.g. through inserts
2224/45478	Iridium (Ir) as principal constituent	2224/45578	being disposed next to each other, e.g. side-to-side arrangements
2224/45479	Niobium (Nb) as principal constituent	2224/45599	Material
2224/4548	Molybdenum (Mo) as principal constituent	2224/456	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/45481	Tantalum (Ta) as principal constituent	2224/45601	the principal constituent melting at a temperature of less than 400°C
2224/45483	Rhenium (Re) as principal constituent	2224/45605	Gallium (Ga) as principal constituent
2224/45484	Tungsten (W) as principal constituent	2224/45609	Indium (In) as principal constituent
2224/45486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45611	Tin (Sn) as principal constituent
2224/45487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45488)	2224/45613	Bismuth (Bi) as principal constituent
2224/45488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45614	Thallium (Tl) as principal constituent
2224/4549	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45616	Lead (Pb) as principal constituent
2224/45491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/454 - H01L 2224/45491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45618	Zinc (Zn) as principal constituent
		2224/4562	Antimony (Sb) as principal constituent
		2224/45623	Magnesium (Mg) as principal constituent
		2224/45624	Aluminium (Al) as principal constituent
		2224/45638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C

2224/45639	Silver (Ag) as principal constituent	2224/45693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/456 - H01L 2224/45691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/45644	Gold (Au) as principal constituent	2224/45694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/456 - H01L 2224/45691
2224/45647	Copper (Cu) as principal constituent	2224/45695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/456 - H01L 2224/45691
2224/45649	Manganese (Mn) as principal constituent	2224/45698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/45655	Nickel (Ni) as principal constituent	2224/45699	Material of the matrix
2224/45657	Cobalt (Co) as principal constituent	2224/457	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/4566	Iron (Fe) as principal constituent	2224/45701	the principal constituent melting at a temperature of less than 400°C
2224/45663	the principal constituent melting at a temperature of greater than 1550°C	2224/45705	Gallium (Ga) as principal constituent
2224/45664	Palladium (Pd) as principal constituent	2224/45709	Indium (In) as principal constituent
2224/45666	Titanium (Ti) as principal constituent	2224/45711	Tin (Sn) as principal constituent
2224/45669	Platinum (Pt) as principal constituent	2224/45713	Bismuth (Bi) as principal constituent
2224/4567	Zirconium (Zr) as principal constituent	2224/45714	Thallium (Tl) as principal constituent
2224/45671	Chromium (Cr) as principal constituent	2224/45716	Lead (Pb) as principal constituent
2224/45672	Vanadium (V) as principal constituent	2224/45717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45673	Rhodium (Rh) as principal constituent	2224/45718	Zinc (Zn) as principal constituent
2224/45676	Ruthenium (Ru) as principal constituent	2224/4572	Antimony (Sb) as principal constituent
2224/45678	Iridium (Ir) as principal constituent	2224/45723	Magnesium (Mg) as principal constituent
2224/45679	Niobium (Nb) as principal constituent	2224/45724	Aluminium (Al) as principal constituent
2224/4568	Molybdenum (Mo) as principal constituent	2224/45738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45681	Tantalum (Ta) as principal constituent	2224/45739	Silver (Ag) as principal constituent
2224/45683	Rhenium (Re) as principal constituent	2224/45744	Gold (Au) as principal constituent
2224/45684	Tungsten (W) as principal constituent	2224/45747	Copper (Cu) as principal constituent
2224/45686	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/45687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45688)		
2224/45688	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/4569	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		
2224/45691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		

2224/45749	Manganese (Mn) as principal constituent	2224/45794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/457 - H01L 2224/45791
2224/45755	Nickel (Ni) as principal constituent	2224/45795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/457 - H01L 2224/45791
2224/45757	Cobalt (Co) as principal constituent	2224/45798	Fillers
2224/4576	Iron (Fe) as principal constituent	2224/45799	Base material
2224/45763	the principal constituent melting at a temperature of greater than 1550°C	2224/458	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/45764	Palladium (Pd) as principal constituent	2224/45801	the principal constituent melting at a temperature of less than 400°C
2224/45766	Titanium (Ti) as principal constituent	2224/45805	Gallium (Ga) as principal constituent
2224/45769	Platinum (Pt) as principal constituent	2224/45809	Indium (In) as principal constituent
2224/4577	Zirconium (Zr) as principal constituent	2224/45811	Tin (Sn) as principal constituent
2224/45771	Chromium (Cr) as principal constituent	2224/45813	Bismuth (Bi) as principal constituent
2224/45772	Vanadium (V) as principal constituent	2224/45814	Thallium (Tl) as principal constituent
2224/45773	Rhodium (Rh) as principal constituent	2224/45816	Lead (Pb) as principal constituent
2224/45776	Ruthenium (Ru) as principal constituent	2224/45817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45778	Iridium (Ir) as principal constituent	2224/45818	Zinc (Zn) as principal constituent
2224/45779	Niobium (Nb) as principal constituent	2224/4582	Antimony (Sb) as principal constituent
2224/4578	Molybdenum (Mo) as principal constituent	2224/45823	Magnesium (Mg) as principal constituent
2224/45781	Tantalum (Ta) as principal constituent	2224/45824	Aluminium (Al) as principal constituent
2224/45783	Rhenium (Re) as principal constituent	2224/45838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45784	Tungsten (W) as principal constituent	2224/45839	Silver (Ag) as principal constituent
2224/45786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45844	Gold (Au) as principal constituent
2224/45787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45788)	2224/45847	Copper (Cu) as principal constituent
2224/45788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45849	Manganese (Mn) as principal constituent
2224/4579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45855	Nickel (Ni) as principal constituent
2224/45791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45857	Cobalt (Co) as principal constituent
2224/45793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/457 - H01L 2224/45791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/4586	Iron (Fe) as principal constituent
		2224/45863	the principal constituent melting at a temperature of greater than 1550°C

2224/45864	Palladium (Pd) as principal constituent	2224/45898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/45866	Titanium (Ti) as principal constituent	2224/45899	Coating material
2224/45869	Platinum (Pt) as principal constituent	2224/459	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/4587	Zirconium (Zr) as principal constituent	2224/45901	the principal constituent melting at a temperature of less than 400°C
2224/45871	Chromium (Cr) as principal constituent	2224/45905	Gallium (Ga) as principal constituent
2224/45872	Vanadium (V) as principal constituent	2224/45909	Indium (In) as principal constituent
2224/45873	Rhodium (Rh) as principal constituent	2224/45911	Tin (Sn) as principal constituent
2224/45876	Ruthenium (Ru) as principal constituent	2224/45913	Bismuth (Bi) as principal constituent
2224/45878	Iridium (Ir) as principal constituent	2224/45914	Thallium (Tl) as principal constituent
2224/45879	Niobium (Nb) as principal constituent	2224/45916	Lead (Pb) as principal constituent
2224/4588	Molybdenum (Mo) as principal constituent	2224/45917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45881	Tantalum (Ta) as principal constituent	2224/45918	Zinc (Zn) as principal constituent
2224/45883	Rhenium (Re) as principal constituent	2224/4592	Antimony (Sb) as principal constituent
2224/45884	Tungsten (W) as principal constituent	2224/45923	Magnesium (Mg) as principal constituent
2224/45886	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45924	Aluminium (Al) as principal constituent
2224/45887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45888)	2224/45938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45888	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45939	Silver (Ag) as principal constituent
2224/4589	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45944	Gold (Au) as principal constituent
2224/45891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45947	Copper (Cu) as principal constituent
2224/45893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/458 - H01L 2224/45891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45949	Manganese (Mn) as principal constituent
2224/45894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/458 - H01L 2224/45891	2224/45955	Nickel (Ni) as principal constituent
2224/45895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/458 - H01L 2224/45891	2224/45957	Cobalt (Co) as principal constituent
		2224/4596	Iron (Fe) as principal constituent
		2224/45963	the principal constituent melting at a temperature of greater than 1550°C
		2224/45964	Palladium (Pd) as principal constituent

2224/45966	...	Titanium (Ti) as principal constituent	2224/45999	...	Shape or distribution of the fillers
2224/45969	...	Platinum (Pt) as principal constituent	2224/46	...	of a plurality of wire connectors
2224/4597	...	Zirconium (Zr) as principal constituent	2224/47	...	Structure, shape, material or disposition of the wire connectors after the connecting process
2224/45971	...	Chromium (Cr) as principal constituent	2224/48	...	of an individual wire connector
2224/45972	...	Vanadium (V) as principal constituent	2224/4801	...	Structure
2224/45973	...	Rhodium (Rh) as principal constituent	2224/48011	...	Length
2224/45976	...	Ruthenium (Ru) as principal constituent	2224/4805	...	Shape
2224/45978	...	Iridium (Ir) as principal constituent	2224/4807	...	of bonding interfaces, e.g. interlocking features
2224/45979	...	Niobium (Nb) as principal constituent	2224/4809	...	Loop shape
2224/4598	...	Molybdenum (Mo) as principal constituent	2224/48091	...	Arched
2224/45981	...	Tantalum (Ta) as principal constituent	2224/48092	...	Helix
2224/45983	...	Rhenium (Re) as principal constituent	2224/48095	...	Kinked
2224/45984	...	Tungsten (W) as principal constituent	2224/48096	...	the kinked part being in proximity to the bonding area on the semiconductor or solid-state body
2224/45986	...	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/48097	...	the kinked part being in proximity to the bonding area outside the semiconductor or solid-state body
2224/45987	...	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45988)	2224/481	...	Disposition
2224/45988	...	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/48101	...	Connecting bonding areas at the same height, e.g. horizontal bond
2224/4599	...	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/48105	...	Connecting bonding areas at different heights
2224/45991	...	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/48106	...	the connector being orthogonal to a side surface of the semiconductor or solid-state body, e.g. parallel layout
2224/45993	...	with a principal constituent of the material being a solid not provided for in groups H01L 2224/459 - H01L 2224/45991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/48108	...	the connector not being orthogonal to a side surface of the semiconductor or solid-state body, e.g. fanned-out connectors, radial layout
2224/45994	...	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/459 - H01L 2224/45991	2224/4811	...	Connecting to a bonding area of the semiconductor or solid-state body located at the far end of the body with respect to the bonding area outside the semiconductor or solid-state body
2224/45995	...	with a principal constituent of the material being a gas not provided for in groups H01L 2224/459 - H01L 2224/45991	2224/48111	...	the wire connector extending above another semiconductor or solid-state body
2224/45998	...	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/4813	...	Connecting within a semiconductor or solid-state body, i.e. fly wire, bridge wire
			2224/48132	...	with an intermediate bond, e.g. continuous wire daisy chain
			2224/48135	...	Connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip
			2224/48137	...	the bodies being arranged next to each other, e.g. on a common substrate
			2224/48138	...	the wire connector connecting to a bonding area disposed in a recess of the surface
			2224/48139	...	with an intermediate bond, e.g. continuous wire daisy chain
			2224/4814	...	the wire connector connecting to a bonding area protruding from the surface
			2224/48141	...	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
			2224/48145	...	the bodies being stacked
			2224/48147	...	with an intermediate bond, e.g. continuous wire daisy chain

2224/48148	the wire connector connecting to a bonding area disposed in a recess of the surface	2224/48247	connecting the wire to a bond pad of the item
2224/48149	the wire connector connecting to a bonding area protruding from the surface	2224/48248	the bond pad being disposed in a recess of the surface of the item
2224/48151	Connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive	2224/48249	the bond pad protruding from the surface of the item
2224/48153	the body and the item being arranged next to each other, e.g. on a common substrate	2224/48253	connecting the wire to a potential ring of the item
2224/48155	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/48257	connecting the wire to a die pad of the item
2224/48157	connecting the wire to a bond pad of the item	2224/4826	Connecting between the body and an opposite side of the item with respect to the body
2224/48158	the bond pad being disposed in a recess of the surface of the item	2224/48265	the item being a discrete passive component
2224/48159	the bond pad protruding from the surface of the item	2224/484	Connecting portions
2224/4816	connecting the wire to a pin of the item	2224/4845	Details of ball bonds
2224/48163	connecting the wire to a potential ring of the item	2224/48451	Shape
2224/48165	connecting the wire to a via metallisation of the item	2224/48453	of the interface with the bonding area
2224/48175	the item being metallic	2224/48455	Details of wedge bonds
2224/48177	connecting the wire to a bond pad of the item	2224/48456	Shape
2224/48178	the bond pad being disposed in a recess of the surface of the item	2224/48458	of the interface with the bonding area
2224/48179	the bond pad protruding from the surface of the item	2224/4846	with multiple bonds on the same bonding area
2224/48183	connecting the wire to a potential ring of the item	2224/48463	the connecting portion on the bonding area of the semiconductor or solid-state body being a ball bond
2224/48195	the item being a discrete passive component	2224/48464	the other connecting portion not on the bonding area also being a ball bond, i.e. ball-to-ball
2224/48221	the body and the item being stacked	2224/48465	the other connecting portion not on the bonding area being a wedge bond, i.e. ball-to-wedge, regular stitch
2224/48225	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/4847	the connecting portion on the bonding area of the semiconductor or solid-state body being a wedge bond
2224/48227	connecting the wire to a bond pad of the item	2224/48471	the other connecting portion not on the bonding area being a ball bond, i.e. wedge-to-ball, reverse stitch
2224/48228	the bond pad being disposed in a recess of the surface of the item	2224/48472	the other connecting portion not on the bonding area also being a wedge bond, i.e. wedge-to-wedge
2224/48229	the bond pad protruding from the surface of the item	2224/48475	connected to auxiliary connecting means on the bonding areas, e.g. pre-ball, wedge-on-ball, ball-on-ball
2224/4823	connecting the wire to a pin of the item	2224/48476	between the wire connector and the bonding area
2224/48233	connecting the wire to a potential ring of the item	2224/48477	being a pre-ball (i.e. a ball formed by capillary bonding)
2224/48235	connecting the wire to a via metallisation of the item	2224/48478	the connecting portion being a wedge bond, i.e. wedge on pre-ball
2224/48237	connecting the wire to a die pad of the item	2224/48479	on the semiconductor or solid-state body
2224/4824	Connecting between the body and an opposite side of the item with respect to the body	2224/4848	outside the semiconductor or solid-state body
2224/48245	the item being metallic	2224/48481	the connecting portion being a ball bond, i.e. ball on pre-ball
			2224/48482	on the semiconductor or solid-state body

2224/48483	outside the semiconductor or solid-state body	2224/48618	Zinc (Zn) as principal constituent
2224/48484	being a plurality of pre-balls disposed side-to-side	2224/4862	Antimony (Sb) as principal constituent
2224/48485	the connecting portion being a wedge bond, i.e. wedge on pre-ball	2224/48623	Magnesium (Mg) as principal constituent
2224/48486	on the semiconductor or solid-state body	2224/48624	Aluminium (Al) as principal constituent
2224/48487	outside the semiconductor or solid-state body	2224/48638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/48488	the connecting portion being a ball bond, i.e. ball on pre-ball	2224/48639	Silver (Ag) as principal constituent
2224/48489	on the semiconductor or solid-state body	2224/48644	Gold (Au) as principal constituent
2224/4849	outside the semiconductor or solid-state body	2224/48647	Copper (Cu) as principal constituent
2224/48491	being an additional member attached to the bonding area through an adhesive or solder, e.g. buffer pad	2224/48649	Manganese (Mn) as principal constituent
2224/48496	not being interposed between the wire connector and the bonding area	2224/48655	Nickel (Ni) as principal constituent
2224/48499	Material of the auxiliary connecting means	2224/48657	Cobalt (Co) as principal constituent
2224/485	Material	2224/4866	Iron (Fe) as principal constituent
2224/48505	at the bonding interface	2224/48663	the principal constituent melting at a temperature of greater than 1550°C
2224/48506	comprising an eutectic alloy	2224/48664	Palladium (Pd) as principal constituent
2224/48507	comprising an intermetallic compound	2224/48666	Titanium (Ti) as principal constituent
2224/4851	Morphology of the connecting portion, e.g. grain size distribution	2224/48669	Platinum (Pt) as principal constituent
2224/48511	Heat affected zone [HAZ]	2224/4867	Zirconium (Zr) as principal constituent
2224/4852	Bonding interface between the connecting portion and the bonding area	2224/48671	Chromium (Cr) as principal constituent
2224/48599	Principal constituent of the connecting portion of the wire connector being Gold (Au)	2224/48672	Vanadium (V) as principal constituent
2224/486	with a principal constituent of the bonding area being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/48673	Rhodium (Rh) as principal constituent
2224/48601	the principal constituent melting at a temperature of less than 400°C	2224/48678	Iridium (Ir) as principal constituent
2224/48605	Gallium (Ga) as principal constituent	2224/48679	Niobium (Nb) as principal constituent
2224/48609	Indium (In) as principal constituent	2224/4868	Molybdenum (Mo) as principal constituent
2224/48611	Tin (Sn) as principal constituent	2224/48681	Tantalum (Ta) as principal constituent
2224/48613	Bismuth (Bi) as principal constituent	2224/48683	Rhenium (Re) as principal constituent
2224/48614	Thallium (Tl) as principal constituent	2224/48684	Tungsten (W) as principal constituent
2224/48616	Lead (Pb) as principal constituent	2224/48686	with a principal constituent of the bonding area being a non metallic, non metalloid inorganic material
2224/48617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950 °C	2224/48687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/48688)
		2224/48688	Glasses, e.g. amorphous oxides, nitrides or fluorides

2224/4869	with a principal constituent of the bonding area being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/48739	Silver (Ag) as principal constituent
2224/48691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/48744	Gold (Au) as principal constituent
2224/48693	with a principal constituent of the bonding area being a solid not provided for in groups H01L 2224/486 - H01L 2224/4869 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/48747	Copper (Cu) as principal constituent
2224/48694	with a principal constituent of the bonding area being a liquid not provided for in groups H01L 2224/486 - H01L 2224/4869	2224/48749	Manganese (Mn) as principal constituent
2224/48698	with a principal constituent of the bonding area being a combination of two or more material regions, i.e. being a hybrid material, e.g. segmented structures, island patterns	2224/48755	Nickel (Ni) as principal constituent
2224/48699	Principal constituent of the connecting portion of the wire connector being Aluminium (Al)	2224/48757	Cobalt (Co) as principal constituent
2224/487	with a principal constituent of the bonding area being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/4876	Iron (Fe) as principal constituent
2224/48701	the principal constituent melting at a temperature of less than 400°C	2224/48763	the principal constituent melting at a temperature of greater than 1550°C
2224/48705	Gallium (Ga) as principal constituent	2224/48764	Palladium (Pd) as principal constituent
2224/48709	Indium (In) as principal constituent	2224/48766	Titanium (Ti) as principal constituent
2224/48711	Tin (Sn) as principal constituent	2224/48769	Platinum (Pt) as principal constituent
2224/48713	Bismuth (Bi) as principal constituent	2224/4877	Zirconium (Zr) as principal constituent
2224/48714	Thallium (Tl) as principal constituent	2224/48771	Chromium (Cr) as principal constituent
2224/48716	Lead (Pb) as principal constituent	2224/48772	Vanadium (V) as principal constituent
2224/48717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950 °C	2224/48773	Rhodium (Rh) as principal constituent
2224/48718	Zinc (Zn) as principal constituent	2224/48778	Iridium (Ir) as principal constituent
2224/4872	Antimony (Sb) as principal constituent	2224/48779	Niobium (Nb) as principal constituent
2224/48723	Magnesium (Mg) as principal constituent	2224/4878	Molybdenum (Mo) as principal constituent
2224/48724	Aluminium (Al) as principal constituent	2224/48781	Tantalum (Ta) as principal constituent
2224/48738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/48783	Rhenium (Re) as principal constituent
			2224/48784	Tungsten (W) as principal constituent
			2224/48786	with a principal constituent of the bonding area being a non metallic, non metalloid inorganic material
			2224/48787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/48788)
			2224/48788	Glasses, e.g. amorphous oxides, nitrides or fluorides
			2224/4879	with a principal constituent of the bonding area being a polymer, e.g. polyester, phenolic based polymer, epoxy
			2224/48791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene

2224/48793	with a principal constituent of the bonding area being a solid not provided for in groups H01L 2224/487 - H01L 2224/4879 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/48855	Nickel (Ni) as principal constituent
2224/48794	with a principal constituent of the bonding area being a liquid not provided for in groups H01L 2224/487 - H01L 2224/4879	2224/48857	Cobalt (Co) as principal constituent
2224/48798	with a principal constituent of the bonding area being a combination of two or more material regions, i.e. being a hybrid material, e.g. segmented structures, island patterns	2224/4886	Iron (Fe) as principal constituent
2224/48799	Principal constituent of the connecting portion of the wire connector being Copper (Cu)	2224/48863	the principal constituent melting at a temperature of greater than 1550°C
2224/488	with a principal constituent of the bonding area being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/48864	Palladium (Pd) as principal constituent
2224/48801	the principal constituent melting at a temperature of less than 400°C	2224/48866	Titanium (Ti) as principal constituent
2224/48805	Gallium (Ga) as principal constituent	2224/48869	Platinum (Pt) as principal constituent
2224/48809	Indium (In) as principal constituent	2224/4887	Zirconium (Zr) as principal constituent
2224/48811	Tin (Sn) as principal constituent	2224/48871	Chromium (Cr) as principal constituent
2224/48813	Bismuth (Bi) as principal constituent	2224/48872	Vanadium (V) as principal constituent
2224/48814	Thallium (Tl) as principal constituent	2224/48873	Rhodium (Rh) as principal constituent
2224/48816	Lead (Pb) as principal constituent	2224/48878	Iridium (Ir) as principal constituent
2224/48817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950 °C	2224/48879	Niobium (Nb) as principal constituent
2224/48818	Zinc (Zn) as principal constituent	2224/4888	Molybdenum (Mo) as principal constituent
2224/4882	Antimony (Sb) as principal constituent	2224/48881	Tantalum (Ta) as principal constituent
2224/48823	Magnesium (Mg) as principal constituent	2224/48883	Rhenium (Re) as principal constituent
2224/48824	Aluminium (Al) as principal constituent	2224/48884	Tungsten (W) as principal constituent
2224/48838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/48886	with a principal constituent of the bonding area being a non metallic, non metalloid inorganic material
2224/48839	Silver (Ag) as principal constituent	2224/48887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/48888)
2224/48844	Gold (Au) as principal constituent	2224/48888	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/48847	Copper (Cu) as principal constituent	2224/4889	with a principal constituent of the bonding area being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/48849	Manganese (Mn) as principal constituent	2224/48891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/48893	with a principal constituent of the bonding area being a solid not provided for in groups H01L 2224/488 - H01L 2224/4889 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
		2224/48894	with a principal constituent of the bonding area being a liquid not provided for in groups H01L 2224/488 - H01L 2224/4889

2224/48898	with a principal constituent of the bonding area being a combination of two or more material regions, i.e. being a hybrid material, e.g. segmented structures, island patterns	2224/49179	Corner adaptations, i.e. disposition of the wire connectors at the corners of the semiconductor or solid-state body
2224/4899	Auxiliary members for wire connectors, e.g. flow-barriers, reinforcing structures, spacers, alignment aids	2224/4918	being disposed on at least two different sides of the body, e.g. dual array
2224/48991	being formed on the semiconductor or solid-state body to be connected	2224/494	Connecting portions
2224/48992	Reinforcing structures	2224/4941	the connecting portions being stacked
2224/48993	Alignment aids	2224/4942	Ball bonds
2224/48996	being formed on an item to be connected not being a semiconductor or solid-state body	2224/49421	on the semiconductor or solid-state body
2224/48997	Reinforcing structures	2224/49422	outside the semiconductor or solid-state body
2224/48998	Alignment aids	2224/49425	Wedge bonds
2224/49	of a plurality of wire connectors	2224/49426	on the semiconductor or solid-state body
2224/4901	Structure	2224/49427	outside the semiconductor or solid-state body
2224/4903	Connectors having different sizes, e.g. different diameters	2224/49429	Wedge and ball bonds
2224/4905	Shape	2224/4943	the connecting portions being staggered
2224/49051	Connectors having different shapes	2224/49431	on the semiconductor or solid-state body
2224/49052	Different loop heights	2224/49433	outside the semiconductor or solid-state body
2224/4909	Loop shape arrangement	2224/4945	Wire connectors having connecting portions of different types on the semiconductor or solid-state body, e.g. regular and reverse stitches
2224/49095	parallel in plane	2224/495	Material
2224/49096	horizontal	2224/49505	Connectors having different materials
2224/49097	vertical	2224/50	Tape automated bonding [TAB] connectors, i.e. film carriers; Manufacturing methods related thereto
2224/491	Disposition	2224/63	Connectors not provided for in any of the groups H01L 2224/10 - H01L 2224/50 and subgroups; Manufacturing methods related thereto
2224/49105	Connecting at different heights	2224/64	Manufacturing methods
2224/49107	on the semiconductor or solid-state body	2224/65	Structure, shape, material or disposition of the connectors prior to the connecting process
2224/49109	outside the semiconductor or solid-state body	2224/66	of an individual connector
2224/4911	the connectors being bonded to at least one common bonding area, e.g. daisy chain	2224/67	of a plurality of connectors
2224/49111	the connectors connecting two common bonding areas, e.g. Litz or braid wires	2224/68	Structure, shape, material or disposition of the connectors after the connecting process
2224/49112	the connectors connecting a common bonding area on the semiconductor or solid-state body to different bonding areas outside the body, e.g. diverging wires	2224/69	of an individual connector
2224/49113	the connectors connecting different bonding areas on the semiconductor or solid-state body to a common bonding area outside the body, e.g. converging wires	2224/70	of a plurality of connectors
2224/4912	Layout	2224/71	Means for bonding not being attached to, or not being formed on, the surface to be connected
2224/4917	Crossed wires	2224/72	Detachable connecting means consisting of mechanical auxiliary parts connecting the device, e.g. pressure contacts using springs or clips
2224/49171	Fan-out arrangements	2224/73	Means for bonding being of different types provided for in two or more of groups H01L 2224/10 , H01L 2224/18 , H01L 2224/26 , H01L 2224/34 , H01L 2224/42 , H01L 2224/50 , H01L 2224/63 , H01L 2224/71
2224/49173	Radial fan-out arrangements	2224/731	Location prior to the connecting process
2224/49174	Stacked arrangements	2224/73101	on the same surface
2224/49175	Parallel arrangements	2224/73103	Bump and layer connectors
2224/49176	Wire connectors having the same loop shape and height	2224/73104	the bump connector being embedded into the layer connector
2224/49177	Combinations of different arrangements	2224/73151	on different surfaces
			2224/73153	Bump and layer connectors
			2224/732	Location after the connecting process
			2224/73201	on the same surface

2224/73203	Bump and layer connectors	2224/75161	Means for screen printing, e.g. roller, squeegee, screen stencil
2224/73204	the bump connector being embedded into the layer connector	2224/7517	Means for applying a preform, e.g. laminator
2224/73205	Bump and strap connectors	2224/75171	including a vacuum-bag
2224/73207	Bump and wire connectors	2224/7518	Means for blanket deposition
2224/73209	Bump and HDI connectors	2224/75181	for spin coating, i.e. spin coater
2224/73211	Bump and TAB connectors	2224/75182	for curtain coating
2224/73213	Layer and strap connectors	2224/75183	for immersion coating, i.e. bath
2224/73215	Layer and wire connectors	2224/75184	for spray coating, i.e. nozzle
2224/73217	Layer and HDI connectors	2224/75185	Means for physical vapour deposition [PVD], e.g. evaporation, sputtering
2224/73219	Layer and TAB connectors	2224/75186	Means for sputtering, e.g. target
2224/73221	Strap and wire connectors	2224/75187	Means for evaporation
2224/73223	Strap and HDI connectors	2224/75188	Means for chemical vapour deposition [CVD], e.g. for laser CVD
2224/73225	Strap and TAB connectors	2224/75189	Means for plating, e.g. for electroplating, electroless plating
2224/73227	Wire and HDI connectors	2224/752	Protection means against electrical discharge
2224/73229	Wire and TAB connectors	2224/7525	Means for applying energy, e.g. heating means
2224/73231	HDI and TAB connectors	2224/75251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/73251	on different surfaces	2224/75252	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/73253	Bump and layer connectors	2224/75253	adapted for localised heating
2224/73255	Bump and strap connectors	2224/7526	Polychromatic heating lamp
2224/73257	Bump and wire connectors	2224/75261	Laser
2224/73259	Bump and HDI connectors	2224/75262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/73261	Bump and TAB connectors	2224/75263	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/73263	Layer and strap connectors	2224/75264	by induction heating, i.e. coils
2224/73265	Layer and wire connectors	2224/75265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/73267	Layer and HDI connectors	2224/75266	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/73269	Layer and TAB connectors	2224/75267	Flame torch, e.g. hydrogen torch
2224/73271	Strap and wire connectors	2224/75268	Discharge electrode
2224/73273	Strap and HDI connectors	2224/75269	Shape of the discharge electrode
2224/73275	Strap and TAB connectors	2224/7527	Material of the discharge electrode
2224/73277	Wire and HDI connectors	2224/75271	Circuitry of the discharge electrode
2224/73279	Wire and TAB connectors	2224/75272	Oven
2224/73281	HDI and TAB connectors	2224/7528	Resistance welding electrodes, i.e. for ohmic heating
2224/74	Apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies and for methods related thereto	2224/75281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/741	Apparatus for manufacturing means for bonding, e.g. connectors	2224/75282	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/742	Apparatus for manufacturing bump connectors	2224/75283	by infrared heating, e.g. infrared heating lamp
2224/743	Apparatus for manufacturing layer connectors	2224/753	by means of pressure
2224/744	Apparatus for manufacturing strap connectors	2224/75301	Bonding head
2224/745	Apparatus for manufacturing wire connectors	2224/75302	Shape
2224/749	Tools for reworking, e.g. for shaping	2224/75303	of the pressing surface
2224/75	Apparatus for connecting with bump connectors or layer connectors	2224/75304	being curved
2224/75001	Calibration means	2224/75305	comprising protrusions
2224/7501	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma	2224/7531	of other parts
2224/751	Means for controlling the bonding environment, e.g. valves, vacuum pumps	2224/75312	Material
2224/75101	Chamber	2224/75313	Removable bonding head
2224/75102	Vacuum chamber	2224/75314	Auxiliary members on the pressing surface
2224/7511	High pressure chamber	2224/75315	Elastomer inlay
2224/7515	Means for applying permanent coating, e.g. in-situ coating	2224/75316	with retaining mechanisms
2224/75151	Means for direct writing	2224/75317	Removable auxiliary member
2224/75152	Syringe			
2224/75153	integrated into the bonding head			
2224/75155	Jetting means, e.g. ink jet			
2224/75158	including a laser			

2224/75318	Shape of the auxiliary member	2224/75744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7532	Material of the auxiliary member	2224/75745	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/75343	by ultrasonic vibrations	2224/75753	Means for optical alignment, e.g. sensors
2224/75344	Eccentric cams	2224/75754	Guiding structures
2224/75345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75346	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75756	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/75347	Piezoelectric transducers	2224/758	Means for moving parts
2224/75348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75801	Lower part of the bonding apparatus, e.g. XY table
2224/75349	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75802	Rotational mechanism
2224/7535	Stable and mobile yokes	2224/75803	Pivoting mechanism
2224/75351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75804	Translational mechanism
2224/75352	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75821	Upper part of the bonding apparatus, i.e. bonding head
2224/75353	Ultrasonic horns	2224/75822	Rotational mechanism
2224/75354	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75823	Pivoting mechanism
2224/75355	Design, e.g. of the wave guide	2224/75824	Translational mechanism
2224/755	Cooling means	2224/75841	of the bonding head
2224/75501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75842	Rotational mechanism
2224/75502	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75843	Pivoting mechanism
2224/7555	Mechanical means, e.g. for planarising, pressing, stamping	2224/759	Means for monitoring the connection process
2224/756	Means for supplying the connector to be connected in the bonding apparatus	2224/75901	using a computer, e.g. fully- or semi-automatic bonding
2224/75601	Storing means	2224/7592	Load or pressure adjusting means, e.g. sensors
2224/75611	Feeding means	2224/75925	Vibration adjusting means, e.g. sensors
2224/75621	Holding means	2224/7595	Means for forming additional members
2224/7565	Means for transporting the components to be connected	2224/7598	specially adapted for batch processes
2224/75651	Belt conveyor	2224/75981	Apparatus chuck
2224/75652	Chain conveyor	2224/75982	Shape
2224/75653	Vibrating conveyor	2224/75983	of the mounting surface
2224/75654	Pneumatic conveyor	2224/75984	of other portions
2224/75655	in a fluid	2224/75985	Material
2224/757	Means for aligning	2224/75986	Auxiliary members on the pressing surface
2224/75701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75987	Shape of the auxiliary member
2224/75702	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75988	Material of the auxiliary member
2224/75703	Mechanical holding means	2224/76	Apparatus for connecting with build-up interconnects
2224/75704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76001	Calibration means
2224/75705	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/7601	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma
2224/75723	Electrostatic holding means	2224/761	Means for controlling the bonding environment, e.g. valves, vacuum pumps
2224/75724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76101	Chamber
2224/75725	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/76102	Vacuum chamber
2224/75733	Magnetic holding means	2224/7611	High pressure chamber
2224/75734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7615	Means for depositing
2224/75735	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/76151	Means for direct writing
2224/75743	Suction holding means	2224/76152	Syringe
			2224/76155	Jetting means, e.g. ink jet
			2224/76158	including a laser
			2224/76161	Means for screen printing, e.g. roller, squeegee, screen stencil
			2224/7617	Means for applying a preform, e.g. laminator
			2224/76171	including a vacuum-bag
			2224/7618	Means for blanket deposition

2224/76181	for spin coating, i.e. spin coater	2224/76347	Piezoelectric transducers
2224/76182	for curtain coating	2224/76348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76183	for immersion coating, i.e. bath	2224/76349	in the upper part of the bonding apparatus
2224/76184	for spray coating, i.e. nozzle	2224/7635	Stable and mobile yokes
2224/76185	Means for physical vapour deposition [PVD]	2224/76351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76186	Means for sputtering, e.g. target	2224/76352	in the upper part of the bonding apparatus
2224/76187	Means for evaporation	2224/76353	Ultrasonic horns
2224/76188	Means for chemical vapour deposition [CVD], e.g. for laser CVD	2224/76354	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76189	Means for plating, e.g. for electroplating, electroless plating	2224/76355	Design, e.g. of the wave guide
2224/762	. . .	Protection means against electrical discharge	2224/765	. . .	Cooling means
2224/7625	. . .	Means for applying energy, e.g. heating means	2224/76501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76502	in the upper part of the bonding apparatus
2224/76252	in the upper part of the bonding apparatus	2224/7655	. . .	Mechanical means, e.g. for planarising, pressing, stamping
2224/76253	adapted for localised heating	2224/76552	for drilling
2224/7626	Polychromatic heating lamp	2224/76554	for abrasive blasting, e.g. sand blasting, wet blasting, hydro-blasting, dry ice blasting
2224/76261	Laser	2224/766	. . .	Means for supplying the material of the interconnect
2224/76262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76601	Storing means
2224/76263	in the upper part of the bonding apparatus	2224/76611	Feeding means
2224/76264	by induction heating, i.e. coils	2224/76621	Holding means
2224/76265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7665	Means for transporting the components to be connected
2224/76266	in the upper part of the bonding apparatus	2224/76651	Belt conveyor
2224/76267	Flame torch, e.g. hydrogen torch	2224/76652	Chain conveyor
2224/76268	Discharge electrode	2224/76653	Vibrating conveyor
2224/76269	Shape of the discharge electrode	2224/76654	Pneumatic conveyor
2224/7627	Material of the discharge electrode	2224/76655	in a fluid
2224/76271	Circuitry of the discharge electrode	2224/767	. . .	Means for aligning
2224/76272	Oven	2224/76701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7628	Resistance welding electrodes, i.e. for ohmic heating	2224/76702	in the upper part of the bonding apparatus
2224/76281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76703	Mechanical holding means
2224/76282	in the upper part of the bonding apparatus	2224/76704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76283	by infrared heating, e.g. infrared heating lamp	2224/76705	in the upper part of the bonding apparatus
2224/763	by means of pressure	2224/76723	Electrostatic holding means
2224/76301	Pressing head	2224/76724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76302	Shape	2224/76725	in the upper part of the bonding apparatus
2224/76303	of the pressing surface	2224/76733	Magnetic holding means
2224/76304	being curved	2224/76734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76305	comprising protrusions	2224/76735	in the upper part of the bonding apparatus
2224/7631	of other parts	2224/76743	Suction holding means
2224/76312	Material	2224/76744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76313	Removable pressing head	2224/76745	in the upper part of the bonding apparatus
2224/76314	Auxiliary members on the pressing surface	2224/76753	Means for optical alignment, e.g. sensors
2224/76315	Elastomer inlay	2224/76754	Guiding structures
2224/76316	with retaining mechanisms	2224/76755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76317	Removable auxiliary member	2224/76756	in the upper part of the bonding apparatus
2224/76318	Shape of the auxiliary member	2224/768	. . .	Means for moving parts
2224/7632	Material of the auxiliary member	2224/76801	Lower part of the bonding apparatus, e.g. XY table
2224/76343	by ultrasonic vibrations			
2224/76344	Eccentric cams			
2224/76345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck			
2224/76346	in the upper part of the bonding apparatus			

2224/76802	Rotational mechanism	2224/772	. . .	Protection means against electrical discharge
2224/76803	Pivoting mechanism	2224/7725	. . .	Means for applying energy, e.g. heating means
2224/76804	Translational mechanism	2224/77251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76821	Upper part of the bonding apparatus, i.e. bonding head	2224/77252	in the upper part of the bonding apparatus, e.g. in the wedge
2224/76822	Rotational mechanism	2224/77253	adapted for localised heating
2224/76823	Pivoting mechanism	2224/7726	Polychromatic heating lamp
2224/76824	Translational mechanism	2224/77261	Laser
2224/76841	of the bonding head	2224/77262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76842	Rotational mechanism	2224/77263	in the upper part of the bonding apparatus, e.g. in the wedge
2224/76843	Pivoting mechanism	2224/77264	by induction heating, i.e. coils
2224/769	. . .	Means for monitoring the connection process	2224/77265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76901	using a computer, e.g. fully- or semi-automatic bonding	2224/77266	in the upper part of the bonding apparatus, e.g. in the wedge
2224/7692	Load or pressure adjusting means, e.g. sensors	2224/77267	Flame torch, e.g. hydrogen torch
2224/76925	Vibration adjusting means, e.g. sensors	2224/77268	Discharge electrode
2224/7695	. . .	Means for forming additional members	2224/77269	Shape of the discharge electrode
2224/7698	. . .	specially adapted for batch processes	2224/7727	Material of the discharge electrode
2224/76981	. . .	Apparatus chuck	2224/77271	Circuitry of the discharge electrode
2224/76982	Shape	2224/77272	Oven
2224/76983	of the mounting surface	2224/7728	Resistance welding electrodes, i.e. for ohmic heating
2224/76984	of other portions	2224/77281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76985	Material	2224/77282	in the upper part of the bonding apparatus, e.g. in the wedge
2224/76986	Auxiliary members on the pressing surface	2224/77283	by infrared heating, e.g. infrared heating lamp
2224/76987	Shape of the auxiliary member	2224/773	by means of pressure
2224/76988	Material of the auxiliary member	2224/77313	Wedge
2224/77	. .	Apparatus for connecting with strap connectors	2224/77314	Shape
2224/77001	. . .	Calibration means	2224/77315	of the pressing surface, e.g. tip or head
2224/7701	. . .	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma	2224/77316	comprising protrusions
2224/771	. . .	Means for controlling the bonding environment, e.g. valves, vacuum pumps	2224/77317	of other portions
2224/77101	Chamber	2224/77318	inside the capillary
2224/77102	Vacuum chamber	2224/77319	outside the capillary
2224/7711	High pressure chamber	2224/7732	Removable wedge
2224/7715	. . .	Means for applying permanent coating, e.g. in-situ coating	2224/77321	Material
2224/77151	Means for direct writing	2224/77325	Auxiliary members on the pressing surface
2224/77152	Syringe	2224/77326	Removable auxiliary member
2224/77153	integrated into the capillary or wedge	2224/77327	Shape of the auxiliary member
2224/77155	Jetting means, e.g. ink jet	2224/77328	Material of the auxiliary member
2224/77158	including a laser	2224/77343	by ultrasonic vibrations
2224/77161	Means for screen printing, e.g. roller, squeegee, screen stencil	2224/77344	Eccentric cams
2224/7717	Means for applying a preform, e.g. laminator	2224/77345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77171	including a vacuum-bag	2224/77346	in the upper part of the bonding apparatus, e.g. in the wedge
2224/7718	Means for blanket deposition	2224/77347	Piezoelectric transducers
2224/77181	for spin coating, i.e. spin coater	2224/77348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77182	for curtain coating	2224/77349	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77183	for immersion coating, i.e. bath	2224/7735	Stable and mobile yokes
2224/77184	for spray coating, i.e. nozzle	2224/77351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77185	Means for physical vapour deposition [PVD], e.g. evaporation, sputtering			
2224/77186	Means for sputtering, e.g. target			
2224/77187	Means for evaporation			
2224/77188	Means for chemical vapour deposition [CVD], e.g. for laser CVD			
2224/77189	Means for plating, e.g. for electroplating, electroless plating			

2224/77352	in the upper part of the bonding apparatus, e.g. in the wedge	2224/77821	Upper part of the bonding apparatus, i.e. bonding head, e.g. capillary or wedge
2224/77353	Ultrasonic horns	2224/77822	Rotational mechanism
2224/77354	in the lower part of the bonding apparatus, e.g. in the mounting chuck	2224/77823	Pivoting mechanism
2224/77355	Design, e.g. of the wave guide	2224/77824	Translational mechanism
2224/775	. . .	Cooling means	2224/77841	of the pressing portion, e.g. tip or head
2224/77501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77842	Rotational mechanism
2224/77502	in the upper part of the bonding apparatus, e.g. in the wedge	2224/77843	Pivoting mechanism
2224/7755	. . .	Mechanical means, e.g. for severing, pressing, stamping	2224/779	. . .	Means for monitoring the connection process
2224/776	. . .	Means for supplying the connector to be connected in the bonding apparatus	2224/77901	using a computer, e.g. fully- or semi-automatic bonding
2224/77601	Storing means	2224/7792	Load or pressure adjusting means, e.g. sensors
2224/77611	Feeding means	2224/77925	Vibration adjusting means, e.g. sensors
2224/77621	Holding means, e.g. wire claspers	2224/7795	. . .	Means for forming additional members
2224/77631	Means for wire tension adjustments	2224/7798	. . .	specially adapted for batch processes
2224/7765	. . .	Means for transporting the components to be connected	2224/77981	. . .	Apparatus chuck
2224/77651	Belt conveyor	2224/77982	Shape
2224/77652	Chain conveyor	2224/77983	of the mounting surface
2224/77653	Vibrating conveyor	2224/77984	of other portions
2224/77654	Pneumatic conveyor	2224/77985	Material
2224/77655	in a fluid	2224/77986	Auxiliary members on the pressing surface
2224/777	. . .	Means for aligning	2224/77987	Shape of the auxiliary member
2224/77701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77988	Material of the auxiliary member
2224/77702	in the upper part of the bonding apparatus, e.g. in the wedge	2224/78	. . .	Apparatus for connecting with wire connectors
2224/77703	Mechanical holding means	2224/78001	. . .	Calibration means
2224/77704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7801	. . .	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma
2224/77705	in the upper part of the bonding apparatus, e.g. in the wedge	2224/781	. . .	Means for controlling the bonding environment, e.g. valves, vacuum pumps
2224/77723	Electrostatic holding means	2224/78101	Chamber
2224/77724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78102	Vacuum chamber
2224/77725	in the upper part of the bonding apparatus, e.g. in the wedge	2224/7811	High pressure chamber
2224/77733	Magnetic holding means	2224/7815	. . .	Means for applying permanent coating, e.g. in-situ coating
2224/77734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/782	. . .	Protection means against electrical discharge
2224/77735	in the upper part of the bonding apparatus, e.g. in the wedge	2224/7825	. . .	Means for applying energy, e.g. heating means
2224/77743	Suction holding means	2224/78251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78252	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/77745	in the upper part of the bonding apparatus, e.g. in the wedge	2224/78253	adapted for localised heating
2224/77753	Means for optical alignment, e.g. sensors	2224/7826	Polychromatic heating lamp
2224/77754	Guiding structures	2224/78261	Laser
2224/77755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77756	in the upper part of the bonding apparatus, e.g. in the wedge	2224/78263	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/778	. . .	Means for moving parts	2224/78264	by induction heating, i.e. coils
2224/77801	Lower part of the bonding apparatus, e.g. XY table	2224/78265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77802	Rotational mechanism	2224/78266	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/77803	Pivoting mechanism	2224/78267	Flame torch, e.g. hydrogen torch
2224/77804	Translational mechanism	2224/78268	Discharge electrode
			2224/78269	Shape of the discharge electrode
			2224/7827	Material of the discharge electrode
			2224/78271	Circuitry of the discharge electrode
			2224/78272	Oven
			2224/7828	Resistance welding electrodes, i.e. for ohmic heating

2224/78281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78502	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78282	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/7855	Mechanical means, e.g. for severing, pressing, stamping
2224/78283	by infrared heating, e.g. infrared heating lamp	2224/786	Means for supplying the connector to be connected in the bonding apparatus
2224/783	by means of pressure	2224/78601	Storing means
2224/78301	Capillary	2224/78611	Feeding means
2224/78302	Shape	2224/78621	Holding means, e.g. wire clampers
2224/78303	of the pressing surface, e.g. tip or head	2224/78631	Means for wire tension adjustments
2224/78304	comprising protrusions	2224/7865	Means for transporting the components to be connected
2224/78305	of other portions	2224/78651	Belt conveyor
2224/78306	inside the capillary	2224/78652	Chain conveyor
2224/78307	outside the capillary	2224/78653	Vibrating conveyor
2224/78308	Removable capillary	2224/78654	Pneumatic conveyor
2224/78309	Material	2224/78655	in a fluid
2224/7831	Auxiliary members on the pressing surface	2224/787	Means for aligning
2224/78311	Removable auxiliary member	2224/78701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78312	Shape of the auxiliary member	2224/78702	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78313	Wedge	2224/78703	Mechanical holding means
2224/78314	Shape	2224/78704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78315	of the pressing surface, e.g. tip or head	2224/78705	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78316	comprising protrusions	2224/78723	Electrostatic holding means
2224/78317	of other portions	2224/78724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78318	inside the capillary	2224/78725	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78319	outside the capillary	2224/78733	Magnetic holding means
2224/7832	Removable wedge	2224/78734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78321	Material	2224/78735	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78325	Auxiliary members on the pressing surface	2224/78743	Suction holding means
2224/78326	Removable auxiliary member	2224/78744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78327	Shape of the auxiliary member	2224/78745	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78328	Material of the auxiliary member	2224/78753	Means for optical alignment, e.g. sensors
2224/78343	by ultrasonic vibrations	2224/78754	Guiding structures
2224/78344	Eccentric cams	2224/78755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78756	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78346	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/788	Means for moving parts
2224/78347	Piezoelectric transducers	2224/78801	Lower part of the bonding apparatus, e.g. XY table
2224/78348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78802	Rotational mechanism
2224/78349	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/78803	Pivoting mechanism
2224/7835	Stable and mobile yokes	2224/78804	Translational mechanism
2224/78351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78821	Upper part of the bonding apparatus, i.e. bonding head, e.g. capillary or wedge
2224/78352	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/78822	Rotational mechanism
2224/78353	Ultrasonic horns	2224/78823	Pivoting mechanism
2224/78354	in the lower part of the bonding apparatus, e.g. in the mounting chuck	2224/78824	Translational mechanism
2224/78355	Design, e.g. of the wave guide	2224/78841	of the pressing portion, e.g. tip or head
2224/785	Cooling means	2224/78842	Rotational mechanism
2224/78501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78843	Pivoting mechanism
			2224/789	Means for monitoring the connection process

2224/78901	using a computer, e.g. fully- or semi-automatic bonding	2224/79264	by induction heating, i.e. coils
2224/7892	Load or pressure adjusting means, e.g. sensors	2224/79265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78925	Vibration adjusting means, e.g. sensors	2224/79266	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/7895	Means for forming additional members	2224/79267	Flame torch, e.g. hydrogen torch
2224/7898	specially adapted for batch processes	2224/79268	Discharge electrode
2224/78981	Apparatus chuck	2224/79269	Shape of the discharge electrode
2224/78982	Shape	2224/7927	Material of the discharge electrode
2224/78983	of the mounting surface	2224/79271	Circuitry of the discharge electrode
2224/78984	of other portions	2224/79272	Oven
2224/78985	Material	2224/7928	Resistance welding electrodes, i.e. for ohmic heating
2224/78986	Auxiliary members on the pressing surface	2224/79281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78987	Shape of the auxiliary member	2224/79282	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/78988	Material of the auxiliary member	2224/79283	by infrared heating, e.g. infrared heating lamp
2224/79	Apparatus for Tape Automated Bonding [TAB]	2224/793	by means of pressure
2224/79001	Calibration means	2224/79301	Pressing head
2224/7901	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma	2224/79302	Shape
2224/791	Means for controlling the bonding environment, e.g. valves, vacuum pumps	2224/79303	of the pressing surface
2224/79101	Chamber	2224/79304	being curved
2224/79102	Vacuum chamber	2224/79305	comprising protrusions
2224/7911	High pressure chamber	2224/7931	of other parts
2224/7915	Means for applying permanent coating	2224/79312	Material
2224/79151	Means for direct writing	2224/79313	Removable pressing head
2224/79152	Syringe	2224/79314	Auxiliary members on the pressing surface
2224/79153	integrated into the pressing head	2224/79315	Elastomer inlay
2224/79155	Jetting means, e.g. ink jet	2224/79316	with retaining mechanisms
2224/79158	including a laser	2224/79317	Removable auxiliary member
2224/79161	Means for screen printing, e.g. roller, squeegee, screen stencil	2224/79318	Shape of the auxiliary member
2224/7917	Means for applying a preform, e.g. laminator	2224/7932	Material of the auxiliary member
2224/79171	including a vacuum-bag	2224/79343	by ultrasonic vibrations
2224/7918	Means for blanket deposition	2224/79344	Eccentric cams
2224/79181	for spin coating, i.e. spin coater	2224/79345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79182	for curtain coating	2224/79346	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79183	for immersion coating, i.e. bath	2224/79347	Piezoelectric transducers
2224/79184	for spray coating, i.e. nozzle	2224/79348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79185	Means for physical vapour deposition [PVD], e.g. evaporation, sputtering	2224/79349	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79186	Means for sputtering, e.g. target	2224/7935	Stable and mobile yokes
2224/79187	Means for evaporation	2224/79351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79188	Means for chemical vapour deposition [CVD], e.g. for laser CVD	2224/79352	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79189	Means for plating, e.g. for electroplating, electroless plating	2224/79353	Ultrasonic horns
2224/792	Protection means against electrical discharge	2224/79354	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7925	Means for applying energy, e.g. heating means	2224/79355	Design, e.g. of the wave guide
2224/79251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/795	Cooling means
2224/79252	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/79501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79253	adapted for localised heating	2224/79502	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/7926	Polychromatic heating lamp	2224/7955	Mechanical means, e.g. for pressing, stamping
2224/79261	Laser	2224/796	Means for supplying the connector to be connected in the bonding apparatus
2224/79262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck			
2224/79263	in the upper part of the bonding apparatus, e.g. in the pressing head			

- 2224/79601 Storing means
- 2224/79611 Feeding means
- 2224/79621 Holding means
- 2224/7965 . . . Means for transporting the components to be connected
- 2224/79651 Belt conveyor
- 2224/79652 Chain conveyor
- 2224/79653 Vibrating conveyor
- 2224/79654 Pneumatic conveyor
- 2224/79655 in a fluid
- 2224/797 . . . Means for aligning
- 2224/79701 in the lower part of the bonding apparatus, e.g. in the apparatus chuck
- 2224/79702 in the upper part of the bonding apparatus, e.g. in the pressing head
- 2224/79703 Mechanical holding means
- 2224/79704 in the lower part of the bonding apparatus, e.g. in the apparatus chuck
- 2224/79705 in the upper part of the bonding apparatus, e.g. in the pressing head
- 2224/79723 Electrostatic holding means
- 2224/79724 in the lower part of the bonding apparatus, e.g. in the apparatus chuck
- 2224/79725 in the upper part of the bonding apparatus, e.g. in the pressing head
- 2224/79733 Magnetic holding means
- 2224/79734 in the lower part of the bonding apparatus, e.g. in the apparatus chuck
- 2224/79735 in the upper part of the bonding apparatus, e.g. in the pressing head
- 2224/79743 Suction holding means
- 2224/79744 in the lower part of the bonding apparatus, e.g. in the apparatus chuck
- 2224/79745 in the upper part of the bonding apparatus, e.g. in the pressing head
- 2224/79753 Means for optical alignment, e.g. sensors
- 2224/79754 Guiding structures
- 2224/79755 in the lower part of the bonding apparatus, e.g. in the apparatus chuck
- 2224/79756 in the upper part of the bonding apparatus, e.g. in the pressing head
- 2224/798 . . . Means for moving parts
- 2224/79801 Lower part of the bonding apparatus, e.g. XY table
- 2224/79802 Rotational mechanism
- 2224/79803 Pivoting mechanism
- 2224/79804 Translational mechanism
- 2224/79821 Upper part of the bonding apparatus, i.e. pressing head
- 2224/79822 Rotational mechanism
- 2224/79823 Pivoting mechanism
- 2224/79824 Translational mechanism
- 2224/79841 of the pressing head
- 2224/79842 Rotational mechanism
- 2224/79843 Pivoting mechanism
- 2224/799 . . . Means for monitoring the connection process
- 2224/79901 using a computer, e.g. fully- or semi-automatic bonding
- 2224/7992 Load or pressure adjusting means, e.g. sensors
- 2224/79925 Vibration adjusting means, e.g. sensors
- 2224/7995 . . . Means for forming additional members
- 2224/7998 . . . specially adapted for batch processes
- 2224/79981 . . . Apparatus chuck
- 2224/79982 Shape
- 2224/79983 of the mounting surface
- 2224/79984 of other portions
- 2224/79985 Material
- 2224/79986 Auxiliary members on the pressing surface
- 2224/79987 Shape of the auxiliary member
- 2224/79988 Material of the auxiliary member
- 2224/7999 . . . for disconnecting
- 2224/80 . . . Methods for connecting semiconductor or other solid state bodies using means for bonding being attached to, or being formed on, the surface to be connected
- 2224/80001 . . . by connecting a bonding area directly to another bonding area, i.e. connectorless bonding, e.g. bumpless bonding
- 2224/80003 . . . involving a temporary auxiliary member not forming part of the bonding apparatus
- 2224/80004 being a removable or sacrificial coating
- 2224/80006 being a temporary or sacrificial substrate
- 2224/80007 . . . involving a permanent auxiliary member being left in the finished device, e.g. aids for protecting the bonding area during or after the bonding process
- 2224/80009 . . . Pre-treatment of the bonding area
- 2224/8001 Cleaning the bonding area, e.g. oxide removal step, desmearing
- 2224/80011 Chemical cleaning, e.g. etching, flux
- 2224/80012 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/80013 Plasma cleaning
- 2224/80014 Thermal cleaning, e.g. decomposition, sublimation
- 2224/80019 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8001](#) - [H01L 2224/80014](#)
- 2224/8002 Applying permanent coating to the bonding area in the bonding apparatus, e.g. in-situ coating
- 2224/80024 Applying flux to the bonding area in the bonding apparatus
- 2224/8003 Reshaping the bonding area in the bonding apparatus, e.g. flattening the bonding area
- 2224/80031 by chemical means, e.g. etching, anodisation
- 2224/80035 by heating means
- 2224/80037 using a polychromatic heating lamp
- 2224/80039 using a laser
- 2224/80041 Induction heating, i.e. eddy currents
- 2224/80047 by mechanical means, e.g. severing, pressing, stamping
- 2224/80048 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/80051 Forming additional members
- 2224/80052 . . . Detaching bonding areas, e.g. after testing ([unsoldering in general B23K 1/018](#))
- 2224/80053 . . . Bonding environment
- 2224/80054 Composition of the atmosphere
- 2224/80055 being oxidating
- 2224/80065 being reducing
- 2224/80075 being inert

2224/80085	being a liquid, e.g. for fluidic self-assembly	2224/80211	applying isostatic pressure, e.g. degassing using vacuum or a pressurised liquid
2224/8009	Vacuum	2224/80213	using a reflow oven
2224/80091	Under pressure	2224/80215	with a graded temperature profile
2224/80092	Atmospheric pressure	2224/8022	with energy being in the form of electromagnetic radiation
2224/80093	Transient conditions, e.g. gas-flow	2224/80222	Induction heating, i.e. eddy currents
2224/80095	Temperature settings	2224/80224	using a laser
2224/80096	Transient conditions	2224/8023	Polychromatic or infrared lamp heating
2224/80097	Heating	2224/80232	using an autocatalytic reaction, e.g. exothermic brazing
2224/80098	Cooling	2224/80234	using means for applying energy being within the device, e.g. integrated heater
2224/80099	Ambient temperature	2224/80236	using electro-static corona discharge
2224/8011	. . .	involving protection against electrical discharge, e.g. removing electrostatic charge	2224/80237	using an electron beam (electron beam welding in general B23K 15/00)
2224/8012	. . .	Aligning	2224/80238	using electric resistance welding, i.e. ohmic heating
2224/80121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors	2224/8034	. . .	Bonding interfaces of the bonding area
2224/80122	by detecting inherent features of, or outside, the semiconductor or solid-state body	2224/80345	Shape, e.g. interlocking features
2224/80123	Shape or position of the body	2224/80355	having an external coating, e.g. protective bond-through coating
2224/80125	Bonding areas on the body	2224/80357	being flush with the surface
2224/80127	Bonding areas outside the body	2224/80359	Material
2224/80129	Shape or position of the other item	2224/8036	. . .	Bonding interfaces of the semiconductor or solid state body
2224/8013	using marks formed on the semiconductor or solid-state body	2224/80365	Shape, e.g. interlocking features
2224/80132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"	2224/80375	having an external coating, e.g. protective bond-through coating
2224/80136	involving guiding structures, e.g. spacers or supporting members	2224/80379	Material (material of the bonding area prior to the connecting process H01L 2224/05099 and H01L 2224/05599)
2224/80138	the guiding structures being at least partially left in the finished device	2224/8038	. . .	Bonding interfaces outside the semiconductor or solid-state body
2224/80139	Guiding structures on the body	2224/80385	Shape, e.g. interlocking features
2224/8014	Guiding structures outside the body	2224/80395	having an external coating, e.g. protective bond-through coating
2224/80141	Guiding structures both on and outside the body	2224/80399	Material
2224/80143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium	2224/804	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/80148	involving movement of a part of the bonding apparatus	2224/80401	the principal constituent melting at a temperature of less than 400°C
2224/80149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table	2224/80405	Gallium [Ga] as principal constituent
2224/8015	Rotational movements	2224/80409	Indium [In] as principal constituent
2224/8016	Translational movements	2224/80411	Tin [Sn] as principal constituent
2224/80169	being the upper part of the bonding apparatus, i.e. bonding head	2224/80413	Bismuth [Bi] as principal constituent
2224/8017	Rotational movements	2224/80414	Thallium [Tl] as principal constituent
2224/8018	Translational movements	2224/80416	Lead [Pb] as principal constituent
2224/8019	. . .	Arrangement of the bonding areas prior to mounting	2224/80417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/80194	Lateral distribution of the bonding areas	2224/80418	Zinc [Zn] as principal constituent
2224/802	. . .	Applying energy for connecting	2224/8042	Antimony [Sb] as principal constituent
2224/80201	Compression bonding	2224/80423	Magnesium [Mg] as principal constituent
2224/80203	Thermocompression bonding, e.g. diffusion bonding, pressure joining, thermocompression welding or solid-state welding	2224/80424	Aluminium [Al] as principal constituent
2224/80204	with a graded temperature profile			
2224/80205	Ultrasonic bonding			
2224/80206	Direction of oscillation			
2224/80207	Thermosonic bonding			
2224/80209	applying unidirectional static pressure			

2224/80438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/805	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/80439	Silver [Ag] as principal constituent	2224/80501	the principal constituent melting at a temperature of less than 400°C
2224/80444	Gold [Au] as principal constituent	2224/80505	Gallium [Ga] as principal constituent
2224/80447	Copper [Cu] as principal constituent	2224/80509	Indium [In] as principal constituent
2224/80449	Manganese [Mn] as principal constituent	2224/80511	Tin [Sn] as principal constituent
2224/80455	Nickel [Ni] as principal constituent	2224/80513	Bismuth [Bi] as principal constituent
2224/80457	Cobalt [Co] as principal constituent	2224/80514	Thallium [Tl] as principal constituent
2224/8046	Iron [Fe] as principal constituent	2224/80516	Lead [Pb] as principal constituent
2224/80463	the principal constituent melting at a temperature of greater than 1550°C	2224/80517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/80464	Palladium [Pd] as principal constituent	2224/80518	Zinc [Zn] as principal constituent
2224/80466	Titanium [Ti] as principal constituent	2224/8052	Antimony [Sb] as principal constituent
2224/80469	Platinum [Pt] as principal constituent	2224/80523	Magnesium [Mg] as principal constituent
2224/8047	Zirconium [Zr] as principal constituent	2224/80524	Aluminium [Al] as principal constituent
2224/80471	Chromium [Cr] as principal constituent	2224/80538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/80472	Vanadium [V] as principal constituent	2224/80539	Silver [Ag] as principal constituent
2224/80473	Rhodium [Rh] as principal constituent	2224/80544	Gold [Au] as principal constituent
2224/80476	Ruthenium [Ru] as principal constituent	2224/80547	Copper [Cu] as principal constituent
2224/80478	Iridium [Ir] as principal constituent	2224/80549	Manganese [Mn] as principal constituent
2224/80479	Niobium [Nb] as principal constituent	2224/80555	Nickel [Ni] as principal constituent
2224/8048	Molybdenum [Mo] as principal constituent	2224/80557	Cobalt [Co] as principal constituent
2224/80481	Tantalum [Ta] as principal constituent	2224/8056	Iron [Fe] as principal constituent
2224/80483	Rhenium [Re] as principal constituent	2224/80563	the principal constituent melting at a temperature of greater than 1550°C
2224/80484	Tungsten [W] as principal constituent	2224/80564	Palladium [Pd] as principal constituent
2224/80486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/80566	Titanium [Ti] as principal constituent
2224/80487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80488)	2224/80569	Platinum [Pt] as principal constituent
2224/80488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/8057	Zirconium [Zr] as principal constituent
2224/8049	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/80571	Chromium [Cr] as principal constituent
2224/80491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/80572	Vanadium [V] as principal constituent
2224/80493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/804 - H01L 2224/80491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/80573	Rhodium [Rh] as principal constituent
2224/80494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/804 - H01L 2224/80491	2224/80576	Ruthenium [Ru] as principal constituent
2224/80495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/804 - H01L 2224/80491			
2224/80498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams			
2224/80499	Material of the matrix			

2224/80578	Iridium [Ir] as principal constituent	2224/80617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/80579	Niobium [Nb] as principal constituent	2224/80618	Zinc [Zn] as principal constituent
2224/8058	Molybdenum [Mo] as principal constituent	2224/8062	Antimony [Sb] as principal constituent
2224/80581	Tantalum [Ta] as principal constituent	2224/80623	Magnesium [Mg] as principal constituent
2224/80583	Rhenium [Re] as principal constituent	2224/80624	Aluminium [Al] as principal constituent
2224/80584	Tungsten [W] as principal constituent	2224/80638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/80586	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/80639	Silver [Ag] as principal constituent
2224/80587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80588)	2224/80644	Gold [Au] as principal constituent
2224/80588	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/80647	Copper [Cu] as principal constituent
2224/8059	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/80649	Manganese [Mn] as principal constituent
2224/80591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/80655	Nickel [Ni] as principal constituent
2224/80593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/805 - H01L 2224/80591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/80657	Cobalt [Co] as principal constituent
2224/80594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/805 - H01L 2224/80591	2224/8066	Iron [Fe] as principal constituent
2224/80595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/805 - H01L 2224/80591	2224/80663	the principal constituent melting at a temperature of greater than 1550°C
2224/80598	Fillers	2224/80664	Palladium [Pd] as principal constituent
2224/80599	Base material	2224/80666	Titanium [Ti] as principal constituent
2224/806	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/80669	Platinum [Pt] as principal constituent
2224/80601	the principal constituent melting at a temperature of less than 400°C	2224/8067	Zirconium [Zr] as principal constituent
2224/80605	Gallium [Ga] as principal constituent	2224/80671	Chromium [Cr] as principal constituent
2224/80609	Indium [In] as principal constituent	2224/80672	Vanadium [V] as principal constituent
2224/80611	Tin [Sn] as principal constituent	2224/80673	Rhodium [Rh] as principal constituent
2224/80613	Bismuth [Bi] as principal constituent	2224/80676	Ruthenium [Ru] as principal constituent
2224/80614	Thallium [Tl] as principal constituent	2224/80678	Iridium [Ir] as principal constituent
2224/80616	Lead [Pb] as principal constituent	2224/80679	Niobium [Nb] as principal constituent
			2224/8068	Molybdenum [Mo] as principal constituent
			2224/80681	Tantalum [Ta] as principal constituent
			2224/80683	Rhenium [Re] as principal constituent
			2224/80684	Tungsten [W] as principal constituent
			2224/80686	with a principal constituent of the material being a non metallic, non metalloid inorganic material

2224/80687	...	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80688)	2224/80724	...	Aluminium [Al] as principal constituent
2224/80688	...	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/80738	...	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/8069	...	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/80739	...	Silver [Ag] as principal constituent
2224/80691	...	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/80744	...	Gold [Au] as principal constituent
2224/80693	...	with a principal constituent of the material being a solid not provided for in groups H01L 2224/806 - H01L 2224/80691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/80747	...	Copper [Cu] as principal constituent
2224/80694	...	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/806 - H01L 2224/80691	2224/80749	...	Manganese [Mn] as principal constituent
2224/80695	...	with a principal constituent of the material being a gas not provided for in groups H01L 2224/806 - H01L 2224/80691	2224/80755	...	Nickel [Ni] as principal constituent
2224/80698	...	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/80757	...	Cobalt [Co] as principal constituent
2224/80699	...	Coating material	2224/8076	...	Iron [Fe] as principal constituent
2224/807	...	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/80763	...	the principal constituent melting at a temperature of greater than 1550°C
2224/80701	...	the principal constituent melting at a temperature of less than 400°C	2224/80764	...	Palladium [Pd] as principal constituent
2224/80705	...	Gallium [Ga] as principal constituent	2224/80766	...	Titanium [Ti] as principal constituent
2224/80709	...	Indium [In] as principal constituent	2224/80769	...	Platinum [Pt] as principal constituent
2224/80711	...	Tin [Sn] as principal constituent	2224/8077	...	Zirconium [Zr] as principal constituent
2224/80713	...	Bismuth [Bi] as principal constituent	2224/80771	...	Chromium [Cr] as principal constituent
2224/80714	...	Thallium [Tl] as principal constituent	2224/80772	...	Vanadium [V] as principal constituent
2224/80716	...	Lead [Pb] as principal constituent	2224/80773	...	Rhodium [Rh] as principal constituent
2224/80717	...	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/80776	...	Ruthenium [Ru] as principal constituent
2224/80718	...	Zinc [Zn] as principal constituent	2224/80778	...	Iridium [Ir] as principal constituent
2224/8072	...	Antimony [Sb] as principal constituent	2224/80779	...	Niobium [Nb] as principal constituent
2224/80723	...	Magnesium [Mg] as principal constituent	2224/8078	...	Molybdenum [Mo] as principal constituent
			2224/80781	...	Tantalum [Ta] as principal constituent
			2224/80783	...	Rhenium [Re] as principal constituent
			2224/80784	...	Tungsten [W] as principal constituent
			2224/80786	...	with a principal constituent of the material being a non metallic, non metalloid inorganic material
			2224/80787	...	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80788)
			2224/80788	...	Glasses, e.g. amorphous oxides, nitrides or fluorides
			2224/8079	...	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy

- 2224/80791 The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
- 2224/80793 with a principal constituent of the material being a solid not provided for in groups [H01L 2224/807](#) - [H01L 2224/80791](#), e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
- 2224/80794 with a principal constituent of the material being a liquid not provided for in groups [H01L 2224/807](#) - [H01L 2224/80791](#)
- 2224/80795 with a principal constituent of the material being a gas not provided for in groups [H01L 2224/807](#) - [H01L 2224/80791](#)
- 2224/80798 with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
- 2224/80799 Shape or distribution of the fillers
- 2224/808 . . . Bonding techniques
- 2224/80801 Soldering or alloying
- 2224/80805 involving forming a eutectic alloy at the bonding interface
- 2224/8081 involving forming an intermetallic compound at the bonding interface
- 2224/80815 Reflow soldering
- 2224/8082 Diffusion bonding
- 2224/80825 Solid-liquid interdiffusion
- 2224/8083 Solid-solid interdiffusion
- 2224/8084 Sintering
- 2224/8085 using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
- 2224/80855 Hardening the adhesive by curing, i.e. thermosetting
- 2224/80856 Pre-cured adhesive, i.e. B-stage adhesive
- 2224/80859 Localised curing of parts of the bonding area
- 2224/80862 Heat curing
- 2224/80865 Microwave curing
- 2224/80868 Infrared [IR] curing
- 2224/80871 Visible light curing
- 2224/80874 Ultraviolet [UV] curing
- 2224/80877 Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
- 2224/8088 Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
- 2224/80885 Combinations of two or more hardening methods provided for in at least two different groups from [H01L 2224/80855](#) - [H01L 2224/8088](#), e.g. for hybrid thermoplastic-thermosetting adhesives
- 2224/8089 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/80893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/80894 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/80895 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/80896 between electrically insulating surfaces, e.g. oxide or nitride layers
- 2224/80897 Mechanical interlocking, e.g. anchoring, hook and loop-type fastening or the like
- 2224/80898 Press-fitting, i.e. pushing the parts together and fastening by friction, e.g. by compression of one part against the other
- 2224/80899 using resilient parts in the bonding area
- 2224/809 . . . with the bonding area not providing any mechanical bonding
- 2224/80901 Pressing a bonding area against another bonding area by means of a further bonding area or connector ([detachable pressure contact](#) [H01L 2224/72](#))
- 2224/80902 by means of a further bonding area
- 2224/80903 by means of a bump or layer connector
- 2224/80904 by means of an encapsulation layer or foil
- 2224/80905 . . . Combinations of bonding methods provided for in at least two different groups from [H01L 2224/808](#) - [H01L 2224/80904](#)
- 2224/80906 Specific sequence of method steps
- 2224/80907 Intermediate bonding, i.e. intermediate bonding step for temporarily bonding the semiconductor or solid-state body, followed by at least a further bonding step
- 2224/80908 . . . involving monitoring, e.g. feedback loop
- 2224/80909 . . . Post-treatment of the bonding area
- 2224/8091 Cleaning, e.g. oxide removal step, desmearing
- 2224/80911 Chemical cleaning, e.g. etching, flux
- 2224/80912 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/80913 Plasma cleaning
- 2224/80914 Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
- 2224/80919 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8091](#) - [H01L 2224/80914](#)
- 2224/8092 Applying permanent coating, e.g. protective coating
- 2224/8093 Reshaping
- 2224/80931 by chemical means, e.g. etching
- 2224/80935 by heating means, e.g. reflowing
- 2224/80937 using a polychromatic heating lamp
- 2224/80939 using a laser
- 2224/80941 Induction heating, i.e. eddy currents
- 2224/80943 using a flame torch, e.g. hydrogen torch
- 2224/80945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/80947 by mechanical means, e.g. ?pull-and-cut?, pressing, stamping

2224/80948	Thermal treatments, e.g. annealing, controlled cooling	2224/81093	Transient conditions, e.g. gas-flow
2224/80951	Forming additional members, e.g. for reinforcing	2224/81095	Temperature settings
2224/80986	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence	2224/81096	Transient conditions
2224/81	using a bump connector	2224/81097	Heating
2224/81001	involving a temporary auxiliary member not forming part of the bonding apparatus	2224/81098	Cooling
2224/81002	being a removable or sacrificial coating	2224/81099	Ambient temperature
2224/81005	being a temporary or sacrificial substrate	2224/811	the bump connector being supplied to the parts to be connected in the bonding apparatus
2224/81007	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the bump connector during or after the bonding process	2224/81101	as prepeg comprising a bump connector, e.g. provided in an insulating plate member
2224/81009	Pre-treatment of the bump connector or the bonding area	2224/8111	involving protection against electrical discharge, e.g. removing electrostatic charge
2224/8101	Cleaning the bump connector, e.g. oxide removal step, desmearing	2224/8112	Aligning
2224/81011	Chemical cleaning, e.g. etching, flux	2224/81121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
2224/81012	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/81122	by detecting inherent features of, or outside, the semiconductor or solid-state body
2224/81013	Plasma cleaning	2224/81123	Shape or position of the body
2224/81014	Thermal cleaning, e.g. decomposition, sublimation	2224/81125	Bonding areas on the body
2224/81019	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8101 - H01L 2224/81014	2224/81127	Bonding areas outside the body
2224/8102	Applying permanent coating to the bump connector in the bonding apparatus, e.g. in-situ coating	2224/81129	Shape or position of the other item
2224/81022	Cleaning the bonding area, e.g. oxide removal step, desmearing	2224/8113	using marks formed on the semiconductor or solid-state body
2224/81024	Applying flux to the bonding area	2224/81132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
2224/81026	Applying a precursor material to the bonding area	2224/81136	involving guiding structures, e.g. spacers or supporting members
2224/8103	Reshaping the bump connector in the bonding apparatus, e.g. flattening the bump connector	2224/81138	the guiding structures being at least partially left in the finished device
2224/81031	by chemical means, e.g. etching, anodisation	2224/81139	Guiding structures on the body
2224/81035	by heating means	2224/8114	Guiding structures outside the body
2224/81037	using a polychromatic heating lamp	2224/81141	Guiding structures both on and outside the body
2224/81039	using a laser	2224/81143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
2224/81041	Induction heating, i.e. eddy currents	2224/81148	involving movement of a part of the bonding apparatus
2224/81047	by mechanical means, e.g. severing, pressing, stamping	2224/81149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
2224/81048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling	2224/8115	Rotational movements
2224/81051	Forming additional members	2224/8116	Translational movements
2224/81052	Detaching bump connectors, e.g. after testing (unsoldering in general B23K 1/018)	2224/81169	being the upper part of the bonding apparatus, i.e. bonding head
2224/81053	Bonding environment	2224/8117	Rotational movements
2224/81054	Composition of the atmosphere	2224/8118	Translational movements
2224/81055	being oxidating	2224/8119	Arrangement of the bump connectors prior to mounting
2224/81065	being reducing	2224/81191	wherein the bump connectors are disposed only on the semiconductor or solid-state body
2224/81075	being inert	2224/81192	wherein the bump connectors are disposed only on another item or body to be connected to the semiconductor or solid-state body
2224/81085	being a liquid, e.g. for fluidic self-assembly	2224/81193	wherein the bump connectors are disposed on both the semiconductor or solid-state body and another item or body to be connected to the semiconductor or solid-state body
2224/8109	Vacuum	2224/81194	Lateral distribution of the bump connectors
2224/81091	Under pressure	2224/812	Applying energy for connecting
2224/81092	Atmospheric pressure			

2224/81201	Compression bonding	2224/81417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/81203	Thermocompression bonding, e.g. diffusion bonding, pressure joining, thermocompression welding or solid-state welding	2224/81418	Zinc [Zn] as principal constituent
2224/81204	with a graded temperature profile	2224/8142	Antimony [Sb] as principal constituent
2224/81205	Ultrasonic bonding	2224/81423	Magnesium [Mg] as principal constituent
2224/81206	Direction of oscillation	2224/81424	Aluminium [Al] as principal constituent
2224/81207	Thermosonic bonding	2224/81438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/81208	applying unidirectional static pressure	2224/81439	Silver [Ag] as principal constituent
2224/81209	applying isostatic pressure, e.g. degassing using vacuum or a pressurised liquid	2224/81444	Gold [Au] as principal constituent
2224/8121	using a reflow oven	2224/81447	Copper [Cu] as principal constituent
2224/81211	with a graded temperature profile	2224/81449	Manganese [Mn] as principal constituent
2224/8122	with energy being in the form of electromagnetic radiation	2224/81455	Nickel [Ni] as principal constituent
2224/81222	Induction heating, i.e. eddy currents	2224/81457	Cobalt [Co] as principal constituent
2224/81224	using a laser	2224/8146	Iron [Fe] as principal constituent
2224/8123	Polychromatic or infrared lamp heating	2224/81463	the principal constituent melting at a temperature of greater than 1550°C
2224/81232	using an autocatalytic reaction, e.g. exothermic brazing	2224/81464	Palladium [Pd] as principal constituent
2224/81234	using means for applying energy being within the device, e.g. integrated heater	2224/81466	Titanium [Ti] as principal constituent
2224/81236	using electro-static corona discharge	2224/81469	Platinum [Pt] as principal constituent
2224/81237	using an electron beam (electron beam welding in general B23K 15/00)	2224/8147	Zirconium [Zr] as principal constituent
2224/81238	using electric resistance welding, i.e. ohmic heating	2224/81471	Chromium [Cr] as principal constituent
2224/8134	Bonding interfaces of the bump connector	2224/81472	Vanadium [V] as principal constituent
2224/81345	Shape, e.g. interlocking features	2224/81473	Rhodium [Rh] as principal constituent
2224/81355	having an external coating, e.g. protective bond-through coating	2224/81476	Ruthenium [Ru] as principal constituent
2224/81359	Material	2224/81478	Iridium [Ir] as principal constituent
2224/8136	Bonding interfaces of the semiconductor or solid state body	2224/81479	Niobium [Nb] as principal constituent
2224/81365	Shape, e.g. interlocking features	2224/8148	Molybdenum [Mo] as principal constituent
2224/81375	having an external coating, e.g. protective bond-through coating	2224/81481	Tantalum [Ta] as principal constituent
2224/81379	Material (material of the bump connector prior to the connecting process H01L 2224/13099 and H01L 2224/13599, and subgroups)	2224/81483	Rhenium [Re] as principal constituent
2224/8138	Bonding interfaces outside the semiconductor or solid-state body	2224/81484	Tungsten [W] as principal constituent
2224/81385	Shape, e.g. interlocking features	2224/81486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/81395	having an external coating, e.g. protective bond-through coating	2224/81487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81488)
2224/81399	Material	2224/81488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/814	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/8149	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/81401	the principal constituent melting at a temperature of less than 400°C	2224/81491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/81405	Gallium [Ga] as principal constituent	2224/81493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/814 - H01L 2224/81491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/81409	Indium [In] as principal constituent	2224/81494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/814 - H01L 2224/81491
2224/81411	Tin [Sn] as principal constituent			
2224/81413	Bismuth [Bi] as principal constituent			
2224/81414	Thallium [Tl] as principal constituent			
2224/81416	Lead [Pb] as principal constituent			

2224/81495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/814 - H01L 2224/81491	2224/8157	Zirconium [Zr] as principal constituent
2224/81498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/81571	Chromium [Cr] as principal constituent
2224/81499	Material of the matrix	2224/81572	Vanadium [V] as principal constituent
2224/815	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/81573	Rhodium [Rh] as principal constituent
2224/81501	the principal constituent melting at a temperature of less than 400°C	2224/81576	Ruthenium [Ru] as principal constituent
2224/81505	Gallium [Ga] as principal constituent	2224/81578	Iridium [Ir] as principal constituent
2224/81509	Indium [In] as principal constituent	2224/81579	Niobium [Nb] as principal constituent
2224/81511	Tin [Sn] as principal constituent	2224/8158	Molybdenum [Mo] as principal constituent
2224/81513	Bismuth [Bi] as principal constituent	2224/81581	Tantalum [Ta] as principal constituent
2224/81514	Thallium [Tl] as principal constituent	2224/81583	Rhenium [Re] as principal constituent
2224/81516	Lead [Pb] as principal constituent	2224/81584	Tungsten [W] as principal constituent
2224/81517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/81586	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/81518	Zinc [Zn] as principal constituent	2224/81587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81588)
2224/8152	Antimony [Sb] as principal constituent	2224/81588	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/81523	Magnesium [Mg] as principal constituent	2224/8159	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/81524	Aluminium [Al] as principal constituent	2224/81591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/81538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/81593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/815 - H01L 2224/81591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/81539	Silver [Ag] as principal constituent	2224/81594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/815 - H01L 2224/81591
2224/81544	Gold [Au] as principal constituent	2224/81595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/815 - H01L 2224/81591
2224/81547	Copper [Cu] as principal constituent	2224/81598	Fillers
2224/81549	Manganese [Mn] as principal constituent	2224/81599	Base material
2224/81555	Nickel [Ni] as principal constituent	2224/816	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/81557	Cobalt [Co] as principal constituent	2224/81601	the principal constituent melting at a temperature of less than 400°C
2224/8156	Iron [Fe] as principal constituent	2224/81605	Gallium [Ga] as principal constituent
2224/81563	the principal constituent melting at a temperature of greater than 1550°C			
2224/81564	Palladium [Pd] as principal constituent			
2224/81566	Titanium [Ti] as principal constituent			
2224/81569	Platinum [Pt] as principal constituent			

2224/81609	Indium [In] as principal constituent	2224/8168	Molybdenum [Mo] as principal constituent
2224/81611	Tin [Sn] as principal constituent	2224/81681	Tantalum [Ta] as principal constituent
2224/81613	Bismuth [Bi] as principal constituent	2224/81683	Rhenium [Re] as principal constituent
2224/81614	Thallium [Tl] as principal constituent	2224/81684	Tungsten [W] as principal constituent
2224/81616	Lead [Pb] as principal constituent	2224/81686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/81617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/81687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81688)
2224/81618	Zinc [Zn] as principal constituent	2224/81688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/8162	Antimony [Sb] as principal constituent	2224/8169	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/81623	Magnesium [Mg] as principal constituent	2224/81691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/81624	Aluminium [Al] as principal constituent	2224/81693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/816 - H01L 2224/81691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/81638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/81694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/816 - H01L 2224/81691
2224/81639	Silver [Ag] as principal constituent	2224/81695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/816 - H01L 2224/81691
2224/81644	Gold [Au] as principal constituent	2224/81698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/81647	Copper [Cu] as principal constituent	2224/81699	Coating material
2224/81649	Manganese [Mn] as principal constituent	2224/817	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/81655	Nickel [Ni] as principal constituent	2224/81701	the principal constituent melting at a temperature of less than 400°C
2224/81657	Cobalt [Co] as principal constituent	2224/81705	Gallium [Ga] as principal constituent
2224/8166	Iron [Fe] as principal constituent	2224/81709	Indium [In] as principal constituent
2224/81663	the principal constituent melting at a temperature of greater than 1550°C	2224/81711	Tin [Sn] as principal constituent
2224/81664	Palladium [Pd] as principal constituent	2224/81713	Bismuth [Bi] as principal constituent
2224/81666	Titanium [Ti] as principal constituent	2224/81714	Thallium [Tl] as principal constituent
2224/81669	Platinum [Pt] as principal constituent		
2224/8167	Zirconium [Zr] as principal constituent		
2224/81671	Chromium [Cr] as principal constituent		
2224/81672	Vanadium [V] as principal constituent		
2224/81673	Rhodium [Rh] as principal constituent		
2224/81676	Ruthenium [Ru] as principal constituent		
2224/81678	Iridium [Ir] as principal constituent		
2224/81679	Niobium [Nb] as principal constituent		

2224/81716	Lead [Pb] as principal constituent	2224/81786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/81717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/81787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81788)
2224/81718	Zinc [Zn] as principal constituent	2224/81788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/8172	Antimony [Sb] as principal constituent	2224/8179	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/81723	Magnesium [Mg] as principal constituent	2224/81791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/81724	Aluminium [Al] as principal constituent	2224/81793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/817 - H01L 2224/81791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/81738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/81794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/817 - H01L 2224/81791
2224/81739	Silver [Ag] as principal constituent	2224/81795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/817 - H01L 2224/81791
2224/81744	Gold [Au] as principal constituent	2224/81798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/81747	Copper [Cu] as principal constituent	2224/81799	Shape or distribution of the fillers
2224/81749	Manganese [Mn] as principal constituent	2224/818	Bonding techniques
2224/81755	Nickel [Ni] as principal constituent	2224/81801	Soldering or alloying
2224/81757	Cobalt [Co] as principal constituent	2224/81805	involving forming a eutectic alloy at the bonding interface
2224/8176	Iron [Fe] as principal constituent	2224/8181	involving forming an intermetallic compound at the bonding interface
2224/81763	the principal constituent melting at a temperature of greater than 1550°C	2224/81815	Reflow soldering
2224/81764	Palladium [Pd] as principal constituent	2224/8182	Diffusion bonding
2224/81766	Titanium [Ti] as principal constituent	2224/81825	Solid-liquid interdiffusion
2224/81769	Platinum [Pt] as principal constituent	2224/8183	Solid-solid interdiffusion
2224/8177	Zirconium [Zr] as principal constituent	2224/8184	Sintering
2224/81771	Chromium [Cr] as principal constituent	2224/8185	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
2224/81772	Vanadium [V] as principal constituent	2224/81855	Hardening the adhesive by curing, i.e. thermosetting
2224/81773	Rhodium [Rh] as principal constituent	2224/81856	Pre-cured adhesive, i.e. B-stage adhesive
2224/81776	Ruthenium [Ru] as principal constituent	2224/81859	Localised curing of parts of the bump connector
2224/81778	Iridium [Ir] as principal constituent	2224/81862	Heat curing
2224/81779	Niobium [Nb] as principal constituent	2224/81865	Microwave curing
2224/8178	Molybdenum [Mo] as principal constituent	2224/81868	Infrared [IR] curing
2224/81781	Tantalum [Ta] as principal constituent	2224/81871	Visible light curing
2224/81783	Rhenium [Re] as principal constituent	2224/81874	Ultraviolet [UV] curing
2224/81784	Tungsten [W] as principal constituent		

2224/81877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes	2224/81919	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8191 - H01L 2224/81914
2224/81888	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives	2224/8192	Applying permanent coating, e.g. protective coating
2224/81885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/81855 - H01L 2224/8188 , e.g. for hybrid thermoplastic-thermosetting adhesives	2224/8193	Reshaping
2224/8189	using an inorganic non metallic glass type adhesive, e.g. solder glass	2224/81931	by chemical means, e.g. etching
2224/81893	Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond	2224/81935	by heating means, e.g. reflowing
2224/81894	Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces	2224/81937	using a polychromatic heating lamp
2224/81895	between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding	2224/81939	using a laser
2224/81896	between electrically insulating surfaces, e.g. oxide or nitride layers	2224/81941	Induction heating, i.e. eddy currents
2224/81897	Mechanical interlocking, e.g. anchoring, hook and loop-type fastening or the like	2224/81943	using a flame torch, e.g. hydrogen torch
2224/81898	Press-fitting, i.e. pushing the parts together and fastening by friction, e.g. by compression of one part against the other	2224/81945	using a corona discharge, e.g. electronic flame off [EFO]
2224/81899	using resilient parts in the bump connector or in the bonding area	2224/81947	by mechanical means, e.g. "pull-and-cut", pressing, stamping
2224/819	with the bump connector not providing any mechanical bonding	2224/81948	Thermal treatments, e.g. annealing, controlled cooling
2224/81901	Pressing the bump connector against the bonding areas by means of another connector (detachable pressure contact H01L 2224/72)	2224/81951	Forming additional members, e.g. for reinforcing
2224/81902	by means of another bump connector	2224/81986	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
2224/81903	by means of a layer connector	2224/82	by forming build-up interconnects at chip-level, e.g. for high density interconnects [HDI]
2224/81904	by means of an encapsulation layer or foil	2224/82001	involving a temporary auxiliary member not forming part of the bonding apparatus
2224/81905	Combinations of bonding methods provided for in at least two different groups from H01L 2224/818 - H01L 2224/81904	2224/82002	being a removable or sacrificial coating
2224/81906	Specific sequence of method steps	2224/82005	being a temporary or sacrificial substrate
2224/81907	Intermediate bonding, i.e. intermediate bonding step for temporarily bonding the semiconductor or solid-state body, followed by at least a further bonding step	2224/82007	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting a build-up interconnect during or after the bonding process
2224/81908	involving monitoring, e.g. feedback loop	2224/82009	Pre-treatment of the connector or the bonding area
2224/81909	Post-treatment of the bump connector or bonding area	2224/8201	Cleaning, e.g. oxide removal step, desmearing
2224/8191	Cleaning, e.g. oxide removal step, desmearing	2224/8203	Reshaping, e.g. forming vias
2224/81911	Chemical cleaning, e.g. etching, flux	2224/82031	by chemical means, e.g. etching, anodisation
2224/81912	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/82035	by heating means
2224/81913	Plasma cleaning	2224/82039	using a laser
2224/81914	Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge	2224/82045	using a corona discharge, e.g. electronic flame off [EFO]
			2224/82047	by mechanical means, e.g. severing, pressing, stamping
			2224/82048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
			2224/82051	Forming additional members
			2224/82053	Bonding environment
			2224/82054	Composition of the atmosphere
			2224/82085	being a liquid, e.g. for fluidic self-assembly
			2224/8209	Vacuum
			2224/82091	Under pressure
			2224/82095	Temperature settings
			2224/82096	Transient conditions
			2224/82097	Heating
			2224/82098	Cooling
			2224/82099	Ambient temperature
			2224/821	Forming a build-up interconnect
			2224/82101	by additive methods, e.g. direct writing
			2224/82102	using jetting, e.g. ink jet
			2224/82103	using laser direct writing

- 2224/82104 using screen printing
- 2224/82105 by using a preform
- 2224/82106 by subtractive methods
- 2224/82108 by self-assembly processes
- 2224/82111 involving protection against electrical discharge, e.g. removing electrostatic charge
- 2224/82112 Aligning
- 2224/82121 Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
- 2224/82122 by detecting inherent features of, or outside, the semiconductor or solid-state body
- 2224/8213 using marks formed on the semiconductor or solid-state body
- 2224/82132 using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
- 2224/82136 involving guiding structures, e.g. spacers or supporting members
- 2224/82138 the guiding structures being at least partially left in the finished device
- 2224/82143 Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
- 2224/82148 involving movement of a part of the bonding apparatus
- 2224/82149 being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
- 2224/8215 Rotational movements
- 2224/8216 Translational movements
- 2224/82169 being the upper part of the bonding apparatus, e.g. nozzle
- 2224/8217 Rotational movement
- 2224/8218 Translational movements
- 2224/82181 connecting first on the semiconductor or solid-state body, i.e. on-chip,
- 2224/82186 connecting first outside the semiconductor or solid-state body, i.e. off-chip
- 2224/82191 connecting first both on and outside the semiconductor or solid-state body
- 2224/822 Applying energy for connecting
- 2224/82201 Compression bonding
- 2224/82203 Thermocompression bonding
- 2224/82205 Ultrasonic bonding
- 2224/82207 Thermosonic bonding
- 2224/8221 with energy being in the form of electromagnetic radiation
- 2224/82212 Induction heating, i.e. eddy currents
- 2224/82214 using a laser
- 2224/8223 Polychromatic or infrared lamp heating
- 2224/82232 using an autocatalytic reaction, e.g. exothermic brazing
- 2224/82234 using means for applying energy being within the device, e.g. integrated heater
- 2224/82236 using electro-static corona discharge
- 2224/82237 using electron beam, ([electron beam in general B23K 15/00](#))
- 2224/82238 using electric resistance welding, i.e. ohmic heating
- 2224/8234 Bonding interfaces of the connector
- 2224/82345 Shape, e.g. interlocking features
- 2224/82355 having an external coating, e.g. protective bond-through coating
- 2224/82359 Material
- 2224/8236 Bonding interfaces of the semiconductor or solid state body
- 2224/82365 Shape, e.g. interlocking features
- 2224/82375 having an external coating, e.g. protective bond-through coating
- 2224/82379 Material
- 2224/8238 Bonding interfaces outside the semiconductor or solid-state body
- 2224/82385 Shape, e.g. interlocking features
- 2224/82395 having an external coating, e.g. protective bond-through coating
- 2224/82399 Material
- 2224/828 Bonding techniques
- 2224/82801 Soldering or alloying
- 2224/82805 involving forming a eutectic alloy at the bonding interface
- 2224/8281 involving forming an intermetallic compound at the bonding interface
- 2224/82815 Reflow soldering
- 2224/8282 Diffusion bonding
- 2224/82825 Solid-liquid interdiffusion
- 2224/8283 Solid-solid interdiffusion
- 2224/8284 Sintering
- 2224/8285 using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
- 2224/82855 Hardening the adhesive by curing, i.e. thermosetting
- 2224/82856 Pre-cured adhesive, i.e. B-stage adhesive
- 2224/82859 Localised curing of parts of the connector
- 2224/82862 Heat curing
- 2224/82865 Microwave curing
- 2224/82868 Infrared [IR] curing
- 2224/82871 Visible light curing
- 2224/82874 Ultraviolet [UV] curing
- 2224/82877 Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
- 2224/8288 Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
- 2224/82885 Combinations of two or more hardening methods provided for in at least two different groups from [H01L 2224/82855](#) - [H01L 2224/8288](#), e.g. for hybrid thermoplastic-thermosetting adhesives
- 2224/8289 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/82893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/82895 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/82896 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding

2224/82897	between electrically insulating surfaces, e.g. oxide or nitride layers	2224/83047	by mechanical means, e.g. severing, pressing, stamping
2224/82899	Combinations of bonding methods provided for in at least two different groups from H01L 2224/828 - H01L 2224/82897	2224/83048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
2224/829	involving monitoring, e.g. feedback loop	2224/83051	Forming additional members, e.g. dam structures
2224/82909	Post-treatment of the connector or the bonding area	2224/83052	Detaching layer connectors, e.g. after testing (unsoldering in general B23K 1/018)
2224/8291	Cleaning, e.g. oxide removal step, desmearing	2224/83053	Bonding environment
2224/8293	Reshaping	2224/83054	Composition of the atmosphere
2224/82931	by chemical means, e.g. etching, anodisation	2224/83055	being oxidating
2224/82935	by heating means	2224/83065	being reducing
2224/82939	using a laser	2224/83075	being inert
2224/82945	using a corona discharge, e.g. electronic flame off [EFO]	2224/83085	being a liquid, e.g. for fluidic self-assembly
2224/82947	by mechanical means, e.g. severing, pressing, stamping	2224/8309	Vacuum
2224/82948	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling	2224/83091	Under pressure
2224/82951	Forming additional members	2224/83092	Atmospheric pressure
2224/82986	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence	2224/83093	Transient conditions, e.g. gas-flow
2224/83	using a layer connector	2224/83095	Temperature settings
2224/83001	involving a temporary auxiliary member not forming part of the bonding apparatus	2224/83096	Transient conditions
2224/83002	being a removable or sacrificial coating	2224/83097	Heating
2224/83005	being a temporary or sacrificial substrate	2224/83098	Cooling
2224/83007	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the layer connector during or after the bonding process	2224/83099	Ambient temperature
2224/83009	Pre-treatment of the layer connector or the bonding area	2224/831	the layer connector being supplied to the parts to be connected in the bonding apparatus
2224/8301	Cleaning the layer connector, e.g. oxide removal step, desmearing	2224/83101	as prepeg comprising a layer connector, e.g. provided in an insulating plate member
2224/83011	Chemical cleaning, e.g. etching, flux	2224/83102	using surface energy, e.g. capillary forces
2224/83012	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/83104	by applying pressure, e.g. by injection
2224/83013	Plasma cleaning	2224/8311	involving protection against electrical discharge, e.g. removing electrostatic charge
2224/83014	Thermal cleaning, e.g. decomposition, sublimation	2224/8312	Aligning
2224/83019	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8301 - H01L 2224/83014	2224/83121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
2224/8302	Applying permanent coating to the layer connector in the bonding apparatus, e.g. in-situ coating	2224/83122	by detecting inherent features of, or outside, the semiconductor or solid-state body
2224/83022	Cleaning the bonding area, e.g. oxide removal step, desmearing	2224/83123	Shape or position of the body
2224/83024	Applying flux to the bonding area	2224/83125	Bonding areas on the body
2224/83026	Applying a precursor material to the bonding area	2224/83127	Bonding areas outside the body
2224/8303	Reshaping the layer connector in the bonding apparatus, e.g. flattening the layer connector	2224/83129	Shape or position of the other item
2224/83031	by chemical means, e.g. etching, anodisation	2224/8313	using marks formed on the semiconductor or solid-state body
2224/83035	by heating means	2224/83132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
2224/83037	using a polychromatic heating lamp	2224/83136	involving guiding structures, e.g. spacers or supporting members
2224/83039	using a laser	2224/83138	the guiding structures being at least partially left in the finished device
2224/83041	Induction heating, i.e. eddy currents	2224/83139	Guiding structures on the body
			2224/8314	Guiding structures outside the body
			2224/83141	Guiding structures both on and outside the body
			2224/83143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
			2224/83148	involving movement of a part of the bonding apparatus
			2224/83149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
			2224/8315	Rotational movements

2224/8316	Translational movements	2224/83385	Shape, e.g. interlocking features
2224/83169	being the upper part of the bonding apparatus, i.e. bonding head	2224/83395	having an external coating, e.g. protective bond-through coating
2224/8317	Rotational movements	2224/83399	Material
2224/8318	Translational movements	2224/834	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/8319	Arrangement of the layer connectors prior to mounting	2224/83401	the principal constituent melting at a temperature of less than 400°C
2224/83191	wherein the layer connectors are disposed only on the semiconductor or solid-state body	2224/83405	Gallium [Ga] as principal constituent
2224/83192	wherein the layer connectors are disposed only on another item or body to be connected to the semiconductor or solid-state body	2224/83409	Indium [In] as principal constituent
2224/83193	wherein the layer connectors are disposed on both the semiconductor or solid-state body and another item or body to be connected to the semiconductor or solid-state body	2224/83411	Tin [Sn] as principal constituent
2224/83194	Lateral distribution of the layer connectors	2224/83413	Bismuth [Bi] as principal constituent
2224/832	Applying energy for connecting	2224/83414	Thallium [Tl] as principal constituent
2224/83201	Compression bonding	2224/83416	Lead [Pb] as principal constituent
2224/83203	Thermocompression bonding, e.g. diffusion bonding, pressure joining, thermocompression welding or solid-state welding	2224/83417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/83204	with a graded temperature profile	2224/83418	Zinc [Zn] as principal constituent
2224/83205	Ultrasonic bonding	2224/8342	Antimony [Sb] as principal constituent
2224/83206	Direction of oscillation	2224/83423	Magnesium [Mg] as principal constituent
2224/83207	Thermosonic bonding	2224/83424	Aluminium [Al] as principal constituent
2224/83208	applying unidirectional static pressure	2224/83438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/83209	applying isostatic pressure, e.g. degassing using vacuum or a pressurised liquid	2224/83439	Silver [Ag] as principal constituent
2224/8321	using a reflow oven	2224/83444	Gold [Au] as principal constituent
2224/83211	with a graded temperature profile	2224/83447	Copper [Cu] as principal constituent
2224/8322	with energy being in the form of electromagnetic radiation	2224/83449	Manganese [Mn] as principal constituent
2224/83222	Induction heating, i.e. eddy currents	2224/83455	Nickel [Ni] as principal constituent
2224/83224	using a laser	2224/83457	Cobalt [Co] as principal constituent
2224/8323	Polychromatic or infrared lamp heating	2224/8346	Iron [Fe] as principal constituent
2224/83232	using an autocatalytic reaction, e.g. exothermic brazing	2224/83463	the principal constituent melting at a temperature of greater than 1550°C
2224/83234	using means for applying energy being within the device, e.g. integrated heater	2224/83464	Palladium [Pd] as principal constituent
2224/83236	using electro-static corona discharge	2224/83466	Titanium [Ti] as principal constituent
2224/83237	using an electron beam (electron beam welding in general B23K 15/00)	2224/83469	Platinum [Pt] as principal constituent
2224/83238	using electric resistance welding, i.e. ohmic heating	2224/8347	Zirconium [Zr] as principal constituent
2224/8334	Bonding interfaces of the layer connector	2224/83471	Chromium [Cr] as principal constituent
2224/83345	Shape, e.g. interlocking features	2224/83472	Vanadium [V] as principal constituent
2224/83355	having an external coating, e.g. protective bond-through coating	2224/83473	Rhodium [Rh] as principal constituent
2224/83359	Material	2224/83476	Ruthenium [Ru] as principal constituent
2224/8336	Bonding interfaces of the semiconductor or solid state body	2224/83478	Iridium [Ir] as principal constituent
2224/83365	Shape, e.g. interlocking features	2224/83479	Niobium [Nb] as principal constituent
2224/83375	having an external coating, e.g. protective bond-through coating	2224/8348	Molybdenum [Mo] as principal constituent
2224/83379	Material (material of the layer connector prior to the connecting process H01L 2224/29099 and H01L 2224/29599, and subgroups)	2224/83481	Tantalum [Ta] as principal constituent
2224/8338	Bonding interfaces outside the semiconductor or solid-state body	2224/83483	Rhenium [Re] as principal constituent
			2224/83484	Tungsten [W] as principal constituent
			2224/83486	with a principal constituent of the material being a non metallic, non metalloid inorganic material

2224/83487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83488)	2224/83547	Copper [Cu] as principal constituent
2224/83488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/83549	Manganese [Mn] as principal constituent
2224/8349	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/83555	Nickel [Ni] as principal constituent
2224/83491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/83557	Cobalt [Co] as principal constituent
2224/83493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/834 - H01L 2224/83491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/8356	Iron [Fe] as principal constituent
2224/83494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/834 - H01L 2224/83491	2224/83563	the principal constituent melting at a temperature of greater than 1550°C
2224/83495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/834 - H01L 2224/83491	2224/83564	Palladium [Pd] as principal constituent
2224/83498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/83566	Titanium [Ti] as principal constituent
2224/83499	Material of the matrix	2224/83569	Platinum [Pt] as principal constituent
2224/835	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/8357	Zirconium [Zr] as principal constituent
2224/83501	the principal constituent melting at a temperature of less than 400°C	2224/83571	Chromium [Cr] as principal constituent
2224/83505	Gallium [Ga] as principal constituent	2224/83572	Vanadium [V] as principal constituent
2224/83509	Indium [In] as principal constituent	2224/83573	Rhodium [Rh] as principal constituent
2224/83511	Tin [Sn] as principal constituent	2224/83576	Ruthenium [Ru] as principal constituent
2224/83513	Bismuth [Bi] as principal constituent	2224/83578	Iridium [Ir] as principal constituent
2224/83514	Thallium [Tl] as principal constituent	2224/83579	Niobium [Nb] as principal constituent
2224/83516	Lead [Pb] as principal constituent	2224/8358	Molybdenum [Mo] as principal constituent
2224/83517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/83581	Tantalum [Ta] as principal constituent
2224/83518	Zinc [Zn] as principal constituent	2224/83583	Rhenium [Re] as principal constituent
2224/8352	Antimony [Sb] as principal constituent	2224/83584	Tungsten [W] as principal constituent
2224/83523	Magnesium [Mg] as principal constituent	2224/83586	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/83524	Aluminium [Al] as principal constituent	2224/83587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83588)
2224/83538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/83588	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/83539	Silver [Ag] as principal constituent	2224/8359	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/83544	Gold [Au] as principal constituent	2224/83591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
			2224/83593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/835 - H01L 2224/83591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/83594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/835 - H01L 2224/83591	2224/83664	Palladium [Pd] as principal constituent
2224/83595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/835 - H01L 2224/83591	2224/83666	Titanium [Ti] as principal constituent
2224/83598	Fillers	2224/83669	Platinum [Pt] as principal constituent
2224/83599	Base material	2224/8367	Zirconium [Zr] as principal constituent
2224/836	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/83671	Chromium [Cr] as principal constituent
2224/83601	the principal constituent melting at a temperature of less than 400°C	2224/83672	Vanadium [V] as principal constituent
2224/83605	Gallium [Ga] as principal constituent	2224/83673	Rhodium [Rh] as principal constituent
2224/83609	Indium [In] as principal constituent	2224/83676	Ruthenium [Ru] as principal constituent
2224/83611	Tin [Sn] as principal constituent	2224/83678	Iridium [Ir] as principal constituent
2224/83613	Bismuth [Bi] as principal constituent	2224/83679	Niobium [Nb] as principal constituent
2224/83614	Thallium [Tl] as principal constituent	2224/8368	Molybdenum [Mo] as principal constituent
2224/83616	Lead [Pb] as principal constituent	2224/83681	Tantalum [Ta] as principal constituent
2224/83617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/83683	Rhenium [Re] as principal constituent
2224/83618	Zinc [Zn] as principal constituent	2224/83684	Tungsten [W] as principal constituent
2224/8362	Antimony [Sb] as principal constituent	2224/83686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/83623	Magnesium [Mg] as principal constituent	2224/83687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83688)
2224/83624	Aluminium [Al] as principal constituent	2224/83688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/83638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/8369	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/83639	Silver [Ag] as principal constituent	2224/83691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/83644	Gold [Au] as principal constituent	2224/83693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/836 - H01L 2224/83691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/83647	Copper [Cu] as principal constituent	2224/83694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/836 - H01L 2224/83691
2224/83649	Manganese [Mn] as principal constituent	2224/83695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/836 - H01L 2224/83691
2224/83655	Nickel [Ni] as principal constituent	2224/83698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/83657	Cobalt [Co] as principal constituent	2224/83699	Coating material
2224/8366	Iron [Fe] as principal constituent		
2224/83663	the principal constituent melting at a temperature of greater than 1550°C		

2224/837	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/83772	Vanadium [V] as principal constituent
2224/83701	the principal constituent melting at a temperature of less than 400°C	2224/83773	Rhodium [Rh] as principal constituent
2224/83705	Gallium [Ga] as principal constituent	2224/83776	Ruthenium [Ru] as principal constituent
2224/83709	Indium [In] as principal constituent	2224/83778	Iridium [Ir] as principal constituent
2224/83711	Tin [Sn] as principal constituent	2224/83779	Niobium [Nb] as principal constituent
2224/83713	Bismuth [Bi] as principal constituent	2224/8378	Molybdenum [Mo] as principal constituent
2224/83714	Thallium [Tl] as principal constituent	2224/83781	Tantalum [Ta] as principal constituent
2224/83716	Lead [Pb] as principal constituent	2224/83783	Rhenium [Re] as principal constituent
2224/83717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/83784	Tungsten [W] as principal constituent
2224/83718	Zinc [Zn] as principal constituent	2224/83786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/8372	Antimony [Sb] as principal constituent	2224/83787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83788)
2224/83723	Magnesium [Mg] as principal constituent	2224/83788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/83724	Aluminium [Al] as principal constituent	2224/8379	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/83738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/83791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/83739	Silver [Ag] as principal constituent	2224/83793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/837 - H01L 2224/83791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/83744	Gold [Au] as principal constituent	2224/83794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/837 - H01L 2224/83791
2224/83747	Copper [Cu] as principal constituent	2224/83795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/837 - H01L 2224/83791
2224/83749	Manganese [Mn] as principal constituent	2224/83798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/83755	Nickel [Ni] as principal constituent	2224/83799	Shape or distribution of the fillers
2224/83757	Cobalt [Co] as principal constituent	2224/838	Bonding techniques
2224/8376	Iron [Fe] as principal constituent	2224/83801	Soldering or alloying
2224/83763	the principal constituent melting at a temperature of greater than 1550°C	2224/83805	involving forming a eutectic alloy at the bonding interface
2224/83764	Palladium [Pd] as principal constituent	2224/8381	involving forming an intermetallic compound at the bonding interface
2224/83766	Titanium [Ti] as principal constituent	2224/83815	Reflow soldering
2224/83769	Platinum [Pt] as principal constituent	2224/8382	Diffusion bonding
2224/8377	Zirconium [Zr] as principal constituent	2224/83825	Solid-liquid interdiffusion
2224/83771	Chromium [Cr] as principal constituent		

2224/8383	Solid-solid interdiffusion	2224/83901	Pressing the layer connector against the bonding areas by means of another connector
2224/8384	Sintering	2224/83902	by means of another layer connector
2224/8385	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester	2224/83903	by means of a bump connector
2224/83851	being an anisotropic conductive adhesive	2224/83904	by means of an encapsulation layer or foil
2224/83855	Hardening the adhesive by curing, i.e. thermosetting	2224/83905	Combinations of bonding methods provided for in at least two different groups from H01L 2224/838 - H01L 2224/83904
2224/83856	Pre-cured adhesive, i.e. B-stage adhesive	2224/83906	Specific sequence of method steps
2224/83859	Localised curing of parts of the layer connector	2224/83907	Intermediate bonding, i.e. intermediate bonding step for temporarily bonding the semiconductor or solid-state body, followed by at least a further bonding step
2224/83862	Heat curing	2224/83908	involving monitoring, e.g. feedback loop
2224/83865	Microwave curing	2224/83909	Post-treatment of the layer connector or bonding area
2224/83868	Infrared [IR] curing	2224/8391	Cleaning, e.g. oxide removal step, desmearing
2224/83871	Visible light curing	2224/83911	Chemical cleaning, e.g. etching, flux
2224/83874	Ultraviolet [UV] curing	2224/83912	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
2224/83877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes	2224/83913	Plasma cleaning
2224/8388	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives	2224/83914	Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
2224/83885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/83855 - H01L 2224/8388 , e.g. for hybrid thermoplastic-thermosetting adhesives	2224/83919	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8391 - H01L 2224/83914
2224/83886	Involving a self-assembly process, e.g. self-agglomeration of a material dispersed in a fluid	2224/8392	Applying permanent coating, e.g. protective coating
2224/83887	Auxiliary means therefor, e.g. for self-assembly activation	2224/8393	Reshaping
2224/83888	with special adaptation of the surface of the body to be connected, e.g. surface shape specially adapted for the self-assembly process	2224/83931	by chemical means, e.g. etching
2224/83889	involving the material of the bonding area, e.g. bonding pad	2224/83935	by heating means, e.g. reflowing
2224/8389	using an inorganic non metallic glass type adhesive, e.g. solder glass	2224/83937	using a polychromatic heating lamp
2224/83893	Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond	2224/83939	using a laser
2224/83894	Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces	2224/83941	Induction heating, i.e. eddy currents
2224/83895	between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding	2224/83943	using a flame torch, e.g. hydrogen torch
2224/83896	between electrically insulating surfaces, e.g. oxide or nitride layers	2224/83945	using a corona discharge, e.g. electronic flame off [EFO]
2224/83897	Mechanical interlocking, e.g. anchoring, hook and loop-type fastening or the like	2224/83947	by mechanical means, e.g. "pull-and-cut", pressing, stamping
2224/83898	Press-fitting, i.e. pushing the parts together and fastening by friction, e.g. by compression of one part against the other	2224/83948	Thermal treatments, e.g. annealing, controlled cooling
2224/83899	using resilient parts in the layer connector or in the bonding area	2224/83951	Forming additional members, e.g. for reinforcing, fillet sealant
2224/839	with the layer connector not providing any mechanical bonding	2224/83986	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
			2224/84	using a strap connector
			2224/84001	involving a temporary auxiliary member not forming part of the bonding apparatus
			2224/84002	being a removable or sacrificial coating
			2224/84005	being a temporary substrate
			2224/84007	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the strap connector during or after the bonding process
			2224/84009	Pre-treatment of the connector and/or the bonding area
			2224/8401	Cleaning, e.g. oxide removal step, desmearing
			2224/84011	Chemical cleaning, e.g. etching, flux

- 2224/84012 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/84013 Plasma cleaning
- 2224/84014 Thermal cleaning, e.g. decomposition, sublimation
- 2224/84019 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8401](#) - [H01L 2224/84014](#)
- 2224/8402 Applying permanent coating, e.g. in-situ coating
- 2224/8403 Reshaping
- 2224/84031 by chemical means, e.g. etching, anodisation
- 2224/84035 by heating means, e.g. "free-air-ball"
- 2224/84037 using a polychromatic heating lamp
- 2224/84039 using a laser
- 2224/84041 Induction heating, i.e. eddy currents
- 2224/84043 using a flame torch, e.g. hydrogen torch
- 2224/84045 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/84047 by mechanical means, e.g. severing, pressing, stamping
- 2224/84048 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/84051 Forming additional members
- 2224/84053 . . . Bonding environment
- 2224/84054 Composition of the atmosphere
- 2224/84055 being oxidating
- 2224/84065 being reducing
- 2224/84075 being inert
- 2224/84085 being a liquid (e.g. for fluidic self-assembly)
- 2224/8409 Vacuum
- 2224/84091 Under pressure
- 2224/84092 Atmospheric pressure
- 2224/84093 Transient conditions, e.g. gas-flow
- 2224/84095 Temperature settings
- 2224/84096 Transient conditions
- 2224/84097 Heating
- 2224/84098 Cooling
- 2224/84099 Ambient temperature
- 2224/841 . . . the connector being supplied to the parts to be connected in the bonding apparatus
- 2224/8411 . . . involving protection against electrical discharge, e.g. removing electrostatic charge
- 2224/8412 . . . Aligning
- 2224/84121 . . . Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
- 2224/84122 by detecting inherent features of, or outside, the semiconductor or solid-state body
- 2224/84123 Shape or position of the body
- 2224/84125 Bonding areas on the body
- 2224/84127 Bonding areas outside the body
- 2224/84129 Shape or position of the other item
- 2224/8413 using marks formed on the semiconductor or solid-state body
- 2224/84132 using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
- 2224/84136 involving guiding structures, e.g. spacers or supporting members
- 2224/84138 the guiding structures being at least partially left in the finished device
- 2224/84143 Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
- 2224/84148 involving movement of a part of the bonding apparatus
- 2224/84149 being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
- 2224/8415 Rotational movements
- 2224/8416 Translational movements
- 2224/84169 being the upper part of the bonding apparatus, i.e. bonding head,
- 2224/8417 Rotational movements
- 2224/8418 Translational movements
- 2224/84181 connecting first on the semiconductor or solid-state body, i.e. on-chip, regular stitch
- 2224/84186 connecting first outside the semiconductor or solid-state body, i.e. off-chip, reverse stitch
- 2224/84191 connecting first both on and outside the semiconductor or solid-state body, i.e. regular and reverse stitches
- 2224/84196 involving intermediate connecting steps before cutting the strap connector
- 2224/842 . . . Applying energy for connecting
- 2224/84201 Compression bonding
- 2224/84203 Thermocompression bonding
- 2224/84205 Ultrasonic bonding
- 2224/84206 Direction of oscillation
- 2224/84207 Thermosonic bonding
- 2224/8421 with energy being in the form of electromagnetic radiation
- 2224/84212 Induction heating, i.e. eddy currents
- 2224/84214 using a laser
- 2224/8423 Polychromatic or infrared lamp heating
- 2224/84232 using an autocatalytic reaction, e.g. exothermic brazing
- 2224/84234 using means for applying energy being within the device, e.g. integrated heater
- 2224/84236 using electro-static corona discharge
- 2224/84237 using an electron beam ([electron beam welding in general B23K 15/00](#))
- 2224/84238 using electric resistance welding, i.e. ohmic heating
- 2224/8434 . . . Bonding interfaces of the connector
- 2224/84345 Shape, e.g. interlocking features
- 2224/84355 having an external coating, e.g. protective bond-through coating
- 2224/84359 Material
- 2224/8436 . . . Bonding interfaces of the semiconductor or solid state body
- 2224/84365 Shape, e.g. interlocking features
- 2224/84375 having an external coating, e.g. protective bond-through coating
- 2224/84379 Material
- 2224/8438 . . . Bonding interfaces outside the semiconductor or solid-state body
- 2224/84385 Shape, e.g. interlocking features

2224/84395	having an external coating, e.g. protective bond-through coating	2224/84487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84488)
2224/84399	Material	2224/84488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/844	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/8449	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/84401	the principal constituent melting at a temperature of less than 400°C	2224/84491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/84405	Gallium [Ga] as principal constituent	2224/84493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/844 - H01L 2224/84491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/84409	Indium [In] as principal constituent	2224/84494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/844 - H01L 2224/84491
2224/84411	Tin [Sn] as principal constituent	2224/84495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/844 - H01L 2224/84491
2224/84413	Bismuth [Bi] as principal constituent	2224/84498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/84414	Thallium [Tl] as principal constituent	2224/84499	Material of the matrix
2224/84416	Lead [Pb] as principal constituent	2224/845	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/84417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/84501	the principal constituent melting at a temperature of less than 400°C
2224/84418	Zinc [Zn] as principal constituent	2224/84505	Gallium [Ga] as principal constituent
2224/8442	Antimony [Sb] as principal constituent	2224/84509	Indium [In] as principal constituent
2224/84423	Magnesium [Mg] as principal constituent	2224/84511	Tin [Sn] as principal constituent
2224/84424	Aluminium [Al] as principal constituent	2224/84513	Bismuth [Bi] as principal constituent
2224/84438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/84514	Thallium [Tl] as principal constituent
2224/84439	Silver [Ag] as principal constituent	2224/84516	Lead [Pb] as principal constituent
2224/84444	Gold [Au] as principal constituent	2224/84517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/84447	Copper [Cu] as principal constituent	2224/84518	Zinc [Zn] as principal constituent
2224/84449	Manganese [Mn] as principal constituent	2224/8452	Antimony [Sb] as principal constituent
2224/84455	Nickel [Ni] as principal constituent	2224/84523	Magnesium [Mg] as principal constituent
2224/84457	Cobalt [Co] as principal constituent	2224/84524	Aluminium [Al] as principal constituent
2224/8446	Iron [Fe] as principal constituent	2224/84538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/84463	the principal constituent melting at a temperature of greater than 1550°C	2224/84539	Silver [Ag] as principal constituent
2224/84464	Palladium [Pd] as principal constituent	2224/84544	Gold [Au] as principal constituent
2224/84466	Titanium [Ti] as principal constituent			
2224/84469	Platinum [Pt] as principal constituent			
2224/8447	Zirconium [Zr] as principal constituent			
2224/84471	Chromium [Cr] as principal constituent			
2224/84472	Vanadium [V] as principal constituent			
2224/84473	Rhodium [Rh] as principal constituent			
2224/84476	Ruthenium [Ru] as principal constituent			
2224/84478	Iridium [Ir] as principal constituent			
2224/84479	Niobium [Nb] as principal constituent			
2224/8448	Molybdenum [Mo] as principal constituent			
2224/84481	Tantalum [Ta] as principal constituent			
2224/84483	Rhenium [Re] as principal constituent			
2224/84484	Tungsten [W] as principal constituent			
2224/84486	with a principal constituent of the material being a non metallic, non metalloid inorganic material			

2224/84547	Copper [Cu] as principal constituent	2224/84594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/845 - H01L 2224/84591
2224/84549	Manganese [Mn] as principal constituent	2224/84595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/845 - H01L 2224/84591
2224/84555	Nickel [Ni] as principal constituent	2224/84598	Fillers
2224/84557	Cobalt [Co] as principal constituent	2224/84599	Base material
2224/8456	Iron [Fe] as principal constituent	2224/846	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/84563	the principal constituent melting at a temperature of greater than 1550°C	2224/84601	the principal constituent melting at a temperature of less than 400°C
2224/84564	Palladium [Pd] as principal constituent	2224/84605	Gallium [Ga] as principal constituent
2224/84566	Titanium [Ti] as principal constituent	2224/84609	Indium [In] as principal constituent
2224/84569	Platinum [Pt] as principal constituent	2224/84611	Tin [Sn] as principal constituent
2224/8457	Zirconium [Zr] as principal constituent	2224/84613	Bismuth [Bi] as principal constituent
2224/84571	Chromium [Cr] as principal constituent	2224/84614	Thallium [Tl] as principal constituent
2224/84572	Vanadium [V] as principal constituent	2224/84616	Lead [Pb] as principal constituent
2224/84573	Rhodium [Rh] as principal constituent	2224/84617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/84576	Ruthenium [Ru] as principal constituent	2224/84618	Zinc [Zn] as principal constituent
2224/84578	Iridium [Ir] as principal constituent	2224/8462	Antimony [Sb] as principal constituent
2224/84579	Niobium [Nb] as principal constituent	2224/84623	Magnesium [Mg] as principal constituent
2224/8458	Molybdenum [Mo] as principal constituent	2224/84624	Aluminium [Al] as principal constituent
2224/84581	Tantalum [Ta] as principal constituent	2224/84638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/84583	Rhenium [Re] as principal constituent	2224/84639	Silver [Ag] as principal constituent
2224/84584	Tungsten [W] as principal constituent	2224/84644	Gold [Au] as principal constituent
2224/84586	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/84647	Copper [Cu] as principal constituent
2224/84587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84588)	2224/84649	Manganese [Mn] as principal constituent
2224/84588	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/84655	Nickel [Ni] as principal constituent
2224/8459	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/84657	Cobalt [Co] as principal constituent
2224/84591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/8466	Iron [Fe] as principal constituent
2224/84593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/845 - H01L 2224/84591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/84663	the principal constituent melting at a temperature of greater than 1550°C

2224/84664	Palladium [Pd] as principal constituent	2224/847	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/84666	Titanium [Ti] as principal constituent	2224/84701	the principal constituent melting at a temperature of less than 400°C
2224/84669	Platinum [Pt] as principal constituent	2224/84705	Gallium [Ga] as principal constituent
2224/8467	Zirconium [Zr] as principal constituent	2224/84709	Indium [In] as principal constituent
2224/84671	Chromium [Cr] as principal constituent	2224/84711	Tin [Sn] as principal constituent
2224/84672	Vanadium [V] as principal constituent	2224/84713	Bismuth [Bi] as principal constituent
2224/84673	Rhodium [Rh] as principal constituent	2224/84714	Thallium [Tl] as principal constituent
2224/84676	Ruthenium [Ru] as principal constituent	2224/84716	Lead [Pb] as principal constituent
2224/84678	Iridium [Ir] as principal constituent	2224/84717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/84679	Niobium [Nb] as principal constituent	2224/84718	Zinc [Zn] as principal constituent
2224/8468	Molybdenum [Mo] as principal constituent	2224/8472	Antimony [Sb] as principal constituent
2224/84681	Tantalum [Ta] as principal constituent	2224/84723	Magnesium [Mg] as principal constituent
2224/84683	Rhenium [Re] as principal constituent	2224/84724	Aluminium [Al] as principal constituent
2224/84684	Tungsten [W] as principal constituent	2224/84738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/84686	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/84739	Silver [Ag] as principal constituent
2224/84687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84688)	2224/84744	Gold [Au] as principal constituent
2224/84688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/84747	Copper [Cu] as principal constituent
2224/8469	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/84749	Manganese [Mn] as principal constituent
2224/84691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/84755	Nickel [Ni] as principal constituent
2224/84693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/846 - H01L 2224/84691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/84757	Cobalt [Co] as principal constituent
2224/84694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/846 - H01L 2224/84691	2224/8476	Iron [Fe] as principal constituent
2224/84695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/846 - H01L 2224/84691	2224/84763	the principal constituent melting at a temperature of greater than 1550°C
2224/84698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/84764	Palladium [Pd] as principal constituent
2224/84699	Coating material	2224/84766	Titanium [Ti] as principal constituent
		2224/84769	Platinum [Pt] as principal constituent
		2224/8477	Zirconium [Zr] as principal constituent
		2224/84771	Chromium [Cr] as principal constituent

2224/84772	Vanadium [V] as principal constituent	2224/8483	Solid-solid interdiffusion
2224/84773	Rhodium [Rh] as principal constituent	2224/8484	Sintering
2224/84776	Ruthenium [Ru] as principal constituent	2224/8485	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
2224/84778	Iridium [Ir] as principal constituent	2224/84855	Hardening the adhesive by curing, i.e. thermosetting
2224/84779	Niobium [Nb] as principal constituent	2224/84856	Pre-cured adhesive, i.e. B-stage adhesive
2224/8478	Molybdenum [Mo] as principal constituent	2224/84859	Localised curing of parts of the connector
2224/84781	Tantalum [Ta] as principal constituent	2224/84862	Heat curing
2224/84783	Rhenium [Re] as principal constituent	2224/84865	Microwave curing
2224/84784	Tungsten [W] as principal constituent	2224/84868	Infrared [IR] curing
2224/84786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/84871	Visible light curing
2224/84787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84788)	2224/84874	Ultraviolet [UV] curing
2224/84788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/84877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
2224/8479	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/8488	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
2224/84791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/84885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/84855 - H01L 2224/8488 , e.g. for hybrid thermoplastic-thermosetting adhesives
2224/84793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/847 - H01L 2224/84791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/8489	using an inorganic non metallic glass type adhesive, e.g. solder glass
2224/84794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/847 - H01L 2224/84791	2224/84893	Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
2224/84795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/847 - H01L 2224/84791	2224/84895	Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
2224/84798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/84897	between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
2224/84799	Shape or distribution of the fillers	2224/84898	between electrically insulating surfaces, e.g. oxide or nitride layersg
2224/848	Bonding techniques	2224/84899	Combinations of bonding methods provided for in at least two different groups from H01L 2224/848 - H01L 2224/84898
2224/84801	Soldering or alloying	2224/849	involving monitoring, e.g. feedback loop
2224/84805	involving forming a eutectic alloy at the bonding interface	2224/84909	Post-treatment of the connector or bonding area
2224/8481	involving forming an intermetallic compound at the bonding interface	2224/8491	Cleaning, e.g. oxide removal step, desmearing
2224/84815	Reflow soldering	2224/84911	Chemical cleaning, e.g. etching, flux
2224/8482	Diffusion bonding	2224/84912	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
2224/84825	Solid-liquid interdiffusion	2224/84913	Plasma cleaning
		2224/84914	Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
		2224/84919	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8491 - H01L 2224/84914
		2224/8492	Applying permanent coating, e.g. protective coating
		2224/8493	Reshaping, e.g. for severing the strap, modifying the loop shape

2224/84931	by chemical means, e.g. etching	2224/85053	Bonding environment
2224/84935	by heating means, e.g. reflowing	2224/85054	Composition of the atmosphere
2224/84937	using a polychromatic heating lamp	2224/85055	being oxidating
2224/84939	using a laser	2224/85065	being reducing
2224/84941	Induction heating, i.e. eddy currents	2224/85075	being inert
2224/84943	using a flame torch, e.g. hydrogen torch	2224/85085	being a liquid, e.g. for fluidic self-assembly
2224/84945	using a corona discharge, e.g. electronic flame off [EFO]	2224/8509	Vacuum
2224/84947	by mechanical means, e.g. pressing, stamping	2224/85091	Under pressure
2224/84948	Thermal treatments, e.g. annealing, controlled cooling	2224/85092	Atmospheric pressure
2224/84951	Forming additional members, e.g. for reinforcing	2224/85093	Transient conditions, e.g. gas-flow
2224/84986	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence	2224/85095	Temperature settings
2224/85	using a wire connector	2224/85096	Transient conditions
2224/85001	involving a temporary auxiliary member not forming part of the bonding apparatus, e.g. removable or sacrificial coating, film or substrate	2224/85097	Heating
2224/85002	being a removable or sacrificial coating	2224/85098	Cooling
2224/85005	being a temporary or sacrificial substrate	2224/85099	Ambient temperature
2224/85007	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the wire connector during or after the bonding process	2224/851	the connector being supplied to the parts to be connected in the bonding apparatus
2224/85009	Pre-treatment of the connector or the bonding area	2224/8511	involving protection against electrical discharge, e.g. removing electrostatic charge
2224/8501	Cleaning, e.g. oxide removal step, desmearing	2224/8512	Aligning
2224/85011	Chemical cleaning, e.g. etching, flux	2224/85121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
2224/85012	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/85122	by detecting inherent features of, or outside, the semiconductor or solid-state body
2224/85013	Plasma cleaning	2224/85123	Shape or position of the body
2224/85014	Thermal cleaning, e.g. decomposition, sublimation	2224/85125	Bonding areas on the body
2224/85016	using a laser	2224/85127	Bonding areas outside the body
2224/85017	Electron beam cleaning	2224/85129	Shape or position of the other item
2224/85019	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8501 - H01L 2224/85014	2224/8513	using marks formed on the semiconductor or solid-state body
2224/8502	Applying permanent coating, e.g. in-situ coating	2224/85132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
2224/8503	Reshaping, e.g. forming the ball or the wedge of the wire connector	2224/85136	involving guiding structures, e.g. spacers or supporting members
2224/85031	by chemical means, e.g. etching, anodisation	2224/85138	the guiding structures being at least partially left in the finished device
2224/85035	by heating means, e.g. "free-air-ball"	2224/85143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
2224/85037	using a polychromatic heating lamp	2224/85148	involving movement of a part of the bonding apparatus
2224/85039	using a laser	2224/85149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
2224/85041	Induction heating, i.e. eddy currents	2224/8515	Rotational movements
2224/85043	using a flame torch, e.g. hydrogen torch	2224/8516	Translational movements
2224/85045	using a corona discharge, e.g. electronic flame off [EFO]	2224/85169	being the upper part of the bonding apparatus, i.e. bonding head, e.g. capillary or wedge
2224/85047	by mechanical means, e.g. severing, pressing, stamping	2224/8517	Rotational movements
2224/85048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling	2224/8518	Translational movements
2224/85051	Forming additional members, e.g. for "wedge-on-ball", "ball-on-wedge", "ball-on-ball" connections	2224/85181	connecting first on the semiconductor or solid-state body, i.e. on-chip, regular stitch
			2224/85186	connecting first outside the semiconductor or solid-state body, i.e. off-chip, reverse stitch
			2224/85191	connecting first both on and outside the semiconductor or solid-state body, i.e. regular and reverse stitches

2224/85196	involving intermediate connecting steps before cutting the wire connector	2224/85438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/852	. . .	Applying energy for connecting	2224/85439	Silver (Ag) as principal constituent
2224/85201	Compression bonding	2224/85444	Gold (Au) as principal constituent
2224/85203	Thermocompression bonding	2224/85447	Copper (Cu) as principal constituent
2224/85205	Ultrasonic bonding	2224/85449	Manganese (Mn) as principal constituent
2224/85206	Direction of oscillation	2224/85455	Nickel (Ni) as principal constituent
2224/85207	Thermosonic bonding	2224/85457	Cobalt (Co) as principal constituent
2224/8521	with energy being in the form of electromagnetic radiation	2224/8546	Iron (Fe) as principal constituent
2224/85212	Induction heating, i.e. eddy currents	2224/85463	the principal constituent melting at a temperature of greater than 1550°C
2224/85214	using a laser	2224/85464	Palladium (Pd) as principal constituent
2224/8523	Polychromatic or infrared lamp heating	2224/85466	Titanium (Ti) as principal constituent
2224/85232	using an autocatalytic reaction, e.g. exothermic brazing	2224/85469	Platinum (Pt) as principal constituent
2224/85234	using means for applying energy being within the device, e.g. integrated heater	2224/8547	Zirconium (Zr) as principal constituent
2224/85236	using electro-static corona discharge	2224/85471	Chromium (Cr) as principal constituent
2224/85237	using electron beam (using electron beam in general B23K 15/00)	2224/85472	Vanadium (V) as principal constituent
2224/85238	using electric resistance welding, i.e. ohmic heating	2224/85473	Rhodium (Rh) as principal constituent
2224/8534	. . .	Bonding interfaces of the connector	2224/85476	Ruthenium (Ru) as principal constituent
2224/85345	Shape, e.g. interlocking features	2224/85478	Iridium (Ir) as principal constituent
2224/85355	having an external coating, e.g. protective bond-through coating	2224/85479	Niobium (Nb) as principal constituent
2224/85359	Material	2224/8548	Molybdenum (Mo) as principal constituent
2224/8536	. . .	Bonding interfaces of the semiconductor or solid state body	2224/85481	Tantalum (Ta) as principal constituent
2224/85365	Shape, e.g. interlocking features	2224/85483	Rhenium (Re) as principal constituent
2224/85375	having an external coating, e.g. protective bond-through coating	2224/85484	Tungsten (W) as principal constituent
2224/85379	Material	2224/85486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/8538	. . .	Bonding interfaces outside the semiconductor or solid-state body	2224/85487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85488)
2224/85385	Shape, e.g. interlocking features	2224/85488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/85395	having an external coating, e.g. protective bond-through coating	2224/8549	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/85399	Material	2224/85491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/854	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/85493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/854 - H01L 2224/85491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/85401	the principal constituent melting at a temperature of less than 400°C	2224/85494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/854 - H01L 2224/85491
2224/85405	Gallium (Ga) as principal constituent	2224/85495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/854 - H01L 2224/85491
2224/85409	Indium (In) as principal constituent	2224/85498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/85411	Tin (Sn) as principal constituent	2224/85499	Material of the matrix
2224/85413	Bismuth (Bi) as principal constituent			
2224/85414	Thallium (Tl) as principal constituent			
2224/85416	Lead (Pb) as principal constituent			
2224/85417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C			
2224/85418	Zinc (Zn) as principal constituent			
2224/8542	Antimony (Sb) as principal constituent			
2224/85423	Magnesium (Mg) as principal constituent			
2224/85424	Aluminium (Al) as principal constituent			

2224/855	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/85578	Iridium (Ir) as principal constituent
2224/85501	the principal constituent melting at a temperature of less than 400°C	2224/85579	Niobium (Nb) as principal constituent
2224/85505	Gallium (Ga) as principal constituent	2224/8558	Molybdenum (Mo) as principal constituent
2224/85509	Indium (In) as principal constituent	2224/85581	Tantalum (Ta) as principal constituent
2224/85511	Tin (Sn) as principal constituent	2224/85583	Rhenium (Re) as principal constituent
2224/85513	Bismuth (Bi) as principal constituent	2224/85584	Tungsten (W) as principal constituent
2224/85514	Thallium (Tl) as principal constituent	2224/85586	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/85516	Lead (Pb) as principal constituent	2224/85587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85588)
2224/85517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/85588	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/85518	Zinc (Zn) as principal constituent	2224/8559	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/8552	Antimony (Sb) as principal constituent	2224/85591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/85523	Magnesium (Mg) as principal constituent	2224/85593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/855 - H01L 2224/85591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/85524	Aluminium (Al) as principal constituent	2224/85594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/855 - H01L 2224/85591
2224/85538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/85595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/855 - H01L 2224/85591
2224/85539	Silver (Ag) as principal constituent	2224/85598	Fillers
2224/85544	Gold (Au) as principal constituent	2224/85599	Base material
2224/85547	Copper (Cu) as principal constituent	2224/856	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/85549	Manganese (Mn) as principal constituent	2224/85601	the principal constituent melting at a temperature of less than 400°C
2224/85555	Nickel (Ni) as principal constituent	2224/85605	Gallium (Ga) as principal constituent
2224/85557	Cobalt (Co) as principal constituent	2224/85609	Indium (In) as principal constituent
2224/8556	Iron (Fe) as principal constituent	2224/85611	Tin (Sn) as principal constituent
2224/85563	the principal constituent melting at a temperature of greater than 1550°C	2224/85613	Bismuth (Bi) as principal constituent
2224/85564	Palladium (Pd) as principal constituent	2224/85614	Thallium (Tl) as principal constituent
2224/85566	Titanium (Ti) as principal constituent	2224/85616	Lead (Pb) as principal constituent
2224/85569	Platinum (Pt) as principal constituent		
2224/8557	Zirconium (Zr) as principal constituent		
2224/85571	Chromium (Cr) as principal constituent		
2224/85572	Vanadium (V) as principal constituent		
2224/85573	Rhodium (Rh) as principal constituent		
2224/85576	Ruthenium (Ru) as principal constituent		

2224/85617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/85687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85688)
2224/85618	Zinc (Zn) as principal constituent	2224/85688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/8562	Antimony (Sb) as principal constituent	2224/8569	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/85623	Magnesium (Mg) as principal constituent	2224/85691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/85624	Aluminium (Al) as principal constituent	2224/85693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/856 - H01L 2224/85691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/85638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/85694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/856 - H01L 2224/85691
2224/85639	Silver (Ag) as principal constituent	2224/85695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/856 - H01L 2224/85691
2224/85644	Gold (Au) as principal constituent	2224/85698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/85647	Copper (Cu) as principal constituent	2224/85699	Coating material
2224/85649	Manganese (Mn) as principal constituent	2224/857	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/85655	Nickel (Ni) as principal constituent	2224/85701	the principal constituent melting at a temperature of less than 400°C
2224/85657	Cobalt (Co) as principal constituent	2224/85705	Gallium (Ga) as principal constituent
2224/8566	Iron (Fe) as principal constituent	2224/85709	Indium (In) as principal constituent
2224/85663	the principal constituent melting at a temperature of greater than 1550°C	2224/85711	Tin (Sn) as principal constituent
2224/85664	Palladium (Pd) as principal constituent	2224/85713	Bismuth (Bi) as principal constituent
2224/85666	Titanium (Ti) as principal constituent	2224/85714	Thallium (Tl) as principal constituent
2224/85669	Platinum (Pt) as principal constituent	2224/85716	Lead (Pb) as principal constituent
2224/8567	Zirconium (Zr) as principal constituent	2224/85717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/85671	Chromium (Cr) as principal constituent	2224/85718	Zinc (Zn) as principal constituent
2224/85672	Vanadium (V) as principal constituent	2224/8572	Antimony (Sb) as principal constituent
2224/85673	Rhodium (Rh) as principal constituent	2224/85723	Magnesium (Mg) as principal constituent
2224/85676	Ruthenium (Ru) as principal constituent		
2224/85678	Iridium (Ir) as principal constituent		
2224/85679	Niobium (Nb) as principal constituent		
2224/8568	Molybdenum (Mo) as principal constituent		
2224/85681	Tantalum (Ta) as principal constituent		
2224/85683	Rhenium (Re) as principal constituent		
2224/85684	Tungsten (W) as principal constituent		
2224/85686	with a principal constituent of the material being a non metallic, non metalloid inorganic material		

2224/85724	Aluminium (Al) as principal constituent	2224/85791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/85738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/85793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/857 - H01L 2224/85791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/85739	Silver (Ag) as principal constituent	2224/85794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/857 - H01L 2224/85791
2224/85744	Gold (Au) as principal constituent	2224/85795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/857 - H01L 2224/85791
2224/85747	Copper (Cu) as principal constituent	2224/85798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/85749	Manganese (Mn) as principal constituent	2224/85799	Shape or distribution of the fillers
2224/85755	Nickel (Ni) as principal constituent	2224/858	Bonding techniques
2224/85757	Cobalt (Co) as principal constituent	2224/85801	Soldering or alloying
2224/8576	Iron (Fe) as principal constituent	2224/85805	involving forming a eutectic alloy at the bonding interface
2224/85763	the principal constituent melting at a temperature of greater than 1550°C	2224/8581	involving forming an intermetallic compound at the bonding interface
2224/85764	Palladium (Pd) as principal constituent	2224/85815	Reflow soldering
2224/85766	Titanium (Ti) as principal constituent	2224/8582	Diffusion bonding
2224/85769	Platinum (Pt) as principal constituent	2224/85825	Solid-liquid interdiffusion
2224/8577	Zirconium (Zr) as principal constituent	2224/8583	Solid-solid interdiffusion, e.g. "direct bonding"
2224/85771	Chromium (Cr) as principal constituent	2224/8584	Sintering
2224/85772	Vanadium (V) as principal constituent	2224/8585	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
2224/85773	Rhodium (Rh) as principal constituent	2224/85855	Hardening the adhesive by curing, i.e. thermosetting
2224/85776	Ruthenium (Ru) as principal constituent	2224/85856	Pre-cured adhesive, i.e. B-stage adhesive
2224/85778	Iridium (Ir) as principal constituent	2224/85859	Localised curing of parts of the connector
2224/85779	Niobium (Nb) as principal constituent	2224/85862	Heat curing
2224/8578	Molybdenum (Mo) as principal constituent	2224/85865	Microwave curing
2224/85781	Tantalum (Ta) as principal constituent	2224/85868	Infrared [IR] curing
2224/85783	Rhenium (Re) as principal constituent	2224/85871	Visible light curing
2224/85784	Tungsten (W) as principal constituent	2224/85874	Ultraviolet [UV] curing
2224/85786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/85877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
2224/85787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85788)	2224/8588	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
2224/85788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/85885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/85855 - H01L 2224/8588 , e.g. for hybrid thermoplastic-thermosetting adhesives
2224/8579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/8589	using an inorganic non metallic glass type adhesive, e.g. solder glass

- 2224/85893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/85895 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/85897 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/85898 between electrically insulating surfaces, e.g. oxide or nitride layers
- 2224/85899 Combinations of bonding methods provided for in at least two different groups from [H01L 2224/858](#) - [H01L 2224/85898](#)
- 2224/859 involving monitoring, e.g. feedback loop
- 2224/85909 Post-treatment of the connector or wire bonding area
- 2224/8591 Cleaning, e.g. oxide removal step, desmearing
- 2224/85911 Chemical cleaning, e.g. etching, flux
- 2224/85912 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/85913 Plasma cleaning
- 2224/85914 Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
- 2224/85916 using a laser
- 2224/85917 Electron beam cleaning
- 2224/85919 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8591](#) - [H01L 2224/85914](#)
- 2224/8592 Applying permanent coating, e.g. protective coating
- 2224/8593 Reshaping, e.g. for severing the wire, modifying the wedge or ball or the loop shape
- 2224/85931 by chemical means, e.g. etching
- 2224/85935 by heating means, e.g. reflowing
- 2224/85937 using a polychromatic heating lamp
- 2224/85939 using a laser
- 2224/85941 Induction heating, i.e. eddy currents
- 2224/85943 using a flame torch, e.g. hydrogen torch
- 2224/85945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/85947 by mechanical means, e.g. "pull-and-cut", pressing, stamping
- 2224/85948 Thermal treatments, e.g. annealing, controlled cooling
- 2224/85951 Forming additional members, e.g. for reinforcing
- 2224/85986 Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
- 2224/86 using tape automated bonding [TAB]
- 2224/86001 involving a temporary auxiliary member not forming part of the bonding apparatus
- 2224/86002 being a removable or sacrificial coating
- 2224/86005 being a temporary or sacrificial substrate
- 2224/86007 involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the TAB connector during or after the bonding process
- 2224/86009 Pre-treatment of the connector or the bonding area
- 2224/8601 Cleaning, e.g. oxide removal step, desmearing
- 2224/8603 Reshaping
- 2224/86031 by chemical means, e.g. etching, anodisation
- 2224/86035 by heating
- 2224/86039 using a laser
- 2224/86045 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/86047 by mechanical means, e.g. severing, pressing, stamping
- 2224/86048 Thermal treatment, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/86051 Forming additional members
- 2224/86053 Bonding environment
- 2224/86054 Composition of the atmosphere
- 2224/86085 being a liquid, e.g. fluidic self-assembly
- 2224/8609 Vacuum
- 2224/86091 Under pressure
- 2224/86095 Temperature settings
- 2224/86096 Transient conditions
- 2224/86097 Heating
- 2224/86098 Cooling
- 2224/86099 Ambient temperature
- 2224/861 the connector being supplied to the parts to be connected in the bonding apparatus
- 2224/8611 involving protection against electrical discharge, e.g. removing electrostatic charge
- 2224/8612 Aligning
- 2224/86121 Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
- 2224/86122 by detecting inherent features of, or outside, the semiconductor or solid-state body
- 2224/8613 using marks formed on the semiconductor or solid-state body
- 2224/86132 using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
- 2224/86136 involving guiding structures, e.g. spacers or supporting members
- 2224/86138 the guiding structures being at least partially left in the finished device
- 2224/86143 Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
- 2224/86148 involving movement of a part of the bonding apparatus
- 2224/86149 being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
- 2224/8615 Rotational movements
- 2224/8616 Translational movements
- 2224/86169 being the upper part of the bonding apparatus, e.g. nozzle
- 2224/8617 Rotational movement
- 2224/8618 Translational movements
- 2224/86181 connecting first on the semiconductor or solid-state body, i.e. on-chip,

- 2224/86186 connecting first outside the semiconductor or solid-state body, i.e. off-chip
- 2224/86191 connecting first both on and outside the semiconductor or solid-state body
- 2224/862 . . . Applying energy for connecting
- 2224/86201 Compression bonding
- 2224/86203 Thermo-compression bonding
- 2224/86205 Ultrasonic bonding
- 2224/86207 Thermosonic bonding
- 2224/8621 with energy being in the form of electromagnetic radiation
- 2224/86212 Induction heating, i.e. eddy currents
- 2224/86214 using a laser
- 2224/8623 Polychromatic or infrared lamp heating
- 2224/86232 using an autocatalytic reaction, e.g. exothermic brazing
- 2224/86234 using means for applying energy being within the device, e.g. integrated heater
- 2224/86236 using electro-static corona discharge
- 2224/86237 using electron beam ([electron beam in general B23K 15/00](#))
- 2224/86238 using electric resistance welding, i.e. ohmic heating
- 2224/8634 . . . Bonding interfaces of the connector
- 2224/86345 Shape, e.g. interlocking features
- 2224/86355 having an external coating, e.g. protective bond-through coating
- 2224/86359 Material
- 2224/8636 . . . Bonding interfaces of the semiconductor or solid state body
- 2224/86365 Shape, e.g. interlocking features
- 2224/86375 having an external coating, e.g. protective bond-through coating
- 2224/86379 Material
- 2224/8638 . . . Bonding interfaces outside the semiconductor or solid-state body
- 2224/86385 Shape, e.g. interlocking features
- 2224/86395 having an external coating, e.g. protective bond-through coating
- 2224/86399 Material
- 2224/868 . . . Bonding techniques
- 2224/86801 Soldering or alloying
- 2224/86805 involving forming a eutectic alloy at the bonding interface
- 2224/8681 involving forming an intermetallic compound at the bonding interface
- 2224/86815 Reflow soldering
- 2224/8682 Diffusion bonding
- 2224/86825 Solid-liquid interdiffusion
- 2224/8683 Solid-solid interdiffusion
- 2224/8684 Sintering
- 2224/8685 using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
- 2224/86855 Hardening the adhesive by curing, i.e. thermosetting
- 2224/86856 Pre-cured adhesive, i.e. B-stage adhesive
- 2224/86859 Localised curing of parts of the connector
- 2224/86862 Heat curing
- 2224/86865 Microwave curing
- 2224/86868 Infrared [IR] curing
- 2224/86871 Visible light curing
- 2224/86874 Ultraviolet [UV] curing
- 2224/86877 Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
- 2224/8688 Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
- 2224/86885 Combinations of two or more hardening methods provided for in at least two different groups selected from [H01L 2224/86855](#) - [H01L 2224/8688](#), e.g. hybrid thermoplastic-thermosetting adhesives
- 2224/8689 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/86893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/86895 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/86896 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/86897 between electrically insulating surfaces, e.g. oxide or nitride layers
- 2224/86899 Combinations of bonding methods provided for in at least two different groups from [H01L 2224/868](#) - [H01L 2224/86897](#)
- 2224/869 . . . involving monitoring, e.g. feedback loop
- 2224/86909 . . . Post-treatment of the connector or the bonding area
- 2224/8691 Cleaning, e.g. oxide removal step, desmearing
- 2224/8693 Reshaping
- 2224/86931 by chemical means, e.g. etching, anodisation
- 2224/86935 by heating means
- 2224/86939 using a laser
- 2224/86945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/86947 by mechanical means, e.g. severing, pressing, stamping
- 2224/86948 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/86951 Forming additional members
- 2224/86986 Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
- 2224/89 . . . using at least one connector not provided for in any of the groups [H01L 2224/81](#) - [H01L 2224/86](#)
- 2224/90 . . . Methods for connecting semiconductor or solid state bodies using means for bonding not being attached to, or not being formed on, the body surface to be connected, e.g. pressure contacts using springs or clips
- 2224/91 . . . Methods for connecting semiconductor or solid state bodies including different methods provided for in two or more of groups [H01L 2224/80](#) - [H01L 2224/90](#)
- 2224/92 . . . Specific sequence of method steps

2224/9201	. . .	Forming connectors during the connecting process, e.g. in-situ formation of bumps	2224/92172	the first connecting process involving a TAB connector
2224/9202	. . .	Forming additional connectors after the connecting process	2224/92173	the second connecting process involving a bump connector
2224/9205	. . .	Intermediate bonding steps, i.e. partial connection of the semiconductor or solid-state body during the connecting process	2224/92174	the second connecting process involving a build-up interconnect
2224/921	. . .	Connecting a surface with connectors of different types	2224/92175	the second connecting process involving a layer connector
2224/9211	Parallel connecting processes	2224/92176	the second connecting process involving a strap connector
2224/9212	Sequential connecting processes	2224/92177	the second connecting process involving a wire connector
2224/92122	the first connecting process involving a bump connector	2224/922	. . .	Connecting different surfaces of the semiconductor or solid-state body with connectors of different types
2224/92124	the second connecting process involving a build-up interconnect	2224/9221	Parallel connecting processes
2224/92125	the second connecting process involving a layer connector	2224/9222	Sequential connecting processes
2224/92127	the second connecting process involving a wire connector	2224/92222	the first connecting process involving a bump connector
2224/92132	the first connecting process involving a build-up interconnect	2224/92224	the second connecting process involving a build-up interconnect
2224/92133	the second connecting process involving a bump connector	2224/92225	the second connecting process involving a layer connector
2224/92135	the second connecting process involving a layer connector	2224/92226	the second connecting process involving a strap connector
2224/92136	the second connecting process involving a strap connector	2224/92227	the second connecting process involving a wire connector
2224/92137	the second connecting process involving a wire connector	2224/92228	the second connecting process involving a TAB connector
2224/92138	the second connecting process involving a TAB connector	2224/92242	the first connecting process involving a layer connector
2224/92142	the first connecting process involving a layer connector	2224/92244	the second connecting process involving a build-up interconnect
2224/92143	the second connecting process involving a bump connector	2224/92246	the second connecting process involving a strap connector
2224/92144	the second connecting process involving a build-up interconnect	2224/92247	the second connecting process involving a wire connector
2224/92147	the second connecting process involving a wire connector	2224/92248	the second connecting process involving a TAB connector
2224/92148	the second connecting process involving a TAB connector	2224/92252	the first connecting process involving a strap connector
2224/92152	the first connecting process involving a strap connector	2224/92253	the second connecting process involving a bump connector
2224/92153	the second connecting process involving a bump connector	2224/92255	the second connecting process involving a layer connector
2224/92155	the second connecting process involving a layer connector	2224/93	. .	Batch processes
2224/92157	the second connecting process involving a wire connector	2224/94	. .	at wafer-level, i.e. with connecting carried out on a wafer comprising a plurality of undiced individual devices
2224/92158	the second connecting process involving a TAB connector	2224/95	. .	at chip-level, i.e. with connecting carried out on a plurality of singulated devices, i.e. on diced chips
2224/92162	the first connecting process involving a wire connector	2224/95001	. . .	involving a temporary auxiliary member not forming part of the bonding apparatus, e.g. removable or sacrificial coating, film or substrate
2224/92163	the second connecting process involving a bump connector	2224/95053	. . .	Bonding environment
2224/92164	the second connecting process involving a build-up interconnect	2224/95085	being a liquid, e.g. for fluidic self-assembly
2224/92165	the second connecting process involving a layer connector	2224/95091	Under pressure
2224/92166	the second connecting process involving a strap connector	2224/95092	Atmospheric pressure, e.g. dry self-assembly
2224/92168	the second connecting process involving a TAB connector	2224/95093	Transient conditions, e.g. assisted by a gas flow or a liquid flow
			2224/951	. . .	Supplying the plurality of semiconductor or solid-state bodies

- 2224/95101 in a liquid medium
- 2224/95102 being a colloidal droplet
- 2224/95111 using a rack or rail
- 2224/95115 using a roll-to-roll transfer technique
- 2224/95112 . . . Aligning the plurality of semiconductor or solid-state bodies
- 2224/95121 Active alignment, i.e. by apparatus steering
- 2224/95122 by applying vibration
- 2224/95123 by applying a pressurised fluid flow, e.g. liquid or gas flow
- 2224/95133 by applying an electromagnetic field
- 2224/95134 Electrowetting, i.e. by changing the surface energy of a droplet
- 2224/95136 involving guiding structures, e.g. shape matching, spacers or supporting members
- 2224/95143 Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
- 2224/95144 Magnetic alignment, i.e. using permanent magnetic parts in the semiconductor or solid-state body
- 2224/95145 Electrostatic alignment, i.e. polarity alignment with Coulomb charges
- 2224/95146 by surface tension
- 2224/95147 by molecular lock-key, e.g. by DNA
- 2224/95148 involving movement of a part of the bonding apparatus
- 2224/96 . . . the devices being encapsulated in a common layer, e.g. neo-wafer or pseudo-wafer, said common layer being separable into individual assemblies after connecting
- 2224/97 . . . the devices being connected to a common substrate, e.g. interposer, said common substrate being separable into individual assemblies after connecting
- 2224/98 . . . Methods for disconnecting semiconductor or solid-state bodies
- 2225/00** **Details relating to assemblies covered by the group [H01L 25/00](#) but not provided for in its subgroups**
- 2225/03 . . . All the devices being of a type provided for in the same subgroup of groups [H01L 27/00](#) - [H01L 51/00](#)
- 2225/04 . . . the devices not having separate containers
- 2225/065 . . . the devices being of a type provided for in group [H01L 27/00](#)
- 2225/06503 Stacked arrangements of devices
- 2225/06506 Wire or wire-like electrical connections between devices
- 2225/0651 Wire or wire-like electrical connections from device to substrate
- 2225/06513 Bump or bump-like direct electrical connections between devices, e.g. flip-chip connection, solder bumps
- 2225/06517 Bump or bump-like direct electrical connections from device to substrate
- 2225/0652 Bump or bump-like direct electrical connections from substrate to substrate
- 2225/06524 Electrical connections formed on device or on substrate, e.g. a deposited or grown layer
- 2225/06527 Special adaptation of electrical connections, e.g. rewiring, engineering changes, pressure contacts, layout
- 2225/06531 Non-galvanic coupling, e.g. capacitive coupling
- 2225/06534 Optical coupling
- 2225/06537 Electromagnetic shielding
- 2225/06541 Conductive via connections through the device, e.g. vertical interconnects, through silicon via [TSV] ([manufacturing via connections per se H01L 21/76898](#))
- 2225/06544 Design considerations for via connections, e.g. geometry or layout
- 2225/06548 Conductive via connections through the substrate, container, or encapsulation
- 2225/06551 Conductive connections on the side of the device
- 2225/06555 Geometry of the stack, e.g. form of the devices, geometry to facilitate stacking
- 2225/06558 the devices having passive surfaces facing each other, i.e. in a back-to-back arrangement
- 2225/06562 at least one device in the stack being rotated or offset
- 2225/06565 the devices having the same size and there being no auxiliary carrier between the devices
- 2225/06568 the devices decreasing in size, e.g. pyramidal stack
- 2225/06572 Auxiliary carrier between devices, the carrier having an electrical connection structure
- 2225/06575 Auxiliary carrier between devices, the carrier having no electrical connection structure
- 2225/06579 TAB carriers; beam leads
- 2225/06582 Housing for the assembly, e.g. chip scale package [CSP]
- 2225/06586 Housing with external bump or bump-like connectors
- 2225/06589 Thermal management, e.g. cooling
- 2225/06593 Mounting aids permanently on device; arrangements for alignment ([use of temporary supports H01L 21/6835](#))
- 2225/06596 Structural arrangements for testing ([testing or measuring during manufacture or treatment H01L 22/00](#); [testing electrical properties or locating electrical faults G01R 31/00](#))
- 2225/10 . . . the devices having separate containers
- 2225/1005 . . . the devices being of a type provided for in group [H01L 27/00](#)
- 2225/1011 the containers being in a stacked arrangement
- 2225/1017 the lowermost container comprising a device support
- 2225/1023 the support being an insulating substrate
- 2225/1029 the support being a lead frame
- 2225/1035 the device being entirely enclosed by the support, e.g. high-density interconnect [HDI]
- 2225/1041 Special adaptations for top connections of the lowermost container, e.g. redistribution layer, integral interposer
- 2225/1047 Details of electrical connections between containers
- 2225/1052 Wire or wire-like electrical connections

2225/1058 Bump or bump-like electrical connections, e.g. balls, pillars, posts	2251/554	. . . Oxidation-reduction potential
2225/1064 Electrical connections provided on a side surface of one or more of the containers	2251/556	. . . Temperature
2225/107 Indirect electrical connections, e.g. via an interposer, a flexible substrate, using TAB (printed circuits H05K 1/00)	2251/558	. . . Thickness
2225/1076 Shape of the containers	2251/56	. . Processes specially adapted for the manufacture or treatment of OLED
2225/1082 for improving alignment between containers, e.g. interlocking features	2251/562	. . . Aging
2225/1088 Arrangements to limit the height of the assembly	2251/564	. . . Application of alternating current
2225/1094 Thermal management, e.g. cooling	2251/566	. . . Division of substrate, e.g. for manufacturing of OLED displays
2225/1094 Thermal management, e.g. cooling	2251/568	. . . Repairing
2227/00	Indexing scheme for devices consisting of a plurality of semiconductor or other solid state components formed in or on a common substrate covered by group H01L 27/00	2924/00	Indexing scheme for arrangements or methods for connecting or disconnecting semiconductor or solid-state bodies as covered by H01L 24/00
2227/32	. Devices including an organic light emitting device [OLED], e.g. OLED display	2924/0001	. Technical content checked by a classifier
2227/323	. . Multistep processes for AMOLED		NOTE
2227/326	. . Use of temporary substrate, e.g. for manufacturing of OLED displays having an inorganic driving circuit		Codes H01L 2924/0001 - H01L 2924/0002 are used to describe the status of reclassification; they do not relate to technical features as such
2229/00	Indexing scheme for semiconductor devices adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential-jump barrier or surface barrier, for details of semiconductor bodies or of electrodes thereof, or for multistep manufacturing processes therefor	2924/00011	. . Not relevant to the scope of the group, the symbol of which is combined with the symbol of this group
2251/00	Indexing scheme relating to organic semiconductor devices covered by group H01L 51/00	2924/00012	. . Relevant to the scope of the group, the symbol of which is combined with the symbol of this group
2251/10	. Processes specially adapted for the manufacture or treatment of organic semiconductor devices	2924/00013	. . Fully indexed content
2251/105	. . Patterning of a layer by embossing, e.g. to form trenches in an insulating layer	2924/00014	. . the subject-matter covered by the group, the symbol of which is combined with the symbol of this group, being disclosed without further technical details
2251/30	. Materials	2924/00015	. . the subject-matter covered by the group, the symbol of which is combined with the symbol of this group, being disclosed as prior art
2251/301	. . Inorganic materials	2924/0002	. . Not covered by any one of groups H01L 24/00 , H01L 24/00 and H01L 2224/00
2251/303	. . . Oxides, e.g. metal oxides	2924/01	. Chemical elements
2251/305 Transparent conductive oxides [TCO]	2924/01001	. . Hydrogen [H]
2251/306 composed of tin oxides, e.g. F doped SnO ₂	2924/01002	. . Helium [He]
2251/308 composed of indium oxides, e.g. ITO	2924/01003	. . Lithium [Li]
2251/50	. Organic light emitting devices	2924/01004	. . Beryllium [Be]
2251/53	. . Structure	2924/01005	. . Boron [B]
2251/5307	. . . specially adapted for controlling the direction of light emission	2924/01006	. . Carbon [C]
2251/5315 Top emission	2924/01007	. . Nitrogen [N]
2251/5323 Two-side emission, i.e. TOLED	2924/01008	. . Oxygen [O]
2251/533 End-face emission	2924/01009	. . Fluorine [F]
2251/5338	. . . Flexible OLED	2924/0101	. . Neon [Ne]
2251/5346	. . . Graded composition	2924/01011	. . Sodium [Na]
2251/5353	. . . Inverted OLED	2924/01012	. . Magnesium [Mg]
2251/5361	. . . OLED lamp	2924/01013	. . Aluminum [Al]
2251/5369	. . . Nanoparticles used in whatever layer except emissive layer, e.g. in packaging	2924/01014	. . Silicon [Si]
2251/5376	. . . Combination of fluorescent and phosphorescent emission	2924/01015	. . Phosphorus [P]
2251/5384	. . . Multiple hosts in the emissive layer	2924/01016	. . Sulfur [S]
2251/5392	. . . Short-circuit prevention	2924/01017	. . Chlorine [Cl]
2251/55	. . characterised by parameters	2924/01018	. . Argon [Ar]
2251/552	. . . HOMO-LUMO-EF	2924/01019	. . Potassium [K]
		2924/0102	. . Calcium [Ca]
		2924/01021	. . Scandium [Sc]
		2924/01022	. . Titanium [Ti]
		2924/01023	. . Vanadium [V]
		2924/01024	. . Chromium [Cr]
		2924/01025	. . Manganese [Mn]
		2924/01026	. . Iron [Fe]
		2924/01027	. . Cobalt [Co]

2924/01028	. . Nickel [Ni]	2924/01089	. . Actinium [Ac]
2924/01029	. . Copper [Cu]	2924/0109	. . Thorium [Th]
2924/0103	. . Zinc [Zn]	2924/01091	. . Protactinium [Pa]
2924/01031	. . Gallium [Ga]	2924/01092	. . Uranium [U]
2924/01032	. . Germanium [Ge]	2924/01093	. . Neptunium [Np]
2924/01033	. . Arsenic [As]	2924/01094	. . Plutonium [Pu]
2924/01034	. . Selenium [Se]	2924/011	. Groups of the periodic table
2924/01035	. . Bromine [Br]	2924/01101	. . Alkali metals
2924/01036	. . Krypton [Kr]	2924/01102	. . Alkali earth metals
2924/01037	. . Rubidium [Rb]	2924/01103	. . Transition metals
2924/01038	. . Strontium [Sr]	2924/01104	. . Refractory metals
2924/01039	. . Yttrium [Y]	2924/01105	. . Rare earth metals
2924/0104	. . Zirconium [Zr]	2924/01106	. . . Lanthanides, i.e. Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu
2924/01041	. . Niobium [Nb]	2924/01107	. . . Actinides, i.e. Th, Pa, U, Np, Pu, Am, Cm, Bk, Cf, Es, Fm, Md, No, Lr
2924/01042	. . Molybdenum [Mo]	2924/01108	. . Noble metals
2924/01043	. . Technetium [Tc]	2924/01109	. . Metalloids or Semi-metals
2924/01044	. . Ruthenium [Ru]	2924/0111	. . Chalcogens
2924/01045	. . Rhodium [Rh]	2924/01111	. . Halogens
2924/01046	. . Palladium [Pd]	2924/01112	. . Noble gases
2924/01047	. . Silver [Ag]	2924/012	. Semiconductor purity grades
2924/01048	. . Cadmium [Cd]	2924/01201	. . 1N purity grades, i.e. 90%
2924/01049	. . Indium [In]	2924/01202	. . 2N purity grades, i.e. 99%
2924/0105	. . Tin [Sn]	2924/01203	. . 3N purity grades, i.e. 99.9%
2924/01051	. . Antimony [Sb]	2924/01204	. . 4N purity grades, i.e. 99.99%
2924/01052	. . Tellurium [Te]	2924/01205	. . 5N purity grades, i.e. 99.999%
2924/01053	. . Iodine [I]	2924/01206	. . 6N purity grades, i.e. 99.9999%
2924/01054	. . Xenon [Xe]	2924/01207	. . 7N purity grades, i.e. 99.99999%
2924/01055	. . Cesium [Cs]	2924/01208	. . 8N purity grades, i.e. 99.999999%
2924/01056	. . Barium [Ba]	2924/013	. Alloys
2924/01057	. . Lanthanum [La]	2924/0132	. . Binary Alloys
2924/01058	. . Cerium [Ce]	2924/01321	. . . Isomorphous Alloys
2924/01059	. . Praseodymium [Pr]	2924/01322	. . . Eutectic Alloys, i.e. obtained by a liquid transforming into two solid phases
2924/0106	. . Neodymium [Nd]	2924/01323 Hypoeutectic alloys i.e. with compositions lying to the left of the eutectic point
2924/01061	. . Promethium [Pm]	2924/01324 Hypereutectic alloys i.e. with compositions lying to the right of the eutectic point
2924/01062	. . Samarium [Sm]	2924/01325	. . . Peritectic Alloys, i.e. obtained by a liquid and a solid transforming into a new and different solid phase
2924/01063	. . Europium [Eu]	2924/01326	. . . Monotectics, i.e. obtained by a liquid transforming into a solid and a new and different liquid phase
2924/01064	. . Gadolinium [Gd]	2924/01327	. . . Intermediate phases, i.e. intermetallics compounds
2924/01065	. . Terbium [Tb]	2924/0133	. . Ternary Alloys
2924/01066	. . Dysprosium [Dy]	2924/0134	. . Quaternary Alloys
2924/01067	. . Holmium [Ho]	2924/0135	. . Quinary Alloys
2924/01068	. . Erbium [Er]	2924/014	. Solder alloys
2924/01069	. . Thulium [Tm]	2924/01402	. . Invar, i.e. single-phase alloy of around 36% nickel and 64% iron
2924/0107	. . Ytterbium [Yb]	2924/01403	. . Kovar, i.e. FeNiCo alloys
2924/01071	. . Lutetium [Lu]	2924/01404	. . Alloy 42, i.e. FeNi42
2924/01072	. . Hafnium [Hf]	2924/01405	. . Inovco, i.e. Fe-33Ni-4.5Co
2924/01073	. . Tantalum [Ta]	2924/042	. Borides composed of metals from groups of the periodic table
2924/01074	. . Tungsten [W]	2924/0421	. . 1st Group
2924/01075	. . Rhenium [Re]	2924/0422	. . 2nd Group
2924/01076	. . Osmium [Os]	2924/0423	. . 3rd Group
2924/01077	. . Iridium [Ir]	2924/0424	. . 4th Group
2924/01078	. . Platinum [Pt]		
2924/01079	. . Gold [Au]		
2924/0108	. . Mercury [Hg]		
2924/01081	. . Thallium [Tl]		
2924/01082	. . Lead [Pb]		
2924/01083	. . Bismuth [Bi]		
2924/01084	. . Polonium [Po]		
2924/01085	. . Astatine [At]		
2924/01086	. . Radon [Rn]		
2924/01087	. . Francium [Fr]		
2924/01088	. . Radium [Ra]		

2924/0425	. . 5th Group	2924/0486	. . Actinides
2924/0426	. . 6th Group	2924/0489	. . being a combination of two or more materials provided in the groups H01L 2924/0471 - H01L 2924/0486
2924/0427	. . 7th Group	2924/04891	. . having a monocrystalline microstructure
2924/0428	. . 8th Group	2924/04892	. . having a polycrystalline microstructure
2924/0429	. . 9th Group	2924/04894	. . having an amorphous microstructure, i.e. glass
2924/044	. . 10th Group	2924/049	. Nitrides composed of metals from groups of the periodic table
2924/0441	. . 11th Group	2924/0491	. . 1st Group
2924/0442	. . 12th Group	2924/0492	. . 2nd Group
2924/0443	. . 13th Group	2924/0493	. . 3rd Group
2924/0444	. . 14th Group	2924/0494	. . 4th Group
2924/0445	. . Lanthanides	2924/04941	. . . TiN
2924/0446	. . Actinides	2924/0495	. . 5th Group
2924/0449	. . being a combination of two or more materials provided in the groups H01L 2924/0421 - H01L 2924/0446	2924/04953	. . . TaN
2924/04491	. . having a monocrystalline microstructure	2924/0496	. . 6th Group
2924/04492	. . having a polycrystalline microstructure	2924/0497	. . 7th Group
2924/04494	. . having an amorphous microstructure, i.e. glass	2924/0498	. . 8th Group
2924/045	. Carbides composed of metals from groups of the periodic table	2924/0499	. . 9th Group
2924/0451	. . 1st Group	2924/05	. . 10th Group
2924/0452	. . 2nd Group	2924/0501	. . 11th Group
2924/0453	. . 3rd Group	2924/0502	. . 12th Group
2924/0454	. . 4th Group	2924/0503	. . 13th Group
2924/04541	. . . TiC	2924/05032	. . . AlN
2924/0455	. . 5th Group	2924/0504	. . 14th Group
2924/0456	. . 6th Group	2924/05042	. . . Si ₃ N ₄
2924/04563	. . . WC	2924/0505	. . Lanthanides
2924/0457	. . 7th Group	2924/0506	. . Actinides
2924/0458	. . 8th Group	2924/0509	. . being a combination of two or more materials provided in the groups H01L 2924/0491 - H01L 2924/0506
2924/0459	. . 9th Group	2924/05091	. . having a monocrystalline microstructure
2924/046	. . 10th Group	2924/05092	. . having a polycrystalline microstructure
2924/0461	. . 11th Group	2924/05094	. . having an amorphous microstructure, i.e. glass
2924/0462	. . 12th Group	2924/051	. Phosphides composed of metals from groups of the periodic table
2924/0463	. . 13th Group	2924/0511	. . 1st Group
2924/0464	. . 14th Group	2924/0512	. . 2nd Group
2924/04642	. . . SiC	2924/0513	. . 3rd Group
2924/0465	. . Lanthanides	2924/0514	. . 4th Group
2924/0466	. . Actinides	2924/0515	. . 5th Group
2924/0469	. . being a combination of two or more materials provided in the groups H01L 2924/0451 - H01L 2924/0466	2924/0516	. . 6th Group
2924/04691	. . having a monocrystalline microstructure	2924/0517	. . 7th Group
2924/04692	. . having a polycrystalline microstructure	2924/0518	. . 8th Group
2924/04694	. . having an amorphous microstructure, i.e. glass	2924/0519	. . 9th Group
2924/047	. Silicides composed of metals from groups of the periodic table	2924/052	. . 10th Group
2924/0471	. . 1st Group	2924/0521	. . 11th Group
2924/0472	. . 2nd Group	2924/0522	. . 12th Group
2924/0473	. . 3rd Group	2924/0523	. . 13th Group
2924/0474	. . 4th Group	2924/0524	. . 14th Group
2924/0475	. . 5th Group	2924/0525	. . Lanthanides
2924/0476	. . 6th Group	2924/0526	. . Actinides
2924/0477	. . 7th Group	2924/0529	. . being a combination of two or more materials provided in the groups H01L 2924/0511 - H01L 2924/0526
2924/0478	. . 8th Group	2924/05291	. . having a monocrystalline microstructure
2924/0479	. . 9th Group	2924/05292	. . having a polycrystalline microstructure
2924/048	. . 10th Group	2924/05294	. . having an amorphous microstructure, i.e. glass
2924/0481	. . 11th Group	2924/053	. Oxides composed of metals from groups of the periodic table
2924/0482	. . 12th Group	2924/0531	. . 1st Group
2924/0483	. . 13th Group		
2924/0484	. . 14th Group		
2924/0485	. . Lanthanides		

2924/0532	. . 2nd Group	2924/058	. . 10th Group
2924/0533	. . 3rd Group	2924/0581	. . 11th Group
2924/0534	. . 4th Group	2924/0582	. . 12th Group
2924/05341	. . . TiO ₂	2924/0583	. . 13th Group
2924/05342	. . . ZrO ₂	2924/0584	. . 14th Group
2924/0535	. . 5th Group	2924/0585	. . Lanthanides
2924/0536	. . 6th Group	2924/0586	. . Actinides
2924/0537	. . 7th Group	2924/0589	. . being a combination of two or more materials provided in the groups H01L 2924/0571 - H01L 2924/0586
2924/0538	. . 8th Group		
2924/05381	. . . FeOx	2924/05891	. . having a monocrystalline microstructure
2924/0539	. . 9th Group	2924/05892	. . having a polycrystalline microstructure
2924/054	. . 10th Group	2924/05894	. . having an amorphous microstructure, i.e. glass
2924/0541	. . 11th Group	2924/059	. Being combinations of any of the materials from the groups H01L 2924/042 - H01L 2924/0584 , e.g. oxynitrides
2924/0542	. . 12th Group		
2924/0543	. . 13th Group	2924/05991	. . having a monocrystalline microstructure
2924/05432	. . . Al ₂ O ₃	2924/05992	. . having a polycrystalline microstructure
2924/0544	. . 14th Group	2924/05994	. . having an amorphous microstructure, i.e. glass
2924/05442	. . . SiO ₂	2924/06	. Polymers (polymers per se C08 ; polymer adhesives C09J)
2924/0545	. . Lanthanides		
2924/0546	. . Actinides	2924/061	. . Polyolefin polymer
2924/0549	. . being a combination of two or more materials provided in the groups H01L 2924/0531 - H01L 2924/0546	2924/0615	. . Styrenic polymer
		2924/062	. . Halogenated polymer
2924/05491	. . having a monocrystalline microstructure	2924/0625	. . Polyvinyl alcohol
2924/05492	. . having a polycrystalline microstructure	2924/063	. . Polyvinyl acetate
2924/05494	. . having an amorphous microstructure, i.e. glass	2924/0635	. . Acrylic polymer
2924/055	. Chalcogenides other than oxygen i.e. sulfides, selenides and tellurides composed of metals from groups of the periodic table	2924/064	. . Graft polymer
		2924/0645	. . Block copolymer
2924/0551	. . 1st Group	2924/065	. . ABS
2924/0552	. . 2nd Group	2924/0655	. . Polyacetal
2924/0553	. . 3rd Group	2924/066	. . Phenolic resin
2924/0554	. . 4th Group	2924/0665	. . Epoxy resin
2924/0555	. . 5th Group	2924/067	. . Polyphenylene
2924/0556	. . 6th Group	2924/0675	. . Polyester
2924/0557	. . 7th Group	2924/068	. . Polycarbonate
2924/0558	. . 8th Group	2924/0685	. . Polyether
2924/0559	. . 9th Group	2924/069	. . Polyurethane
2924/056	. . 10th Group	2924/0695	. . Polyamide
2924/0561	. . 11th Group	2924/07	. . Polyamine or polyimide
2924/0562	. . 12th Group	2924/07001	. . . Polyamine
2924/0563	. . 13th Group	2924/07025	. . . Polyimide
2924/0564	. . 14th Group	2924/0705	. . Sulfur containing polymer
2924/0565	. . Lanthanides	2924/0715	. . Polysiloxane
2924/0566	. . Actinides	2924/078	. . Adhesive characteristics other than chemical
2924/0569	. . being a combination of two or more materials provided in the groups H01L 2924/0551 - H01L 2924/0566	2924/07802	. . . not being an ohmic electrical conductor
		2924/0781	. . . being an ohmic electrical conductor
2924/05691	. . having a monocrystalline microstructure	2924/07811 Extrinsic, i.e. with electrical conductive fillers
2924/05692	. . having a polycrystalline microstructure		
2924/05694	. . having an amorphous microstructure, i.e. glass	2924/07812 Intrinsic, e.g. polyaniline [PANI]
2924/057	. Halides composed of metals from groups of the periodic table	2924/0782	. . . being pressure sensitive
		2924/095	. with a principal constituent of the material being a combination of two or more materials provided in the groups H01L 2924/013 - H01L 2924/0715
2924/0571	. . 1st Group		
2924/0572	. . 2nd Group	2924/0951	. . Glass epoxy laminates
2924/0573	. . 3rd Group	2924/09511	. . . FR-4
2924/0574	. . 4th Group	2924/09512	. . . FR-5
2924/0575	. . 5th Group	2924/09522	. . . G10
2924/0576	. . 6th Group	2924/09523	. . . G11
2924/0577	. . 7th Group	2924/096	. . Cermets, i.e. composite material composed of ceramic and metallic materials
2924/0578	. . 8th Group		
2924/0579	. . 9th Group	2924/097	. . Glass-ceramics, e.g. devitrified glass

2924/09701	. . . Low temperature co-fired ceramic [LTCC]	2924/10353 Indium arsenide antimonide phosphide [InAsSbP]
2924/10	. Details of semiconductor or other solid state devices to be connected	2924/10354 Aluminium indium arsenide phosphide [AlInAsP]
2924/1011	. . Structure	2924/10355 Aluminium gallium arsenide nitride [AlGaAsN]
2924/1015	. . Shape	2924/10356 Indium gallium arsenide nitride [InGaAsN]
2924/10155	. . . being other than a cuboid	2924/10357 Indium aluminium arsenide nitride [InAlAsN]
2924/10156 at the periphery	2924/10358 Gallium arsenide antimonide nitride [GaAsSbN]
2924/10157 at the active surface	2924/10359 Gallium indium nitride arsenide antimonide [GaInNAsSb]
2924/10158 at the passive surface	2924/1036 Gallium indium arsenide antimonide phosphide [GaInAsSbP]
2924/1016	. . . being a cuboid	2924/1037 II-VI
2924/10161 with a rectangular active surface	2924/10371 Cadmium selenide [CdSe]
2924/10162 with a square active surface	2924/10372 Cadmium sulfide [CdS]
2924/1017	. . . being a sphere	2924/10373 Cadmium telluride [CdTe]
2924/102	. . Material of the semiconductor or solid state bodies	2924/10375 Zinc selenide [ZnSe]
2924/1025	. . . Semiconducting materials	2924/10376 Zinc sulfide [ZnS]
2924/10251 Elemental semiconductors, i.e. Group IV	2924/10377 Zinc telluride [ZnTe]
2924/10252 Germanium [Ge]	2924/10378 Cadmium zinc telluride, i.e. CZT [CdZnTe]
2924/10253 Silicon [Si]	2924/10379 Mercury cadmium telluride [HgZnTe]
2924/10254 Diamond [C]	2924/1038 Mercury zinc telluride [HgZnSe]
2924/1026 Compound semiconductors	2924/10381 Mercury zinc selenide [HgZnSe]
2924/1027 IV	2924/1042 I-VII
2924/10271 Silicon-germanium [SiGe]	2924/10421 Cuprous chloride [CuCl]
2924/10272 Silicon Carbide [SiC]	2924/1047 I-VI
2924/1032 III-V	2924/10471 Copper sulfide [CuS]
2924/10321 Aluminium antimonide [AlSb]	2924/1052 IV-VI
2924/10322 Aluminium arsenide [AlAs]	2924/10521 Lead selenide [PbSe]
2924/10323 Aluminium nitride [AlN]	2924/10522 Lead(II)sulfide [PbS]
2924/10324 Aluminium phosphide [AlP]	2924/10523 Lead telluride [PbTe]
2924/10325 Boron nitride [BN], e.g. cubic, hexagonal, nanotube	2924/10524 Tin sulfide [SnS, SnS ₂]
2924/10326 Boron phosphide [BP]	2924/10525 Tin telluride [SnTe]
2924/10327 Boron arsenide [BAS, B ₁₂ As ₂]	2924/10526 Lead tin telluride [PbSnTe]
2924/10328 Gallium antimonide [GaSb]	2924/10527 Thallium tin telluride [Tl ₂ SnTe ₅]
2924/10329 Gallium arsenide [GaAs]	2924/10528 Thallium germanium telluride [Tl ₂ GeTe ₅]
2924/1033 Gallium nitride [GaN]	2924/1057 V-VI
2924/10331 Gallium phosphide [GaP]	2924/10571 Bismuth telluride [Bi ₂ Te ₃]
2924/10332 Indium antimonide [InSb]	2924/1062 II-V
2924/10333 Indium arsenide [InAs]	2924/10621 Cadmium phosphide [Cd ₃ P ₂]
2924/10334 Indium nitride [InN]	2924/10622 Cadmium arsenide [Cd ₃ As ₂]
2924/10335 Indium phosphide [InP]	2924/10623 Cadmium antimonide [Cd ₃ Sb ₂]
2924/10336 Aluminium gallium arsenide [AlGaAs]	2924/10624 Zinc phosphide [Zn ₃ P ₂]
2924/10337 Indium gallium arsenide [InGaAs]	2924/10625 Zinc arsenide [Zn ₃ As ₂]
2924/10338 Indium gallium phosphide [InGaP]	2924/10626 Zinc antimonide [Zn ₃ Sb ₂]
2924/10339 Aluminium indium arsenide [AlInAs]	2924/1067 Oxide
2924/1034 Aluminium indium antimonide [AlInSb]	2924/10671 Titanium dioxide, anatase, rutile, brookite [TiO ₂]
2924/10341 Gallium arsenide nitride [GaAsN]	2924/10672 Copper(I)oxide [Cu ₂ O]
2924/10342 Gallium arsenide phosphide [GaAsP]	2924/10673 Copper(II)oxide [CuO]
2924/10343 Gallium arsenide antimonide [GaAsSb]	2924/10674 Uranium dioxide [UO ₂]
2924/10344 Aluminium gallium nitride [AlGaN]	2924/10675 Uranium trioxide [UO ₃]
2924/10345 Aluminium gallium phosphide [AlGaP]	2924/10676 Bismuth trioxide [Bi ₂ O ₃]
2924/10346 Indium gallium nitride [InGaN]	2924/10677 Tin dioxide [SnO ₂]
2924/10347 Indium arsenide antimonide [InAsSb]	2924/10678 Barium titanate [BaTiO ₃]
2924/10348 Indium gallium antimonide [InGaSb]		
2924/10349 Aluminium gallium indium phosphide [AlGaInP]		
2924/1035 Aluminium gallium arsenide phosphide [AlGaInP]		
2924/10351 Indium gallium arsenide phosphide [InGaAsP]		
2924/10352 Indium gallium arsenide antimonide [InGaAsSb]		

2924/10679	Strontium titanate [SrTiO ₃]	2924/13014	Breakover Diode [BOD]
2924/1068	Lithium niobate [LiNbO ₃]	2924/13015	DIAC - Bidirectional trigger device
2924/10681	Lanthanum copper oxide [La ₂ CuO ₄]	2924/13016	Dynistor - Unidirectional switching device
2924/1072	Layered	2924/13017	Shockley diode - Unidirectional trigger and switching device
2924/10721	Lead(II)iodide [PbI ₂]	2924/13018	SIDAC - Bidirectional switching device
2924/10722	Molybdenum disulfide [MoS ₂]	2924/13019	Trisil, SIDACTor - Bidirectional protection devices
2924/10723	Gallium selenide [GaSe]	2924/1302	GTO - Gate Turn-Off thyristor
2924/10724	Tin sulfide [SnS]	2924/13021	DB-GTO - Distributed Buffer Gate Turn-Off thyristor
2924/10725	Bismuth sulfide [Bi ₂ S ₃]	2924/13022	MA-GTO - Modified Anode Gate Turn-Off thyristor
2924/1077	Magnetic diluted [DMS]	2924/13023	IGCT - Integrated Gate Commutated Thyristor
2924/10771	Gallium manganese arsenide [GaMnAs]	2924/13024	LASCR - Light Activated SCR, or LTT - Light triggered thyristor
2924/10772	Indium manganese arsenide [InMnAs]	2924/13025	Light Activated Semiconducting Switch [LASS]
2924/10773	Cadmium manganese telluride [CdMnTe]	2924/13026	MCT - MOSFET Controlled Thyristor - It contains two additional FET structures for on/off control
2924/10774	Lead manganese telluride [PbMnTe]	2924/13027	BRT - Base Resistance Controlled Thyristor
2924/10775	Lanthanum calcium manganate [La _{0.7} Ca _{0.3} MnO ₃]	2924/13028	RCT - Reverse Conducting Thyristor
2924/10776	Iron(II)oxide [FeO]	2924/13029	PUT or PUJT - Programmable Unijunction Transistor - A thyristor with gate on n-type layer near to the anode used as a functional replacement for unijunction transistor
2924/10777	Nickel(II)oxide [NiO]	2924/1303	SCS - Silicon Controlled Switch or Thyristor Tetrode - A thyristor with both cathode and anode gates
2924/10778	Europium(II)oxide [EuO]	2924/13032	SITH - Static Induction Thyristor, or FCTh - Field Controlled Thyristor - containing a gate structure that can shut down anode current flow
2924/10779	Europium(II)sulfide [EuS]	2924/13033	TRIAC - Triode for Alternating Current - A bidirectional switching device containing two thyristor structures with common gate contact
2924/1078	Chromium(III)bromide [CrBr ₃]	2924/13034	Silicon Controlled Rectifier [SCR]
2924/1082	Other	2924/13035	Asymmetrical SCR [ASCR]
2924/10821	Copper indium gallium selenide, CIGS [Cu[In,Ga]Se ₂]	2924/1304	Transistor
2924/10822	Copper zinc tin sulfide, CZTS [Cu ₂ ZnSnS ₄]	2924/1305	Bipolar Junction Transistor [BJT]
2924/10823	Copper indium selenide, CIS [CuInSe ₂]	2924/13051	Heterojunction bipolar transistor [HBT]
2924/10824	Silver gallium sulfide [AgGaS ₂]	2924/13052	Schottky transistor
2924/10825	Zinc silicon phosphide [ZnSiP ₂]	2924/13053	Avalanche transistor
2924/10826	Arsenic selenide [As ₂ S ₃]	2924/13054	Darlington transistor
2924/10827	Platinum silicide [PtSi]	2924/13055	Insulated gate bipolar transistor [IGBT]
2924/10828	Bismuth(III)iodide [BiI ₃]	2924/13056	Photo transistor
2924/10829	Mercury(II)iodide [HgI ₂]	2924/1306	Field-effect transistor [FET]
2924/1083	Thallium(I)bromide [TlBr]	2924/13061	Carbon nanotube field-effect transistor [CNFET]
2924/10831	Selenium [Se]	2924/13062	Junction field-effect transistor [JFET]
2924/10832	Silver sulfide [Ag ₂ S]	2924/13063	Metal-Semiconductor Field-Effect Transistor [MESFET]
2924/10833	Iron disulfide [FeS ₂]	2924/13064	High Electron Mobility Transistor [HEMT, HFET [heterostructure FET], MODFET]
2924/11	. .	Device type	2924/13066	Inverted-T field effect transistor [ITFET]
2924/12	. . .	Passive devices, e.g. 2 terminal devices	2924/13067	FinFET, source/drain region shapes fins on the silicon surface
2924/1203	Rectifying Diode			
2924/12031	PIN diode			
2924/12032	Schottky diode			
2924/12033	Gunn diode			
2924/12034	Varactor			
2924/12035	Zener diode			
2924/12036	PN diode			
2924/12037	Cat's whisker diode			
2924/12038	Point contact			
2924/1204	Optical Diode			
2924/12041	LED			
2924/12042	LASER			
2924/12043	Photo diode			
2924/12044	OLED			
2924/1205	Capacitor			
2924/1206	Inductor			
2924/1207	Resistor			
2924/13	. . .	Discrete devices, e.g. 3 terminal devices			
2924/1301	Thyristor			
2924/13011	Anode Gate Thyristor [AGT]			
2924/13013	Bidirectional Control Thyristor [BCT]			

2924/13068	Fast-reverse epitaxial diode field-effect transistor [FREDFET]	2924/1436	Dynamic random-access memory [DRAM]
2924/13069	Thin film transistor [TFT]	2924/14361	Synchronous dynamic random access memory [SDRAM]
2924/1307	Organic Field-Effect Transistor [OFET]	2924/14362	RAS Only Refresh [ROR]
2924/13071	Ballistic transistor	2924/14363	CAS before RAS refresh [CBR]
2924/13072	Sensor FET	2924/14364	Multibank DRAM [MDRAM]
2924/13073	ion-sensitive field-effect transistor [ISFET]	2924/14365	Video DRAM [VRAM]
2924/13074	Electrolyte-oxide-semiconductor field effect transistor [EOSFET], e.g. Neurochip	2924/14366	Window DRAM [WRAM]
2924/13075	Deoxyribonucleic acid field-effect transistor [DNAFET]	2924/14367	Fast page mode DRAM [FPM DRAM]
2924/13076	DEPFET	2924/14368	Extended data out DRAM [EDO DRAM]
2924/13078	Unijunction transistors	2924/14369	Burst EDO DRAM [BEDO DRAM]
2924/13079	Single-electron transistors [SET]	2924/1437	Static random-access memory [SRAM]
2924/1308	Nanofluidic transistor	2924/1438	Flash memory
2924/13081	Multigate devices	2924/1441	Ferroelectric RAM [FeRAM or FRAM]
2924/13082	Tetrode transistor	2924/1442	Synchronous graphics RAM [SGRAM]
2924/13083	Pentode transistor	2924/1443	Non-volatile random-access memory [NVRAM]
2924/13084	Trigate transistor	2924/1444	PBRAM
2924/13085	Dual gate FETs	2924/145	Read-only memory [ROM]
2924/13086	Junctionless Nanowire Transistor [JNT]	2924/1451	EPROM
2924/13087	Vertical-Slit Field-Effect Transistor [VeSFET]	2924/14511	EEPROM
2924/13088	Graphene Nanoribbon Field-Effect Transistor [GNRFET]	2924/1453	PROM
2924/13089	Nanoparticle Organic Memory Field-Effect Transistor [NOMFET]	2924/146	Mixed devices
2924/1309	Modulation-Doped Field Effect Transistor [MODFET]	2924/1461	MEMS
2924/13091	Metal-Oxide-Semiconductor Field-Effect Transistor [MOSFET]	2924/15	Details of package parts other than the semiconductor or other solid state devices to be connected
2924/13092	Dual Gate Metal-Oxide-Semiconductor Field-Effect Transistor [DGMOSFET]	2924/151	Die mounting substrate
2924/14	Integrated circuits	2924/1511	Structure
2924/141	Analog devices	2924/1515	Shape
2924/142	HF devices	2924/15151	the die mounting substrate comprising an aperture, e.g. for underfilling, outgassing, window type wire connections
2924/1421	RF devices	2924/15153	the die mounting substrate comprising a recess for hosting the device
2924/14211	Voltage-controlled oscillator [VCO]	2924/15155	the shape of the recess being other than a cuboid
2924/14215	Low-noise amplifier [LNA]	2924/15156	Side view
2924/1422	Mixer	2924/15157	Top view
2924/14221	Electronic mixer	2924/15158	the die mounting substrate being other than a cuboid
2924/14222	Frequency mixer	2924/15159	Side view
2924/1423	Monolithic Microwave Integrated Circuit [MMIC]	2924/15162	Top view
2924/1424	Operational amplifier	2924/15165	Monolayer substrate
2924/1425	Converter	2924/1517	Multilayer substrate
2924/14251	Frequency converter	2924/15172	Fan-out arrangement of the internal vias
2924/14252	Voltage converter	2924/15173	in a single layer of the multilayer substrate
2924/14253	Digital-to-analog converter [DAC]	2924/15174	in different layers of the multilayer substrate
2924/1426	Driver	2924/15182	Fan-in arrangement of the internal vias
2924/1427	Voltage regulator [VR]	2924/15183	in a single layer of the multilayer substrate
2924/143	Digital devices	2924/15184	in different layers of the multilayer substrate
2924/1431	Logic devices	2924/15192	Resurf arrangement of the internal vias
2924/1432	Central processing unit [CPU]	2924/152	Disposition
2924/1433	Application-specific integrated circuit [ASIC]	2924/153	Connection portion
2924/14335	Digital signal processor [DSP]		
2924/1434	Memory		
2924/1435	Random access memory [RAM]		

2924/1531	the connection portion being formed only on the surface of the substrate opposite to the die mounting surface	2924/16151	Cap comprising an aperture, e.g. for pressure control, encapsulation
2924/15311	being a ball array, e.g. BGA	2924/16152	Cap comprising a cavity for hosting the device, e.g. U-shaped cap
2924/15312	being a pin array, e.g. PGA	2924/16153	Cap enclosing a plurality of side-by-side cavities [e.g. E-shaped cap]
2924/15313	being a land array, e.g. LGA	2924/1616	Cavity shape
2924/1532	the connection portion being formed on the die mounting surface of the substrate	2924/1617	Cavity coating
2924/15321	being a ball array, e.g. BGA	2924/16171	Material
2924/15322	being a pin array, e.g. PGA	2924/16172	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2924/15323	being a land array, e.g. LGA	2924/16173	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2924/1533	the connection portion being formed both on the die mounting surface of the substrate and outside the die mounting surface of the substrate	2924/16174	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/16175)
2924/15331	being a ball array, e.g. BGA	2924/16175	Glasses, e.g. amorphous oxides, nitrides or fluorides
2924/15332	being a pin array, e.g. PGA	2924/16176	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2924/15333	being a land array, e.g. LGA	2924/16177	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2924/156	Material	2924/16178	with a principal constituent of the material being a solid not provided for in groups H01L 2924/157 - H01L 2924/15791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2924/157	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2924/16179	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2924/15701	the principal constituent melting at a temperature of less than 400 C	2924/1619	Cavity coating shape
2924/15717	the principal constituent melting at a temperature of greater than or equal to 400 C and less than 950 C	2924/16195	Flat cap [not enclosing an internal cavity]
2924/15724	Aluminium [Al] as principal constituent	2924/16196	Cap forming a cavity, e.g. being a curved metal foil
2924/15738	the principal constituent melting at a temperature of greater than or equal to 950 C and less than 1550 C	2924/162	Disposition
2924/15747	Copper [Cu] as principal constituent	2924/16235	Connecting to a semiconductor or solid-state bodies, i.e. cap-to-chip
2924/1576	Iron [Fe] as principal constituent	2924/16251	Connecting to an item not being a semiconductor or solid-state body, e.g. cap-to-substrate
2924/15763	the principal constituent melting at a temperature of greater than 1550 C	2924/1626	Cap-in-cap assemblies
2924/15786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2924/1627	stacked type assemblies, e.g. stacked multi-cavities
2924/15787	Ceramics, e.g. crystalline carbides, nitrides or oxides	2924/163	Connection portion, e.g. seal
2924/15788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2924/1631	Structure
2924/1579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2924/16315	Shape
2924/15791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2924/1632	Disposition
2924/15793	with a principal constituent of the material being a solid not provided for in groups H01L 2924/157 - H01L 2924/15791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2924/164	Material
2924/15798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams			
2924/161	Cap			
2924/1611	Structure			
2924/1615	Shape			

2924/165	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2924/16798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2924/16586	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2924/171	. . .	Frame
2924/16587	Ceramics, e.g. crystalline carbides, nitrides or oxides	2924/1711	. . .	Structure
2924/16588	Glasses, e.g. amorphous oxides, nitrides or fluorides	2924/1715	. . .	Shape
2924/1659	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2924/17151	Frame comprising an aperture, e.g. for pressure control, encapsulation
2924/16593	with a principal constituent of the material being a solid not provided for in groups H01L 2924/157 - H01L 2924/15791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2924/172	. . .	Disposition
2924/16598	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2924/173	. . .	Connection portion, e.g. seal
2924/166	. . .	Material	2924/176	. . .	Material
2924/167	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2924/177	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2924/16701	the principal constituent melting at a temperature of less than 400 C	2924/17701	the principal constituent melting at a temperature of less than 400 C
2924/16717	the principal constituent melting at a temperature of greater than or equal to 400 C and less than 950 C	2924/17717	the principal constituent melting at a temperature of greater than or equal to 400 C and less than 950 C
2924/16724	Aluminium [Al] as principal constituent	2924/17724	Aluminium [Al] as principal constituent
2924/16738	the principal constituent melting at a temperature of greater than or equal to 950 C and less than 1550 C	2924/17738	the principal constituent melting at a temperature of greater than or equal to 950 C and less than 1550 C
2924/16747	Copper [Cu] as principal constituent	2924/17747	Copper [Cu] as principal constituent
2924/1676	Iron [Fe] as principal constituent	2924/1776	Iron [Fe] as principal constituent
2924/16763	the principal constituent melting at a temperature of greater than 1550 C	2924/17763	the principal constituent melting at a temperature of greater than 1550 C
2924/16786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2924/17786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2924/16787	Ceramics, e.g. crystalline carbides, nitrides or oxides	2924/17787	Ceramics, e.g. crystalline carbides, nitrides or oxides
2924/16788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2924/17788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2924/1679	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2924/1779	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2924/16791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2924/17791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2924/16793	with a principal constituent of the material being a solid not provided for in groups H01L 2924/167 - H01L 2924/16791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2924/17793	with a principal constituent of the material being a solid not provided for in groups H01L 2924/177 - H01L 2924/17791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
			2924/17798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
			2924/181	. . .	Encapsulation
			2924/1811	. . .	Structure
			2924/1815	. . .	Shape
			2924/1816	Exposing the passive side of the semiconductor or solid-state body
			2924/18161	of a flip chip
			2924/18162	of a chip with build-up interconnect
			2924/18165	of a wire bonded chip
			2924/182	. . .	Disposition
			2924/183	. . .	Connection portion, e.g. seal

2924/18301	being an anchoring portion, i.e. mechanical interlocking between the encapsulation resin and another package part	2924/20201	. . .	Gamma radiation, i.e. wavelength less than 0.01 nm
2924/186	. . .	Material	2924/20202	. . .	X-ray radiation, i.e. wavelength 0.01 to 10 nm
2924/19	. . .	Details of hybrid assemblies other than the semiconductor or other solid state devices to be connected	2924/2021	. . .	Ultraviolet radiation
2924/1901	. .	Structure	2924/20211	UV-C 100= \leq W<280 nm
2924/19011	. . .	including integrated passive components	2924/20212	UV-B 280= \leq W<315 nm
2924/19015	. . .	including thin film passive components	2924/20213	UV-A 315= \leq W<400 nm
2924/1902	. . .	including thick film passive components	2924/2024	. . .	Visible spectrum wavelength 390= \leq W<700 nm, i.e. 400-790 THz
2924/1903	. . .	including wave guides	2924/2026	. . .	Infrared radiation 700= \leq W<3000 nm
2924/19031	being a strip line type	2924/20261	IR-A 700= \leq W<1400 nm, i.e. 215 THz-430 THz
2924/19032	being a microstrip line type	2924/20262	IR-B 1400= \leq W<3000 nm, i.e. 100THz-215 THz
2924/19033	being a coplanar line type	2924/20263	IR-C 3000 nm \leq W<1 mm, i.e. 300 GHz-100THz
2924/19038	being a hybrid line type	2924/2027	. . .	Radio 1 mm - km 300 GHz - 3 Hz
2924/19039	impedance transition between different types of wave guides	2924/20271	Microwave radiation 1 mm - 1 meter, i.e. 300 GHz - 300 MHz
2924/1904	. . .	Component type	2924/203	. .	Ultrasonic frequency ranges, i.e. KHz
2924/19041	being a capacitor	2924/20301	. . .	Ultrasonic frequency [f] f<25 kHz
2924/19042	being an inductor	2924/20302	. . .	Ultrasonic frequency [f] 25 KHz= \leq f< 50 KHz
2924/19043	being a resistor	2924/20303	. . .	Ultrasonic frequency [f] 50 KHz= \leq f< 75 KHz
2924/1905	. .	Shape	2924/20304	. . .	Ultrasonic frequency [f] 75 KHz= \leq f< 100 KHz
2924/19051	. . .	Impedance matching structure [e.g. balun]	2924/20305	. . .	Ultrasonic frequency [f] 100 KHz= \leq f< 125 KHz
2924/191	. .	Disposition	2924/20306	. . .	Ultrasonic frequency [f] 125 KHz= \leq f< 150 KHz
2924/19101	. . .	of discrete passive components	2924/20307	. . .	Ultrasonic frequency [f] 150 KHz= \leq f< 175 KHz
2924/19102	in a stacked assembly with the semiconductor or solid state device	2924/20308	. . .	Ultrasonic frequency [f] 175 KHz= \leq f< 200 KHz
2924/19103	interposed between the semiconductor or sold-state device and the die mounting substrate [i.e. chip-on-passive]	2924/20309	. . .	Ultrasonic frequency [f] f \geq 200 KHz
2924/19104	on the semiconductor or sold-state device [i.e. passive-on-chip]	2924/206	. .	Length ranges
2924/19105	in a side-by-side arrangement on a common die mounting substrate	2924/2064	. . .	larger or equal to 1 micron less than 100 microns
2924/19106	in a mirrored arrangement on two different side of a common die mounting substrate	2924/20641	. . .	larger or equal to 100 microns less than 200 microns
2924/19107	off-chip wires	2924/20642	. . .	larger or equal to 200 microns less than 300 microns
2924/20	. .	Parameters	2924/20643	. . .	larger or equal to 300 microns less than 400 microns
2924/201	. .	Temperature ranges	2924/20644	. . .	larger or equal to 400 microns less than 500 microns
2924/20101	. . .	Temperature range T<0 C, T<273.15 K	2924/20645	. . .	larger or equal to 500 microns less than 600 microns
2924/20102	. . .	Temperature range 0 C= \leq T<60 C, 273.15 K \leq T< 333.15K	2924/20646	. . .	larger or equal to 600 microns less than 700 microns
2924/20103	. . .	Temperature range 60 C= \leq T<100 C, 333.15 K \leq T< 373.15K	2924/20647	. . .	larger or equal to 700 microns less than 800 microns
2924/20104	. . .	Temperature range 100 C= \leq T<150 C, 373.15 K \leq T< 423.15K	2924/20648	. . .	larger or equal to 800 microns less than 900 microns
2924/20105	. . .	Temperature range 150 C= \leq T<200 C, 423.15 K \leq T< 473.15K	2924/20649	. . .	larger or equal to 900 microns less than 1000 microns
2924/20106	. . .	Temperature range 200 C= \leq T<250 C, 473.15 K \leq T< 523.15K	2924/2065	. . .	larger or equal to 1000 microns less than 1500 microns
2924/20107	. . .	Temperature range 250 C= \leq T<300 C, 523.15K \leq T< 573.15K	2924/20651	. . .	larger or equal to 1500 microns less than 2000 microns
2924/20108	. . .	Temperature range 300 C= \leq T<350 C, 573.15K \leq T< 623.15K	2924/20652	. . .	larger or equal to 2000 microns less than 2500 microns
2924/20109	. . .	Temperature range 350 C= \leq T<400 C, 623.15K \leq T< 673.15K	2924/20653	. . .	larger or equal to 2500 microns less than 3000 microns
2924/2011	. . .	Temperature range 400 C= \leq T<450 C, 673.15K \leq T< 723.15K			
2924/20111	. . .	Temperature range 450 C= \leq T<500 C, 723.15K \leq T< 773.15K			
2924/202	. .	Electromagnetic wavelength ranges [W]			

2924/20654	. . . larger or equal to 3000 microns less than 4000 microns	2924/386	. . . Wire effects
2924/20655	. . . larger or equal to 4000 microns less than 5000 microns	2924/3861 Sag
2924/20656	. . . larger or equal to 5000 microns less than 6000 microns	2924/3862 Sweep
2924/20657	. . . larger or equal to 6000 microns less than 7000 microns	2924/40	. Details of apparatuses used for either manufacturing connectors or connecting the semiconductor or solid-state body
2924/20658	. . . larger or equal to 7000 microns less than 8000 microns	2924/401	. . . LASER
2924/207	. . Diameter ranges	2924/40101	. . . Mode
2924/2075	. . . larger or equal to 1 micron less than 10 microns	2924/40102 being pulsed
2924/20751	. . . larger or equal to 10 microns less than 20 microns	2924/40103 being continuous
2924/20752	. . . larger or equal to 20 microns less than 30 microns	2924/40105	. . . Beam details
2924/20753	. . . larger or equal to 30 microns less than 40 microns	2924/4015 Shape
2924/20754	. . . larger or equal to 40 microns less than 50 microns	2924/402	. . . Type
2924/20755	. . . larger or equal to 50 microns less than 60 microns	2924/40201 being a chemical
2924/20756	. . . larger or equal to 60 microns less than 70 microns	2924/40202 Deuterium Fluoride [DF] LASER
2924/20757	. . . larger or equal to 70 microns less than 80 microns	2924/40203 Hydrogen Fluoride [HF] LASER
2924/20758	. . . larger or equal to 80 microns less than 90 microns	2924/40207 Dye laser
2924/20759	. . . larger or equal to 90 microns less than 100 microns	2924/4025 being a gas
2924/2076	. . . equal to or larger than 100 microns	2924/40251 argon-ion LASER
2924/30	. Technical effects	2924/40252 CO ₂ LASER
2924/301	. . Electrical effects	2924/40253 HeAg LASER
2924/30101	. . . Resistance	2924/40254 HeNe LASER
2924/30105	. . . Capacitance	2924/40255 NeCu LASER
2924/30107	. . . Inductance	2924/403 being an Excimer
2924/3011	. . . Impedance	2924/40301 ArF LASER
2924/30111 matching	2924/40302 F ₂ LASER
2924/302	. . . Electrostatic	2924/40303 KrCl LASER
2924/30201 Charge	2924/40304 KrF LASER
2924/30205 Discharge	2924/40305 XeCl LASER
2924/3025	. . . Electromagnetic shielding	2924/40306 XeF LASER
2924/35	. . Mechanical effects	2924/4035 being a fiber hosted LASER
2924/351	. . . Thermal stress	2924/404 being a solid state
2924/3511 Warping	2924/40401 Free electron LASER
2924/3512 Cracking	2924/40402 Photonic crystal LASER
2924/35121 Peeling or delaminating	2924/40403 Fiber solid state LASER
2924/36	. . Material effects	2924/40404 Yttrium Aluminium Garnet Nd:YAG LASER
2924/364	. . . Polymers	2924/40405 Yttrium Lithium Fluoride Nd:YLF LASER
2924/3641 Outgassing	2924/40406 Ruby LASER
2924/365	. . . Metallurgical effects	2924/40407 Yb:YAG LASER
2924/3651 Formation of intermetallics	2924/405	. . . Wavelength
2924/36511 Purple plague	2924/40501 UV spectrum
2924/3656 Formation of Kirkendall voids	2924/40502 Visible spectrum
2924/37	. . Effects of the manufacturing process	2924/40503 IR spectrum
2924/37001	. . . Yield	2933/00	Details relating to devices covered by the group H01L 33/00 but not provided for in its subgroups
2924/37002	. . . Shelf life	2933/0008	. Processes
2924/3701	. . . increased through put	2933/0016	. . relating to electrodes
2924/38	. . Effects and problems related to the device integration	2933/0025	. . relating to coatings
2924/381	. . . Pitch distance	2933/0033	. . relating to semiconductor body packages
2924/384	. . . Bump effects	2933/0041	. . relating to wavelength conversion elements
2924/3841 Solder bridging	2933/005	. . relating to encapsulations
		2933/0058	. . relating to optical field-shaping elements
		2933/0066	. . relating to arrangements for conducting electric current to or from the semiconductor body
		2933/0075	. . relating to heat extraction or cooling elements
		2933/0083	. Periodic patterns for optical field-shaping in or on the semiconductor body or semiconductor body package, e.g. photonic bandgap structures

H01L

- 2933/0091 . Scattering means in or on the semiconductor body or semiconductor body package ([H01L 33/22](#) takes precedence)